

Qspice - Device Reference Guide by KSKelvin

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B. Behavioral Source

B. Behavioral Source : Instance Parameters

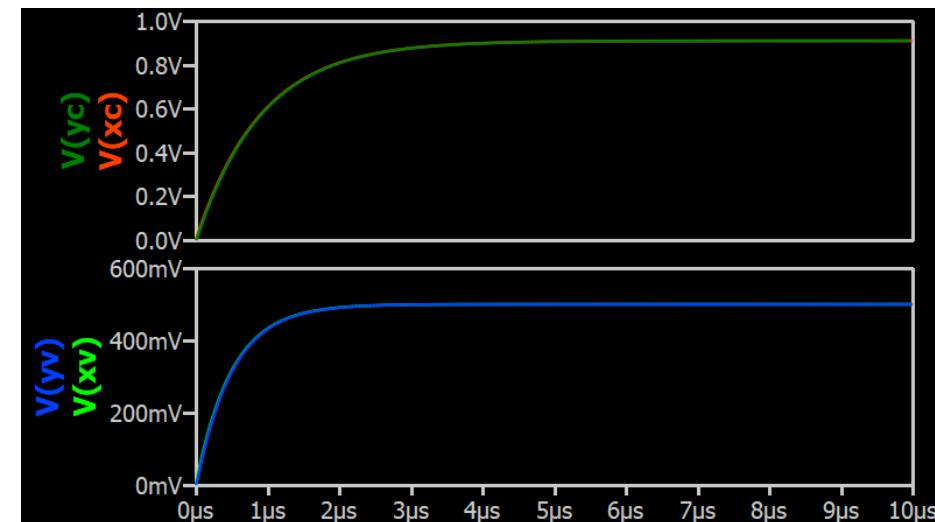
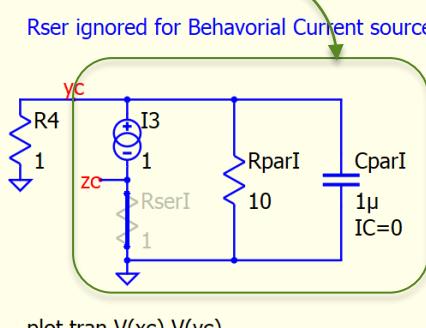
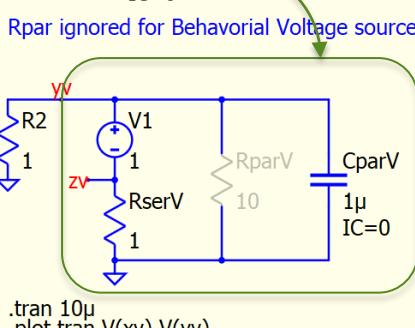
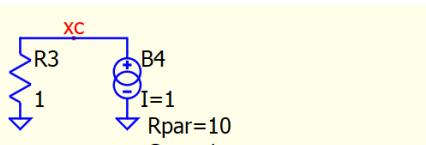
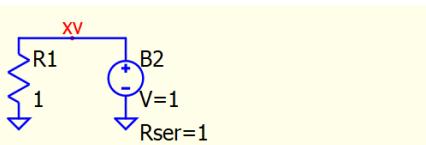
Behavioral Source Instance Parameters

Name	Description	Units	Default
CPAR	Parallel capacitance	F	0.0
I ¹	Expression for current	A	(not set)
IC	Initial value	A or V	0.0
LAPLACE	Frequency dependence		(none)
NORTON	Use a Norton equivalent for a behavioral resistance		(not set)
R ¹	Expression for resistance	Ω	(not set)
RPAR	Parallel resistance Ignore in V	Ω	Infinite
RSER	Series resistance Ignore in I and R (Norton)	Ω	0.0
SYNTHESIZE	Use the synthesized Laplacian circuit even for .AC		(not set)
THEVENIN	Use the Thévenin equivalent for a behavioral resistance		(not set)
V ¹	Expression for voltage	V	(not set)

B. Instance Params : Rser, Rpar and Cpar

Qspice : B Source - Rpar Rser Cpar in V and I.qsch

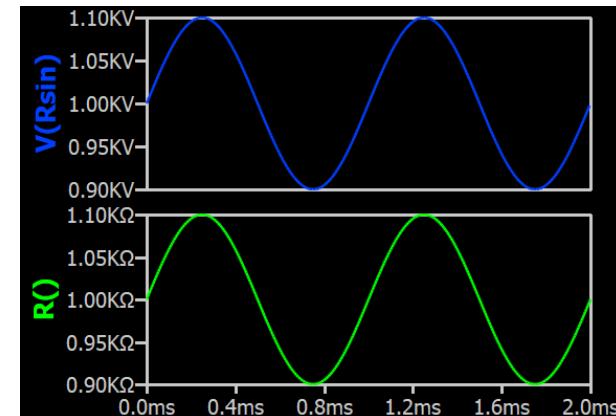
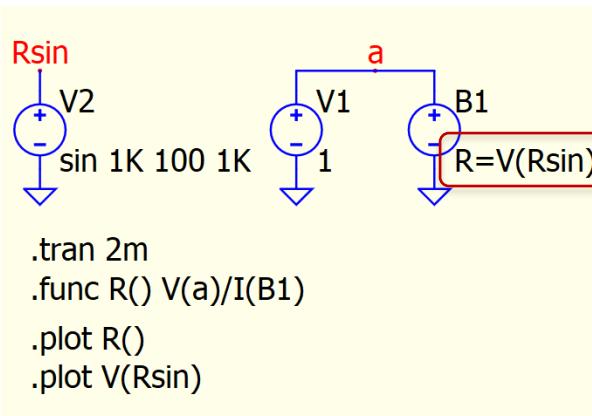
- Rser, Rpar and Cpar in Behavioral Voltage and Current Source
 - Behavioral Voltage ($V=<\text{expression}>$) : Only Rser and Cpar are active
 - Behavioral Current ($I=<\text{expression}>$) : Only Rpar and Cpar are active
 - I don't recommend to use Rser and Rpar in Behavioral Resistance as it will be very confusing depends on Norton or Thevenin equivalent
 - In this example, IC initial value is used to allow 0V or 0A for transient simulation. As behavioral source not have effect in .ac (except for Laplace), .tran is used to reveal these parameters characteristic



B. Instance Params : Behavioral Resistor

Qspice : B Source - Behavioral R.qsch

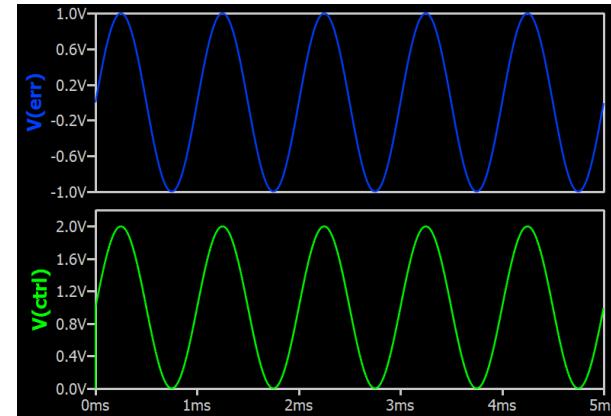
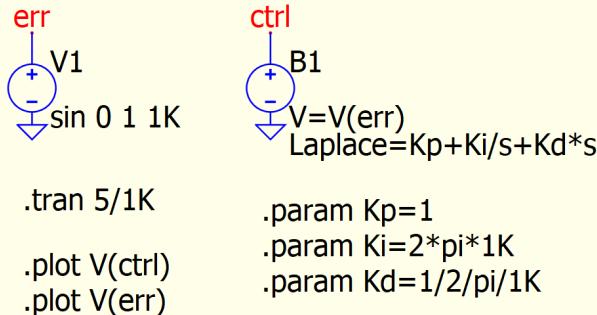
- Behavioral Resistor
 - Syntax : Bnnn n001 n002
 $R = <\text{expression}>$
 - Expression of resistance



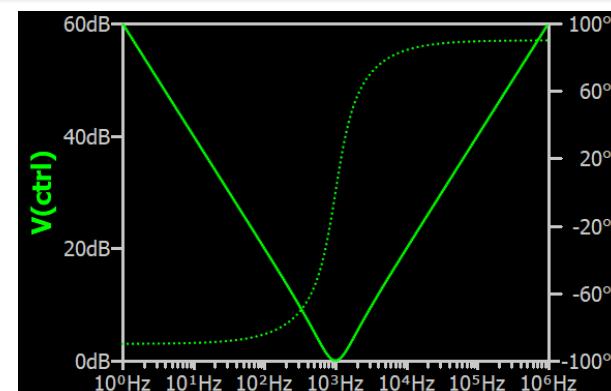
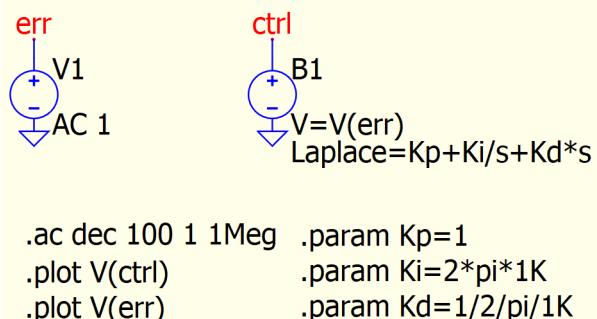
B. Instance Params : Laplace

Qspice : B Source - Laplace (.tran).qsch ; B Source - Laplace (.ac).qsch

- Laplace (.tran)
 - Use Laplace equation, by adding a new attribute Laplace
 - In this simulation
 - $v_{ctrl} = \left(K_p + \frac{K_i}{s} + K_d s \right) v_{err}$



- Laplace (.ac)
 - Laplace supports .ac analysis



B. Function and Operators

HELP > Simulator > Device Reference > B. Behavioral Sources

Functions

Name	Description
abs(x)	Absolute value of x
acos(x)	arc cosine of x
arccos(x)	Synonym for acos()
acosh(x)	arc hyperbolic cosine of x
asin(x)	arc sine of x
arcsin(x)	Synonym for asin()
asinh(x)	Arc hyperbolic sine
atan(x)	Arc tangent of x
arctan(x)	Synonym for atan()
atan2(y,x)	Four quadrant arc tangent of y/x
atanh(x)	Arc hyperbolic tangent
buf(x)	1 if $x > .5$, else 0
ceil(x)	Integer equal or greater than x
cos(x)	Cosine of x
cosh(x)	Hyperbolic cosine of x
ddt(x)	Time derivative x
delay(x,y)	x delayed by y
delay(x,y,z)	x delayed by y, but store no more than z history
dlim(x,y,z)	x bounded by y which it asymptotically starts to approach at y+z as a first inverse order Laurent series
exp(x)	e^x
floor(x)	Integer equal to or less than x
hypot(x,y)	$\sqrt{x^2 + y^2}$
idt(x,y,z)	Time integral of x with initial condition of y reset when $z > .5$
$\int x \, dtimes + y$	

if(x,y,z)	If $x > .5$, then y else z
int(x)	Convert x to integer
inv(x)	0. if $x > .5$, else 1.
limit(x,y,z)	Intermediate value of x, y, and z
In(x)	Natural logarithm of x
log(x)	Alternate syntax for ln()
log10(x)	Base 10 logarithm
max(x,y)	The greater of x or y
min(x,y)	The smaller of x or y
pow(x,y)	x^y
pwr(x,y)	$ x ^y$
pwrs(x,y)	$abs(x)^y$ $sgn(x)*abs(x)^y$
random(x)	Random number from 0. to 1. depending on the integer value of x. Interpolation between random numbers is linear for non-integer x.
sin(x)	sin x
sinh(x)	Hyperbolic sine of x
sqrt(x)	\sqrt{x}
table(x,a,b,c,d,...)	Interpolate x from the look-up table given as a set of pairs of constant values.
tan(x)	Tangent of x.
tanh(x)	Hyperbolic tangent of x
ulim(x,y,z)	x bounded by y which it asymptotically starts to approach at y-z as a first inverse order Laurent series

Operators grouped in reverse order of precedence of evaluation

Operand	Description
&	Boolean AND
	Boolean OR
>	True if expression on the left is greater than the expression on the right.
<	True if expression on the left is less than the expression on the right.
>=	True if expression on the left is greater than or equal the expression on the right.
<=	True if expression on the left is less than or equal the expression on the right.
+	Addition
-	Subtraction
*	Multiplication
/	Division
**	** / ^ Raise left hand side to power of right hand side. Same as '^'.
!	Boolean not the following expression.

Available Function in B source not listed

- Trunc(x) ; floor(x) ; int(x) : rounded down integer
- Rint(x) ; round(x) : rounded to nearest integer
- Ceil(x) : rounded up integer
- Ustep(x) : $x > 0 ? 1 : 0$
- Uramp(x) : $x > 0 ? x : 0$

Available Variable or Constant not listed in HELP

- Time : Simulation Time
- Temp : Temperature
- PI : 3.14159265358979323846
- E : 2.7182818284590452354
- K : 1.380649e-23 J/K
- Q : 1.602176487e-19 Coulomb

B. Function and Operators – delay(x,y) or delay(x,y,z)

Qspice : B Source - delay fix.qsch

- delay(x,y) or delay(x,y,z)
 - Delay(x,y,z) can reduce the amount of waveform memory that must be stored

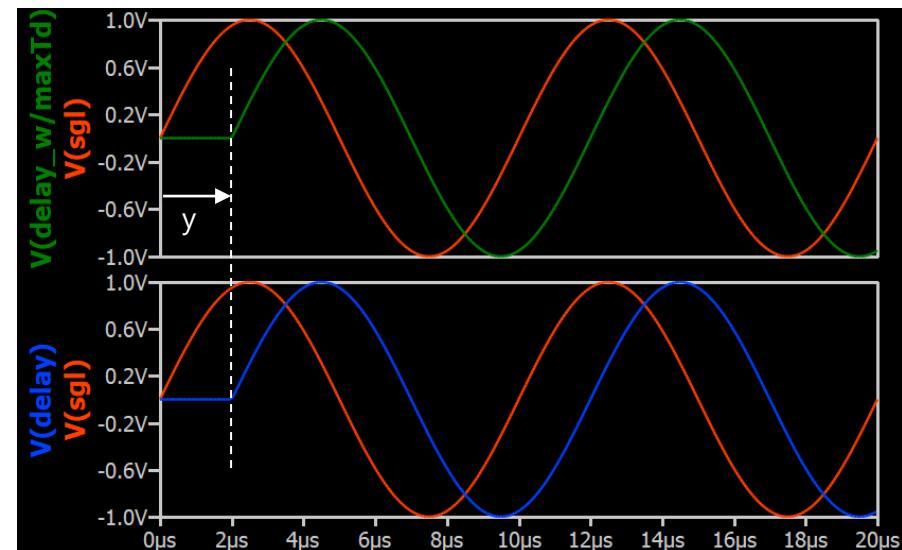
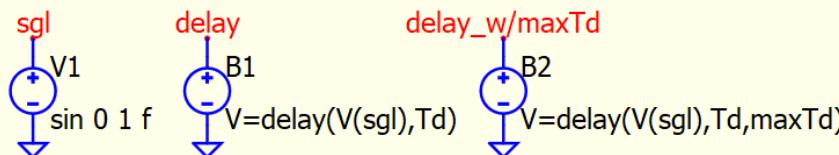
delay(x,y)	x delayed by y
delay(x,y,z) ¹	x delayed by y, but store no more than z history

- y can be parameter and z must be fixed constant
- y must less than z or error will return

Syntax : delay(x,y) - x delayed by y

Syntax : delay(x,y,z) - x delayed by y, but store no more than z history

```
.param f = 100K  
.param Td = 2μ  
.param maxTd = 5μ
```

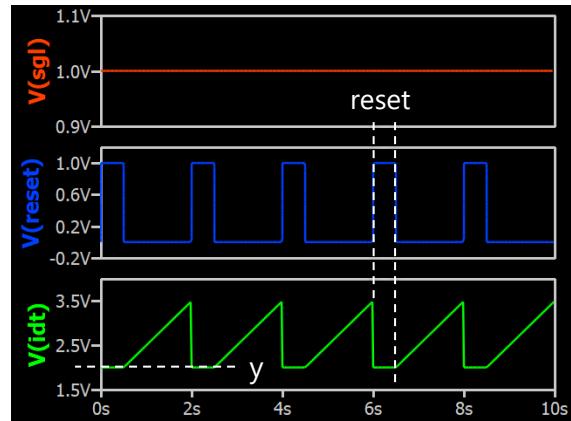
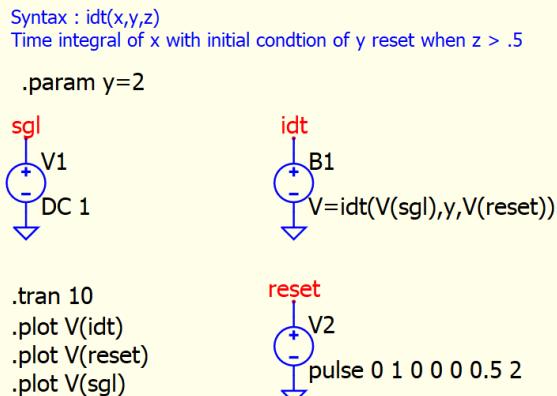


B. Function and Operators – Integral and Time Derivative idt(x,y,z) and ddt(x)

Qspice : B Source - idt.qsch ; B Source - ddt.qsch

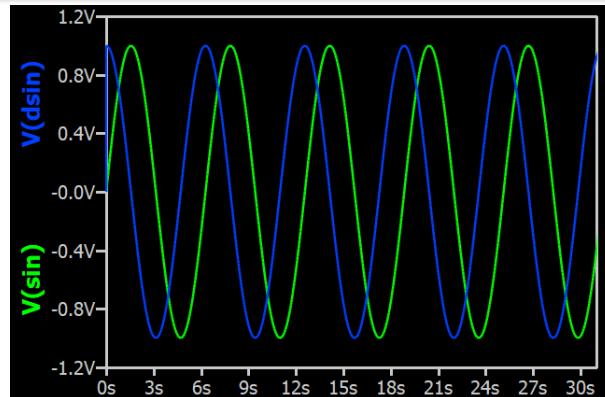
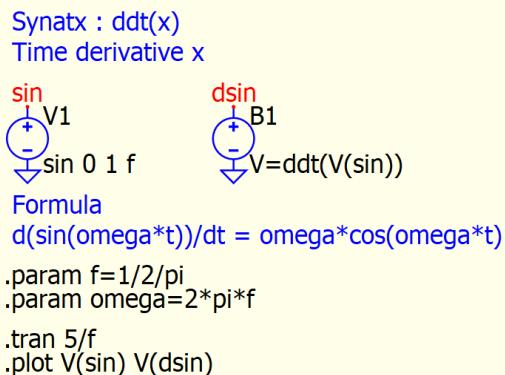
- $\text{idt}(x,y,z)$

- Time Integral of x
- $= \int x dt + y$
- y is initial condition equivalent DC value during integral reset
- z is to reset integral



- $\text{ddt}(x)$

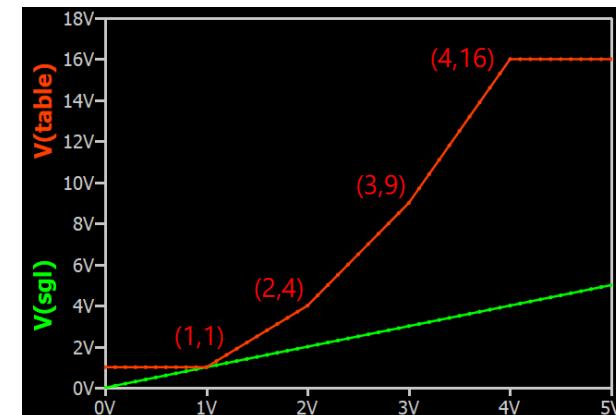
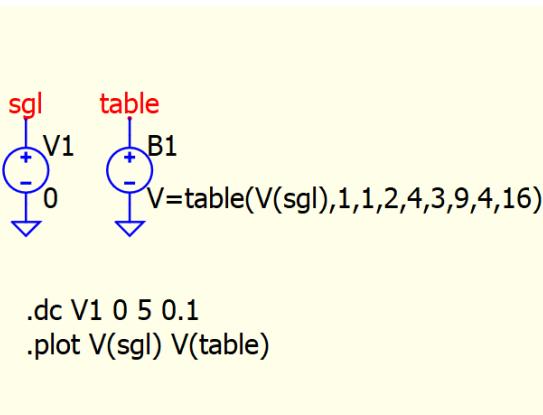
- Time derivative
- $= \frac{dx}{dt}$



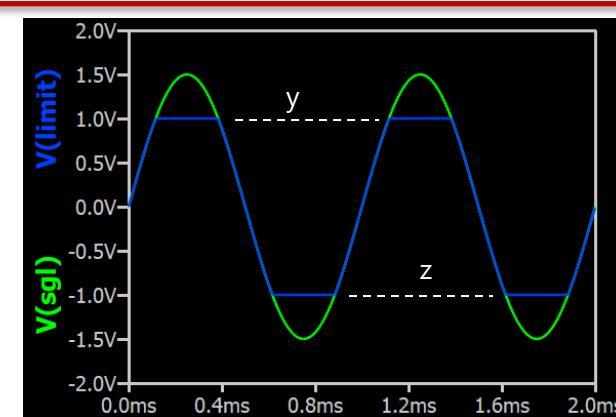
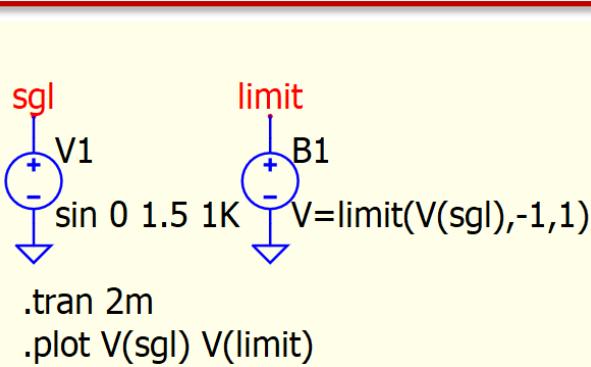
B. Function and Operators – `table(x,a,b,c,d,...)` and `limit(x,y,z)`

Qspice : B Source - `table.qsch` ; B Source - `limit.qsch`

- `Table(x,a,b,c,d,...)`
 - Interpolate x from the look-up table given as a set of pairs of constant values



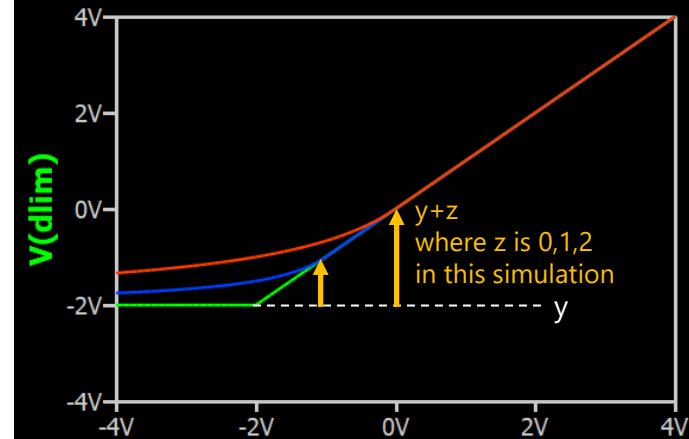
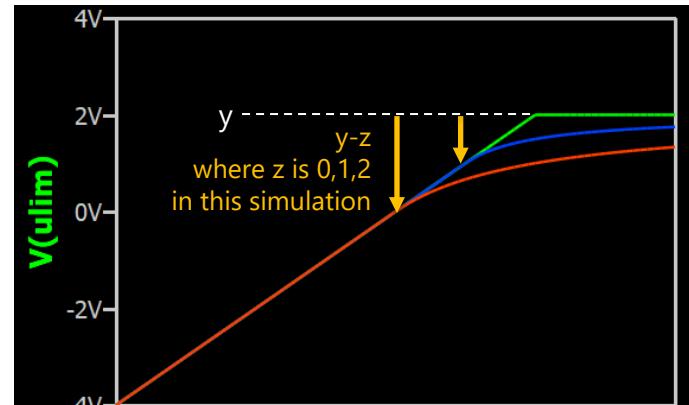
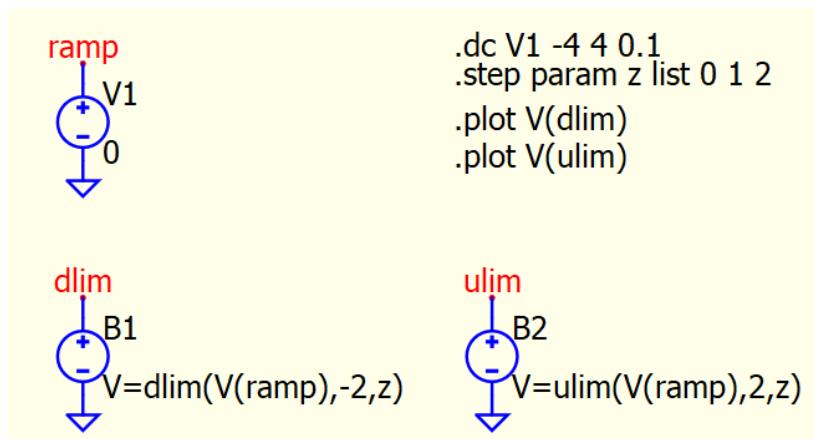
- `limit(x,y,z)`
 - Intermediate value of x, y, and z



B. Function and Operators – dlim(x,y,z) and ulim(x,y,z)

Qspice : B Source - dlim ulim.qsch

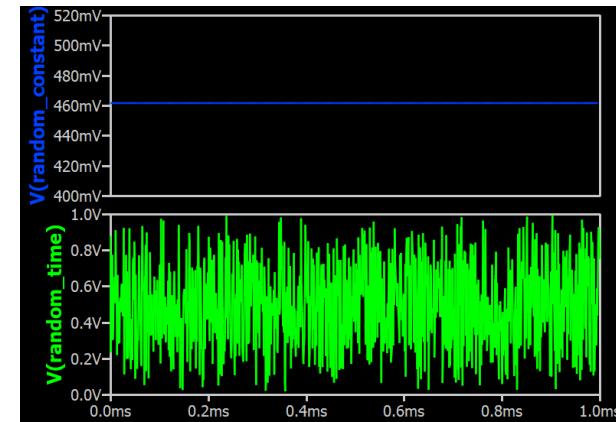
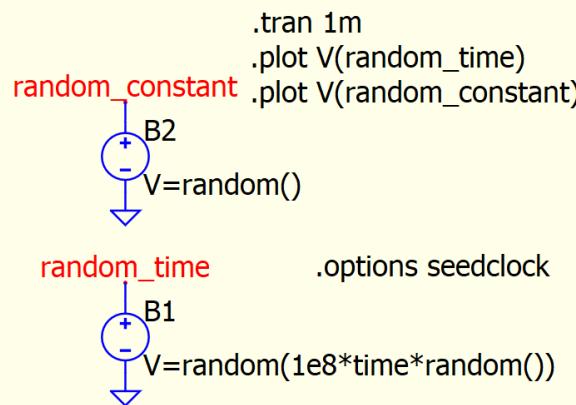
- dlim(x,y,z) and ulim(x,y,z)
 - dlim(x,y,z) : x bounded by y which it asymptotically starts to approach at $y+z$ as a first inverse order Laurent series
 - ulim(x,y,z) : x bounded by y which it asymptotically starts to approach at $y-z$ as a first inverse order Laurent series
 - These functions are used for soft limit



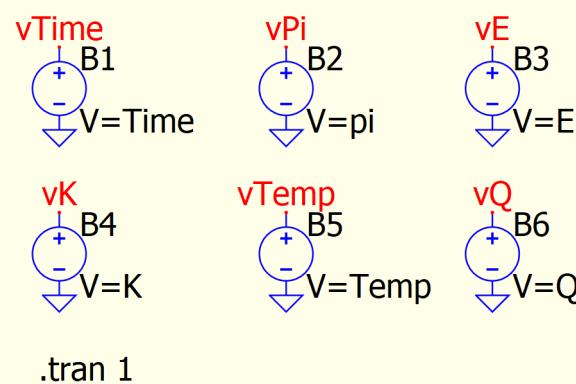
B. Function and Operators – random(x), variable/constant

Qspice : B Source – random.qsch ; B Source - Buildin Variable Constant.qsch

- Random(x)
 - Random number from 0. to 1. depending on the integer value of x
 - The one without arguments must be processed in the preprocessor (explained by Mike Engelhardt)
 - To create a random sequence in transient, x must change in each time step : i.e. random(1e8*time), multiple with 1e8 is for x to be a large integer for random generation



- Build-in Variable / Constant
 - Time : Simulation Time
 - Temp : Temperature
 - PI : 3.14159265358979323846
 - E : 2.7182818284590452354
 - K : 1.380649e-23 J/°K
 - Q : 1.602176487e-19 Coulomb



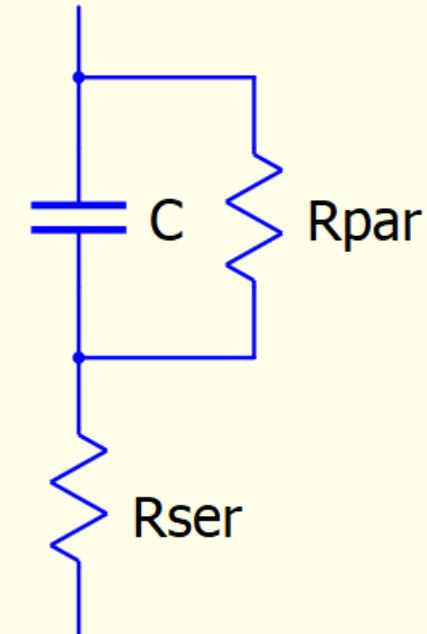
C. Capacitor

C. Capacitor Instance Parameters in Qspice HELP

Rpar and Rser in C model

Capacitor Instance Parameters

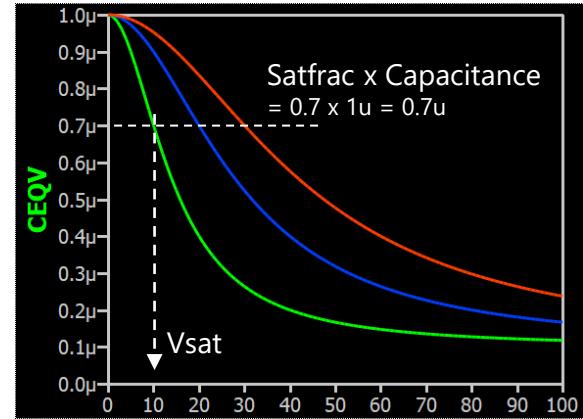
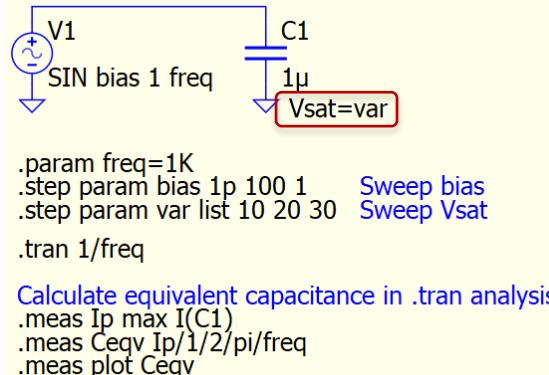
Name	Description	Units	Default
CAPACITANCE	Capacitance(not usually labeled)	F	0.0
CSAT	Capacitance asymptotically approached in saturation	F	10% of CAPACITANCE
IC	Initial voltage on capacitor	V	0.0
L ¹	Length	m	0.0
M	Number of identical parallel devices		1.0
RPAR	Equivalent parallel resistance	Ω	Infinite
RSER	Equivalent series resistance	Ω	0.0
SATFRAC	Fractional drop in capacitance at VSAT		0.7
TEMP	Instance temperature	$^{\circ}\text{C}$	Circuit temperature
VSAT	Voltage that drops capacitance to SATFRAC×CAPACITANCE	V	Infinite
W ¹	Width	m	0.0



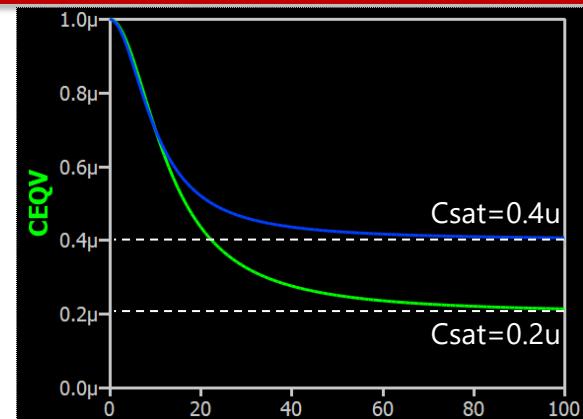
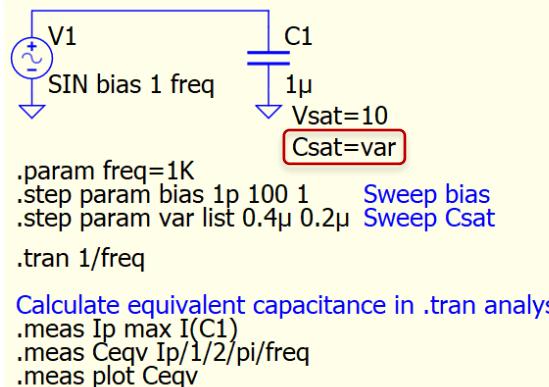
C. Instance Params : Vsat, Csat, Satfrac : For Nonlinear Capacitance

Qspice : C Capacitor - Vsat (.ac).qsch ; C Capacitor - Csat (.tran).qsch

- Vsat and Satfrac
 - Vsat : Voltage that drops capacitance to **Satfrac x Capacitance**
 - Satfrac : Fractional drop in capacitance at Vsat
 - **Default Vsat=Infinite (V)**
 - **Default Satfrac=0.7**



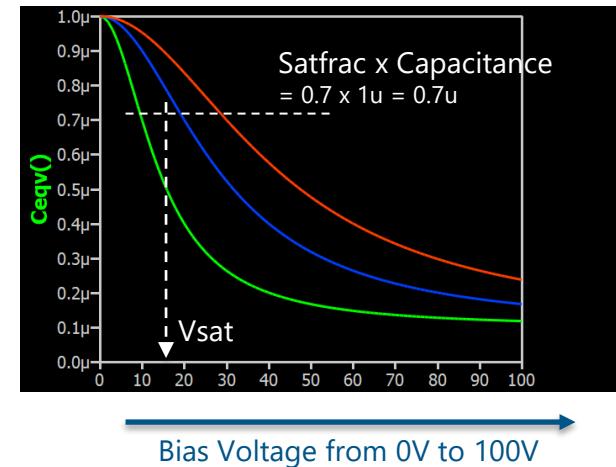
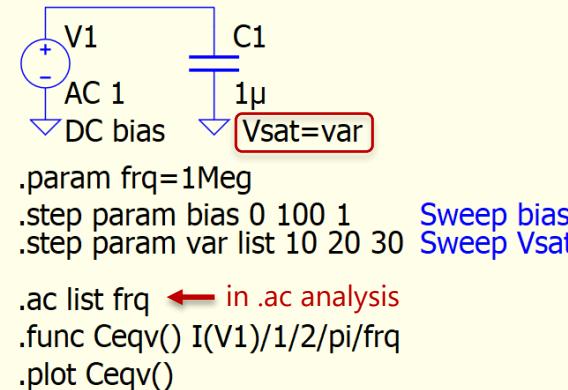
- Csat
 - Csat : Capacitance asymptotically approached in saturation
 - ** Vsat must be set to see its effect
 - **Default Csat=10% of C**



C. Instance Params : Replicate previous graph with .ac analysis

Qspice : C Capacitor - Vsat (.ac).qsch

- Vsat and Satfrac
 - Vsat : Voltage that drops capacitance to **Satfrac x Capacitance**
 - Satfrac : Fractional drop in capacitance at Vsat
 - **Default Vsat=Infinite (V)**
 - **Default Satfrac=0.7**

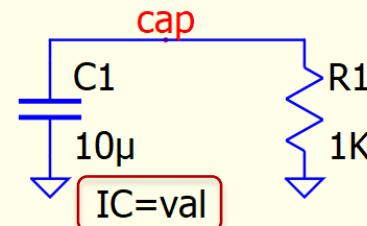


- Capacitance equation
 - $X_C = \frac{1}{\omega C} = \frac{V_c}{I_c}$
 - $C = \frac{|I_c|}{|V_c| \omega} = \frac{|I_c|}{2\pi f |V_c|}$
 - This formula is used to calculate equivalent capacitance (small signal model) at different capacitor bias voltage

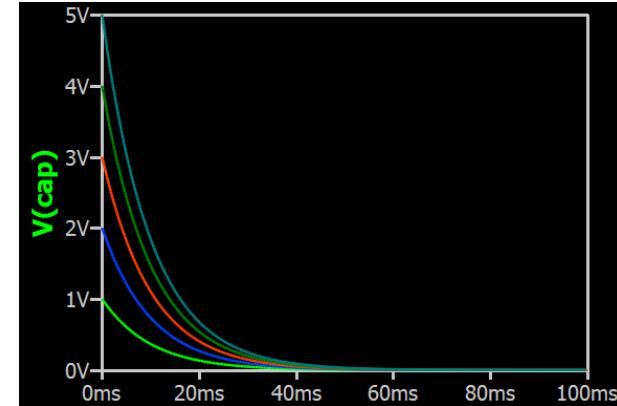
C. Instance Params : IC Initial Condition

Qspice : Capacitor - IC.qsch

- IC
 - IC : Initial Condition
 - **Default IC=0V**
 - Use in transient analysis for initial voltage of capacitor at time=0s



```
.step param val 1 5 1  
.tran 100m  
.plot V(cap)
```



D. Diode

Model Parameters

Diode Model Parameters in Qspice HELP

Diode Instance Parameters			
Name	Description	Units	Default
AREA	Relative area		1.0
M	Number of identical parallel devices		1.0
TEMP	Instance temperature	°C	Circuit temperature

Diode Model Parameters			
Name	Description	Units	Default
AF	Flicker noise exponent	1.	1.0
BV	Reverse breakdown voltage	V	Infinite
CJO	Zero-bias junction capacitance	F	0.0
EG	Activation energy	eV	1.11
FC	Forward-bias depletion capacitance coefficient		0.5
GMAX	Maximum conductivity(straight-line extension)	Ω	10000.
GP	Parallel conductivity added in lieu of global Gmin	Ω	0.
IBV	Current at breakdown voltage	A	1e-10
IBVL	Low-level reverse breakdown knee current	A	0.0
IKF	High-injection knee current	A	1e308
IS	Saturation current	A	1e-14
ISR	Recombination current parameter	A	0.0
KF	Flicker noise coefficient		0.0
M	Grading coefficient		0.5

① N	Emission coefficient	1.0
① NBV	Reverse breakdown emission coefficient	1.0
① NBVL	Low-level reverse breakdown emission coefficient	1.0
① NR	ISR emission coefficient	2.0
① RS	Series resistance	Ω 0.0
TBV1	1st order BV temperature coefficient	°C⁻¹ 0.0
TBV2	2nd order BV temperature coefficient	°C² 0.0
TIKF	IKF temp coefficient	°C⁻¹ 0.0
TNOM	Parameter measurement temperature(aka TREF)	°C 27
TG11	1st order GP temperature coefficient¹	°C⁻¹ 0.0
TGP2	2nd order GP temperature coefficient¹	°C² 0.0
TRS1	1st order RS temperature coefficient¹	°C⁻¹ 0.0
TRS2	2nd order RS temperature coefficient¹	°C² 0.0
① TT	Transit-time²	sec 0.0
① VJ	Junction potential	V 1.0
XTI	Saturation current temperature exponent	3.0

.model available parameters but not in HELP

- VP : Soft reverse recovery parameter (Default VP=0.01)

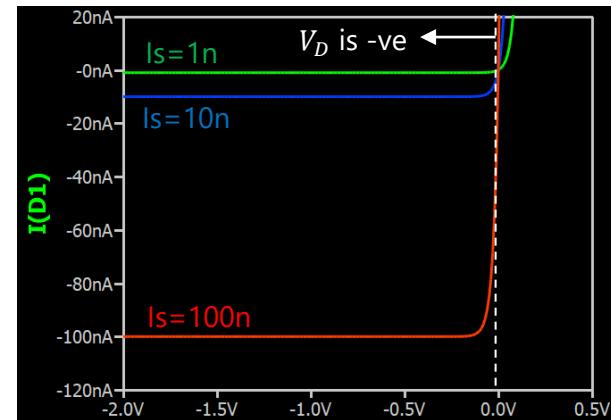
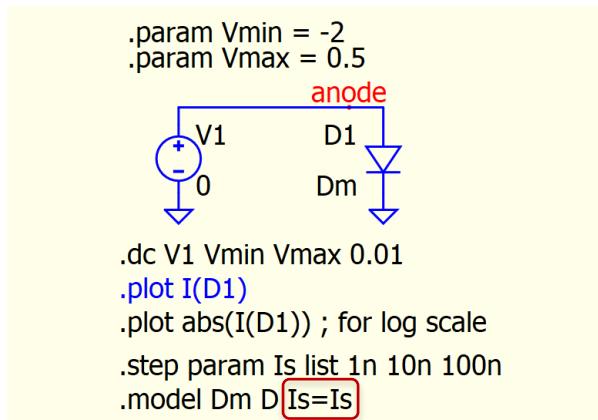
.model parameters only for information display but no electrical behavior

- MFG : manufacturer name
- Vrev : Peak reverse voltage
- Iave : Average current rating

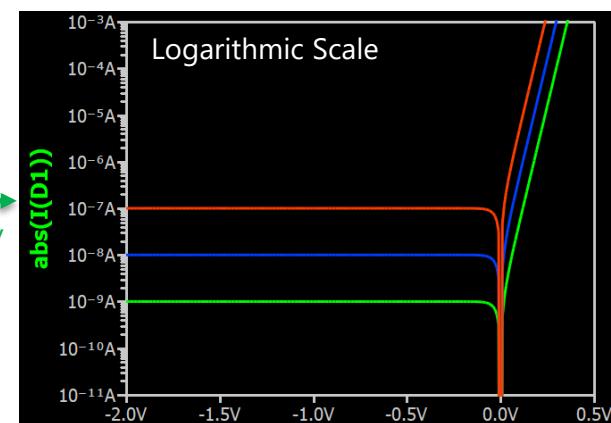
D. Diode Model (I-V Characteristic) : IS

Qspice : Dmodel - IS.qsch

- IS
 - Is : Saturation current
 - Saturation current in reverse region
 - **Default IS = 1e-14A**
 - $I_D = I_s \left(e^{\frac{qV_D}{nkT}} - 1 \right)$
 - $\frac{kT}{q}$ is called thermal voltage
 - q : electronic charge
 - 1.602176487e-19 Coulomb
 - k : Boltzmann constant
 - 1.380649e-23 J/K
 - T : Temperature in Kelvin
 - $T = T_{celsius} + 273.15^\circ C$
 - V_D : Diode voltage
 - n : emission coefficient



$|I_d|$ →
Magnitude only



D. Diode Model (I-V Characteristic) : N and Rs

Qspice : Dmodel - N.qsch / Dmodel - Rs.qsch

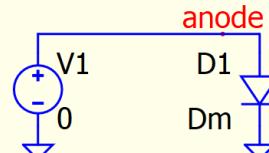
- N
 - n : emission coefficient

Default N=1

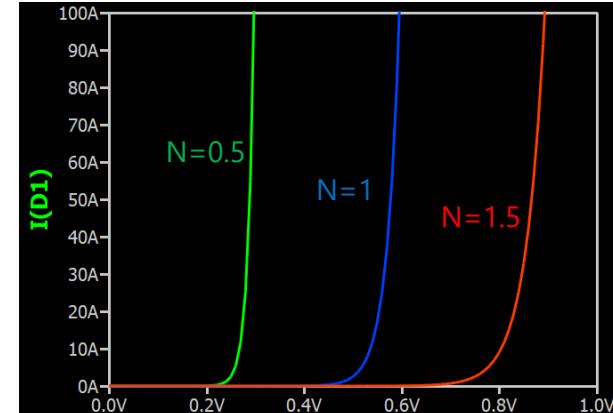
$$I_D = I_s \left(e^{\frac{qV_D}{nkT}} - 1 \right)$$

- N affects threshold voltage in forward bias

```
.param Vmin = 0  
.param Vmax = 1  
.step param n list 0.5 1 1.5
```



```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.model Dm D Is=10n N=n
```



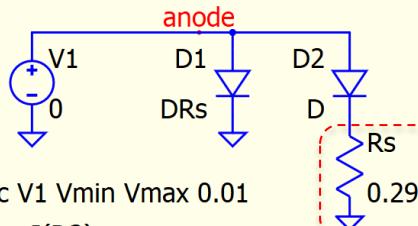
- RS
 - Rs : Series resistance

Default RS=0Ω

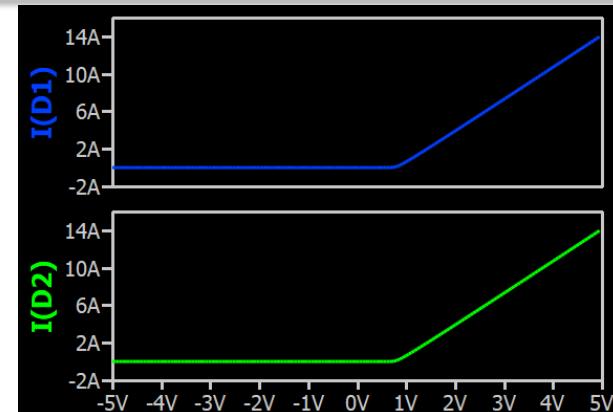
- This is equivalent to resistor added in series to diode

** V_D in $I_D = I_s \left(e^{\frac{qV_D}{nkT}} - 1 \right)$ formula only represent diode model voltage drop. If RS is added, diode model anode to cathode voltage is $V_D + I_D R_s$

```
.param Vmin = -5  
.param Vmax = 5
```



```
.dc V1 Vmin Vmax 0.01  
.plot I(D2)  
.plot I(D1)  
.model DRs D Rs=0.29
```



Forward Voltage (VF) or Threshold @ Specified Forward Current (IF)

** Condition : Recombination current is not used : ISR=0

- Background

- In datasheet, it generally specify forward threshold by defining as forward voltage drop (VF) at a specified forward current level (IF)

- Diode model include RS

- $V_{D,ext} = V_D + I_D R_S$ and $I_d = I_s \left(e^{\frac{qV_D}{nkT}} - 1 \right)$
 - where $V_{D,ext}$ is diode voltage drop including series resistance
- Re-arrange I_d formula : $V_D = n \frac{kT}{q} \ln \left(\frac{I_d}{I_s} + 1 \right)$
- Therefore,
 - $V_{D,ext} = n \frac{kT}{q} \ln \left(\frac{I_d}{I_s} + 1 \right) + I_D R_S$
- Substitute $V_{D,ext}$ by VF and I_D by IF and Qspice .model parameters
 - $V_F = N \frac{kT}{q} \ln \left(\frac{IF}{IS} + 1 \right) + IF \times RS$
 - where Qspice default temperature T is 27°C = 300.15K
 - $k=1.380649e-23 \text{ J/K}$ and $q=1.602176487e-19 \text{ C}$ $\rightarrow \frac{kT}{q} = 2.5865e-2$
 - Equation can be simplified with $IF \gg IS$ where $\left(\frac{IF}{IS} + 1 \right) \rightarrow \frac{IF}{IS}$

- Simplified Results in Qspice

- $VF = 2.5865e-2 * N * \ln(IF/IS) + IF * RS$
 - IS, N and RS are in diode .model
 - IF is specified forward current for diode threshold (e.g. IF=100mA)

Approximation formula to calculate Vd threshold at IF, @27oC
.param VF=2.5865e-2*N*ln(IF/IS)+IF*RS

Model Parameters

```
.param IS=5n  
.param N=2  
.param Rs=.58
```

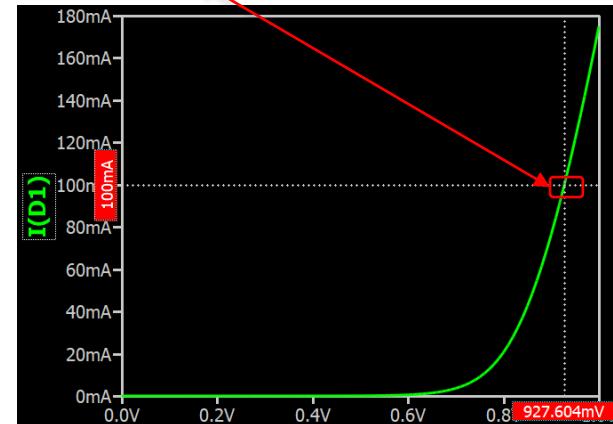
```
.dc V1 0 1 0.01  
.plot I(D1)  
.options listparam
```

IF forward Current

```
.param IF=100m  
.model 1N4148 D Is=5n Rs=.58 n=2  
+Cjo=.87p m=.025 tt=7.9n Nbv=2000  
+BV=100 IBV=150n XTI=6  
+mfg="ON Semiconductor"  
+Vrev=100 Iave=200m
```

Output Window

TEMP	= 27	"CKTTEMP"
IS	= 5N	"5N"
N	= 2	"2"
RS	= 580M	".58"
VF	= 927.646M	"2.5865E-2*N*LN(IF/IS)+IF*RS"
IF	= 100M	"100M"



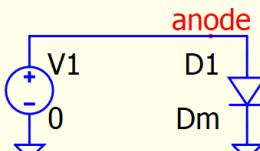
D. Diode Model (I-V Characteristic : Breakdown) : BV, IBV and NBV

Qspice : Dmodel - BV IBV.qsch / Dmodel - NBV.qsch

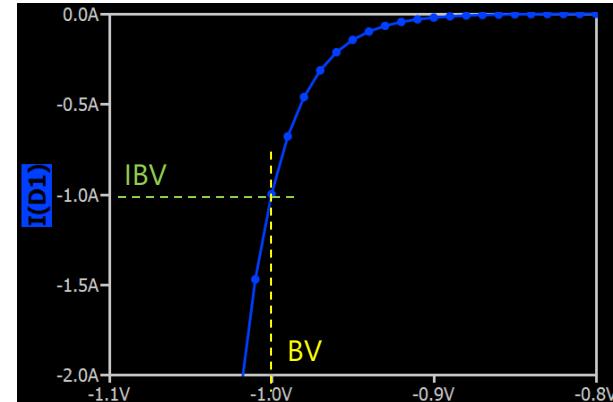
- BV and IBV

- BV : Breakdown Voltage
- IBV : Current at breakdown voltage
- Default BV=Infinite**
- Default IBV=1e-10**
- Breakdown region eqn
 - $I_D = -IBV e^{-\frac{q(BV+V_D)}{kT}}$

```
.param Vmin = -1.2  
.param Vmax = 0
```



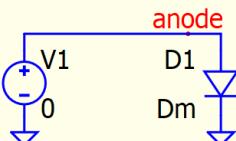
```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.model Dm D BV=1 IBV=1
```



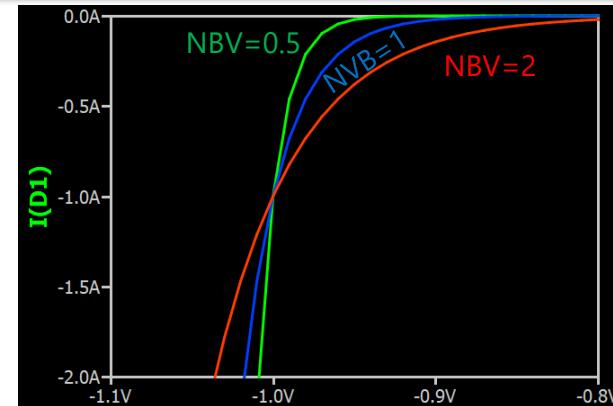
- NBV

- NBV : Reverse breakdown emission coefficient
- Default NBV=1**
- Change the sharpness of breakdown reverse current

```
.param Vmin = -1.2  
.param Vmax = 0
```



```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.model Dm D BV=1 IBV=1 NBV=nbv  
.step param nbv list 0.5 1 2
```



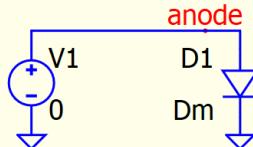
D. Diode Model (I-V Characteristic : Breakdown) : IBVL and NBVL

Qspice : Dmodel - IBVL.qsch / Dmodel - NBVL.qsch

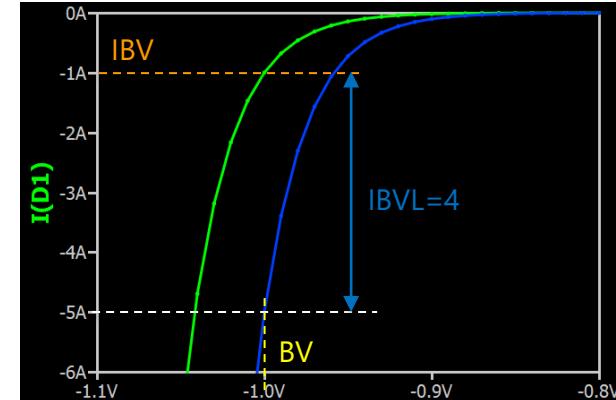
- **IBVL**

- IBVL : low-level reverse breakdown knee current
- **Default IBVL=1**

```
.param Vmin = -1.2  
.param Vmax = -0.6
```



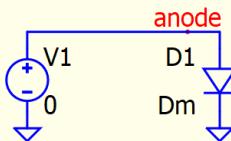
```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.step param ibvl list 0 4  
.model Dm D BV=1 IBV=1 IBVL=ibvl
```



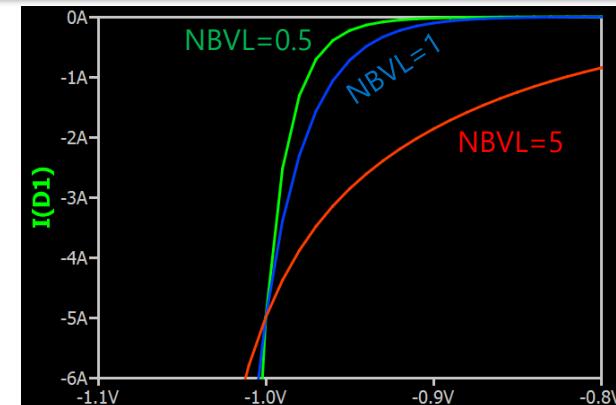
- **NBVL**

- NBVL : Low-level reverse breakdown emission coefficient
- **Default NBVL=1**
- Change the sharpness of breakdown reverse current when IBVL is used

```
.param Vmin = -1.2  
.param Vmax = -0.6
```



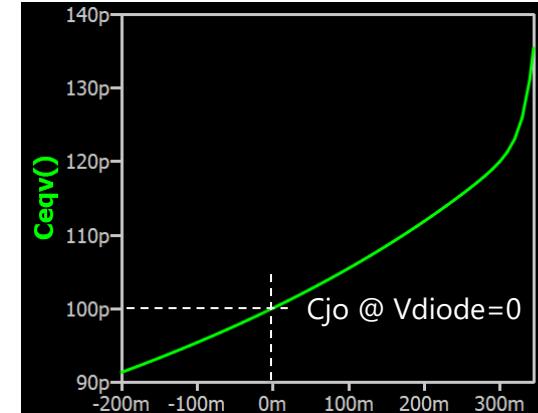
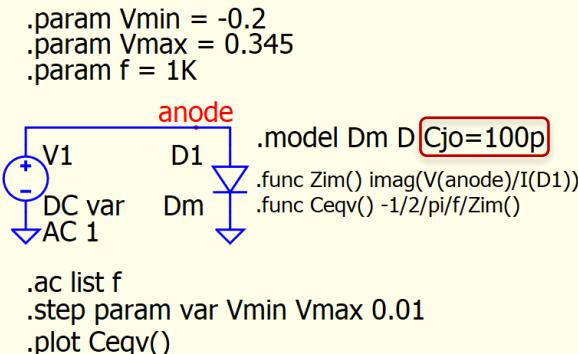
```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.step param nbvl list 0.5 1 5  
.model Dm D BV=1 IBV=1 IBVL=4  
+NBVL=nbvl
```



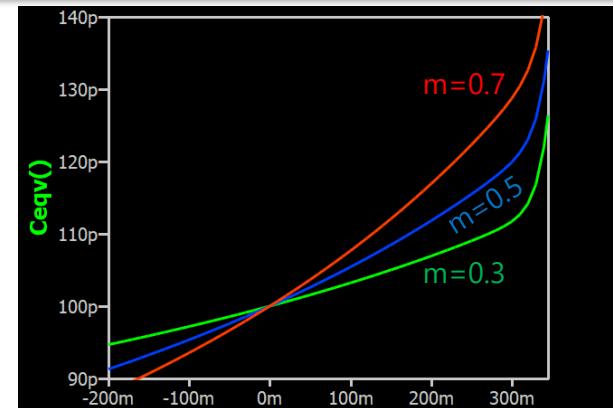
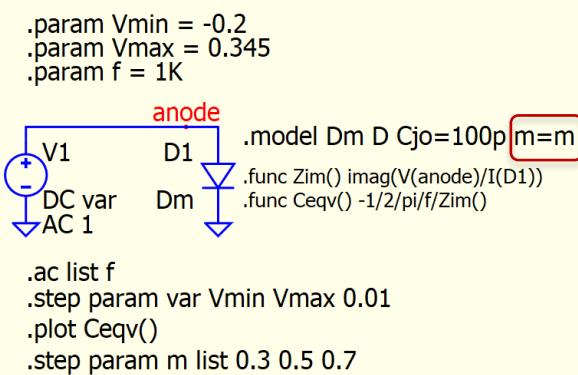
D. Diode Model (Capacitance) : CJO and M

Qspice : Dmodel - CJO.qsch / Dmodel - M.qsch

- CJO
 - C_{jo} : Zero-bias junction capacitance
 - **Default CJO=0F**
 - $C_j = \frac{C_{jo}}{\left(1 - \frac{V_D}{\Phi_0}\right)^m}$
 - Φ_0 : Junction potential (VJ)
 - m : Grading coefficient
 - M = 0.33 : linearly garded
 - M = 0.5 : abrupt junction



- M
 - m : grading coefficient
 - **Default M=0.5**
 - $C_j = \frac{C_{jo}}{\left(1 - \frac{V_D}{\Phi_0}\right)^m}$
 - m : Grading coefficient
 - M = 0.33 : linearly garded
 - M = 0.5 : abrupt junction



D. Diode Model (Capacitance) : VJ and FC

Qspice : Dmodel - VJ.qsch / Dmodel - FC.qsch

- VJ

- V_j : Junction potential

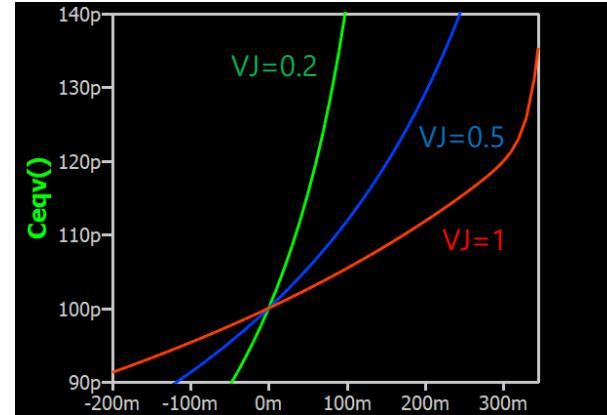
Default $VJ=1V$

- $C_j = \frac{C_{jo}}{\left(1 - \frac{V_D}{\Phi_0}\right)^m}$

- Φ_0 : Junction potential (V_j)
 - may range from 0.2 to 1V

```
.param Vmin = -0.2
.param Vmax = 0.345
.param f = 1K
.anode
V1          .model Dm D Cjo=100p [VJ=vj]
DC var      .func Zim() imag(V(anode)/I(D1))
AC 1        .func Ceqv() -1/2/pi/f/Zim()
D1          Dm
```

.ac list f
.step param var Vmin Vmax 0.01
.plot Ceqv()
.step param vj list 0.2 0.5 1



- FC

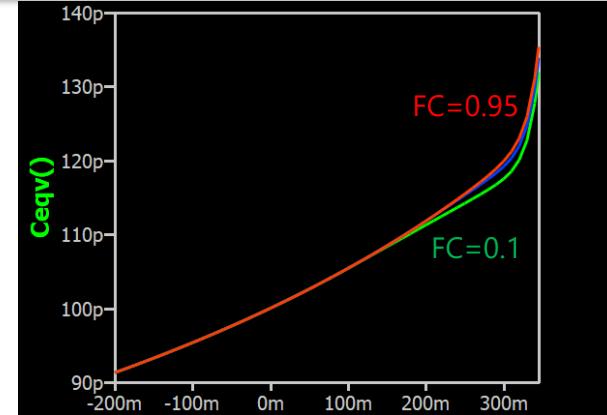
- F_c : Forward-bias depletion capacitance coefficient

Default $FC=0.5$

- A factor between 0 and 0.95 (limit by 0.95 in Qspice), which determines how the junction capacitance is calculated when the junction is forward-biased

```
.param Vmin = -0.2
.param Vmax = 0.345
.param f = 1K
.anode
V1          .model Dm D Cjo=100p [FC=fc]
DC var      .func Zim() imag(V(anode)/I(D1))
AC 1        .func Ceqv() -1/2/pi/f/Zim()
D1          Dm
```

.ac list f
.step param var Vmin Vmax 0.01
.plot Ceqv()
.step param fc list 0.1 0.2 0.95

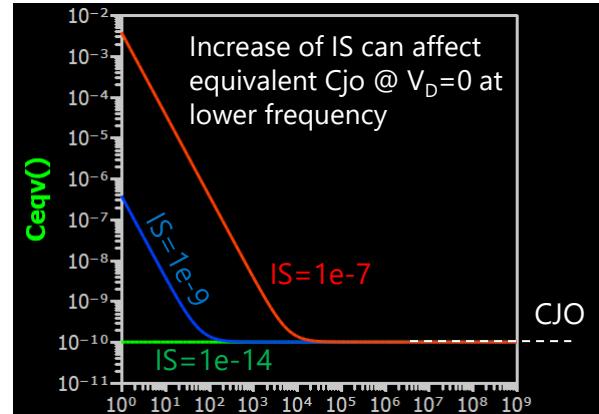


D. Diode Model (Capacitance) : Parameters can affect Cj in frequency

Qspice : Dmodel - Cj Effect – IS.qsch

- Params can affect Cj in frequency
 - IS : Saturation current

```
.param Vmin = -0.2
.param Vmax = 0.345
.param f = 1K
.anode
V1
DC 0
AC 1
D1
Dm
.func Zim() imag(V(anode)/I(D1))
.func Cequiv() -1/2/pi/f/Zim()
.ac list f
.step dec param f 1 1G 10
.plot Cequiv()
.model Dm D Cjo=100p Is=Is
.step param Is list 1e-14 1e-9 1e-7
```



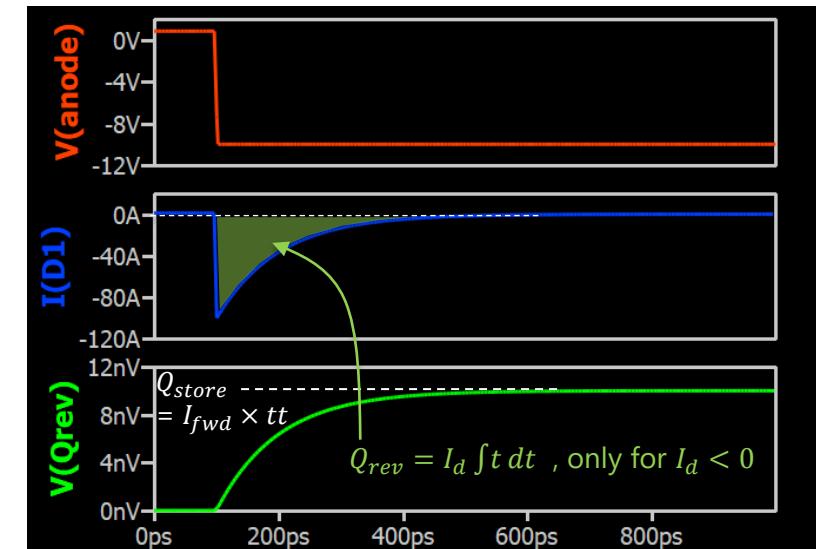
D. Diode Model (Reverse Recovery) : TT

Qspice : Dmodel - TT.qsch

- TT : Transit-time
 - TT is not the time it takes a diode to turn off. It's a measure of **the amount of charge that needs to be pulled out to turn the diode off**. Specifically, **the stored charge is TT times the forward current**. For the product to be Coulomb, the dimensions of TT must be time
 - $Q_{store} = I_{fwd} \times tt$, where tt is transit-time in Qspice
 - **Default TT=0s** [equivalent to disable reverse recovery from TT]
 - ** If TT is used, Rs must be non-zero (it can affect forward I-V characteristic if Rs=0 with a finite TT)

```
.param v fwd=0.834  
.param v rev=-10  
.param td=0.1n  
.param p=1p  
  
anode  
V1 D1 Dm  
pwl 0 v fwd td v fwd td+p v rev
```

```
.tran 10*td  
.option maxstep=p/50  
.plot V(Qrev)  
.plot I(D1)  
.plot V(anode)  
  
.param tt=10n  
.model Dm D Rs=1e-12 Tt=tt  
Mike's comment : If TT isn't zero,  
Rs can not be zero, because of the  
way QSPICE handles dQ/dT soft recovery.  
  
Integral negative diode current :  $Q = I \cdot t$   
Qrev  
B1  
V=idt(uramp(I(V1)),0)  
.meas Ifwd max -I(V1)  
.meas Qstore Ifwd*tt
```



D. Diode Model (Reverse Recovery) : VP

Qspice : Dmodel - VP.qsch

- VP : Soft reverse recovery parameter
 - No description in Qspice HELP
 - **Default VP=1e-2 (i.e. Default VP=0.01)**
 - It affect current amplitude at reverse recovery
 - Increase VP can reduce current amplitude but increase reverse recovery time

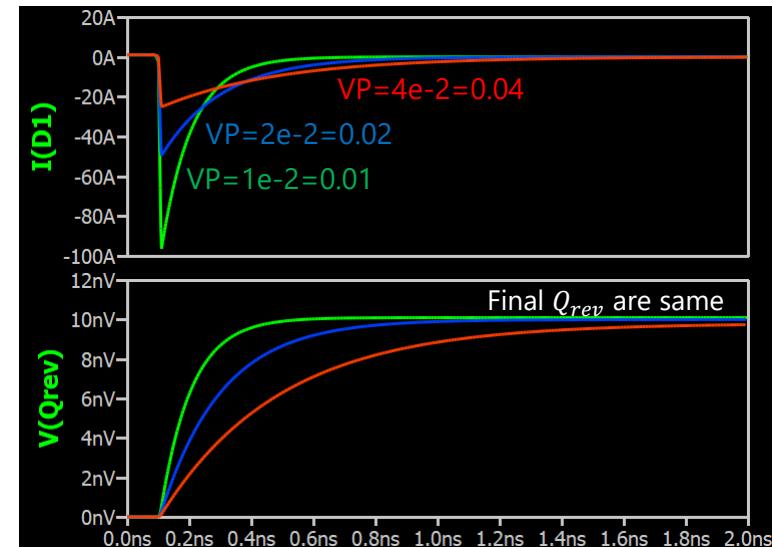
```
.param vfwd=0.834  
.param vrev=-10  
.param td=0.1n  
.param p=1p  
  
anode  
V1 D1 Dm  
  
pwl 0 vfwd td vfwd td+p vrev
```

```
.tran 20*td  
.option maxstep=p/50  
.plot V(Qrev)  
.plot I(D1)  
  
.step param vp list 1e-2 2e-2 4e-2  
.param tt=10n  
.model Dm D Rs=1e-12 Tt=tt Vp=vp
```

Integral negative diode current : $Q = I \cdot t$

Q_{rev}

```
B1  
V=idt(uramp(I(V1)),0)
```



D. Diode Model (Reverse Current) : CJ

Qspice : Dmodel - CJO (RR).qsch

- CJ : Junction capacitance

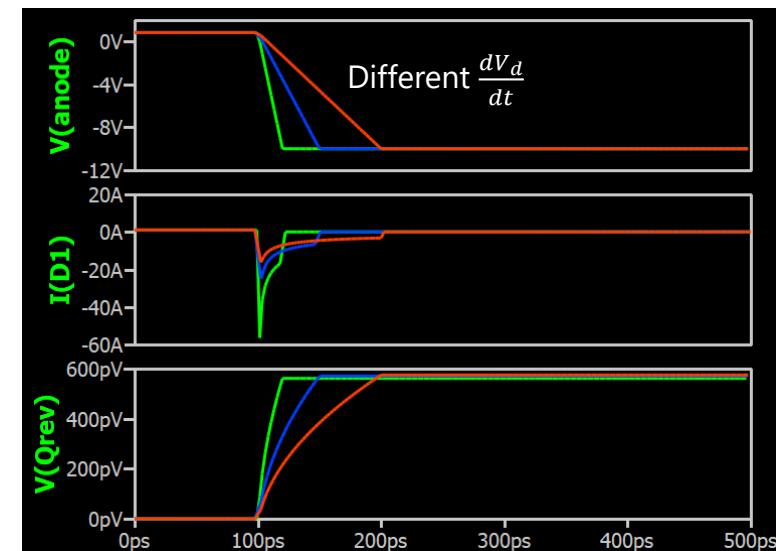
- Junction capacitance leads to reverse current but **NOT** a reverse recovery
 - For example, SiC has negligible reverse recovery and it model may not have TT but with CJO
- Reverse charge depends on junction capacitance and reverse voltage
- $\frac{dV_d}{dt}$ or $\frac{dI_d}{dt}$ are factor can affect peak reverse current in reverse recovery

```
.param vfwd=0.834  
.param vrev=-10  
.param td=0.1n  
.param p=duratio  
  
anode  
V1 D1 Dm  
  
.tran 5*td  
.option maxstep=p/50  
.plot V(Qrev)  
.plot I(D1)  
.plot V(anode)  
  
.step param duration list 20p 50p 100p  
.model Dm D CJO=100p
```

pwl 0 vfwd td vfwd td+p vrev

Integral negative diode current : $Q = I \cdot t$

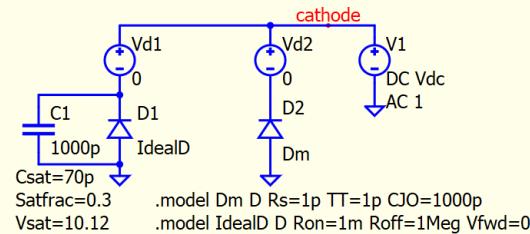
Q_{rev}
B1
 $V = idt(uramp(I(V1)), 0)$



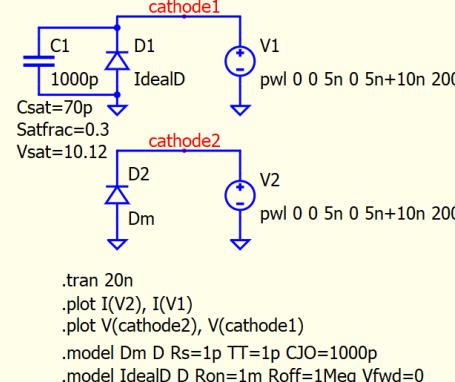
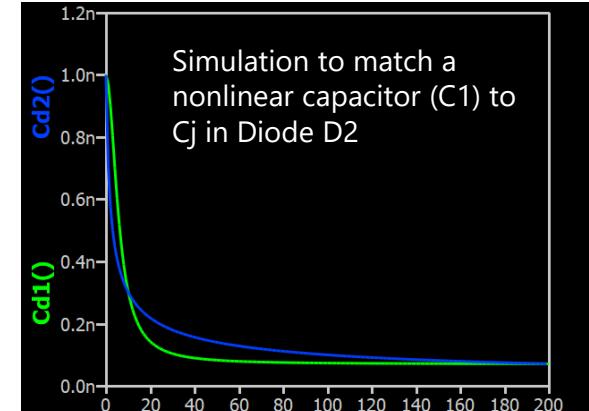
D. Diode Model (Reverse Current) : CJ

Qspice : Dmodel - CJ in Reverse Voltage.qsch / Dmodel - CJ in Reverse Current.qsch

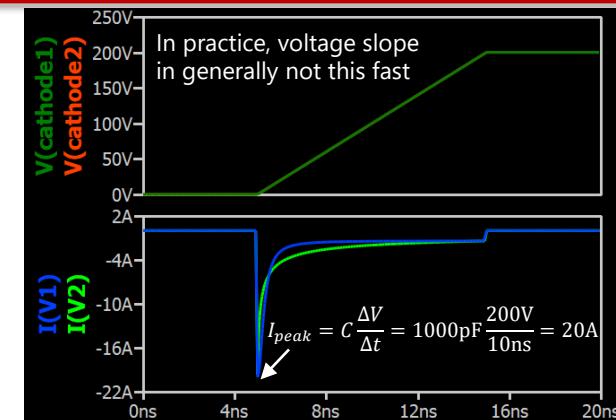
- C_j Explanation
 - Junction capacitance is in parallel to diode and its capacitance is a function of diode reverse voltage
- Simulation #1
 - C_j is nonlinear to diode reverse voltage, to model C_j, it requires use non-linear capacitor with C_{sat}, Satfrac and V_{sat}
- Simulation #2
 - Apply reverse voltage can simulate capacitor charging current, which act like reverse recovery but actually is not
 - Reverse recovery rely on forward current as reverse recovery is to remove this charge to turn off the diode
 - However, C_j is simply a mechanism that current charging a nonlinear capacitor



```
.ac list f      .param f=1Meg      .plot Cd1() Cd2()
.step param Vdc 0 200 1
.func imZD1() imag(V(drain)/I(Vd1))
.func imZD2() imag(V(drain)/I(Vd2))
.func Cd1() -1/2/pi/f/imZD1()
.func Cd2() -1/2/pi/f/imZD2()
```



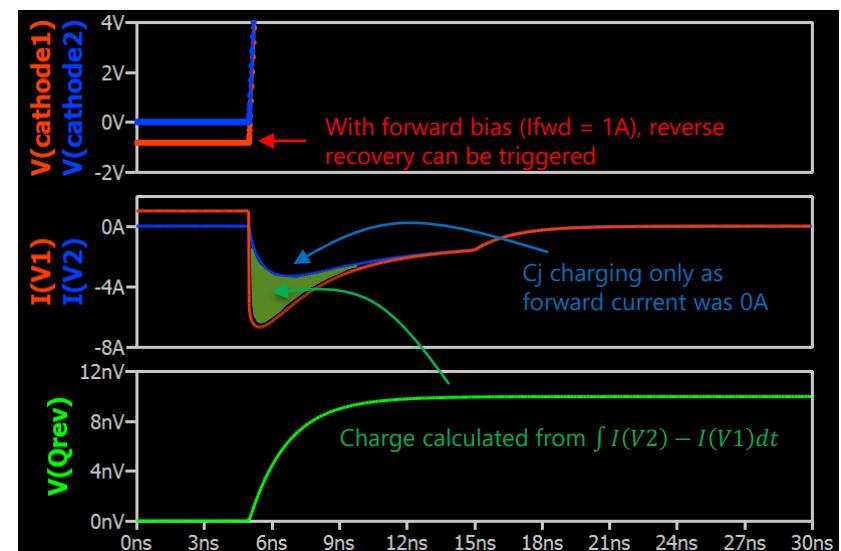
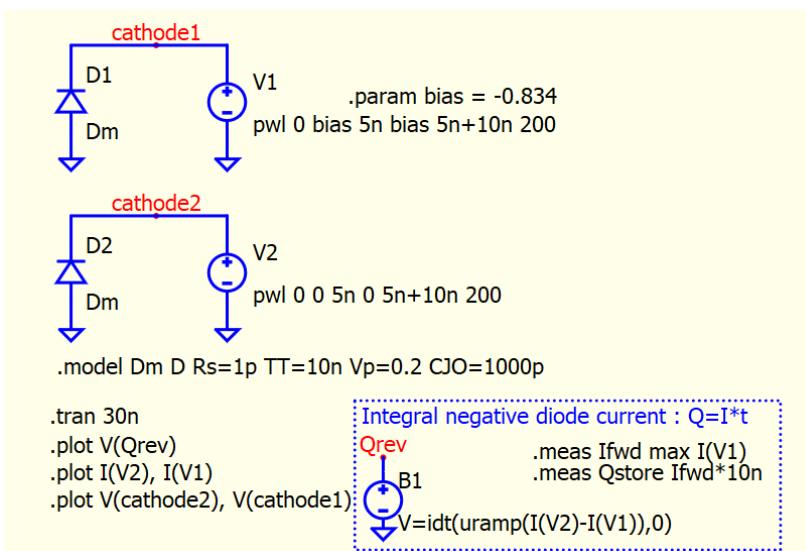
```
.tran 20n
.plot I(V2), I(V1)
.plot V(cathode2), V(cathode1)
.model Dm D Rs=1p TT=1p CJO=1000p
.model IdealD D Ron=1m Roff=1Meg Vfwd=0
```



Explanation of Reverse Recovery and Junction Capacitance Charging

Qspice : Dmodel - Reverse Recovery and Capacitor Charging.qsch

- Explanation of Reverse Recovery and Junction Capacitance Charging Current
 - Reverse Recovery is only preset if forward current is applied
 - If forward current is 0A, reverse current is by charging junction capacitance (C_j), and this is a nonlinear capacitance (capacitance decrease with cathode voltage) and therefore, reverse current reduce over time even ramp of cathode voltage is constant, where $I_d = C_j \frac{dV_d}{dt}$, where C_j is a function of V_d
 - If forward current is preset, reverse recovery is applied (TT and Vp). A extra portion of reverse current is generated and this extra charge equal $I_{fwd} \times TT$



PSPICE Static Model Params (Recombination) : IKF, ISR and NR

** Modeling of Recombination Current

- Semiconductor Device Modeling with SPICE (Section 1.9.1)

- $I_D = (K_{hli}I_F + K_{gen}I_R) - I_{Breakdown}$
 - $I_F = I_S \left(e^{\frac{qV_D}{nkT}} - 1 \right)$
 - I_S is IS : Saturation current (default = 1e-14A)
 - n is N : Emission coefficient (default = 1)
 - $K_{hli} = \sqrt{\frac{I_{KF}}{I_{KF} + I_F}}$ for $I_{KF} > 0$: If $I_{KF} \rightarrow \infty$, $K_{hli} = 1$
 - I_{KF} is IKF : High injection knee current (default = 1e308)
 - $I_R = I_{SR} \left(e^{\frac{qV_D}{n_R kT}} - 1 \right)$
 - I_{SR} is ISR : Recombination current parameter (default = 0A)
 - n_R is NR : ISR emission coefficient (default = 2)
 - $K_{gen} = \sqrt{\left[\left(1 - \frac{V_D}{\Phi_0} \right)^2 + 0.005 \right]^m}$
 - m is M : Grading coefficient (default = 0.5)
 - Φ_0 is VJ : Junction potential (default = 1V)
 - $I_{Breakdown} = IBV e^{-\frac{q(BV+V_D)}{kT}}$
 - IBV is IBV : Current at breakdown voltage (default = 1e-10A)
 - BV is BV : Reverse breakdown voltage (default = Infinite V)
 - This is equation to describe breakdown region. Reverse leakage is described in $(K_{hli}I_F + K_{gen}I_R)$

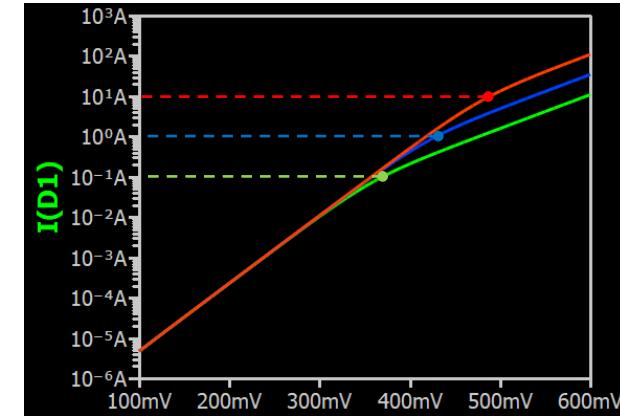
D. Diode Model (Recombination) : IKF

Dmodel - IKF.qsch

- IKF
 - IKF : High injection knee current
 - **Default IKF=1e308**
 - $I_D = (K_{hli}I_F + K_{gen}I_R)$
 - $I_D = K_{hli}I_F$
 - $K_{hli} = \sqrt{\frac{I_{KF}}{I_{KF} + I_F}}$ for $I_{KF} > 0$
 - The modification effect may only be easily observed with ID in log scale

```
.param Vmin = 0.1
.param Vmax = 0.6
.anode
V1 0 D1 Dm
.DC V1 {Vmin} {Vmax} 0.01
.PLOT I(D1)

.step param ikf list 0.1 1 10
.model Dm D Is=100n N=1 IKF={ikf}
```



D. Diode Model (Recombination) : ISR

Qspice : Dmodel - ISR.qsch

- ISR
 - Isr : Recombination current parameter
 - **Default ISR=0A**
 - $I_D = (K_{hli}I_F + K_{gen}I_R)$
 - In following examples, I_F is forced to be negligible as compare to $K_{gen}I_R$ in calculating I_D

$$\bullet I_D = K_{gen} I_{SR} \left(e^{\frac{qV_D}{n_R kT}} - 1 \right)$$

$$\bullet K_{gen} = \sqrt{\left[\left(1 - \frac{V_D}{\Phi_0} \right)^2 + 0.005 \right]^m}$$

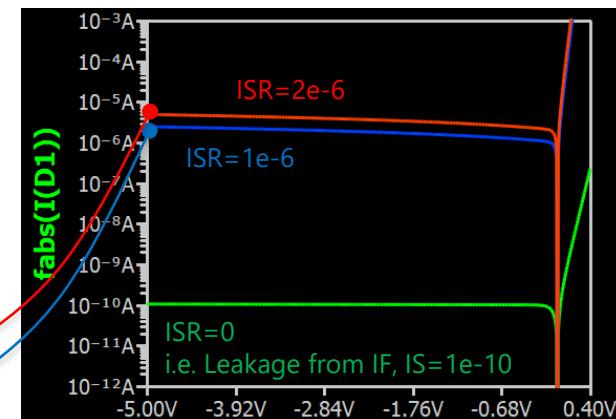
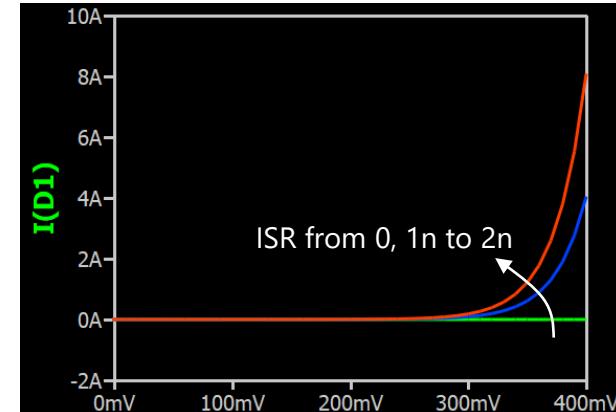
• n_R is NR : default = 2V

• m is M : default = 0.5

• Φ_0 is VJ : default = 1V

```
.param Vmin = -5
.param Vmax = 0.4
.anode
V1 0 D1
Dm
.dc V1 Vmin Vmax 0.01
.plot I(D1)
.step param isr list 0 1e-6 2e-6
.model Dm D Is=1e-10 N=2 ISR=isr NR=1
Is and N are set to equivalent with negligible If as
compare to Ir to demonstrate Ir effect
```

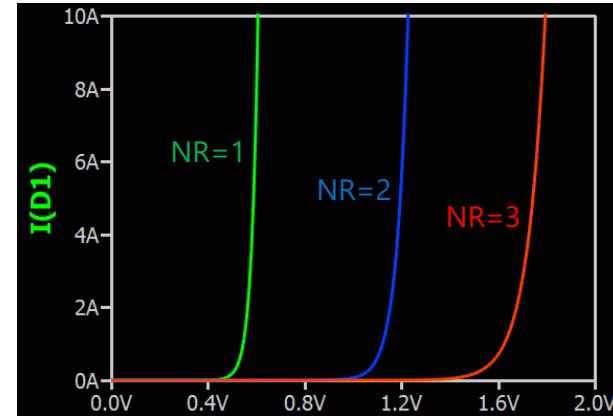
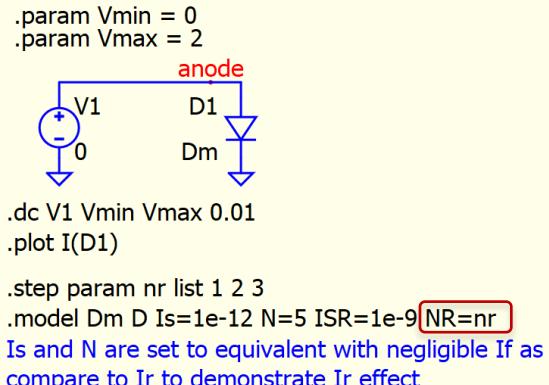
- Remark
 - As IS is set to 1e-12, in reverse and ISR=0, leakage current can still be observed through equation I_F
 - @ $V_D = -5V$
 - Therefore
 - ID for ISR=2e-6, $VD=-5$ is $4.8990\mu A$
 - ID for ISR=1e-6, $VD=-5$ is $2.4495\mu A$



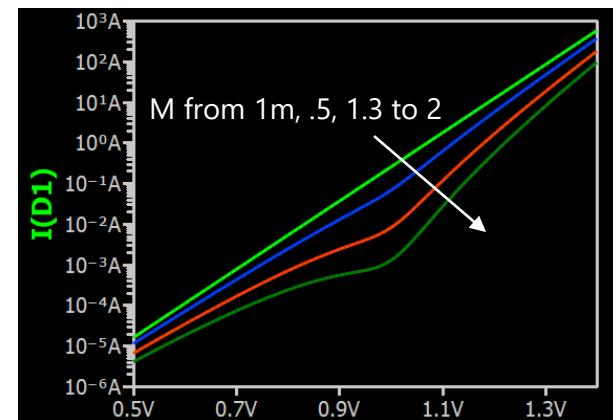
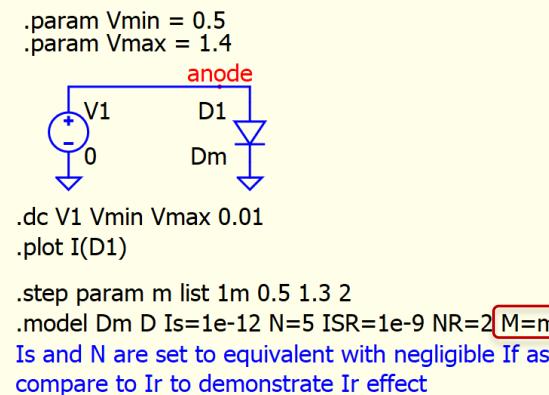
D. Diode Model (Recombination) : NR and M

Qspice : Dmodel - NR.qsch / Dmodel - M (Recombination).qsch

- NR
 - Nr : ISR emission coefficient
 - **Default NR=2**
 - $I_D = K_{gen} I_{SR} \left(e^{\frac{qV_D}{n_R kT}} - 1 \right)$



- M
 - M : Grading coefficient
 - **Default M=0.5**
 - $K_{gen} = \sqrt{\left[\left(1 - \frac{V_D}{\Phi_0} \right)^2 + 0.005 \right]^m}$
 - The modification effect may only be easily observed with ID in log scale

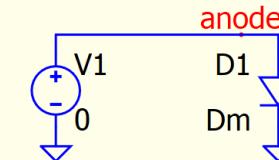


Textbook Diode Modeling

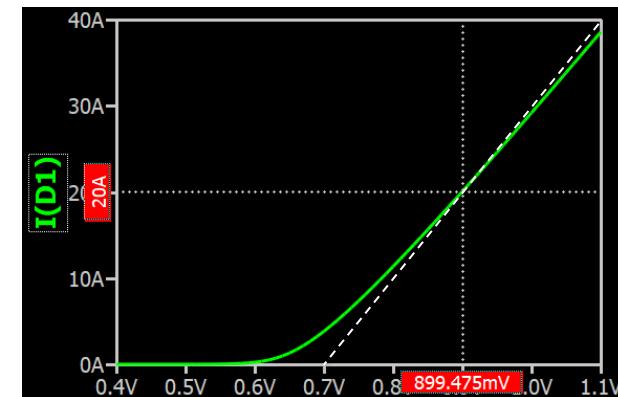
Qspice : Dmodel (Textbook).qsch

- Textbook Diode Modeling
 - $IS=1e-12$ to minimize leakage current when diode is OFF
 - $RS=\frac{\Delta V_D}{\Delta I_D}$ in the region that diode is ON
 - $N=\frac{VF-IF\times RS}{0.025865\times \ln\left(\frac{IF}{IS}\right)}$: IF is current at VF
- Assume textbook requirement is
 - Threshold = 0.7V and $\frac{\Delta I_D}{\Delta V_D} = 100A/V$
 - By $VF = \frac{IF}{\frac{\Delta I_D}{\Delta V_D}} + \text{Threshold}$
 - We use a higher IF to determine the curve,
 - @ IF=20A $\rightarrow VF = \frac{20A}{100A/V} + 0.7V = 0.9V$
 - Therefore
 - $IS=1e-12$
 - $RS=1/100=0.01$
 - $N=\frac{0.9-20\times 0.01}{0.025865\times \ln\left(\frac{20}{1e-12}\right)}=0.883$

```
.param Vmin = 0.4  
.param Vmax = 1.2
```



```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.model Dm D Is=1e-12 N=0.883 RS=0.01
```



D. Diode

Behavioral Diode Model Parameters

Behavioral Diode Model Parameters in Qspice HELP

QSPICE includes a simplified, behavioral, diode. To use those device equations, specify a non-zero RON.

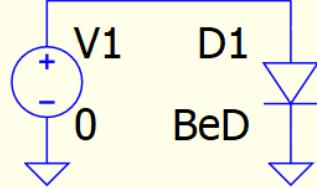
Behavioral Diode Model Parameters

Name	Description	Units	Default
RON	Forward on resistance	Ω	0.0^3
ROFF	Off resistance	Ω	$1./GMIN$
RZEN	Breakdown resistance(aka RREV)	Ω	RON
VFWD	Forward voltage drop	V	0.0
VREV	Reverse voltage drop	V	0.0
EPSILON	Width of quadratic region splining off and on regions	V	0.0
REVEPSILON	Width of quadratic region splining breakdown and on regions	V	0.0
CJO	Shunt capacitance	F	0.0

^{3]} The value of zero means don't use these equations, but the conventional SPICE semiconductor diode equations.

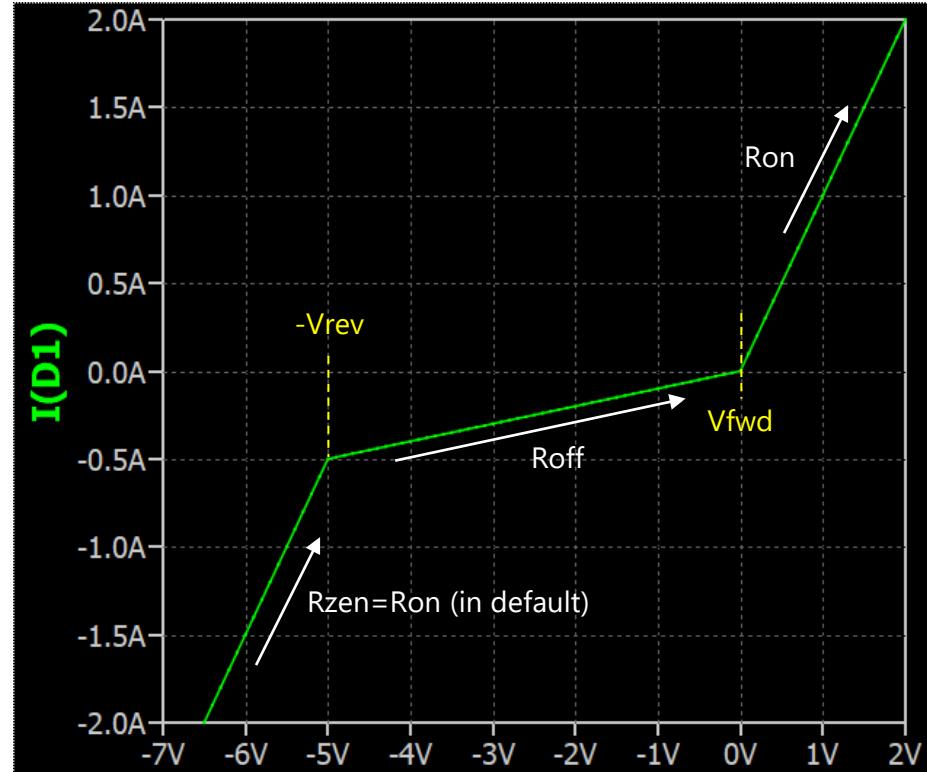
Behavioral Diode Model Params : Ron, Roff, Vfwd, Vrev

Qspice : Behavioral D Model - Ron Roff Vfwd Vrev.qsch



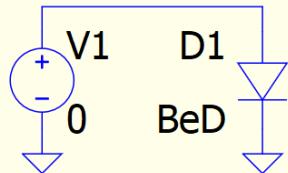
```
.model BeD D Ron=1 Roff=10 Vfwd=0 Vrev=5  
+ Epsilon=0 Revepsilon=0
```

```
.dc V1 -7 2 0.1  
.plot I(D1)
```



Behavioral Diode Model Params : Rzen, Epsilon, Revepsilon

Qspice : Behavioral D Model - Epsilon Revepsilon Rzen.qsch



```
.model BeD D Ron=1 Roff=10Meg Vfwd=0 Vrev=5  
+ Epsilon={val} Revepsilon={val} Rzen=0.5
```

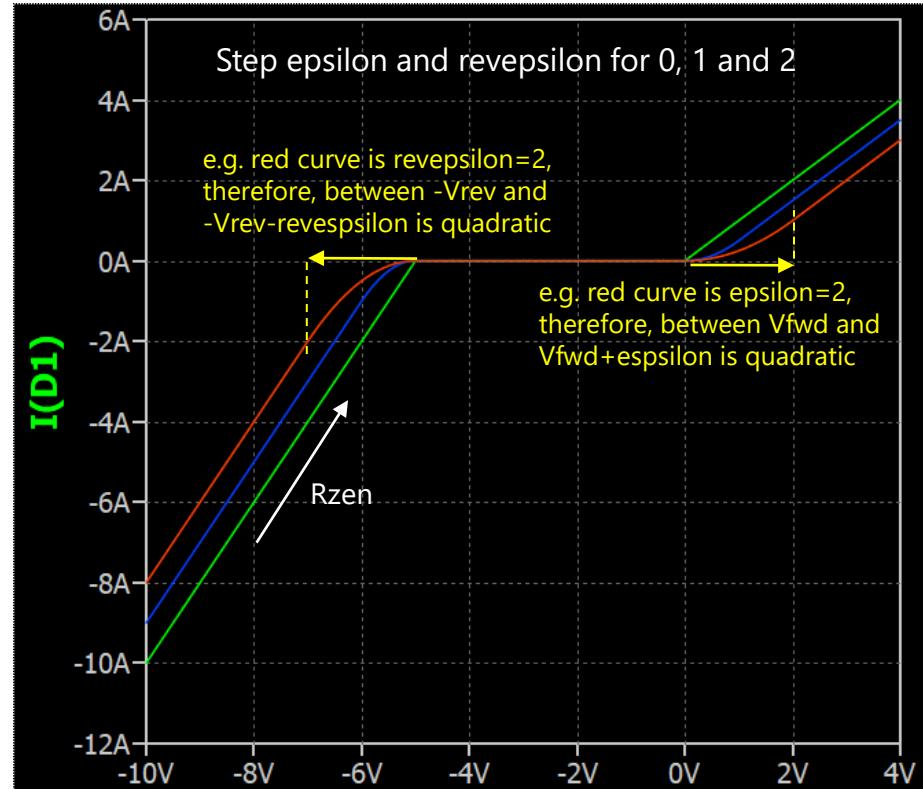
```
.dc V1 -10 4 0.1
```

```
.plot I(D1)
```

```
.param val=0
```

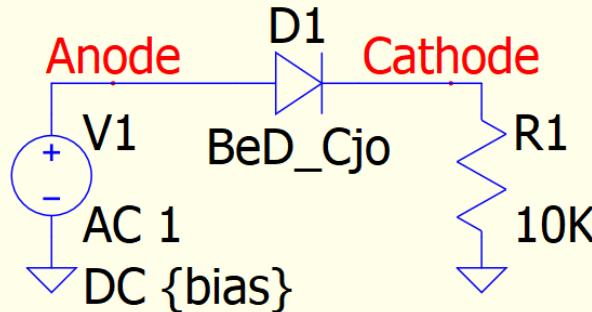
```
.step param val 0 2 1
```

* Roff change to 10Meg in this study



Behavioral Diode Model Params : Cjo

Qspice : Behavioral D Model - Cjo.qsch



```
.param bias = 0
```

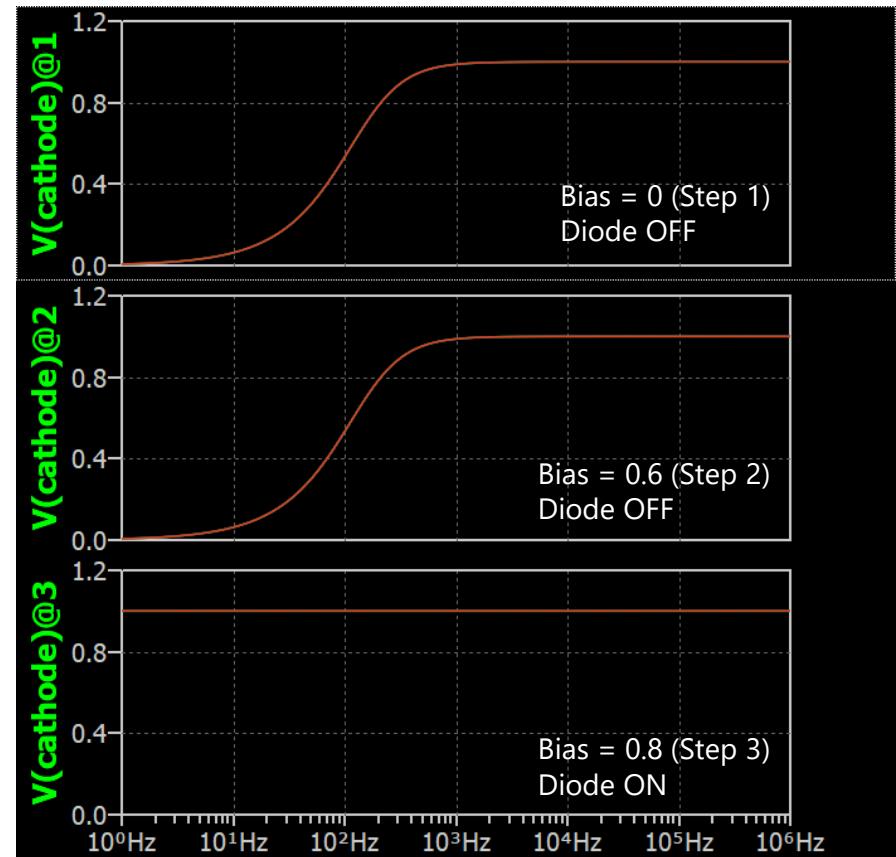
```
.model BeD_Cjo D Ron=1m Roff=1Meg
```

```
+ Vfwd=0.7 Cjo=100n
```

Cjo is equivalent to a capacitor parallel the behavioral diode

```
.ac dec 100 1 1Meg
```

```
.step param bias list 0 0.6 0.8
```



D. Diode Ideal Diode .model

Ideal Diode Model

Qspice : Special - IdealD (.dc).qsch / Special - IdealID (.tran).qsch

- Ideal Diode Characteristic
 - No breakdown current
 - No reverse leakage
 - No capacitance effect
 - No reverse recovery
- Ideal Model with Diode .model
 - .model Idlm D N=0.01 RS=10 μ ; Vf@1A=0
 - .model Idlm D N=0.36 RS=10 μ ; Vf@1A=0.3
 - .model Idlm D N=0.85 RS=10 μ ; Vf@1A=0.7
 - ** RS is added to prevent gmin stepping without series resistance
- Ideal Model with Behavioral Diode .model
 - .model IdealD D Vfwd=0 Ron=1m Roff=100Meg ; Vf,th=0
 - .model IdealD D Vfwd=0.3 Ron=1m Roff=100Meg ; Vf,th=0.3
 - .model IdealD D Vfwd=0.7 Ron=1m Roff=100Meg ; Vf,th=0.7

Diode Type

- Germanium
 - Bandgap : 0.67eV
- Silicon
 - Bandgap : 1.1eV
- Ultra-fast Recovery
- Silicon-Schottky
 - Bandgap : 0.69eV
- SiC-Schottky
 - Bandgap : 3.2eV
- GaN
 - Bandgap : 3.4eV
- Zener

E. F. G. H. Dependent Sources

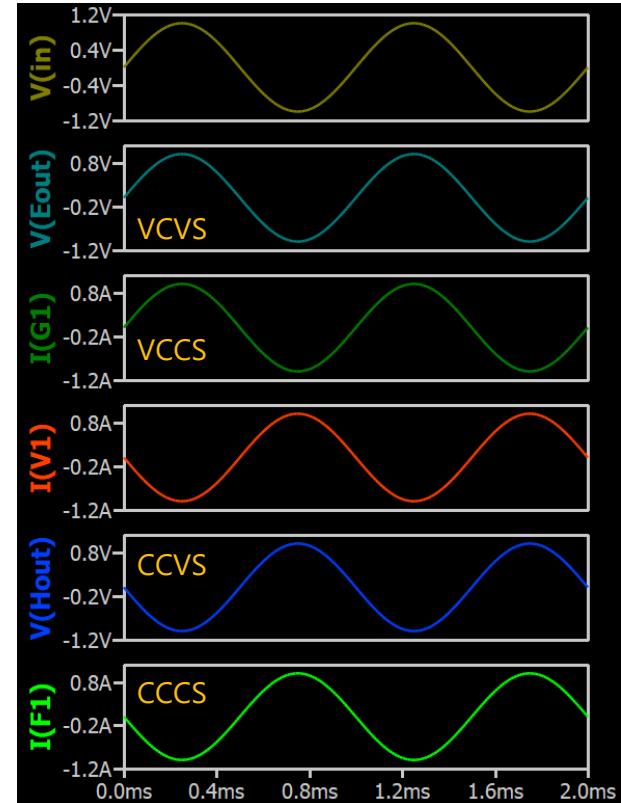
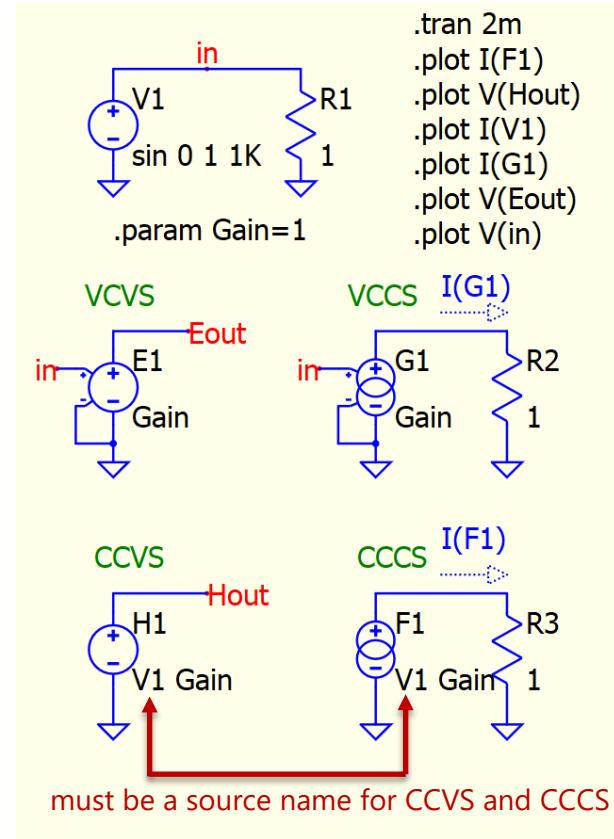
E. F. G. H. Dependent Sources

Qspice : Dependent Source - Basic.qsch

- Dependent Sources
 - [E] VCVS : Voltage Dependent Voltage Source
 - [G] VCCS : Voltage Dependent Current Source
 - [H] CCVS : Current Dependent Voltage Source
 - [F] CCCS : Current Dependent Current Source

- **** Current Dependent Src**

- For current dependent source, it current sense has to come from voltage source instead of current source
- A 0V voltage source can be used for current sensing
- (Explanation from Mike Engelhardt) Sensing the current in a current is complicated because it might have VSAT or VSAT2, meaning it's not a current source



I. Current Source

I. Current Source : Instance Parameters

Current Source Instance Parameters

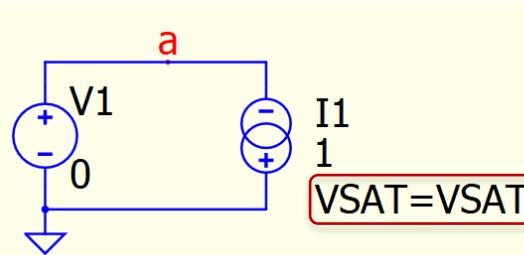
Name	Description	Units	Default
AC	AC magnitude, optionally followed by phase angle	A, °	0.
ACMAG	AC magnitude	A	0.
ACPHASE	AC phase	°	0.
DC	DC value of source	A	0.
EXP	Exponential source description		
LOG	Interpolate between PWL and CHIRP points		(not set)
PULSE	Pulse description		
PWL	Piecewise linear description		
SFFM	Single frequency FM description		
SINE	Sinusoidal source description(aka SIN)		
TIMECTRL	Time step control, one of NONE, LIMITS ¹ , BREAKS ² , or BOTH	String	LIMITS
VSAT ³	Don't source power(example)	V	0.
VSAT2	Don't source power and don't conduct in reverse	V	0.
XTRAP	Extrapolate beyond PWL and CHIRP points		(not set)

I. Instance Params : VSAT

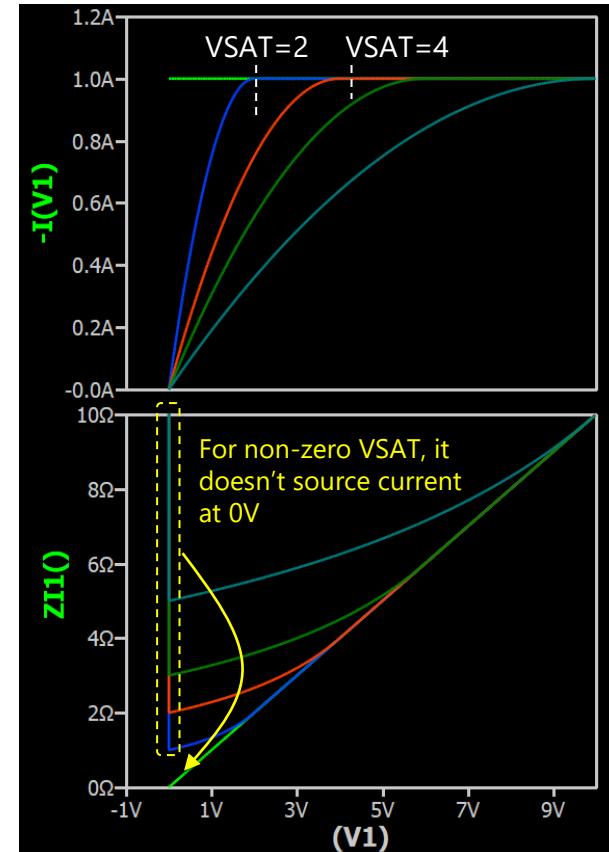
Qspice : I Source - VSAT.qsch

- VSAT

- VSAT : Don't source power
- Default VSAT=0V**
- Characteristic
 - Only source current when $V(-ve,+ve) > VSAT$
 - Current source doesn't source current at $V(-ve,+ve)=0$
 - Equivalent to Open
 - Not to apply negative voltage between $V(-ve,+ve)$ as it will have current flow out from -ve
- Usage
 - Useful for modeling an active load or a bias current in a macromodel



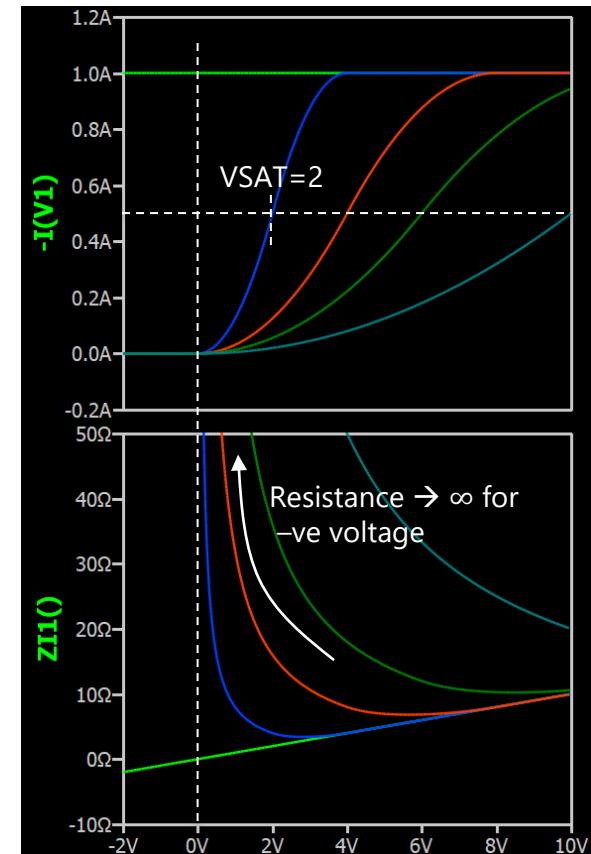
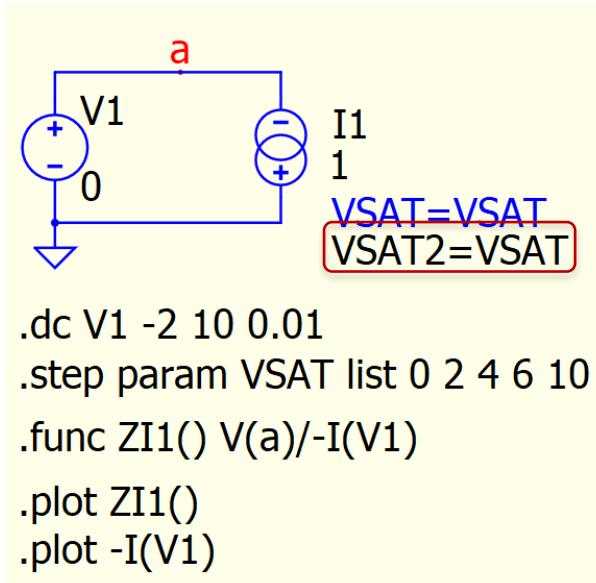
```
.dc V1 0 10 0.1  
.step param VSAT list 0 2 4 6 10  
.func ZI1() V(a)/-I(V1)  
.plot ZI1()  
.plot -I(V1)
```



I. Instance Params : VSAT2

Qspice : I Source - VSAT2.qsch

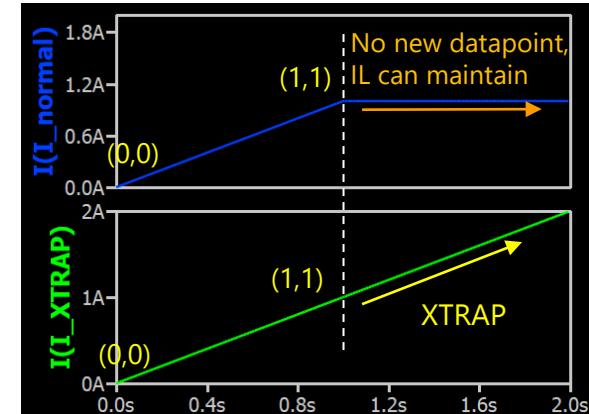
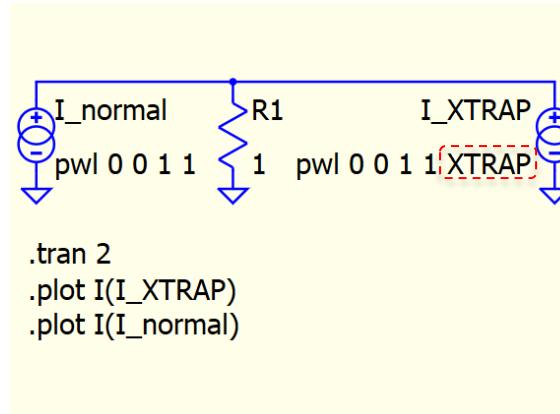
- VSAT2
 - VSAT2 : Don't source power and don't conduct in reverse
 - **Default VSAT2=0V**
 - If VSAT2 is used, VSAT will be override



I. Instance Params : XTRAP

Qspice : I Source - XTRAP.qsch

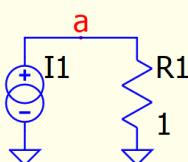
- XTRAP
 - Xtrap : Extrapolate beyond PWL and CHIRP points
 - **Default XTRAP is not set**
 - Without XTRAP, for times after the last time, the current is the last current.



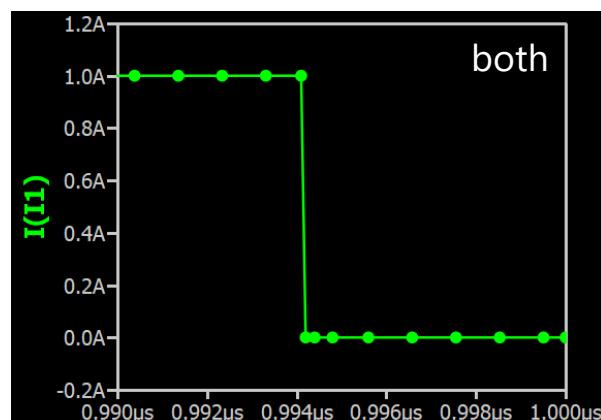
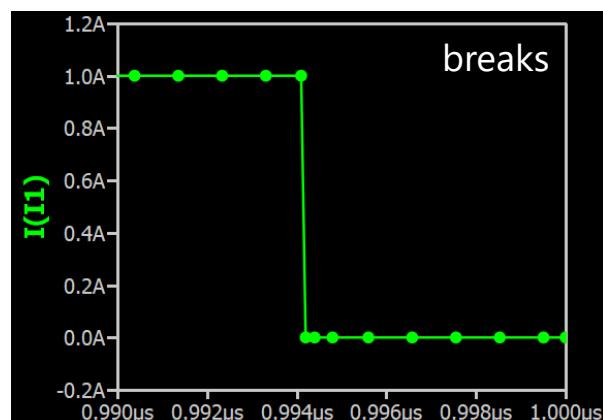
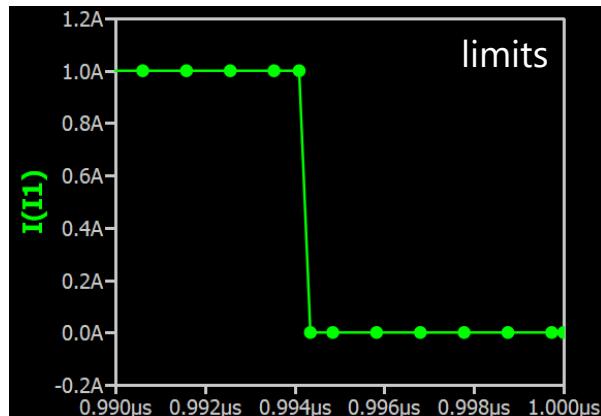
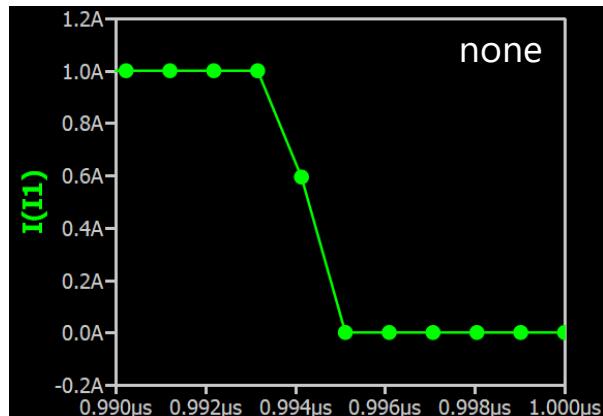
I. Instance Params : Timectrl

Qspice : I Source - TIMECTRL.qsch

- TIMECTRL
 - Timectrl : Time step control
 - None
 - Limits
 - Breaks
 - Both
 - **Default Timectrl=Limits**



```
pulse 0 1 4n 0 0 10n 20n  
Timectrl=none  
Timectrl=limits  
Timectrl=breaks  
Timectrl=both  
.tran 1000n  
.plot I(I1) I(I2)
```



J. JFET Transistor

J. JFET Model Parameters

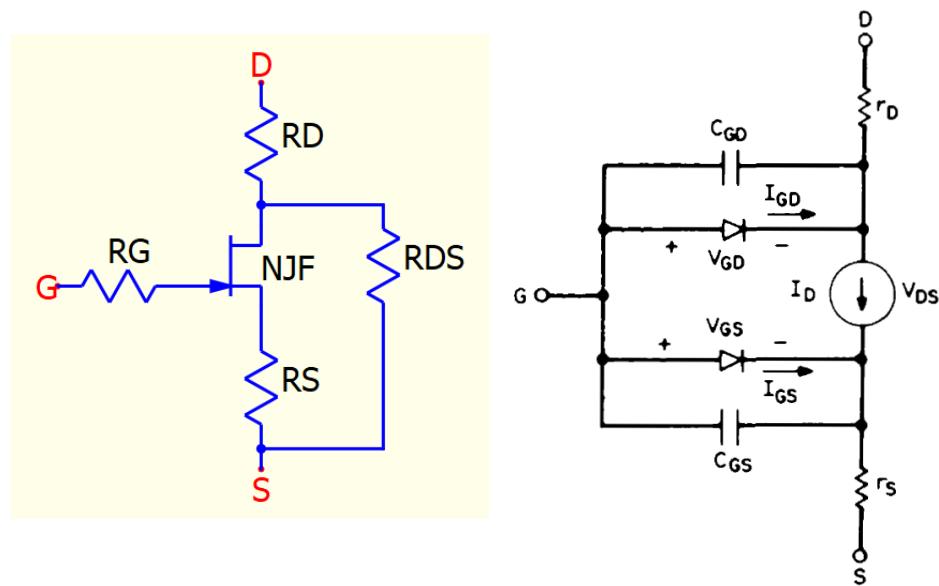
JFET Model Parameters

Name	Description	Units	Default
AF	Flicker noise exponent		1.0
ALPHA	Impact ionization coefficient	V ⁻¹	0.0
B	Doping tail parameter		0.0
BETA	Transconductance parameter	A/V ²	0.0001
BETATCE	Exponential transconductance parameter temperature coefficient	%/°C	0.0
CGD	Zero-bias G-D junction capacitance	F	0.0
CGDO	G-D overlap(i.e. constant) capacitance	F	0.0
CGS	Zero-bias G-S junction capacitance	F	0.0
CGSO	G-S overlap(i.e. constant) capacitance	F	0.0
ETA	Philips, et al.-style subthreshold conduction parameter		0.0
ETATC1	ETA first order tempco	°C ⁻¹	0.0
ETATC2	ETA second order tempco	°C ⁻²	0.0
FC	Forward bias junction fit parameter		0.5
GDSNOI	Shot noise coefficient for nlev = 3	A	2.0
GMAX	Maximum junction conductivity(straight line extension)	Ω	10K
IS	Junction saturation current	A	1e-14
ISR	Recombination current parameter	A	0.0
KF	Flicker Noise Coefficient		0.0
LAMBDA	Channel length modulation parameter	V ⁻¹	1.0
M	Grading coefficient(aka MJ)		0.5
N	Emission coefficient		1.0

NLEV	Noise level(equation selector)		0.0
NR	ISR emission coefficient		2.0
PB	Gate junction potential	V	1.0
RD	Drain resistance	Ω	0.0
RDTC1	RD first order tempco	°C ⁻¹	0.0
RDTC2	RD second order tempco	°C ⁻²	0.0
RDS	Additional Drain-Source leakage resistance	Ω	infinite
RDSTC1	RDS first order tempco	°C ⁻¹	0.0
RDSTC2	RDS second order tempco	°C ⁻²	0.0
RG	Gate resistance	Ω	0.0
RGTC1	RG first order tempco	°C ⁻¹	0.0
RGTC2	RG second order tempco	°C ⁻²	0.0
RONX	Channel conductivity multiplier in linear region ¹		1.0
RS	Source resistance	Ω	0.0
RSTC1	RS first order tempco	°C ⁻¹	0.0
RSTC2	RS second order tempco	°C ⁻²	0.0
TNOM	Parameter measurement temperature(aka TREF)	V	0.0
VK	Impact ionization knee current	V	0.0
VT0	Threshold Voltage(aka VTO or VT)	V	-2.0
VTOTC	Threshold Voltage temperature coefficient	°C ⁻¹	1.0
XTI	Saturation current temperature exponent		3.0

J. JFET Basic Equation

- JFET equation in Semiconductor Device Modeling with SPICE Section 3.1.3)
 - For channel pinched off : $V_{GS} - V_{T0} \leq 0$
 - $I_D = 0$
 - For saturated region : $0 \leq V_{GS} - V_{T0} \leq V_{DS}$
 - $I_D = \beta (V_{GS} - V_{T0})^2 (1 + \lambda V_{DS})$
 - For linear region : $0 < V_{DS} < V_{GS} - V_{T0}$
 - $I_D = \beta [2 (V_{GS} - V_{T0}) - V_{DS}] (1 + \lambda V_{DS})$

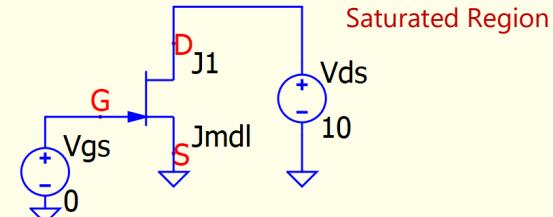


J. JFET Instance Params (I_D) : BETA and VTO

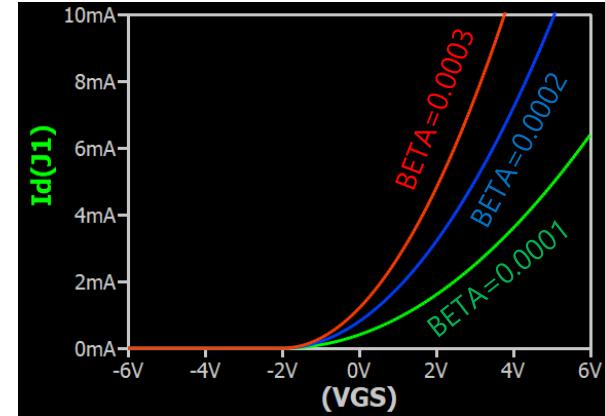
Qspice : JFET - Beta.qsch / JFET - VTO.qsch

- BETA

- Beta : Transconductance parameter
- Default BETA=0.0001A/V²**
- $I_D = \beta (V_{GS} - V_{T0})^2 (1 + \lambda V_{DS})$

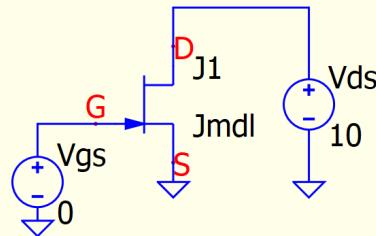


```
.dc Vgs -5 5 0.01  
.plot Id(J1)  
.step param beta list 0.0001 0.0002 0.0003  
.model Jmdl NJF BETA={beta}
```

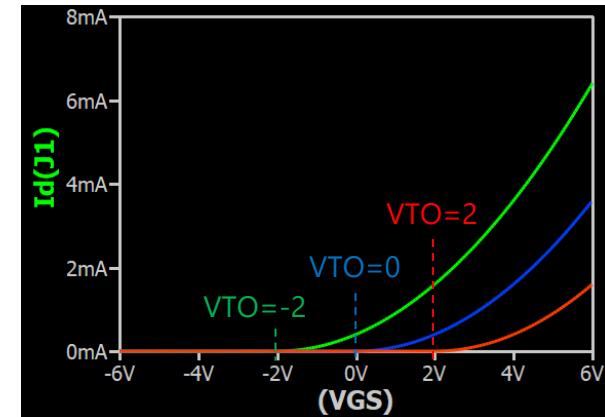


- VTO (aka VT0 or VT)

- VTO : Threshold Voltage
- Default VTO=-2V**
- $I_D = \beta (V_{GS} - V_{T0})^2 (1 + \lambda V_{DS})$



```
.dc Vgs -6 6 0.01  
.plot Id(J1)  
.step param vto list -2 0 2  
.model Jmdl NJF VTO={vto}
```

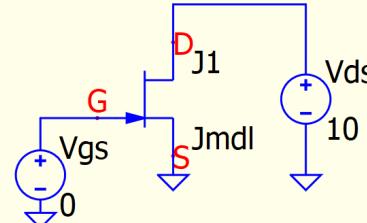


J. JFET Instance Params (I_D) : Lambda and Betatce

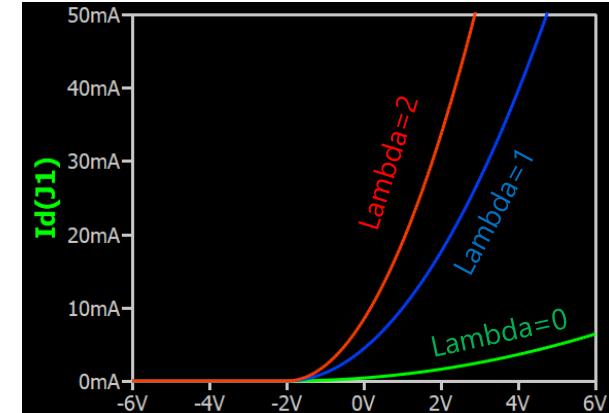
Qspice : JFET - LAMBDA.qsch / JFET - BETATCE.qsch

LAMBDA

- Lambda : Channel length modulation parameter
- **Default LAMBDA=0V⁻¹**
- $I_D = \beta (V_{GS} - V_{T0})^2 (1 + \lambda V_{DS})$

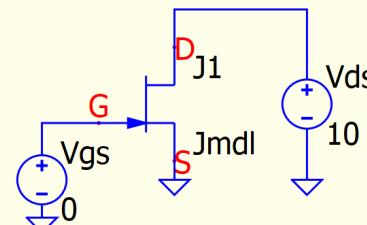


```
.dc Vgs -6 6 0.01  
.plot Id(J1)  
.step param lambda list 0 1 2  
.model Jmdl NJF LAMBDA={lambda}
```

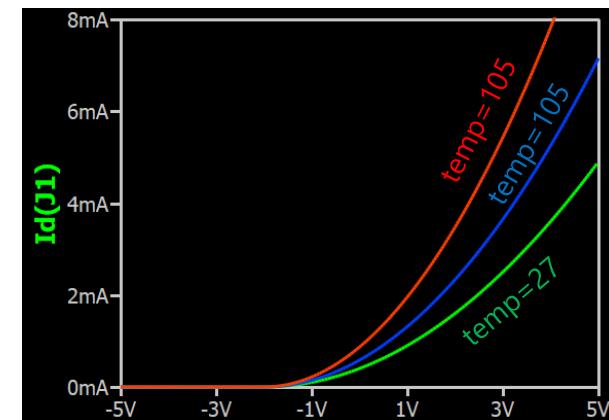


BETATCE

- Betatce : Exponential transconductance parameter temperature coefficient
- **Default BETATCE=0 (%/°C)**



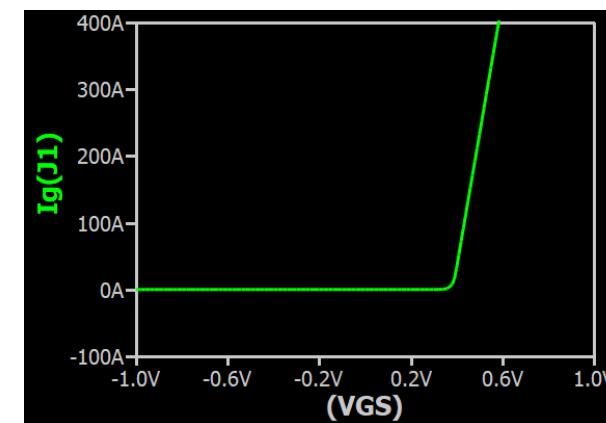
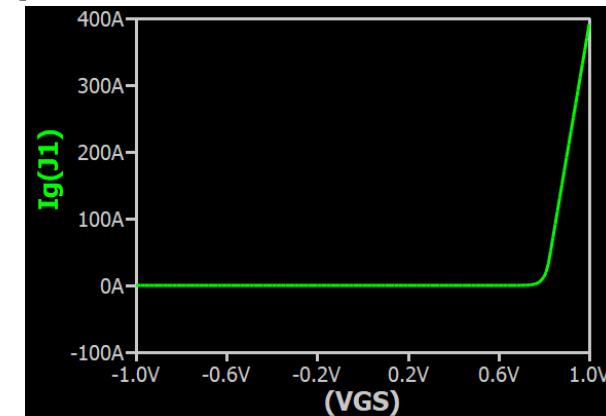
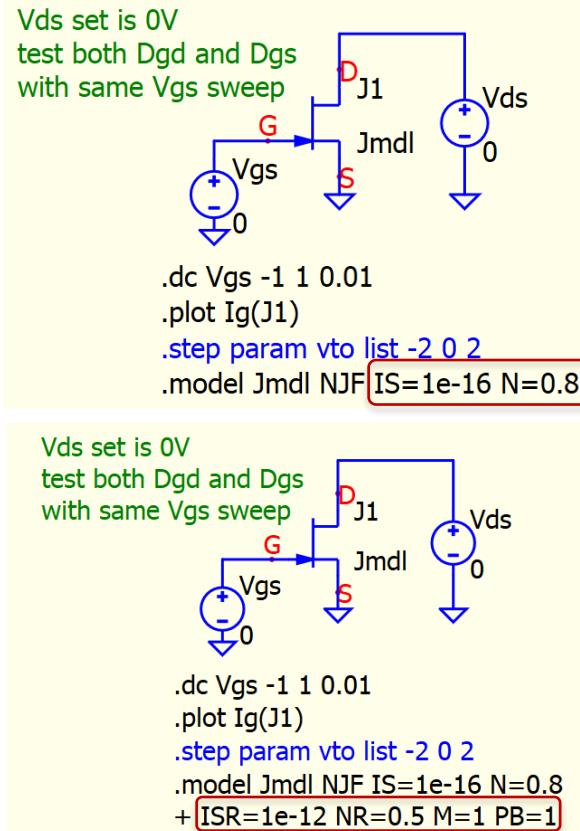
```
.dc Vgs -5 5 0.01 .temp 27 65 105  
.plot Id(J1)  
.param betatce=1  
.model Jmdl NJF BETATCE={betatce}
```



J. JFET Instance Params (Diode GD and GS) : IS, N, ISR, NR, M and PB

Qspice : JFET - IS N.qsch / JFET - ISR NR M PB.qsch

- Two diodes in JFET
 - DGD and DGS
 - These two diodes are identical model, with recombination current included
 - $I_{GS} = (I_F + K_{gen}I_R) + I_I$
 - $I_F = I_S (e^{\frac{qV_D}{nKT}} - 1)$
 - $I_R = I_{SR} (e^{\frac{qV_D}{n_RKT}} - 1)$
 - $K_{gen} = \sqrt{\left[\left(1 - \frac{V_D}{\Phi_0} \right)^2 + 0.005 \right]^m}$
 - I_S : IS Junction saturation current (Default IS=1e-14A)
 - n : N emission coefficient (Default N=1)
 - I_{SR} : ISR Recombination current parameter (Default ISR=0A)
 - n_R : ISR emission coefficient (Default NR=1)
 - m : M Grading coefficient (Default M=0.5)
 - Φ_0 : PB Gate junction potential (Default PB=1V)
- Diode modeling refer to D. Diode section



J. JFET Instance Params (Diode GS) : Alpha and VK

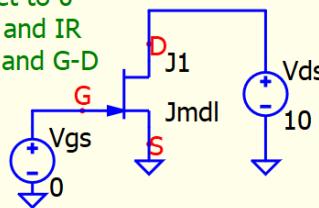
Qspice : JFET - ALPHA VK.qsch

- Gate Source Diode in Pspice model

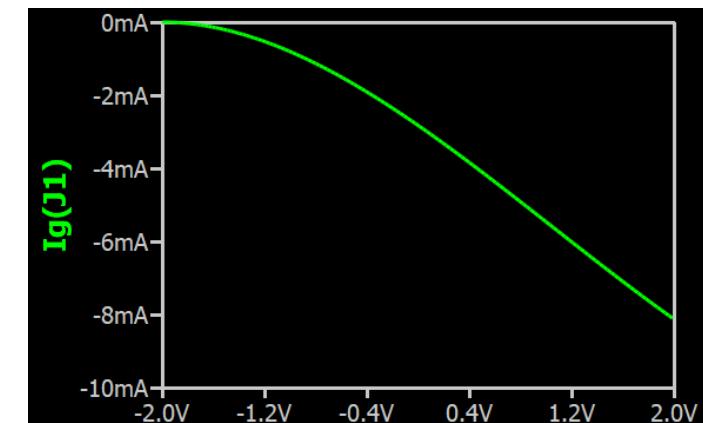
$$I_{GS} = (I_F + K_{gen} I_R) + I_I$$

- $I_I = \alpha I_D [V_{DS} - (V_{GS} - V_{TO})] e^{\frac{V_k}{V_{DS} - (V_{GS} - V_{TO})}}$ for $0 < G_{GS} - V_{TO} < V_{DS}$
- $I_I = 0$ otherwise
- α is ALPHA Impact ionization coefficient (Default ALPHA=0V⁻¹)
- V_k is VK Impact ionization knee current (Default VK=0V)

IS and ISR set to 0
to disable IF and IR
in diode G-S and G-D



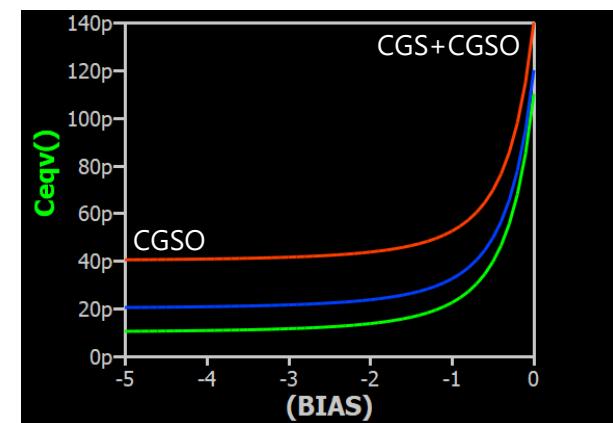
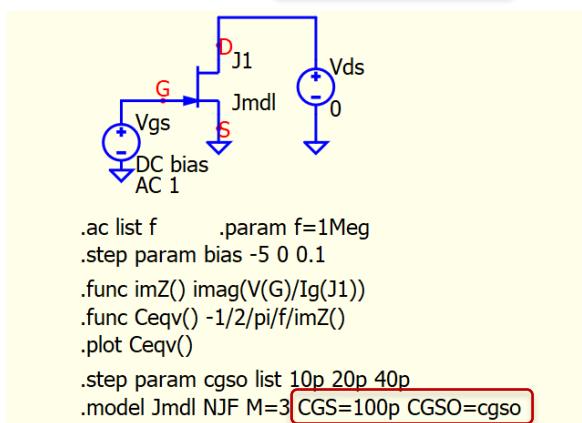
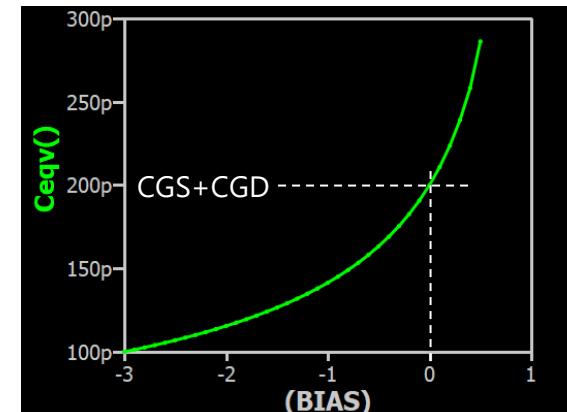
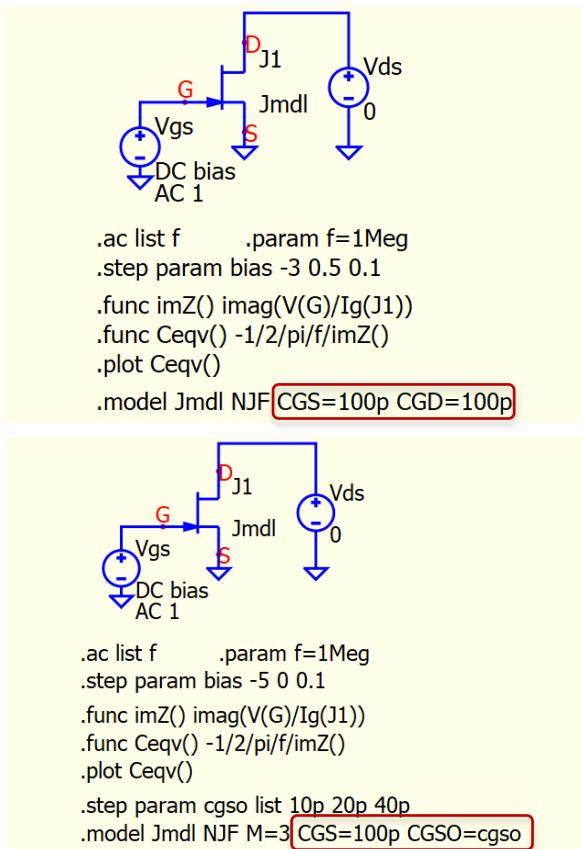
```
.dc Vgs -2 2 0.01
.plot Ig(J1)
.step param vto list -2 0 2
.model Jmdl NJF IS=0 ISR=0
+ALPHA=1 VK=1
```



J. JFET Instance Params (Capacitance) : CGS, CGD, CGSO, CDSO

Qspice : JFET - CGS CGD.qsch / JFET - CGSO CGDO.qsch

- CGS, CGD
 - CGS : Zero-bias G-D junction capacitance
 - CGD : Zero-bias G-S junction capacitance
 - **Default CGS=0F**
 - **Default CGD=0F**
 - This example simulate with both CGS and CGD
- CGSO, CDSO
 - CGSO : G-S overlap capacitance
 - CDSO : D-S overlap capacitance
 - **Default CGSO=0F**
 - **Default CDSO=0F**
 - This example only simulate CGS with CGSO. GDSO has same effect but to affect CDSO
 - ** M, PB, FC has effect in junction capacitance, refer to D. diode



K. Mutual Inductance

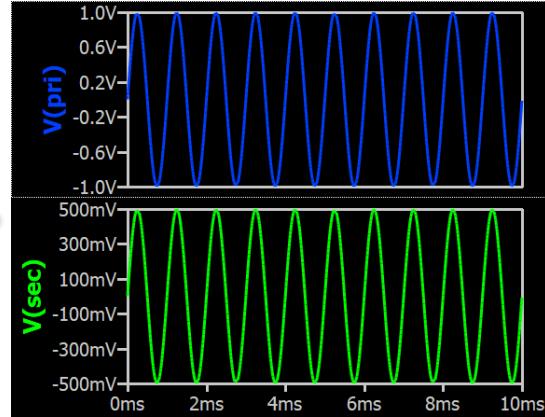
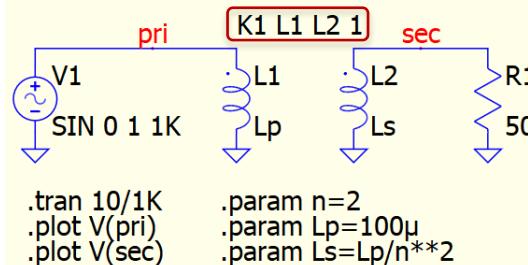
K. Mutual Inductance

Qspice : K Mutual - Two Winding.qsch / K Mutual - Three Winding.qsch

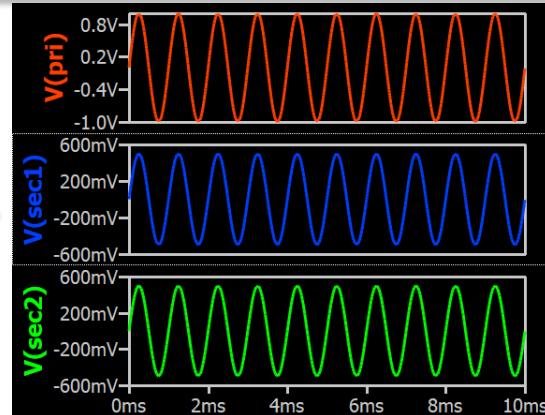
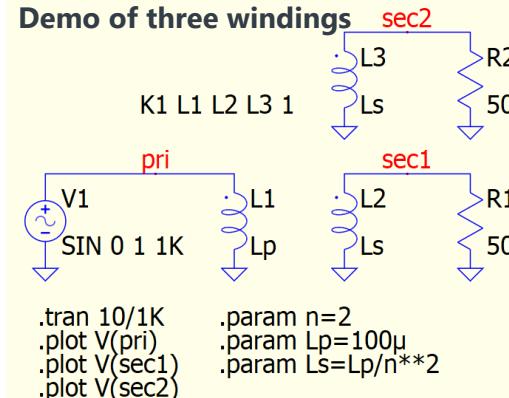
- K Mutual Inductance
 - K : coupling coefficient of coupled inductors
 - Ideal coupling : 1
 - Range : -1 to 1
 - Two or more coupled inductors are required
 - Press L two times to get symbol with a dot notation (not necessary, but recommend for current direction)

- Inductors as Transformer
 - $\frac{L_p}{N_p^2} = \frac{L_s}{N_s^2}$ and $n = \frac{N_p}{N_s}$
 - N is number of turns
 - $L_p = n^2 L_s$ or $L_s = \frac{1}{n^2} L_p$
 - In practice, L_p is measured from primary with secondary open

Demo of two windings



Demo of three windings



L. Inductor

Inductor L Instance Parameters in Qspice HELP

Inductor Instance Parameters

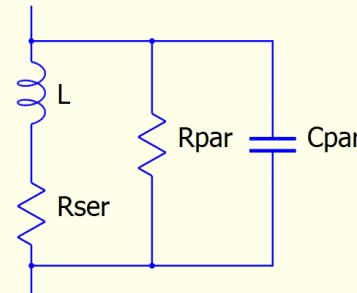
Name	Description	Units	Default
AG	Wire or stripline is made of gold		
AL	Wire or stripline is made of aluminum		see below
AU	Wire or stripline is made of silver		
BEND	Fractional inductance correction for wire bend or proximity effects		1.
CPAR	Parallel capacitance	F	0.
CU	Wire or stripline is made of copper		see below
DIAMETER	Diameter of wire or air coil	m	
FREQUENCY	Frequency at Q. Also used to compute Rser due to skin effect		
HEIGHT	Height of PCB stripline above ground plane	m	
IC	Initial current if uic is specified on .tran statement	A	none
INDUCTANCE	Inductance of inductor	H	0.0
ISAT	Current causing inductance to drop to SATFRAC×INDUCTANCE	A	Infinite
LENGTH	Length of wire, stripline, or air coil	m	
LSAT	Inductance asymptotically approached in saturation	H	10% of INDUCTANCE
M	Number of parallel inductors		1.0
NI	Wire is made of nickel		
Q	Quality factor at FREQUENCY		
RPAR	Equivalent parallel resistance	Ω	Infinite
RSER	Equivalent series resistance	Ω	0.0
SATFRAC	Fractional drop in inductance at ISAT		0.7
THICK	Thickness of stripline on top of a PCB	m	0.0
TURNS	Number of turns of an air coil		
VERBOSE	Print wire L, Rser, Rpar results on the console		(not set)
WIDTH	Width of stripline on top of a PCB	m	

Arbitrary Inductance Device

QSPICE also supports an arbitrary inductance device. To use it, give an equation for the flux due to the inductor. The equation can include any circuit node voltages or device currents of devices modeled as Thévenin equivalents(V-, L-, E-, or H-devices). In the interest of completeness, the device supports transinductance.

Syntax: Cnnn N1 N2 Q=<expression> [additional instance parameters]

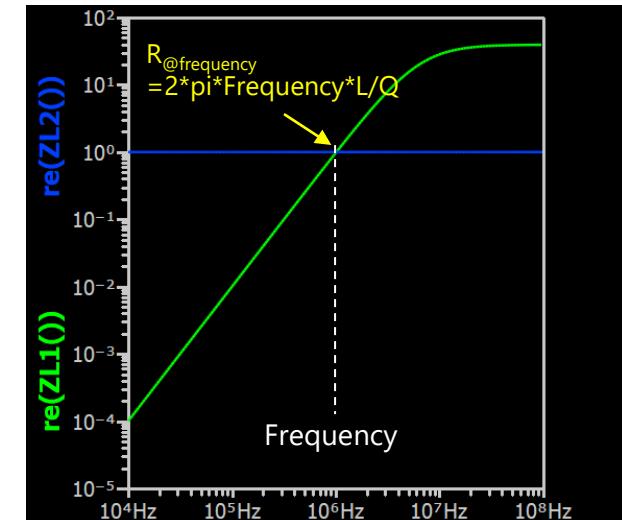
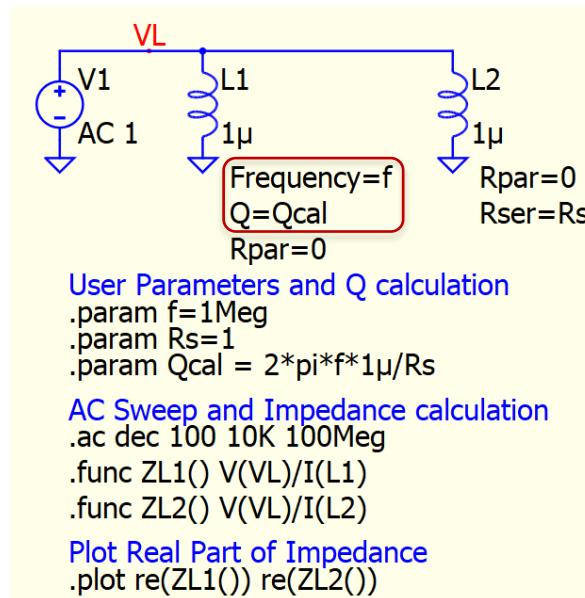
Name	Description	Units	Default
FLUX	Equation of flux(aka F)	Weber	
IC	Initial flux due to the inductor	Weber	
M	Number of identical parallel devices		1.0
RPAR	Equivalent parallel resistance	Ω	Infinite
RSER	Equivalent series resistance	Ω	0.0
NOISELESS	Ignore the noise contribution from RPAR and RSER		not set
TEMP	Instance temperature	°C	Circuit temperature



L. Instance Params : Frequency and Q

Qspice : Inductor - Frequency Q.qsch

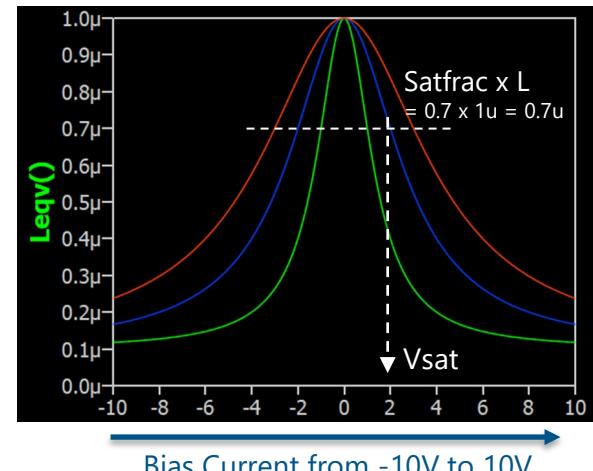
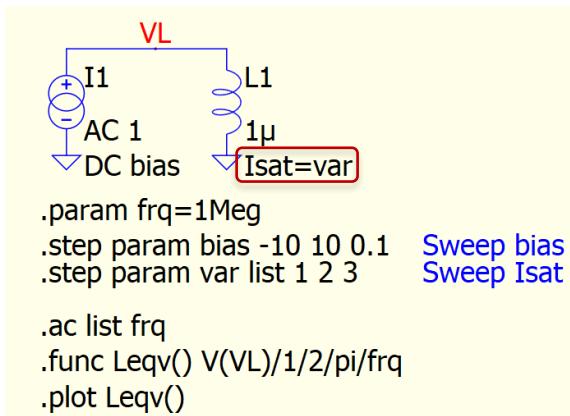
- Frequency and Q
 - Frequency : Frequency at Q
 - Also used to compute Rser due to skin effect
 - Q : Quality factor at FREQUENCY
- Formula
 - $Q = \frac{X_L}{R} = \frac{2\pi f L}{R_{@f}}$
 - Using Frequency and Q is not same as using Rser modeling
 - Rser is a constant over frequency but Frequency/Q pair give Rser with skin effect



L. Instance Params : Isat, Lsat, Satfrac : For Nonlinear Inductance

Qspice : L Inductor - Isat (.ac).qsch

- Isat and Satfrac
 - Isat : Current that drops inductance to **Satfrac x Inductance**
 - Satfrac : Fractional drop in inductance at Isat
 - **Default ISAT=Infinite (A)**
 - **Default SATFRAC=0.7**
 - Nonlinear effect is valid in +ve and -ve current direction

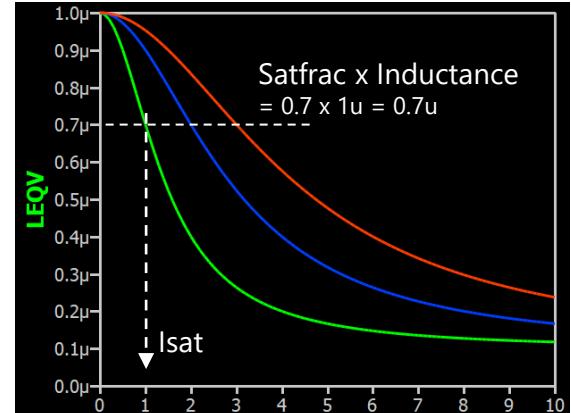
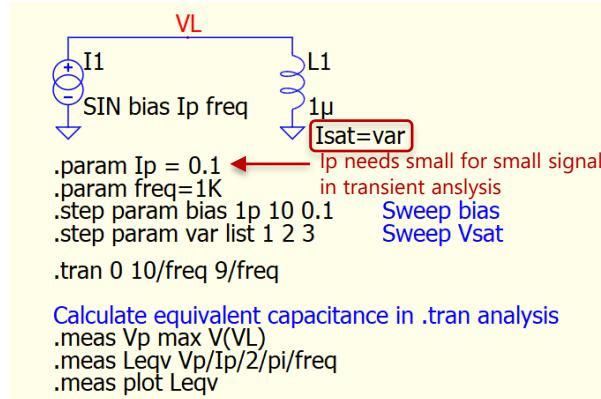


- Inductance equation
 - $X_L = \omega L = \frac{V_L}{I_L}$
 - $L = \frac{|V_L|}{|I_L|} \frac{1}{\omega} = \frac{|V_L|}{2\pi f |I_L|}$
 - This formula is used to calculate equivalent inductance (small signal model) at different inductor bias current

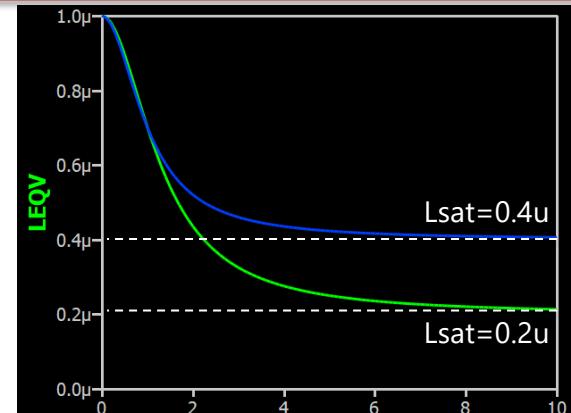
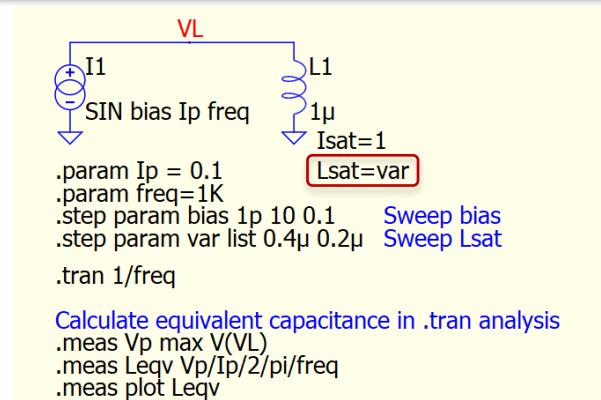
L. Instance Params : Isat, Lsat, Satfrac : For Nonlinear Inductance

Qspice : L Inductor - Isat (.tran).qsch / L Inductor - Lsat (.tran).qsch

- Isat and Satfrac
 - **Isat** : Current that drops inductance to **Satfrac x Inductance**
 - **Satfrac** : Fractional drop in inductance at Isat
 - **Default ISAT=Infinite (A)**
 - **Default SATFRAC=0.7**



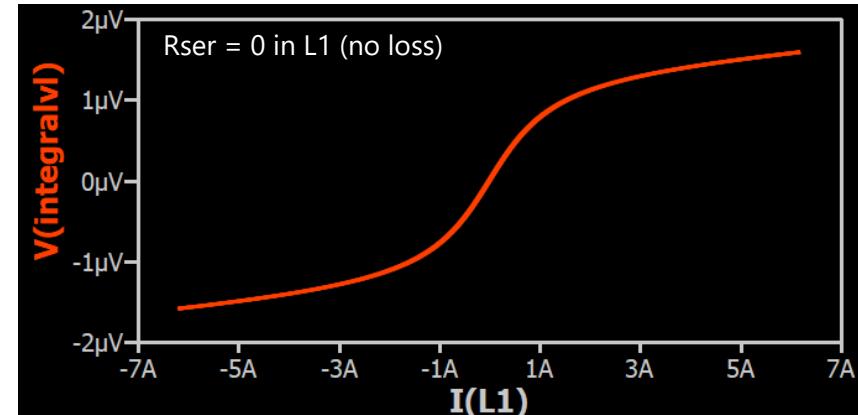
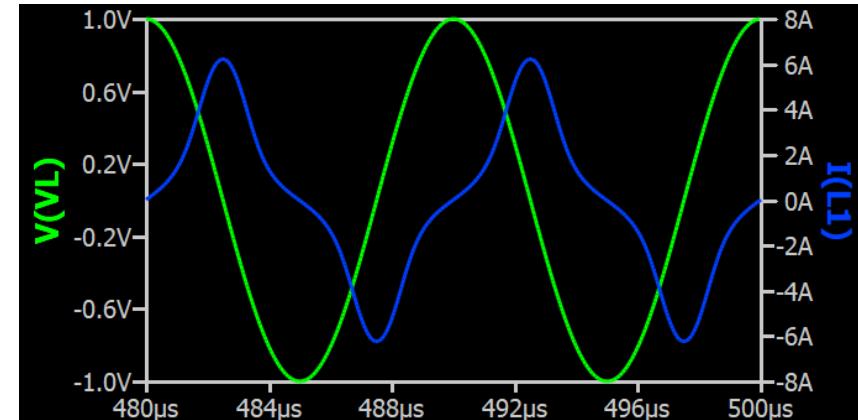
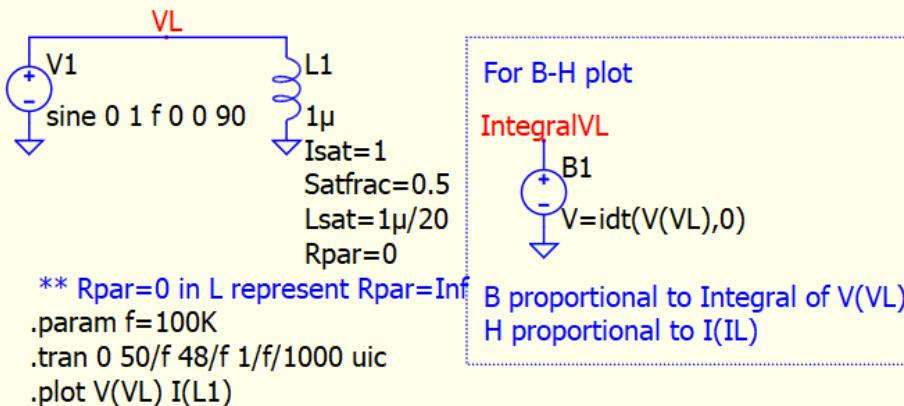
- Lsat
 - **Lsat** : Inductance asymptotically approached in saturation
 - ** Lsat must be set to see its effect
 - **Default LSAT=10% of L**



Demonstration of Nonlinear Inductor (model B-H saturation)

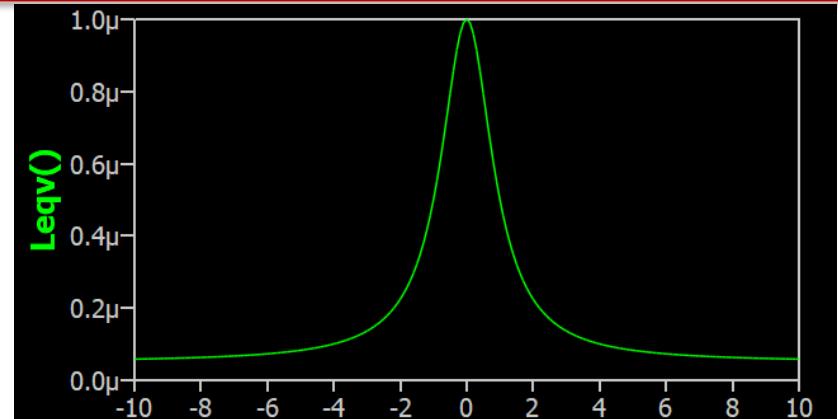
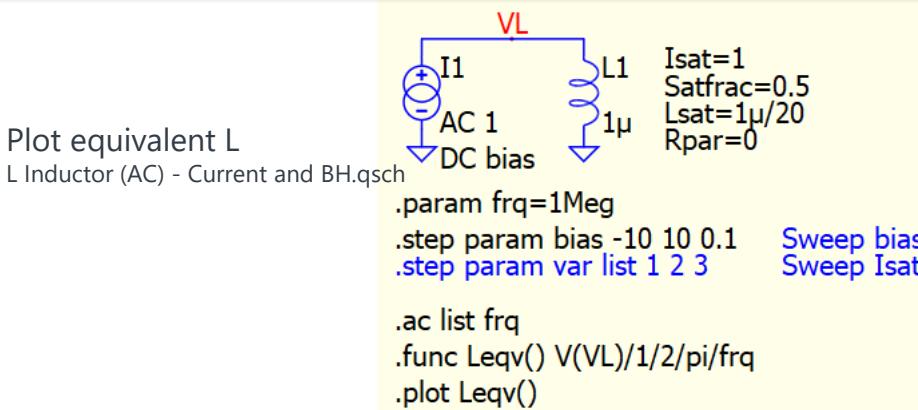
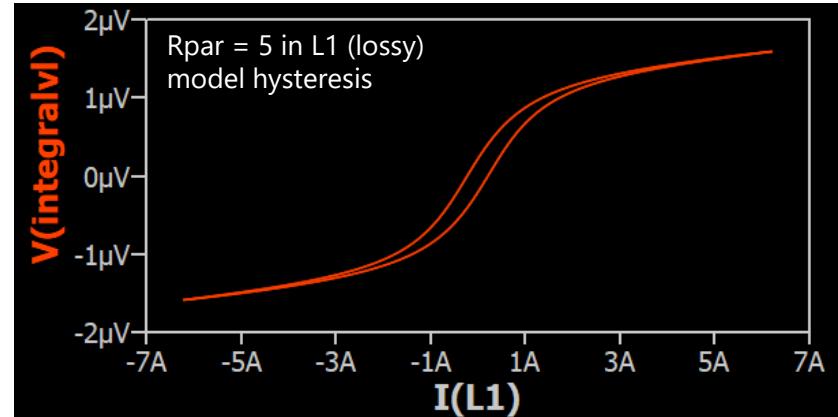
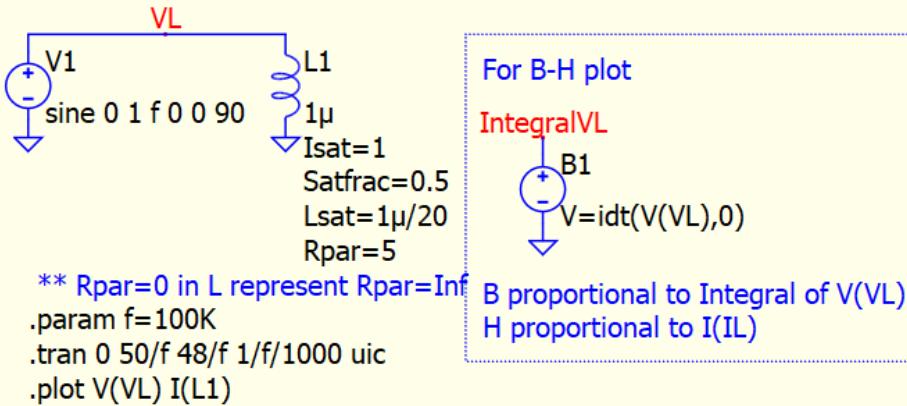
Qspice : L Inductor Nonlinear (Tran) - Current and BH.qsch

- Nonlinear Inductor in Qspice
 - This simulation demonstrate transient of non-linear inductor with a sinusoidal voltage source, which can expect a non-linear current
- Reference : B and H for inductor
 - Magnetic field intensity $H = \frac{B}{\mu} = \frac{N}{l_e} i_L$ (unit : A/m)
 - Magnetic field strength $B = \frac{\phi_B}{A_e} = \frac{1}{N A_e} \int v_L dt$ (unit : Tesla)
 - B also called magnetic flux density



Demonstration of Nonlinear Inductor (model B-H hysteresis : lossy)

Qspice : L Inductor Nonlinear (Tran) - Current and BH.qsch



Comment about Saturation and Hysteresis of B-H curve

Isat, Lsat and Satfrac are key parameters in Qspice for non-linear inductance modeling. General interest is just a saturating include. This represents inductor saturating when current reach certain level (i.e. inductance drop according to current, which can model by Isat, Lsat and Satfrac). This characteristic is saturation in B-H curve.

For hysteresis of B-H curve, it can generally model with a parallel resistor Rpar to represent loss.

May be some people prefer to model non-linear inductor with other way, but I found Qspice definition generally good enough as L vs bias current can be easily measure practically.

L. Arbitrary Inductance : Inductor modeling with FLUX

Qspice : Flux formula.qsch

- Basic equation of Inductor

- [equation 1] : Voltage v_L and Flux ϕ Relationship : $v_L = \frac{d\phi}{dt}$
- [equation 2] : Voltage v_L and Current i_L Relationship : $v_L = L \frac{di_L}{dt}$
- Therefore, by $\frac{d\phi}{dt} = L \frac{di_L}{dt}$, **Inductor $L = \frac{d\phi}{di_L}$**

- Qspice inductor modeling with Flux ϕ

- For linear inductor, $\frac{d\phi}{di_L}$ is constant $\rightarrow \phi = L i_L$

- Therefore, $L = \frac{\phi}{i_L}$

- In Qspice : $\text{flux} = L * I(L1)$, where L1 is inductor name

- For nonlinear inductor, ϕ can be approximate by $\phi = a \tanh(b i_L)$

- Therefore, $L = \frac{d\phi}{di_L} = \frac{d a \tanh(b i_L)}{di_L} = a b (1 - \tanh^2(b i_L))$

-

- In Qspice : $\text{flux} = a * \tanh(b * I(L1))$

- L0A @ 0A = $a * b$

- b determines the spread

- If $b i_L$ is large, $(1 - \tanh^2(b i_L)) = 0$, therefore, this formula will give 0H inductance when i_L is large

- It can combine nonlinear and linear to handle 0H inductance when i_L is large

- In Qspice : $\text{flux} = a * \tanh(b * I(Ln)) + Lmin * I(Ln)$

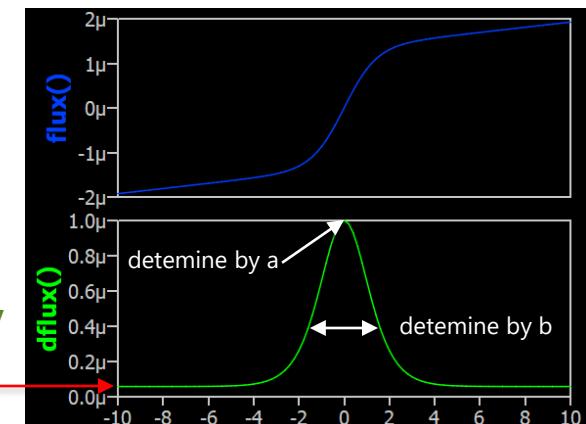
- L0A @ $i_L = 0$: $a * b - Lmin$

- $Lmin @ i_L = \infty$: $Lmin$

- b determines the spread

Assum flux formula is $a * \tanh(b * IL) + Lmin * IL$

```
.param b = 0.7
.param L0A = 1μ
.param a = (L0A-Lmin)/b
.param Lmin=58n
.func flux() a*tanh(b*IL)+Lmin*IL
Calculate dflux/dIL
.func dflux() D(flux())
Sweep IL from -10A to 10A
.step param IL -10 10 0.2
.op
.plot dflux()
.plot flux()
```



$$\text{dflux}(i_L) = L_{eqv}$$

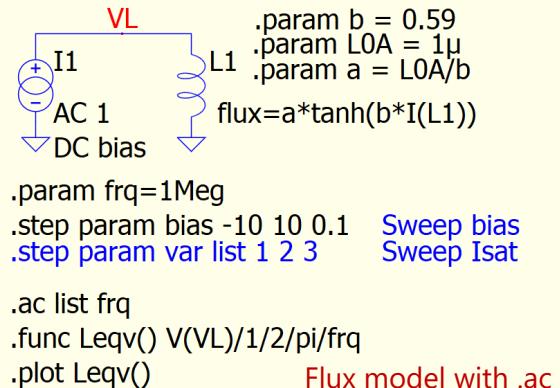
determine by $Lmin$

L. Arbitrary Inductance : Inductor modeling with FLUX

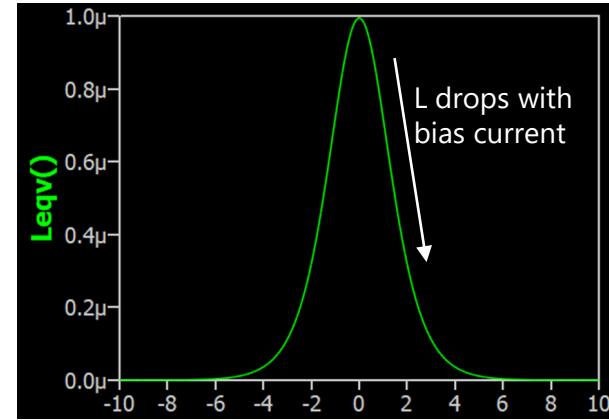
Qspice : L Inductor (AC) - Flux eqn 1.qsch ; L Inductor Nonlinear (Tran) - Flux eqn 1.qsch

- Flux model

- .ac is used to calculate inductance and bias current relationship
- .tran is used to demonstrate non-linear inductor current and proportional B-H curve
- Flux equation uses format
 - Flux = $a \tanh(b \cdot I(L1))$

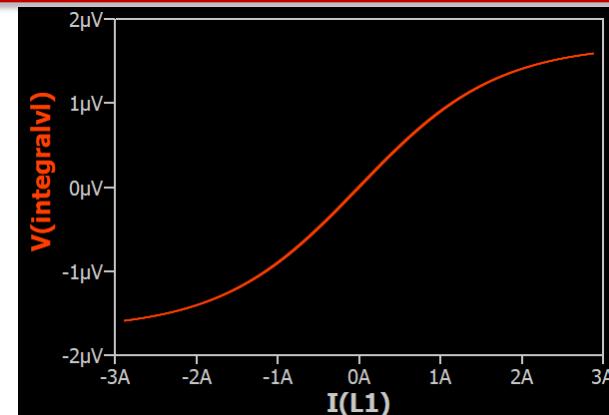
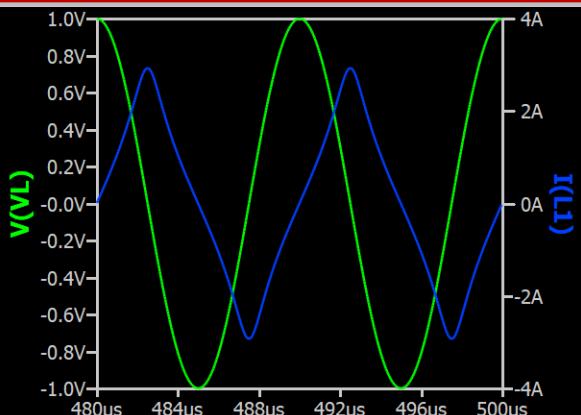
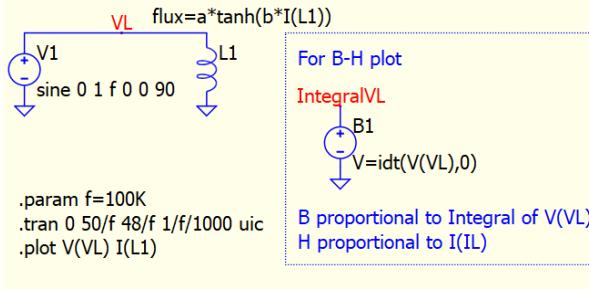


Flux model with .ac



Flux model with .tran

```
.param b = 0.59  
.param L0A = 1μ  
.param a = L0A/b  
flux=a*tanh(b*I(L1))
```



L. Arbitrary Inductance : Inductor modeling with FLUX – Nonlinear with Lmin

Qspice : L Inductor (AC) - Flux eqn 2.qsch ; L Inductor Nonlinear (Tran) - Flux eqn 2.qsch

- Flux Model

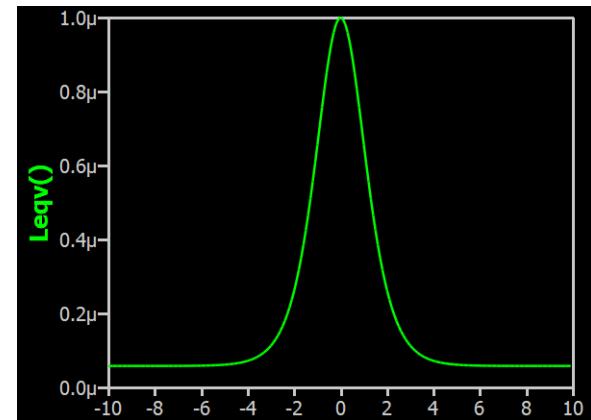
- This is nonlinear flux model include Lmin at large inductor current
- Flux equation uses format
 - $\text{Flux} = a * \tanh(b * I(L1)) + Lmin * I(L1)$

```

.param b = 0.7
.param LOA = 1μ
.param a = (LOA-Lmin)/b
.param Lmin=58n
flux=a*tanh(b*I(L1))+Lmin*I(L1)

.param frq=1Meg
.step param bias -10 10 0.1 Sweep bias
.step param var list 1 2 3 Sweep Isat

.ac list frq
.func Leqv() V(VL)/1/2/pi/frq
.plot Leqv()
  
```

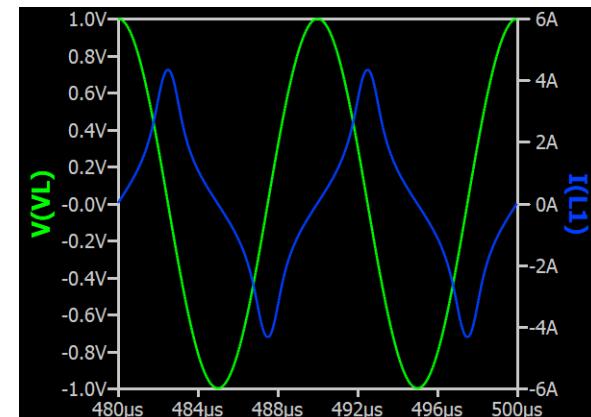


```

.param b = 0.7
.param LOA = 1μ
.param a = (LOA-Lmin)/b
.param Lmin=58n
flux=a*tanh(b*I(L1))+Lmin*I(L1)

.sine 0 1 f 0 0 90
.param f=100K
.tran 0 50/f 48/f 1/f/1000 uic
.plot V(VL) I(L1)

For B-H plot
IntegralVL
B1
V=idt(V(VL),0)
B proportional to Integral of V(VL)
H proportional to I(IL)
  
```



L. Inductor

Parameter : Rpar
(Special Topic)

Inductor L Parameter : Rpar

- In Help, L. Inductor section, RPAR is mentioned default = Infinite

RPAR	Equivalent parallel resistance	Ω	Infinite
RSER	Equivalent series resistance	Ω	0.0

- However, this is not absolute truth according to Mike Engelhardt in a Qspice forum, default Rpar = $\frac{1\text{Meg}}{L}$

 Engelhardt 17d

I think it's hard to find an inductor with less parallel loss than the minimum added by default in QSPICE.

But if you don't like QSPICE'S help on this, you can add an attribute "Rpar=0" to the inductor.

You might want to do the same for the capacitors.

- Setting Rpar = 0 can force equivalent parallel resistance to truly infinite

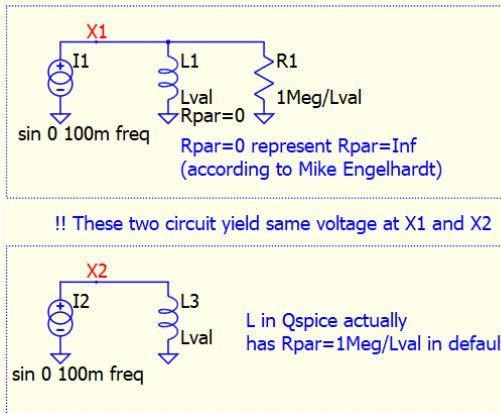
Prove Rpar = 1Meg/L in Default

Actual Rpar in Default L model - Tran.qsch

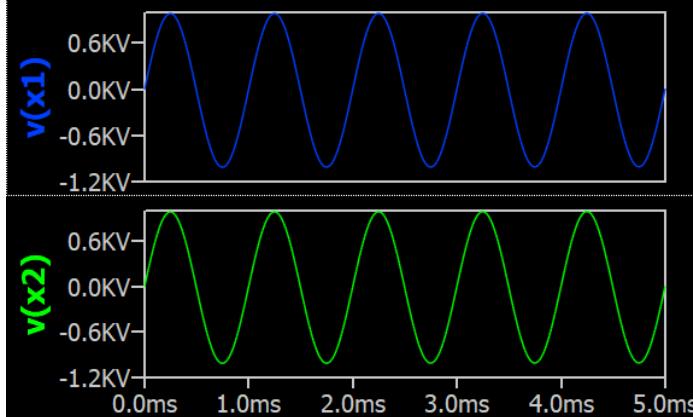
In .tran

Forced Rpar=0 (equal INF)

By adding a 1Meg/L resistor in parallel to L1, its simulation result is same as default L3



```
.param freq=1000  
.tran 5/freq uic  
.plot v(x2)  
.plot v(x1)  
.param Lval=100
```

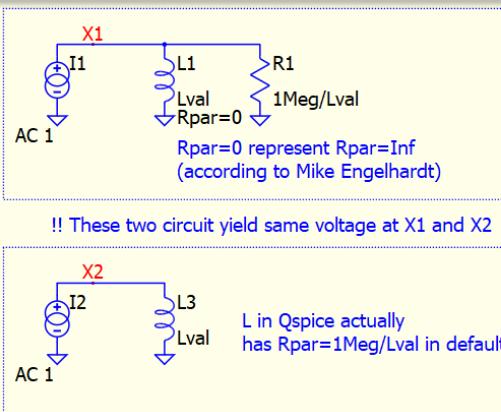


Actual Rpar in Default L model - AC.qsch

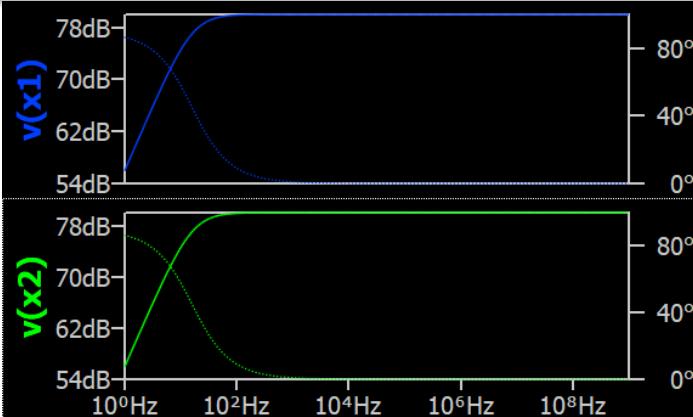
In .ac

Forced Rpar=0 (equal INF)

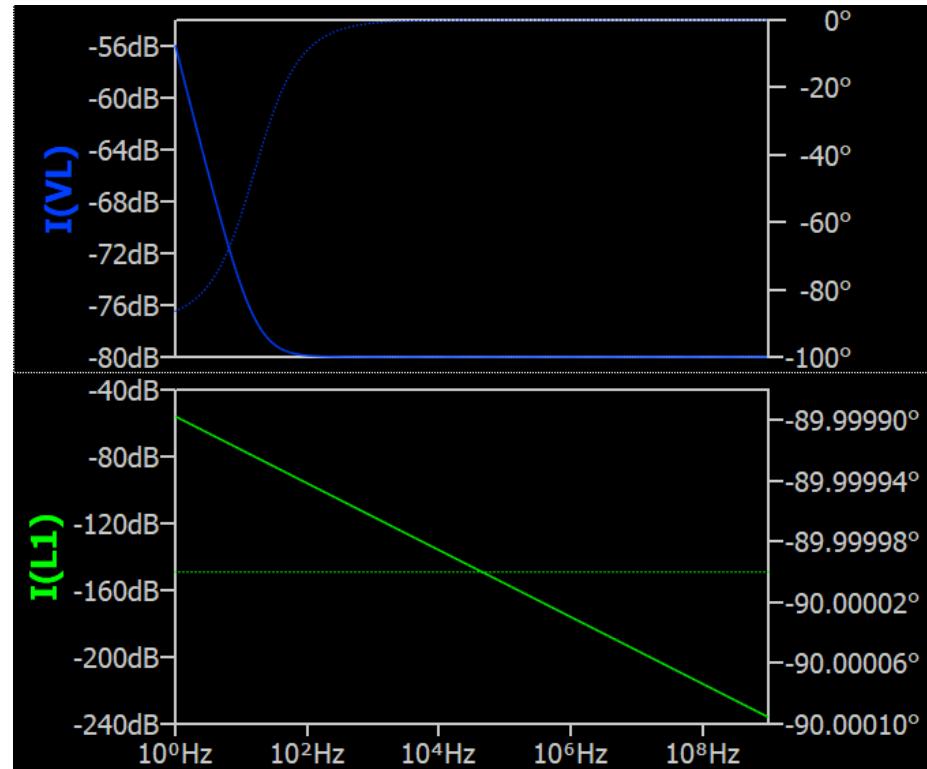
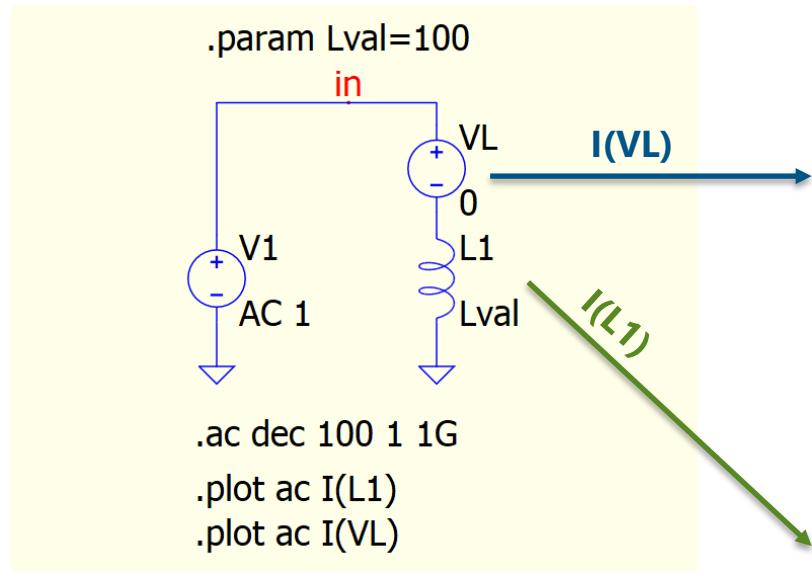
By adding a 1Meg/L resistor in parallel to L1, its simulation result is same as default L3



```
.ac dec 100 1 1G  
.plot v(x2)  
.plot v(x1)  
.param Lval=100
```



What Inductor Current Actually Measured?



L_1 has a $R_{par} = 1\text{Meg}/L$ resistor in parallel

But current probe $I(L_1)$ only return current through L but not R_{par} ,
that is why $I(VL) \neq I(L_1)$ as $I(VL)$ measures total current of L and R_{par}

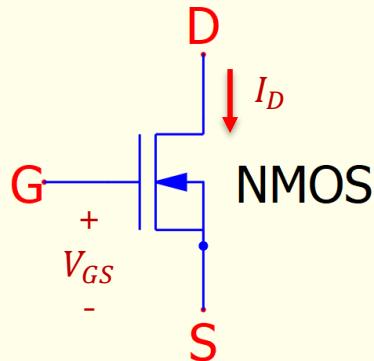
Therefore, user may not aware there is a finite R_{par} if using voltage source across L and measure current of it

M. MOSFET

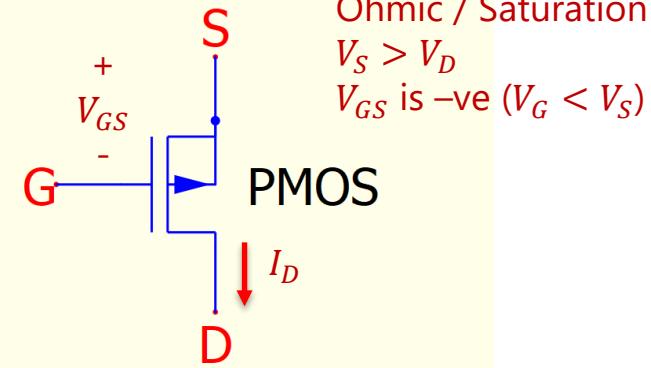
(VDMOS)

** VDMOS with different
default as monolithic MOSFET
models, it popularly used in
board level SMPS

M. MOSFET NMOS and PMOS



Ohmic / Saturation
 $V_D > V_S$
 V_{GS} is +ve ($V_G > V_S$)

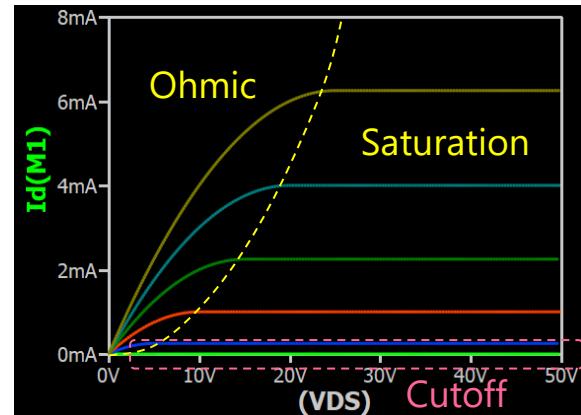
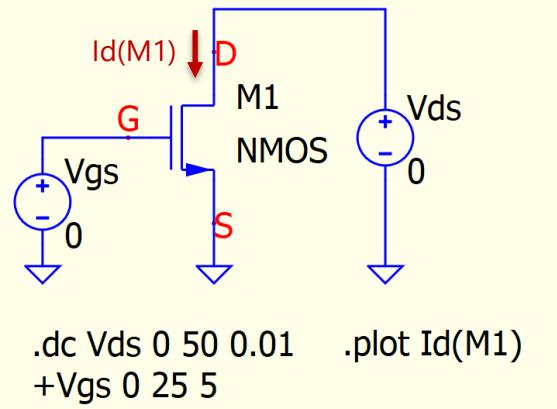
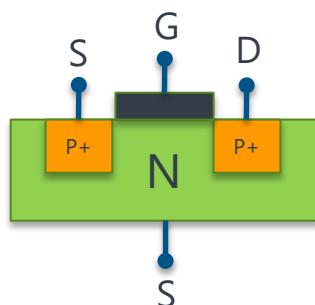


Ohmic / Saturation
 $V_S > V_D$
 V_{GS} is -ve ($V_G < V_S$)

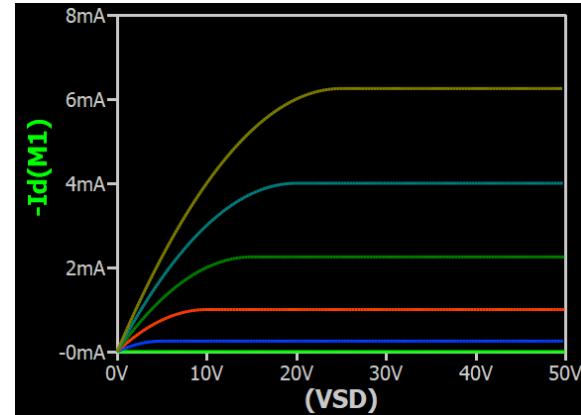
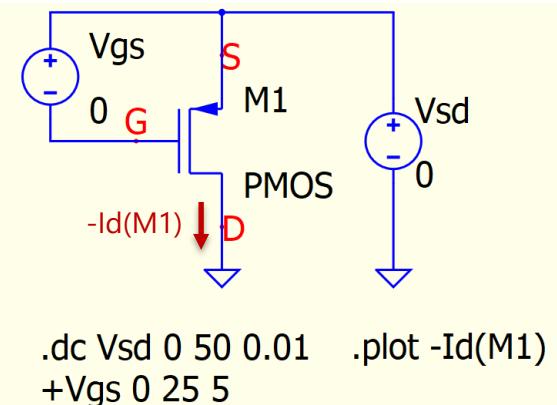
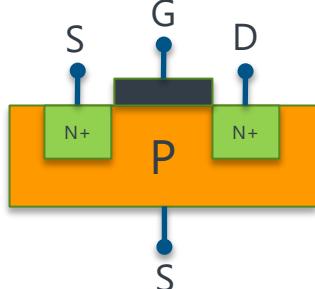
Voltage Relations	NMOS
$V_{GS} > V_{th}$ $V_{DS} < V_{GS} - V_{th}$	Ohmic (Triode/Linear)
$V_{GS} > V_{th}$ $V_{DS} \leq V_{GS} - V_{th}$	Saturation (Active)
$V_{GS} < V_{th}$	Cutoff

M. MOSFET NMOS and PMOS Ohmic, Saturation and Cutoff

- NMOS
 - N-channel MOSFET



- PMOS
 - P-channel MOSFET



MOSFET Level 1 Model Parameters

MOSFET Level 1 Model Parameters

Name	Description	Units	Default
A	Additional non-linear Gate-drain capacitance abruptness		1.0
AD	Default drain area	m ²	0.0
AF	Flicker noise exponent		1.0
AS	Default source area	m ²	0.0
BV	Body diode breakdown voltage	V	Infinite
CAPOP ⁹	Charge(Capacitance) model		1
CBD	Zero-bias B-D junction capacitance	F	0.0
CBS	B-S junction capacitance	F	0.0
CGBO	Gate-bulk overlap capacitance	F/m	0.0
CGDMAX ⁸	Maximum additional non-linear Gate-Drain capacitance	F	0.0
CGDMIN ⁸	Minimum additional non-linear Gate-Drain capacitance	F	0.0
CGDO	Gate-drain overlap capacitance	F/m	0.0
CGS	Gate-source capacitance that doesn't scale with width	F	0.0
CGSO	Gate-source overlap capacitance	F/m	0.0
CJ	Bottom junction cap per area	F/m ²	0.0
CJO	Body diode zero-bias capacitance	F	0.0
CJSW	Side junction cap per length	F/m	0.0
EG	Body diode activation energy	V	1.11
ETA ⁸	Philips, et al.-style subthreshold conduction parameter		0.0
ETA2	Inverse sharpness of Ids limit for non-square law variation		0.0
FC	Forward bias junction fit parameter		0.5
GAMMA	Bulk threshold parameter	V ^{1/2}	0.0
GDSNOI	Channel shot noise coefficient(nlev=3)		1.0
GM	Ideal transconductance for non-square law variation	Ω	none
GMAX	Maximum bulk PN conductivity	Ω	1000.
IBV	Body diode current at breakdown voltage	A	1e-10
IDS	Maximum drain current for non-square law variation	A	Infinite
IGSS	Gate-Source leakage current	A	0.0
IS	Bulk junction saturation current	A	1e-14
JS	Bulk junction saturation current density	A/m ²	0.0
K1 ¹⁰	Threshold voltage sensitivity to bulk node	V ^{1/2}	0.25
KF	Flicker noise coefficient		0.0
KP	Transconductance parameter	A/V ²	2e-5
L	Default channel length	m	1e-5
LAMBDA	Channel length modulation	V ⁻¹	0.0

LD	Lateral diffusion	m	0.0
MJ	Bulk grading coefficient		0.5
MJSW	Side grading coefficient		0.33
N	Bulk(or Body) PN junction emission coefficient		1.0
NBV	Body diode breakdown emission coefficient		1.0
NLEV	Noise level(equation selector)		0
NRD	Default drain squares		0.0
NRB	Default bulk squares		0.0
NRG	Default gate squares		0.0
NRS	Default source squares		0.0
NSS	Surface state density	cm ⁻²	0.0
NSUB	Substrate doping	cm ⁻²	0.0
PB	Bulk junction potential	V	1.0
PD	Default drain perimeter	m	0.0
PHI	Surface potential	V	1.0
PCHAN	Flag to specify vertical PMOS geometry		not set
PS	Default source perimeter	m	0.0
RB	Bulk resistance	Ω	0.0
RD	Drain resistance	Ω	0.0
RDS	Additional Drain-Source shunt resistance	Ω	Infinite
RG	Gate resistance	Ω	0.0
RON	Ron at zero drain current for non-square law variation	Ω	none
RONX ⁸	Channel conductivity multiplier in linear region		1.0
RS	Source resistance	Ω	0.0
RSH	Sheet resistance	Ω/□	0.0
TNOM	Parameter measurement temperature(aka TREF)	°C	27.0
TOX	Oxide thickness	m	1.5e-8
TPG	Gate type		1
TT	Bulk PN junction Transit-time	sec	0.0
U0	Surface mobility(aka UO)	cm ² /V×sec	600
VDMOS ⁸	Flag to specify vertical geometry		not set
VFB ¹⁰	Flat band voltage	V	-1.0
VIGSS	Voltage at which IGSS was measured	V	5.0
VJ	Body diode Junction potential	V	1.0
VT0	Threshold voltage(aka VTO)	V	0.0
W	Default channel width	m	1e-5
XPART ¹⁰	Channel charge partitioning		1
XTI	Body diode Saturation current temperature exponent		3

Display purpose only

- Vds : VDS rating
- Qq : Gate charge
- Mfg : manufacturer

Linear and Saturation Region : VTO, KP, W, L, LD, LAMBDA

- From Semiconductor Device Modeling with Spice (Section 4.2.3)

- Linear region : $V_{GS} > V_{TH}$ and $V_{DS} < V_{GS} - V_{TH}$
 - $I_{DS} = KP \frac{W}{L-2X_{jl}} \left(V_{GS} - V_{TH} - \frac{V_{DS}}{2} \right) V_{DS} (1 + \lambda V_{DS})$
- Saturation region : $V_{GS} > V_{TH}$ and $V_{DS} > V_{GS} - V_{TH}$
 - $I_{DS} = \frac{KP}{2} \frac{W}{L-2X_{jl}} (V_{GS} - V_{TH})^2 (1 + \lambda V_{DS})$
- where
 - V_{TH} : VTO , zero-bias threshold voltage (Default VTO=0 V)
 - KP : KP , transconductance (Default KP=1 A/V²)
 - W : W, channel width (Default W=1e-4 m)
 - L : L, channel length (Default L=1e-4 m)
 - X_{jl} : LD, lateral diffusion (Default LD=0 m)
 - λ : LAMBDA channel-length modulation (Default LAMBDA=0 V⁻¹)

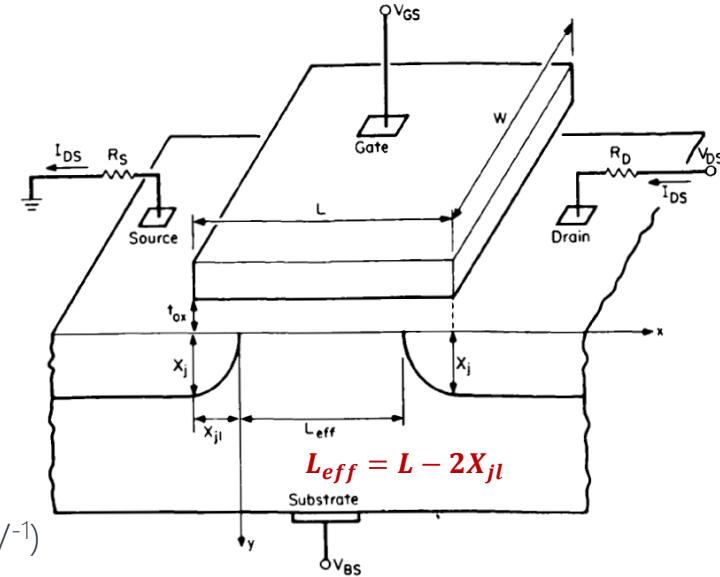


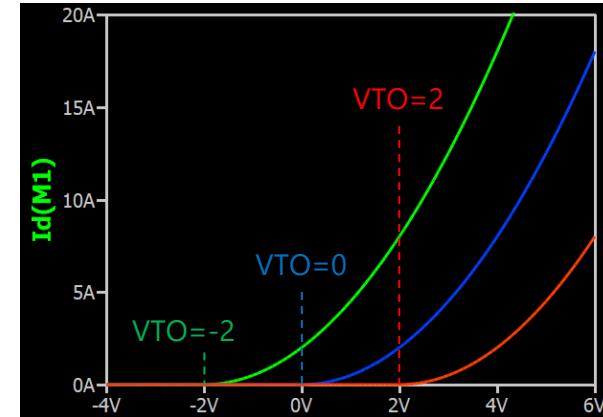
Figure 4-1 Structure of the MOST.

M. MOSFET Params : VTO, KP, W and L

Qspice : VDMOS - VTO.qsch / VDMOS - KP.qsch / VDMOS - W.qsch / VDMOS - L.qsch

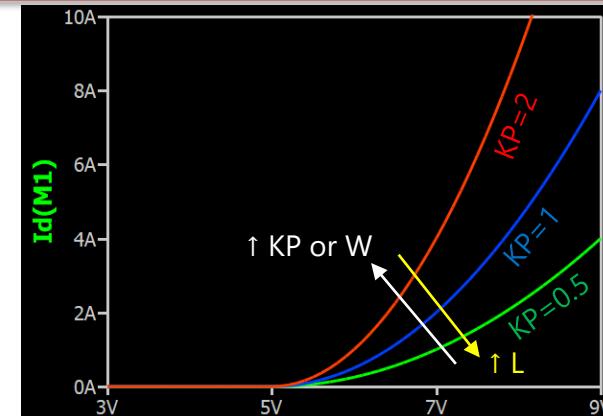
- VTO
 - VTO : Zero-bias threshold voltage
 - **Default VTO=0V**

```
.param Vdrain=10  
.dc Vgate -4 6 0.1 .plot Id(M1)  
  
d  
M1  
Mmdl  
V2  
Vdrain  
Vgate 0  
  
.step param vto list -2 0 2  
.model Mmdl VDMOS VTO=vto
```



- KP
 - KP : transconductance
 - **Default KP=1 A/V²**

```
.param Vdrain=10  
.dc Vgate 3 9 0.1 .plot Id(M1)  
  
d  
M1  
Mmdl  
V2  
Vdrain  
Vgate 0  
  
.step param kp list 0.5 1 2  
.model Mmdl VDMOS VTO=5 KP=kp
```



- W and L
 - W : Channel Width (Default 1e-4)
 - L : Channel Length (Default 1e-4)
 - Effect is similar to KP as a gain
 - $\frac{KP}{2} \frac{W}{L-2X_{jl}}$ (for saturation region)

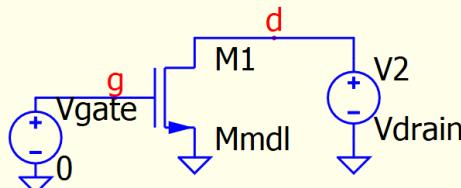
M. MOSFET Params : LD and ETA

Qspice : VDMOS - LD.qsch / VDMOS - ETA.qsch

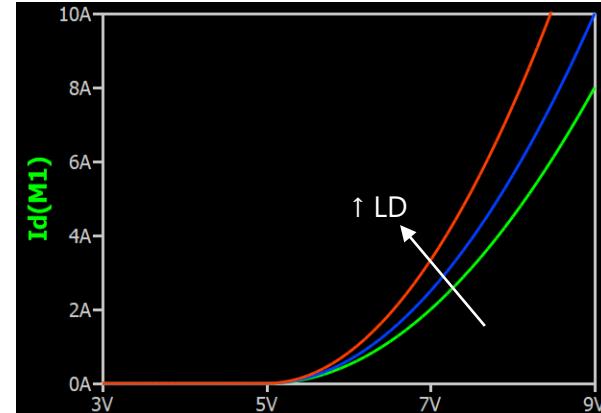
- LD

- LD : lateral diffusion
- **Default LD=0 m**
- $L_{eff} = L - 2LD > 0$
 - Therefore, $0 < LD < \frac{L}{2}$

```
.param Vdrain=10  
.dc Vgate 3 9 0.1 .plot Id(M1)
```



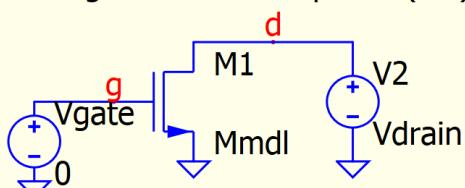
```
.step param Id list 0 0.1e-4 0.2e-4  
.model Mmdl VDMOS VTO=5 LD=Id
```



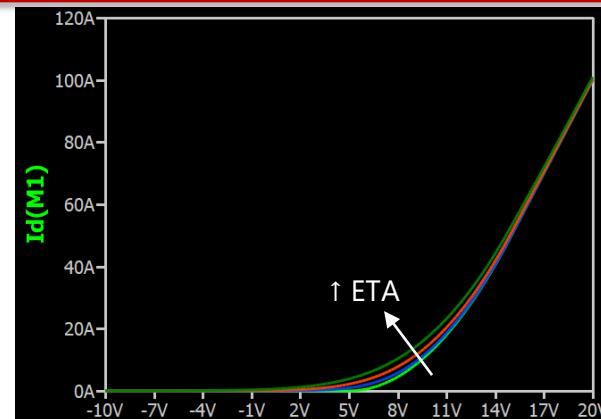
- ETA (aka ksubthres)

- ETA : Vds dependence of threshold voltage
- Static feedback on threshold voltage
- **Default ETA=0**
- Qspice accepts parameter name as ETA or ksubthres

```
.param Vdrain=10  
.dc Vgate -10 20 0.1.plot Id(M1)
```



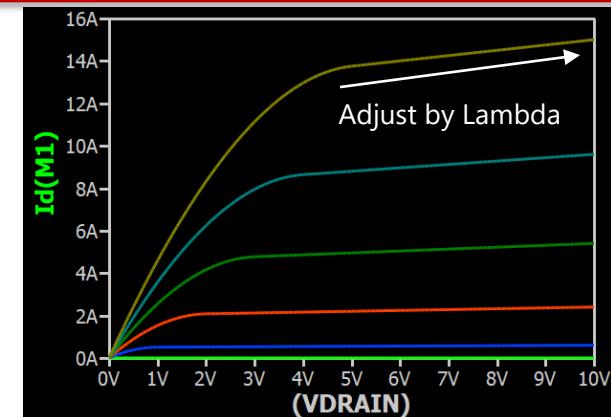
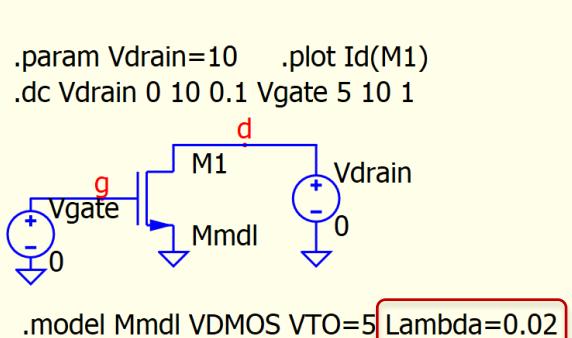
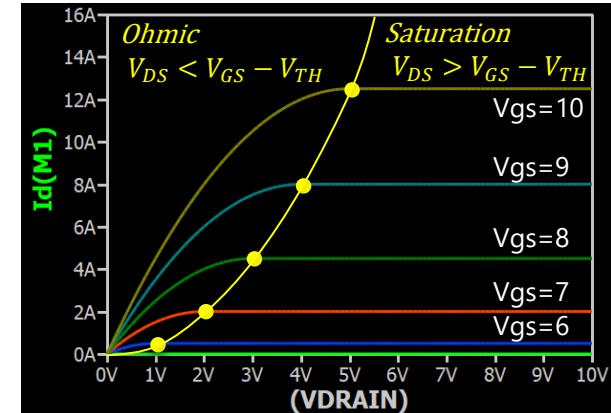
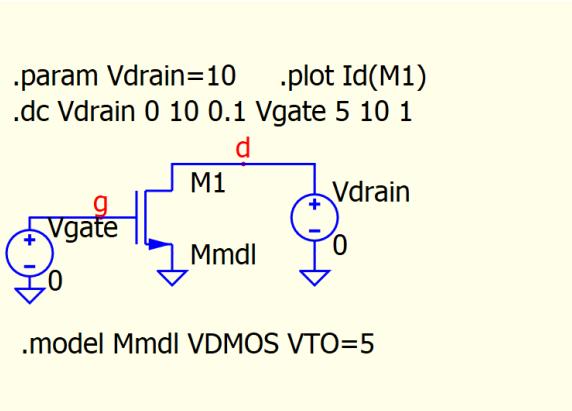
```
.step param eta list 0 2 3 4  
.model Mmdl VDMOS VTO=5 ETA=eta
```



M. MOSFET Params : Lambda

Qspice : VDMOS -LAMBDA.qsch

- LAMBDA
 - Labmda : channel-length modulation
 - Default LAMBDA=0 V⁻¹**

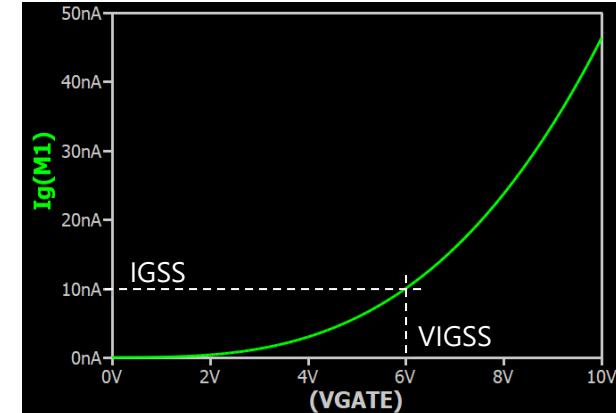
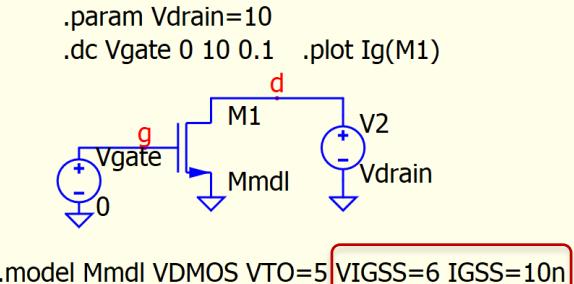


M. MOSFET Params (Gate) : VIGSS and IGSS, RG and CGS

Qspice : VDMOS - VIGSS IGSS.qsch / VDMOS - Rg Cgs.qsch

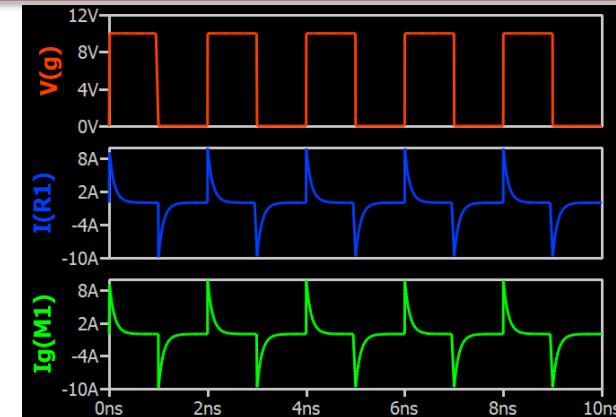
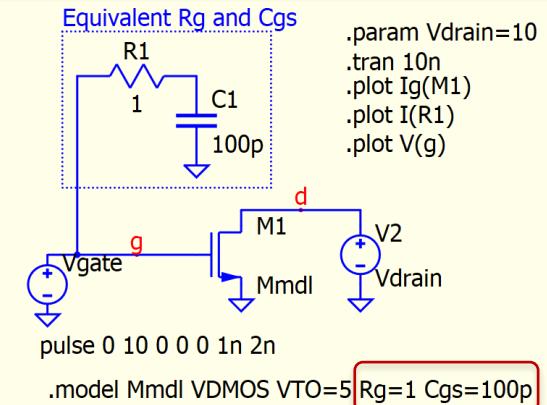
VIGSS and IGSS

- Vigss : Voltage at which IGSS was measured
- Igss : Gate-Source leakage current
- **Default VIGSS=5V**
- **Default IGSS=0A**
- Parameters to determine Igss in relates to Vgs



RG and CGS

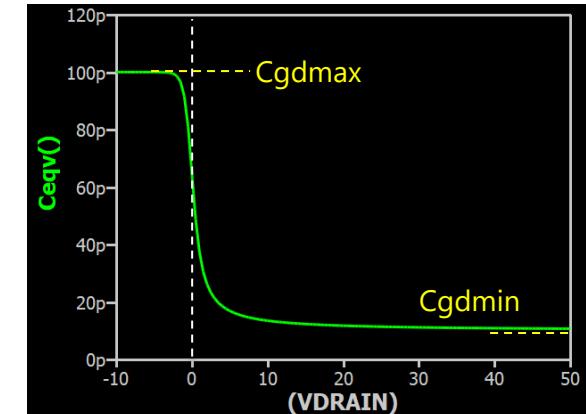
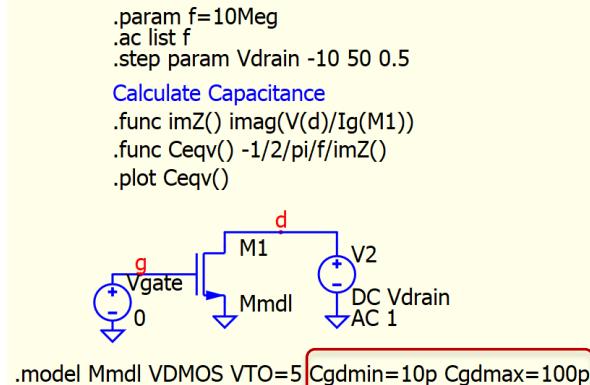
- Rg : Gate Resistance
- Cgs : Gate-source capacitance that doesn't scale with width
- **Default RG=0Ω**
- **Default CGS=0F**
- Parameters to determine gate resistance and capacitoance



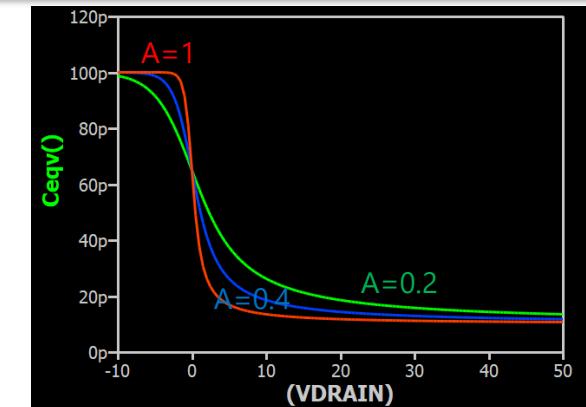
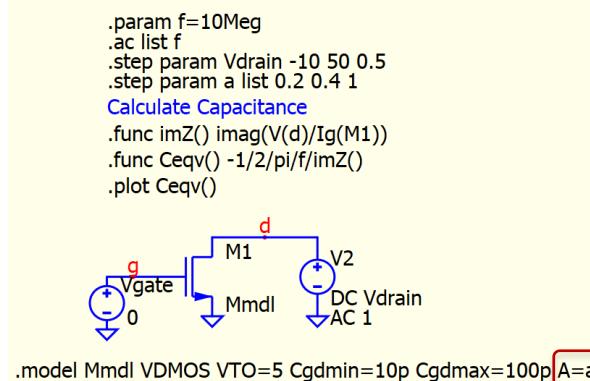
M. MOSFET Params (Cgd) : CGDMAX, CGDMIN and A

Qspice : VDMOS - CGDMIN CGDMAX.qsch / VDMOS - A.qsch

- CGDMAX and CGDMIN
 - Cgdmax : Maximum additional non-linear Gate-Drain capacitance
 - Cgdmin : Minimum additional non-linear Gate-Drain capacitance
 - Default Cgdmax=0F**
 - Default Cgdmin=0F**
 - Model non-linear of Cgd capacitance



- A
 - A : Additional non-linear Gate-drain capacitance abruptness
 - Default A=1**
 - Modify Cgd vs drain voltage profile

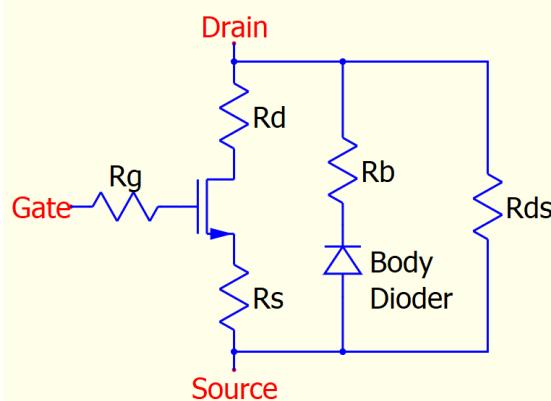


M. MOSFET Params :

Qspice : VDMOS - BodeDiode.qsch / VDMOS - Rb Rd Rds Rg Rs.qsch

- Resistance

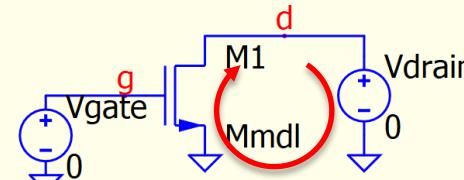
- R_b : Bulk resistance
- R_d : Drain resistance
- R_{ds} : Additional Drain-Source shunt resistance
- R_g : Gate resistance
- R_s : Source resistance
- **Default R_b=R_d=R_g=R_s=0Ω**
- **Default R_{ds}=Infinite**



- Body Diode

- Parameters same as diode model parameters
- Refer to section : D. Diode Diode Model Parameters
- This ideal diode also provide C_{ds} capacitance with its junction capacitance C_j

```
.dc Vdrain -1 4 0.01  
.plot Id(M1)
```



```
.model Mmdl VDMOS VTO=5 N=0.3
```



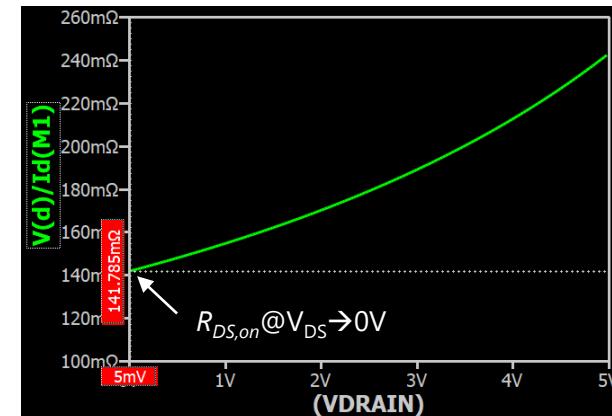
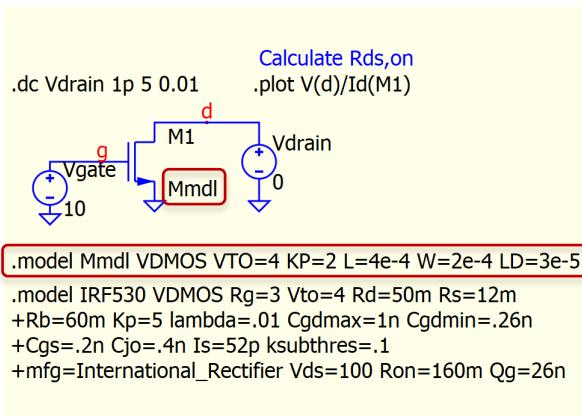
M. MOSFET : Drain-Source Turn ON Resistance : R_{ds,on}

- R_{ds,on}
 - This is not a direct parameters, but as to design SMPS, you may want to know what parameters in MOSFET model affect R_{ds,on}
 - In SMPS, R_{ds,on} is generally considered as MOSFET fully turn ON, where
 - $V_{GS} \gg V_{TH}$ and V_{DS} is low, MOSFET in linear region, and $R_{DS,ON} = \frac{V_{DS}}{I_{DS}}$
 - Linear region formula : $V_{GS} > V_{TH}$ and $V_{DS} < V_{GS} - V_{TH}$
 - $I_{DS} = KP \frac{W}{L-2X_{jl}} \left(V_{GS} - V_{TH} - \frac{V_{DS}}{2} \right) V_{DS} (1 + \lambda V_{DS})$
 - Therefore
 - $R_{DS,ON} = \frac{V_{DS}}{I_{DS}} = \frac{V_{DS}}{KP \frac{W}{L-2X_{jl}} \left(V_{GS} - V_{TH} - \frac{V_{DS}}{2} \right) V_{DS} (1 + \lambda V_{DS})} = \frac{1}{KP \frac{W}{L-2X_{jl}} \left(V_{GS} - V_{TH} - \frac{V_{DS}}{2} \right) (1 + \lambda V_{DS})}$
 - $\lim_{V_{DS} \rightarrow 0} R_{DS,ON} = \frac{1}{KP \frac{W}{L-2X_{jl}} \left(V_{GS} - V_{TH} - \frac{0}{2} \right) (1 + \lambda \times 0)} = \frac{1}{KP \frac{W}{L-2X_{jl}} (V_{GS} - V_{TH})} = \frac{L-2X_{jl}}{KP \cdot W \cdot (V_{GS} - V_{TH})}$
 - With Qspice model parameters, also consider drain and source resistance in model
 - @ $V_{DS} \rightarrow 0V$: $R_{DS,ON} = \frac{L-2 LD}{KP \cdot W \cdot (V_{GS} - VTO)} + RD + RS$
 - Where in default, VTO=0, KP=1, L=1e-4, W=1e-4, LD=0, RD=0 and RS=0

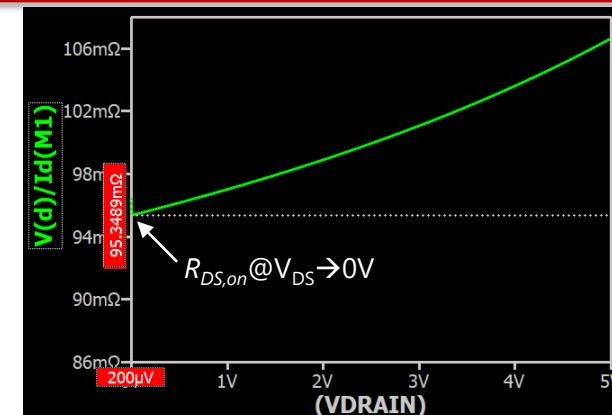
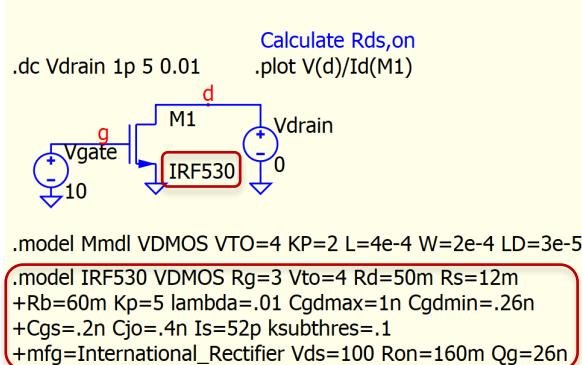
M. MOSFET : Drain-Source Turn ON Resistance : R_{ds,on}

Qspice : VDMOS - (Calculate) Rdson.qsch

- Example #1
 - Mmdl model
 - @V_{DS} → 0V
 - $R_{DS,ON} = \frac{L-2 LD}{KP \cdot W \cdot (V_{GS}-VTO)} + RD + RS$
 - RD=0
 - RS=0
 - $R_{DS,ON} @ V_{DS} \rightarrow 0V = 141.67m\Omega$



- Example #2
 - Mmdl model
 - @V_{DS} → 0V
 - $R_{DS,ON} = \frac{L-2 LD}{KP \cdot W \cdot (V_{GS}-VTO)} + RD + RS$
 - VTO=4, KP=5
 - L=W=1e-4, LD=0
 - RD=50m
 - RS=12m
 - $R_{DS,ON} @ V_{DS} \rightarrow 0V = 95.33m\Omega$



M. MOSFET
Level 2010 (SiC FET)
Model

M. MOSFET Level 2010 (SiC FET) Model

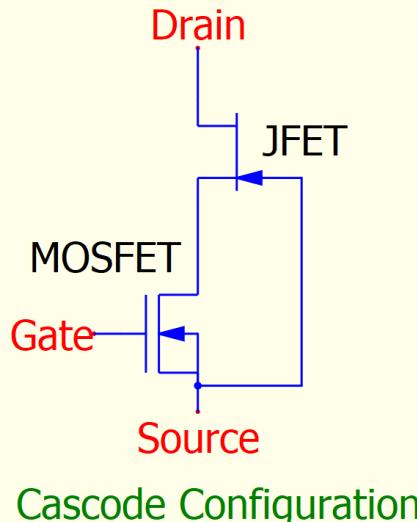
Name	Description	Units	Default
A	Sharpness of transition from CGDMIN to CGDMAX		1.0
AF	MOSFET Flicker noise exponent		1.0
BV	Body diode breakdown voltage	V	Infinite
CGDMAX	Gate-Drain maximum capacitance	F	0.0
CGDMIN	Gate-Drain minimum capacitance	F	0.0
CGS	Gate-source overlap capacitance	F	0.0
CJO	Body diode zero bias cap	F	0.0
EG	Body diode activation energy	V	1.11
ETA	Philips, et al.-style subthreshold conduction	V	0.0
ETATC1	ETA first order tempco	V/ $^{\circ}$ C ⁻¹	0.0
ETATC2	ETA second order tempco	V/ $^{\circ}$ C ⁻²	0.0
GDSNOI	Noise equation selector		0
GMAX	Maximum conductivity of any PN junction	Ω	1000.
IBV	Body diode current at breakdown voltage	A	1e-10
IGSS	Gate-Source leakage	A	0.0
IS	Body diode saturation current	A	1e-14
JAF	JFET Flicker Noise Exponent		1.0
JALPHA	JFET impact ionization coefficient	V ⁻¹	0.0
JB	JFET doping tail parameter		0.0
JBETA	JFET transconductance parameter	A/V ²	1.0
JBETATCE	JFET exponential temperature coefficient	%/ $^{\circ}$ C	0.0
JCGD	JFET G-D junction cap	F	0.0
JCGDO	JFET G-D junction cap	F	0.0
JCGS	JFET G-S junction capacitance	F	0.0
JCGSO	JFET G-S junction capacitance	F	0.0
JFC	JFET forward bias junction fit parm.		0.5
JIS	JFET gate junction saturation current	A	1e-14
JISR	JFET recombination current parameter	A	0.0
JKF	JFET Flicker Noise Coefficient		0.0
JLAMBDA	JFET Channel length modulation parameter	V ⁻¹	0.0

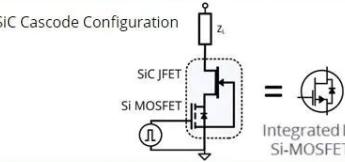
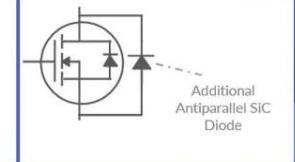
JM	JFET grading coeff.		0.5
JN	JFET emission coefficient		1.0
JNR	JFET Is _r emission coefficient		2.0
JPB	JFET gate junction potential	V	1.0
JRD	JFET drain ohmic resistance	Ω	0.0
JRDS	JFET additional Drain-Source leakage resistance	Ω	Infinite
JRDSTC1	JFET RDS first order tempco	$^{\circ}$ C ⁻¹	0.0
JRDSTC2	JFET RDS second order tempco	$^{\circ}$ C ⁻²	0.0
JRDTCl	JFET RD first order tempco	$^{\circ}$ C ⁻¹	0.0
JRDTC2	JFET RD second order tempco	$^{\circ}$ C ⁻²	0.0
JRG	JFET gate ohmic resistance	Ω	0.0
JRGTC1	JFET RG first order tempco	$^{\circ}$ C ⁻¹	0.0
JRGTC2	JFET RG second order tempco	$^{\circ}$ C ⁻²	0.0
JRONX	JFET channel conductivity multiplier in linear region		1.0
JRS	JFET source ohmic resistance	Ω	0.0
JRSTC1	JFET RS first order tempco	$^{\circ}$ C ⁻¹	0.0
JRSTC2	JFET RS second order tempco	$^{\circ}$ C ⁻²	0.0
JVK	JFET ionization knee current	V	0.0
JVTO	JFET threshold voltage	V	-2.0
JVTOTC	JFET V _{t0} 's temperature coefficient	$^{\circ}$ C ⁻¹	0.0
JXTI	JFET IS temperature coefficient		3.0
KF	MOSFET flicker noise coefficient		0.0
KP	MOSFET transconductance parameter	A/V ²	1.0
LAMBDA	MOSFET channel length modulation	V ⁻¹	0.0
LG	JFET gate inductance	H	0.0
LGRPAR	JFET gate inductance parallel loss	Ω	Infinite
LMID	Inductance making cascode connection	H	0.0
LS	MOSFET Source Inductance	H	0.0
LSRPAR	MOSFET Source inductance parallel loss	Ω	Infinite
LMIDRPAR	Cascade inductance parallel loss	Ω	Infinite
M	Body diode grading coefficient(MJ)	Ω	0.5

N	Bulk diode emission coefficient		1.0
NBV	Body diode breakdown emission coeff		1.0
NLEV	MOSFET noise equation selector		0
NOISELESS	The device does not contribute to a noise		
RB	Body diode series resistance	Ω	0.0
RBTC1	MOSFET RB first order tempco	$^{\circ}$ C ⁻¹	0.0
RBTC2	MOSFET RB second order tempco	$^{\circ}$ C ⁻²	0.0
RD	MOSFET drain ohmic resistance	Ω	
RDS	MOSFET drain-source shunt resistance	Ω	Infinite
RDTC1	MOSFET RD first order tempco	$^{\circ}$ C ⁻¹	0.0
RDTC2	MOSFET RD second order order	$^{\circ}$ C ⁻²	0.0
RG	MOSFET gate resistance	Ω	0.0
RONX	MOSFET conductivity multiplier in linear region		1.0
RS	MOSFET Source ohmic resistance	Ω	0.0
RSTC1	MOSFET RS first order tempco	$^{\circ}$ C ⁻¹	0.0
RSTC2	MOSFET RS second order tempco	$^{\circ}$ C ⁻¹	0.0
THETA	MOSFET V _{gs} dependence on mobility ala mos3	V ⁻¹	0.0
TNOM	Parameter measurement temperature(TNOM)	$^{\circ}$ C	27.0
TRB1	MOSFET RB first order tempco	$^{\circ}$ C ⁻¹	0.0
TRB2	MOSFET RB second order tempco	$^{\circ}$ C ⁻²	0.0
TRD1	MOSFET RD first order tempco	$^{\circ}$ C ⁻¹	0.0
TRD2	MOSFET RD second order tempco	$^{\circ}$ C ⁻²	0.0
TRS1	MOSFET RS first order tempco	$^{\circ}$ C ⁻¹	0.0
TRS2	MOSFET RS second order tempco	$^{\circ}$ C ⁻²	0.0
TT	Bulk diode transit time	s	0.0
VJ	Body diode Junction potential	V	1.0
VTO	MOSFET threshold voltage	V	0.0
VTOTC	MOSFET's V _{t0} tempco	$^{\circ}$ C ⁻¹	0.0
XTI	Body diode Saturation current temperature exp.		3.0

M. MOSFET Level 2010 (SiC FET) Cascode Configuration

- MOSFET Level 2010 (SiC FET) Model Parameters
 - SiC Cascode Configuration for SiC FET, which contains a JFET and MOSFET
 - SiC JFET
 - Si MOSFET
 - Reference
 - "Cascode Configuration Eases Challenges of Applying SiC JFETs", United SiC, App Note USCI_AN0004
 - "Origins of SiC FETs and their evolution towards the perfect switch", United SiC, White Paper

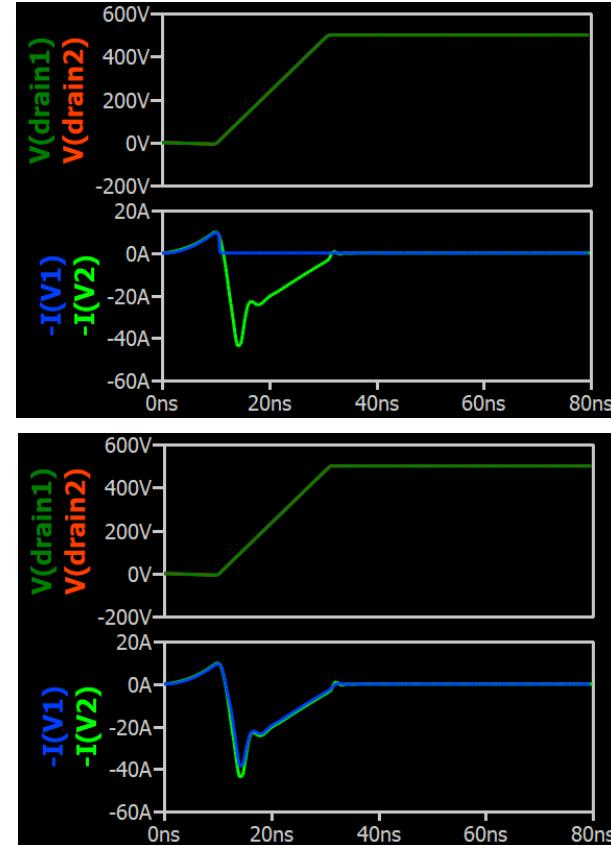
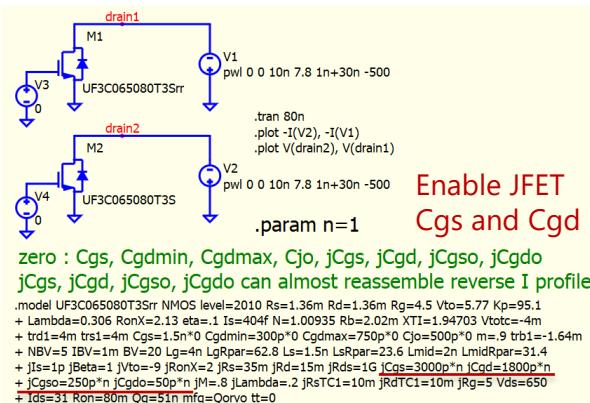
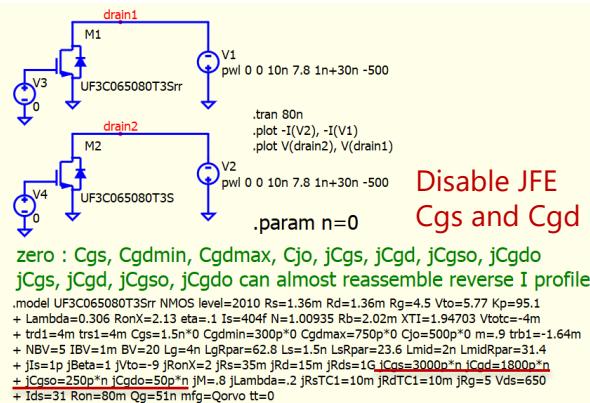


Normally Off UnitedSiC Cascode		Normally Off Typical SiC MOSFET
SiC Cascode Configuration	 = 	
Die Size	(Smaller) $R_{DS(A)} \sim 1.75 \text{ m}\Omega\cdot\text{cm}^2$	(Larger) $R_{DS(A)} \sim 3.1 - 4.5 \text{ m}\Omega\cdot\text{cm}^2$
Gate Drive	(Standard) $V_{GS} = 0V$ to $12V$ OR (SiC) $V_{GS} = -10V$ to $20V$	$V_{GS} = -5V$ to $20V$
Threshold	$V_{GS(TH)} = 5V$ Typical	$V_{GS(TH)} = 2.2V$ Typical
Intrinsic Diode	Low Qrr, +10% Over Temperature	High Qrr, High VF 3X Over Temperature
Avalanche	Yes	Yes
Short Circuit	Yes	Low

M. MOSFET Level 2010 : Reverse Current

Qspice : UF3C065080T3S Reverse Current.qsch

- Reverse Current
 - TT (transit-time) is set to 0 in Qorvo SiC FET, reverse recovery of bulk diode is not be used
 - Reverse current is simulated by parasitic capacitance in SiC FET
 - From Qorvo SiC FET model, reverse current is mainly contributed from Cgs and Cgd of JFET
 - j_{Cgs}, j_{Cgso}
 - j_{Cgd}, j_{Cgdo}

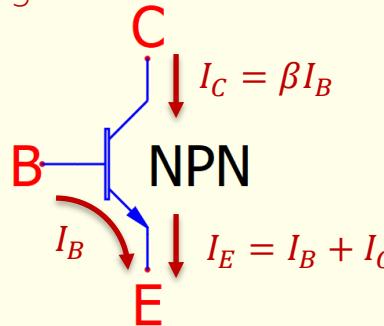


Q. Bipolar Transistor

Q. Bipolar Transistor : NPN and PNP

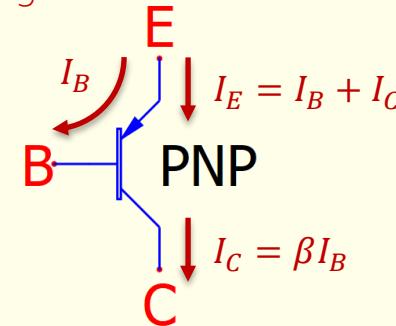
Active Region

$$V_C > V_E$$



Active Region

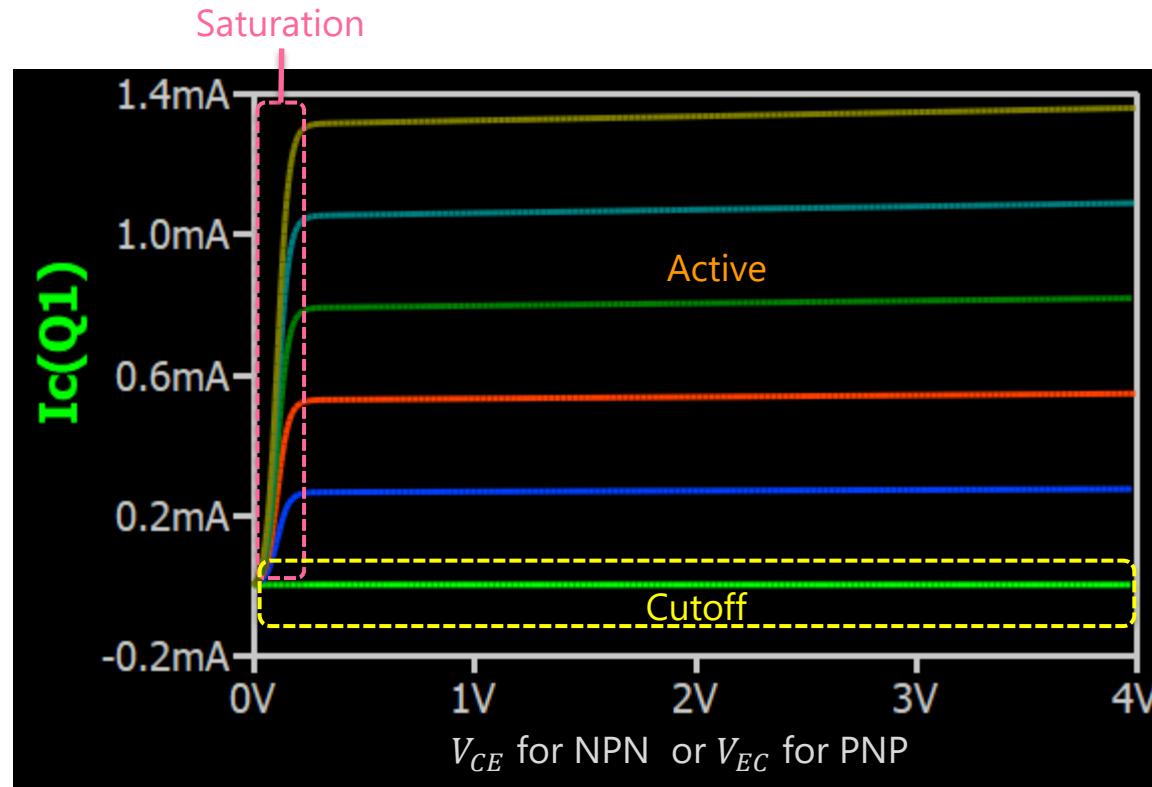
$$V_E > V_C$$



Voltage Relations	NPN
$V_E < V_B < V_C$	Active
$V_E < V_B > V_C$	Saturation
$V_E > V_B < V_C$	Cutoff
$V_E > V_B > V_C$	Reverse

Voltage Relations	PNP
$V_E < V_B < V_C$	Reverse
$V_E < V_B > V_C$	Cutoff
$V_E > V_B < V_C$	Saturation
$V_E > V_B > V_C$	Active

Q. Bipolar Transistor : NPN and PNP : Active, Saturation and Cutoff



Q. Bipolar Transistor Model Parameters

Bipolar Transistor Model Parameters			
Name	Description	Units	Default
AF	Flicker Noise Exponent		1.0
BF	Ideal forward beta		100.
BR	Ideal reverse beta		1.0
BRS	Substrate parasitic transistor beta		.0
CJC	Zero bias B-C capacitance	F	0.0
CJE	Zero bias B-E capacitance	F	0.0
CJS	Zero bias C-S capacitance(aka CCS)	F	0.0
CN ¹	Tempco for hole mobility	°C ⁻¹	NPN: 2.42 PNP: 2.20
D ¹	Tempco for scattering-limited hole carrier velocity	V ⁻¹	NPN: 0.87 PNP: 0.52
EG	Energy gap for IS temp. dependency	V	1.11
FC	Forward bias junction fit parameter		0.5
GAMMA ¹	Epitaxial region doping factor		1e-11
GMAX	Maximum PN conductivity(straight-line extension)	Ω	1000.
IBC	B-C saturation current	A	0.0
IBE	B-E saturation current	A	0.0
IKF	Forward beta roll-off corner current(aka IK)	A	Infinite
IKR	Reverse beta roll-off corner current	A	Infinite
IRB	Current for base resistance=(rb+rbm)/2	A	Infinite
IS	Saturation Current	A	1e-16
ISC	B-C leakage saturation current(aka C4)	A	IS
ISE	B-E leakage saturation current(aka C2)	A	IS
ISS	Substrate junction saturation current	A	0.0 ²
ITF	High current dependence of TF	A	0.0
KF	Flicker Noise Coefficient		0.33
MJC	B-C junction grading coefficient(aka MC)		0.33
MJE	B-E junction grading coefficient(aka ME)		0.0
MJS	Substrate junction grading coefficient(aka MS)		0.0
NC	B-C leakage emission coefficient		2.0
NE	B-E leakage emission coefficient		1.5
NEPI ¹	Epitaxial region emission coefficient		1.0
NF	Forward emission coefficient		1.0
NK	High-current roll-off coefficient		0.5
NR	Reverse emission coefficient		1.0
NS	Substrate junction emission coefficient		1.0
PTF	Excess phase	°	0.0
QCO ¹	Epitaxial region charge factor	C	0.0

QUASIMOD ¹	Temperature dependence equation selector		0
RB	Zero bias base resistance	Ω	0.0
RBM	Minimum base resistance	Ω	0.0
RC	Collector resistance	Ω	0.0
RCO ¹	Epitaxial region resistance	Ω	0.0
RE	Emitter resistance	Ω	0.0
SUBS	Set to 2 to specify lateral geometry.		1
TF	Ideal forward transit time	sec	0.0
TNOM	Parameter measurement temperature(aka TREF)	°C	27.0
TR	Ideal reverse transit time	sec	0.0
TRB1	Rb 1st order temperature coefficient	°C ⁻¹	0.0
TRB2	Rb 2nd order temperature coefficient	°C ⁻²	0.0
TRBM1	Rbm 1st order temperature coefficient(aka TRM1)	°C ⁻¹	0.0
TRBM2	Rbm 2nd order temperature coefficient(aka TRM2)	°C ⁻²	0.0
TRC1	RC 1st order temperature coefficient	°C ⁻¹	0.0
TRC2	RC 2nd order temperature coefficient	°C ⁻²	0.0
TRE1	RE 1st order temperature coefficient	°C ⁻¹	0.0
TRE2	RE 2nd order temperature coefficient	°C ⁻²	0.0
TVAF1	1st order tempco of forward Early voltage	V/°C ¹	0.0
TVAF2	2nd order tempco of forward Early voltage	V/°C ²	0.0
TVAR1	1st order tempco of reverse Early voltage	V/°C ¹	0.0
TVAR2	2nd order tempco of reverse Early voltage	V/°C ²	0.0
VAF	Forward Early voltage(aka VA)	V	Infinite
VAR	Reverse Early voltage(aka VB)	V	Infinite
VG ¹	Extrapolated band gap voltage at 0°K	V	1.206
VJC	B-C junction built in potential(aka PC)	V	0.75
VJE	B-E junction built in potential(aka PE)	V	0.75
VJS	Substrate junction built in potential(aka PS)	V	0.75
VO ¹	Carrier mobility knee voltage	V	10.0
VTF	Voltage giving VBC dependence of TF	V	Infinite
XCJC	Fraction of CJC connected to intrinsic base ³		1.0
XCJC2	Fraction of CJC connected to intrinsic base ⁴		1.0
XCJS	Fraction of CJS connected internally to RE		1.0
XTB	Forward and reverse beta temp. exp.		0.0
XTF	Coefficient for bias dependence of TF		0.0
XTI	Temperature exponent for IS(aka PT)		3.0

Q. Bipolar Transistor Basic Equation

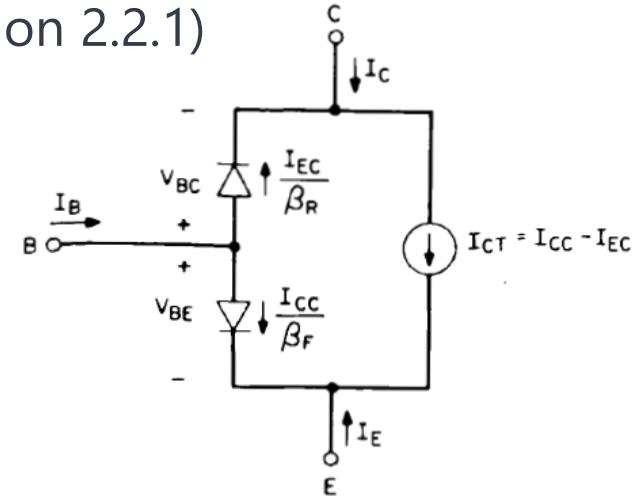
- Semiconductor Device Modeling with SPICE (Section 2.2.1)

- Basic equation from BJT Ebers-Moll static model

- $$\begin{aligned} I_C &= I_{CT} - \frac{I_{EC}}{\beta_R} \\ I_{CT} &= I_{CC} - I_{EC} \\ I_E &= -\frac{I_{CC}}{\beta_F} - I_{CT} \\ I_B &= \frac{I_{CC}}{\beta_F} + \frac{I_{EC}}{\beta_R} \end{aligned}$$

- Therefore

- $$\begin{aligned} I_C &= I_{CC} - I_{EC} - \frac{I_{EC}}{\beta_R} = \beta_F \left(I_B - \frac{I_{EC}}{\beta_R} \right) - I_{EC} - \frac{I_{EC}}{\beta_R} \\ I_C &= \beta_F I_B - \left(\frac{\beta_F}{\beta_R} + \frac{1}{\beta_R} + 1 \right) I_{EC} \end{aligned}$$



- Understanding (Approximation approach)

- If $V_{CE} \gg V_{BE}$, diode D_{BC} is reverse bias, where $I_{EC} \rightarrow 0$

- $$I_C = \beta_F I_B$$

- If $V_{BE} \gg V_{CE}$, diode D_{BC} is forward bias, and with $\beta_F \gg \beta_R$

- $$I_C = \beta_F I_B - \frac{\beta_F}{\beta_R} I_{EC}$$

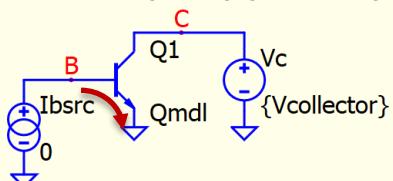
Q. Bipolar Params ($\beta_F | \beta_R$) : BF and BR

Qspice : NPN - BF.qsch / NPN - BR.qsch

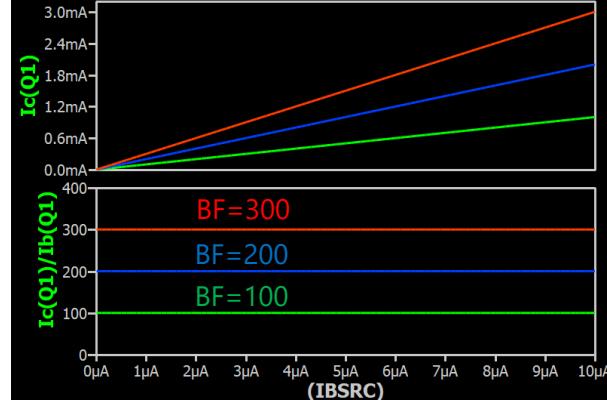
- BF
 - BF : Ideal forward beta
 - **Default BF=100**
 - $I_C = \beta_F I_B$ for $V_{CE} \gg V_{BE}$

- BR
 - BR : Ideal reverse beta
 - **Default BR=1**
 - $I_C = \beta_F I_B - \frac{\beta_F}{\beta_R} I_{EC}$
 - This effect is mainly observed when both BE and BC diode are forward bias, where collector-emitter voltage is close to 0V
 - Smaller β_R , larger $\frac{\beta_F}{\beta_R}$ and less I_C and less $\frac{I_C}{I_B}$

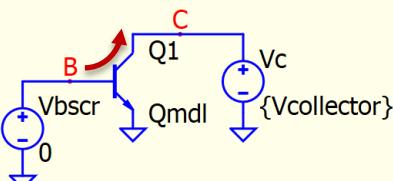
Sweep Parameters
`.param Vcollector = 10
.param Ibmax=10μ
.dc Ibsrc 10n {Ibmax} {Ibmax/100}`



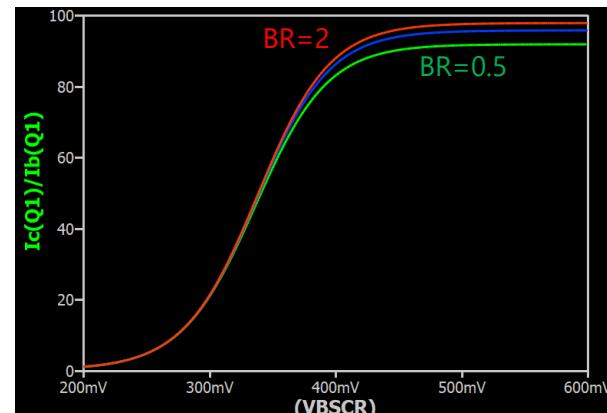
`.step param bf list 100 200 300
.model Qmdl NPN BF={bf}`



Sweep Parameters
`.param Vcollector = 0.2
.param Ibmin=10p
.dc Vbscr 0.2 0.6 0.001`



`.step param br list 0.5 1 2
.model Qmdl NPN BR={br} BF=100`

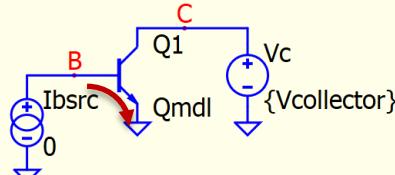


Q. Bipolar Params ($\beta_F | \beta_R$) : IKF

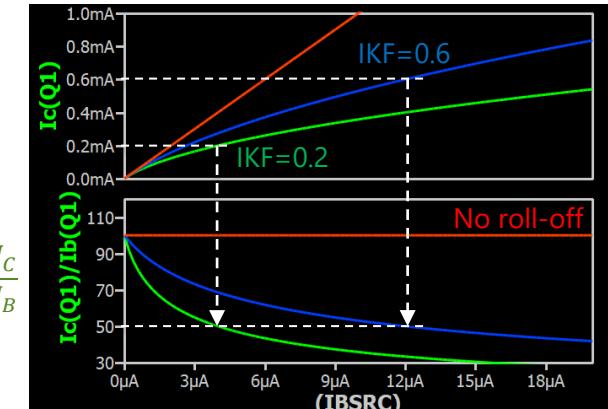
Qspice : NPN - IKF.qsch / NPN - IKR.qsch

- IKF
 - IKF : Forward beta roll-off corner current
 - Default IKF=infinite (A)**
 - IKF models β_F drop when I_C increase
 - IKF is I_C where effective BF (β_F) reduces multiple approximate by $(1-NK)$
 - This example Default NK=0.5, effective BF is reduced to 50 @ $I_C=IKF$

Sweep Parameters
`.param Vcollector = 10
.param Ibmax=20μ
.dc Ibsrc 10n {Ibmax} {Ibmax/100}`

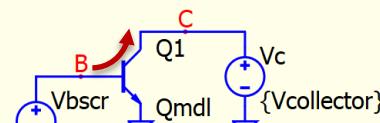


`.step param ikf list 0.2m 0.6m 1e12
.model Qmdl NPN BF=100 IKF=ikf`

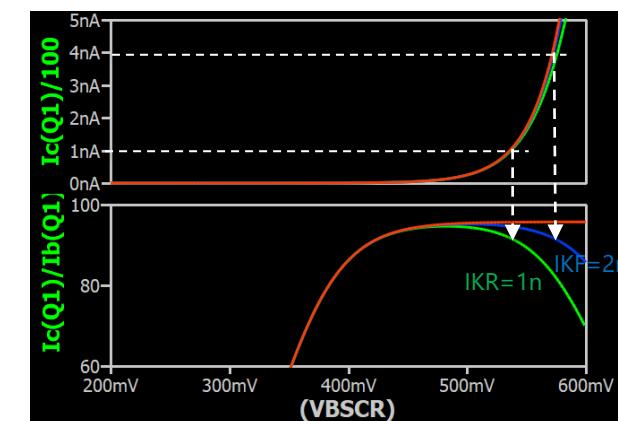


$$\beta_{F,\text{eff}} = \frac{I_C}{I_B}$$

Sweep Parameters
`.param Vcollector = 0.2
.param Ibmin=10p
.dc Vbscr 0.2 0.6 0.001`



`.param bf=100
.step param ikr list 1n 4n 1e12
.model Qmdl NPN BR=1 BF=bf IKR=ikr`



- IKR
 - IKR : Reverse beta roll-off corner current
 - Default IKR=infinite (A)**
 - IKR models β_F drop when I_C increase
 - IKR is $\frac{I_C}{BF}$ where effective BR (β_R) reduces to 50%

Q. Bipolar Params ($\beta_F | \beta_R$) : NK

Qspice : NPN - NK.qsch

- NK
 - NK : High-current roll-off coefficient
 - **Default NK=0.5**
 - This parameter is only be used if IKF not infinite

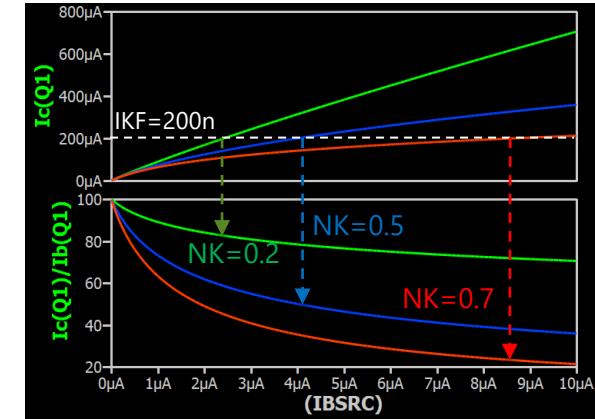
Sweep Parameters
.param Vcollector = 10
.param Ibmax=20 μ
.dc Ibsrc 10n {Ibmax} {Ibmax/100}

Plot Output
.plot Ic(Q1)/Ib(Q1)
.plot Ic(Q1)

Diagram

Model Definition

```
.step param nk list 0.2 0.5 0.7  
.model Qmdl NPN BF=100 IKF=200 $\mu$  NK=nk
```



Q. Bipolar Params (B-E and B-C Diode) : IS, NF, BF, NR, BR

Qspice : NPN - IS NF BF.qsch / NPN - IS NR BR.qsch

- Diode of Base-Emitter
 - **IS** : Saturation Current
 - **NF** : Forward emission coefficient
 - **Default IS = 1e-16A**
 - **Default NF = 1**
 - In this case
 - $I_B = I_{BE} = \frac{I_{CC}}{\beta_F}$
 - $= \frac{1}{\beta_F} I_S \left(e^{\frac{qV_{BE}}{n_F kT}} - 1 \right)$
 - where β_F is **BF**

$$I_B = I_{BE} = \frac{I_{CC}}{\beta_F}$$

$$= \frac{1}{\beta_F} I_S \left(e^{\frac{qV_{BE}}{n_F kT}} - 1 \right)$$

- Diode of Base-Collector
 - **IS** : Saturation Current
 - **NR** : Reverse emission coefficient
 - **Default IS = 1e-16A**
 - **Default NR = 1**
 - In this case
 - $I_B = I_{BC} = \frac{I_{EC}}{\beta_R}$
 - $= \frac{1}{\beta_R} I_S \left(e^{\frac{qV_{BE}}{n_R kT}} - 1 \right)$
 - where β_R is **BR**

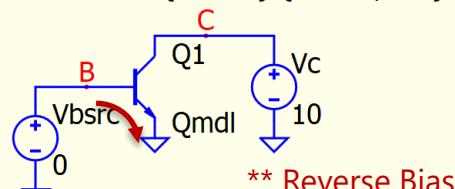
$$I_B = I_{BC} = \frac{I_{EC}}{\beta_R}$$

$$= \frac{1}{\beta_R} I_S \left(e^{\frac{qV_{BE}}{n_R kT}} - 1 \right)$$

Sweep Parameters
.param Vcollector = 10
.param Vbmax=0.8

Plot Output
.plot Ib(Q1)

.dc Vbsrc 0n {Vbmax} {Vbmax/100}



** Reverse Bias D_{BC}

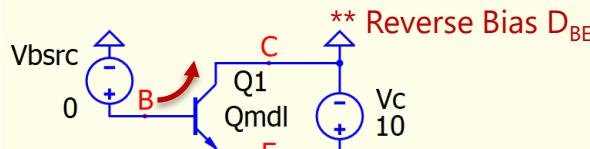
.model Qmdl NPN IS=1e-16 NF=0.7 BF=100

Sweep Parameters
.param Vcollector = 10

Plot Output
.plot Ib(Q1)

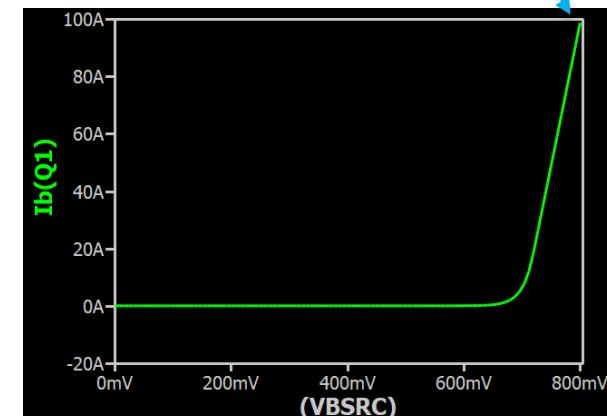
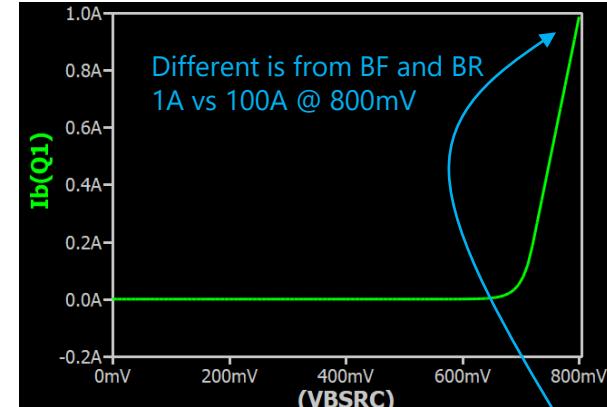
.param Vbmax=0.8

.dc Vbsrc 0n {Vbmax} {Vbmax/100}



** Reverse Bias D_{BE}

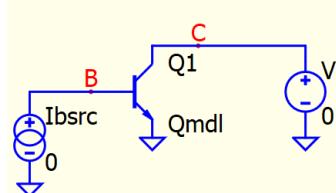
.model Qmdl NPN IS=1e-16 NR=0.7 BR=1



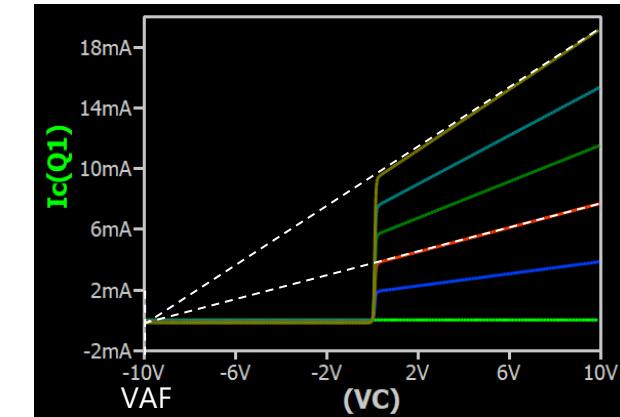
Q. Bipolar Params (Active Region) : VAF

Qspice : NPN - VAF.qsch

- VAF (aka VA)
 - VAF : Forward Early voltage
 - **Default VAF=Infinite (V)**



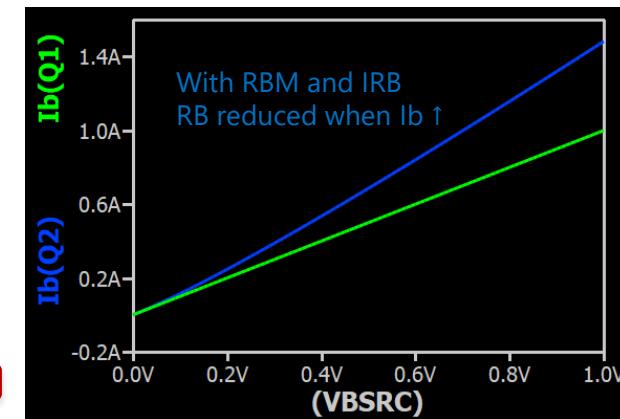
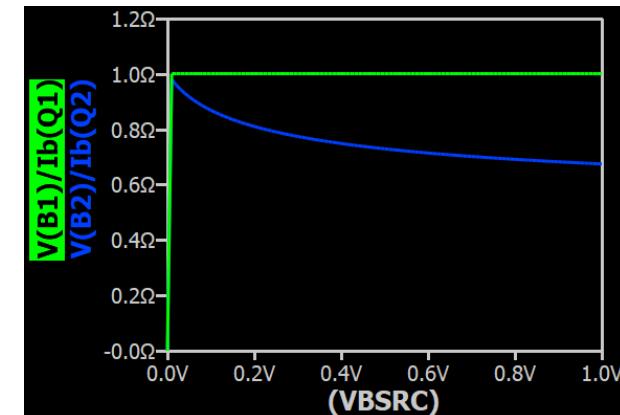
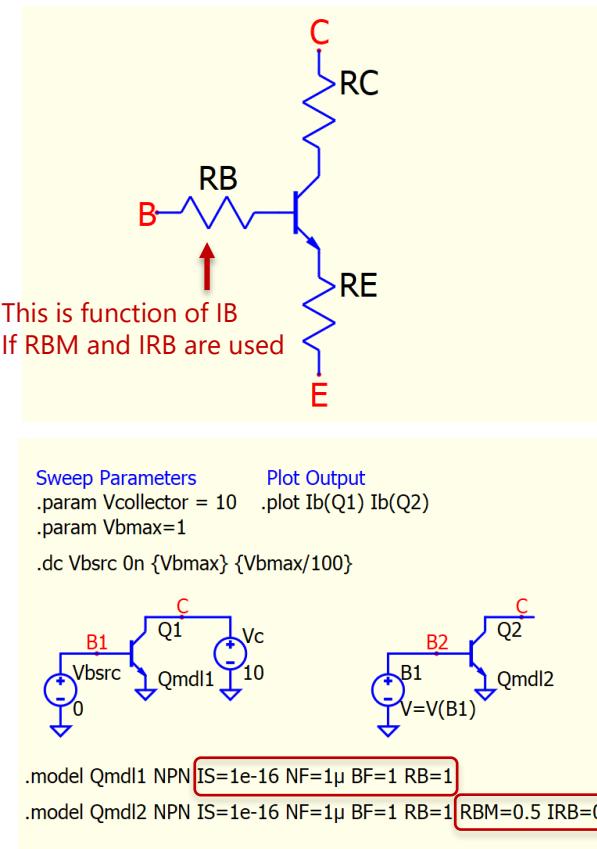
```
.model Qmdl NPN VAF=10
.param Vcmax=10
.param Ibmax=100μ
.dc Vc -10 Vcmax Vcmax/1000 Ibsrc 0 Ibmax Ibmax/5
.plot Ic(Q1)
```



Q. Bipolar Params (Resistance): RB, RC, RE, RBM and IRB

Qspice : NPN - RBM IRB.qsch

- RB, RC, RE
 - RB : Zero bias base resistance
 - If RBM and IRB are used, base resistor is current dependent
 - RC : Collector resistance
 - RE : Emitter resistance
- RBM, IRB
 - RBM : Minimum base resistance
 - IRB : Current for base resistance
 - $R_{B, \text{effective}} @ \text{IRB} = \frac{1}{2} (\text{RB} + \text{RBM})$
 - Default RBM=0Ω
 - Default IRB=Infinite(A)
 - If these 2 parameters are defined, base resistance is function of base current



Q. Bipolar Params (Capacitance) : CJC, MJC, VJC, CJE, MJE, VJE

- B-C, B-E and C-S nonlinear capacitance
 - Model nonlinear capacitor between B-C, B-E and C-S
 - Parameters definition follows diode CJO, M and VJ
 - $C_j = \frac{\text{CJO}}{(1 - \frac{V_D}{V_J})^M}$
 - CJO : Zero-bias junction capacitance
 - M : Grading coefficient
 - VJ : Junction potential

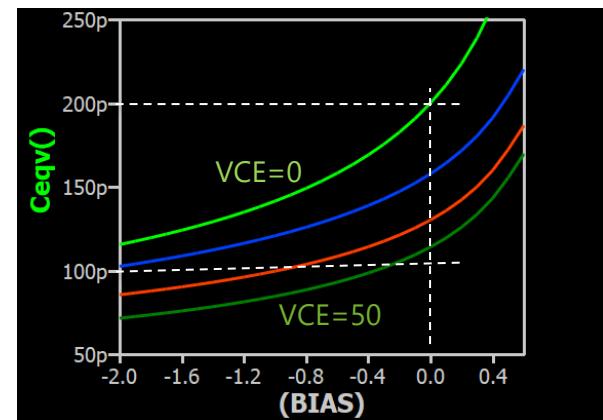
Diode	CJO	M	VJ
B-C	CJC	MJC	VJC
B-E	CJE	MJE	VJE
C-S	CJS	MJS	VJS

- Refer to D. Diode CJO, M and VJ
- C-S normally not modeled

```
.param f=1Meg
.ac list f
.step param bias -2 0.6 0.1
.step param VCE list 0 2 10 50
.func Zim() imag(V(B)/Ib(Q1))
.func Cequiv() -1/2/pi/f/Zim()
.plot Cequiv()

C
Q1
Qmdl
E
V2
VCE
Vbsrc
DC bias AC 1

.model Qmdl NPN CJE=100p MJE=0.5 VJE=1
+CJC=100p MJC=0.5 VJC=1
```



Q. Bipolar Params (Capacitance) : CJC, MJC, VJC, CJE, MJE, VJE

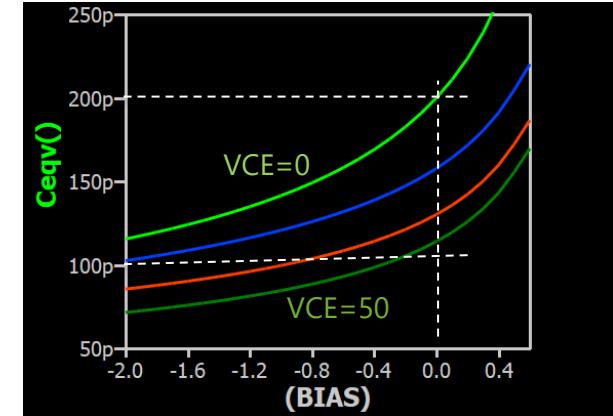
Qspice : NPN - CJC CJE.qsch

- B-C, B-E and C-S nonlinear capacitance
 - Model nonlinear capacitor between B-C, B-E and C-S
 - Parameters definition follows diode CJO, M and VJ
 - $C_j = \frac{C_{JO}}{(1 - \frac{V_D}{V_J})^M}$
 - CJO : Zero-bias junction capacitance
 - M : Grading coefficient
 - VJ : Junction potential
- Simulation
 - This simulation modeled both capacitance between B-C and B-E. Change VCE to observe overall capacitance effect in different bias voltage

```
.param f=1Meg
.ac list f
.step param bias -2 0.6 0.1
.step param VCE list 0 2 10 50
.model Qmdl NPN CJE=100p MJE=0.5 VJE=1
+CJC=100p MJC=0.5 VJC=1
```

Calculate Equivalent C

```
.func Zim() imag(V(B)/Ib(Q1))
.func Ceqv() -1/2/pi/f/Zim()
.plot Ceqv()
```



Diode	CJO	M	VJ
B-C	CJC	MJC	VJC
B-E	CJE	MJE	VJE
C-S	CJS	MJS	VJS

- Refer to D. Diode CJO, M and VJ
- C-S normally not modeled

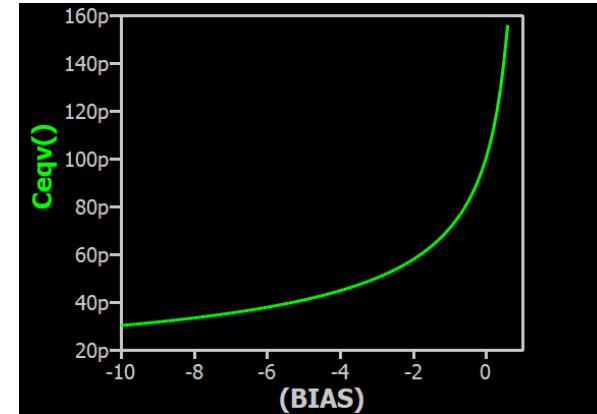
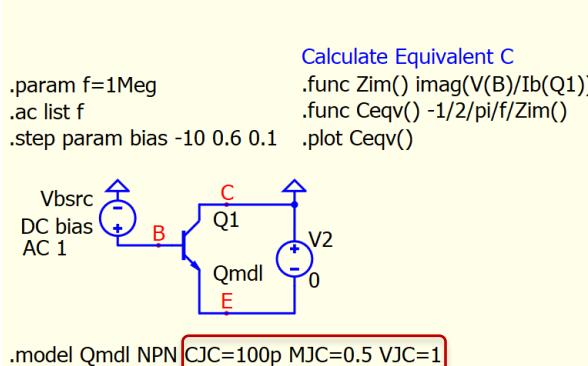
- Simulation Explanation
 - CBC and CBE are nonlinear capacitance of junction diode from B to C and B to E
 - Higher reverse voltage, lower capacitance
 - Therefore, increase VCE, increase reverse voltage of B-C and affects B-C capacitance. However, increase VCE doesn't affect VBE, and no effects in B-E capacitance
 - @VB=0V, when VCE=0, no reverse in both B-C and B-E and capacitance equals CJC+CJE

Q. Bipolar Params (Capacitance) : CJC, MJC, VJC, CJE, MJE, VJE

Qspice : NPN - CJC MJC VJC.qsch / NPN - CJE MJE VJE.qsch

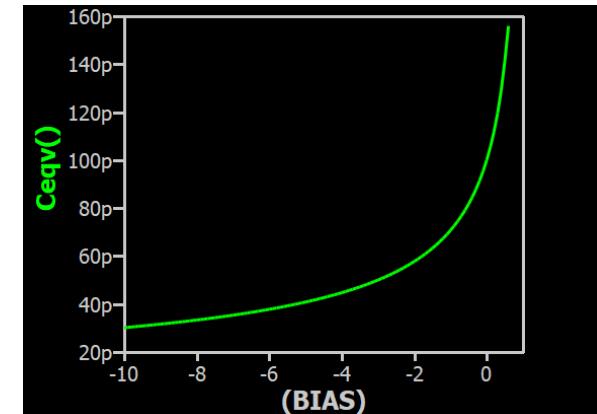
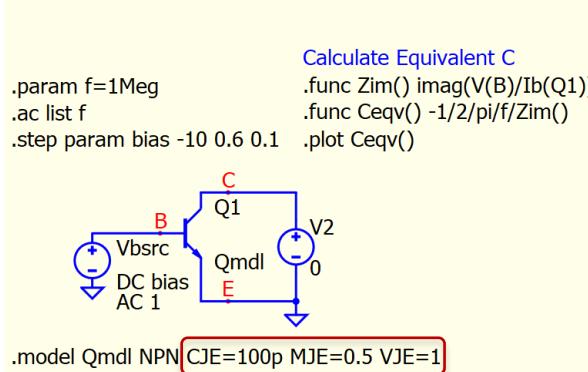
- CJC, MJC and VJC

- CJC : Zero bias B-C capacitance
- MJC : B-C junction grading coefficient
- VJC : B-C junction built in potential
- **Default CJC=0F**
- **Default MJC=0.5**
- **Default VJC=1**



- CJE, MJE and VJE

- CJE : Zero bias B-E capacitance
- MJE : B-E junction grading coefficient
- VJE : B-E junction built in potential
- **Default CJE=0F**
- **Default MJE=0.5**
- **Default VJE=1**



R. Resistor

R. Resistor Instance and Model Parameters

- Resistor Thermal Equation

- $R_T = R_{nom}(1 + T_{C1}\Delta T + T_{C2}\Delta T^2)$, where $\Delta T = T - T_{nom}$
- $R_T = R_{nom} e^{\frac{T_{CE}}{100}\Delta T}$

Resistor Instance Parameters

Name	Description	Units	Default
AC	Value to use for .ac analysis	Ω	RESISTANCE
RESISTANCE	Resistance	Ω	0.0
L ¹	Length	m	1.0
W ¹	Width	m	1.0
M	Number of identical parallel instances		1.0
TEMP	Instance temperature	$^{\circ}\text{C}$	Circuit temperature

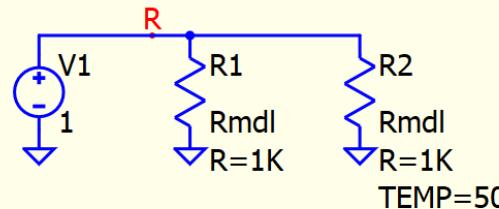
Resistor Model Parameters

Name	Description	Units	Default
DEFW	Default device width	m	1.0
NARROW ¹	Narrowing of resistor	m	1.0
R	Resistor multiplier		1.0
RSH ¹	Sheet resistance(for instance L and W)	Ω/\square	0.0
TC1 ²	1nd order temperature coefficient	$^{\circ}\text{C}^{-1}$	0.0
TC2 ²	2nd order temperature coefficient	$^{\circ}\text{C}^{-2}$	0.0
TCE ²	Exponential order temperature coefficient	$\%/\text{ }^{\circ}\text{C}$	0.0
TNOM	Parameter measurement temperature(aka TREF)	$^{\circ}\text{C}$	27.0

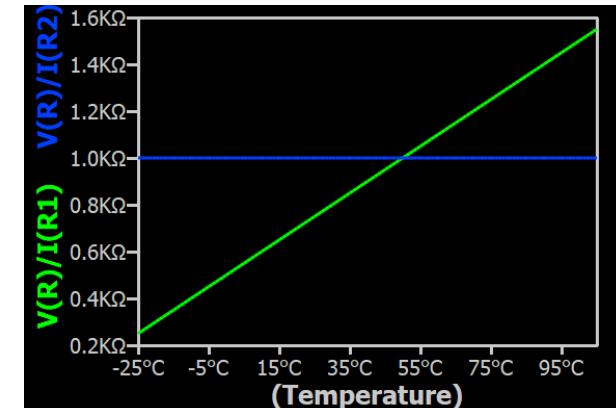
R. Resistor Model Params : Tnom and TEMP (Instance param)

Qspice : R - TNOM TEMP.qsch

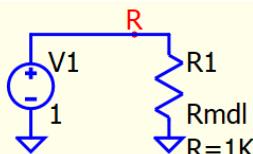
- Tnom and TEMP
 - Tnom : Parameter measurement temperature
 - TEMP : Instance temperature in Instance param
 - **Default Tnom=27°C**
 - **Default TEMP=Circuit Temperature**
 - In this example, instance temperature TEMP is assigned for R2, which forced R2 at TEMP instead of circuit temperature



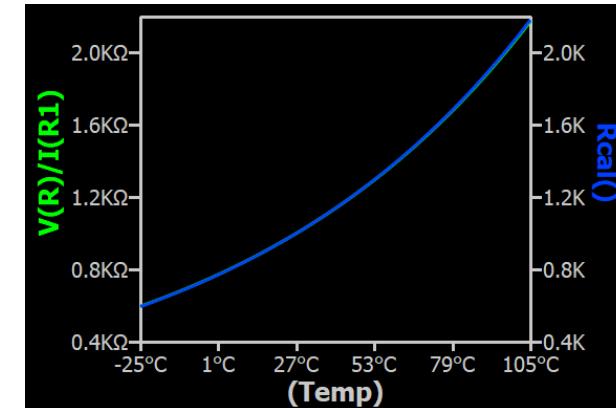
```
.model Rmdl R Tnom=50 TC1=0.01  
.plot V(R)/I(R1) V(R)/I(R2)  
.dc Temp -25 105 1  
.op
```



- TCE
 - TCE : Exponential order temperature coefficient
 - **Default TCE=0%/ $^\circ\text{C}$**
 - $RT = R \cdot \exp((T-T_{nom})/100 \cdot TCE)$
 - If TCE is specified non-zero, TC1 and TC2 are ignored



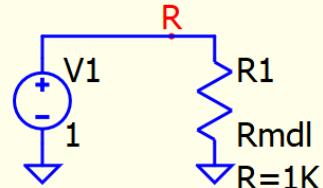
```
.model Rmdl R TCE=1  
.plot V(R)/I(R1) Rcal()  
.dc Temp -25 105 1  
.step param Temp -25 105 1  
.op  
.func Rcal() 1K*exp((Temp-27)/100*1)
```



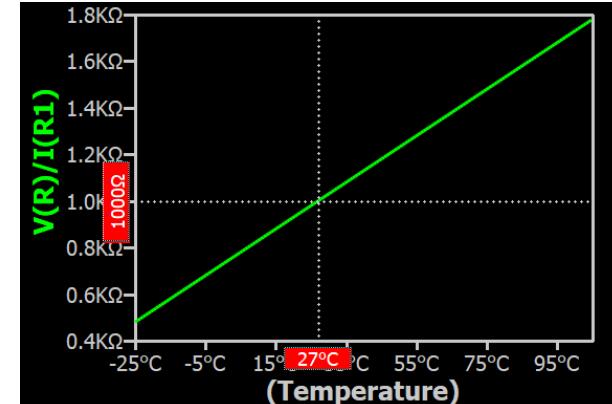
R. Resistor Model Params : TC1 and TC2

Qspice : R - TC1.qsch / R - TC2.qsch

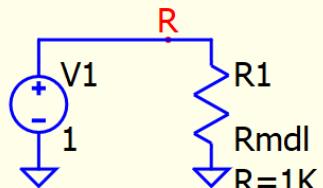
- TC1
 - TC1 : 1nd order temperature coefficient
 - **Default TC1=0°C⁻¹**
 - $RT = R * (1 + TC1 * (T - T_{nom}))$
 - Where T_{nom} is R defined measurement temperature



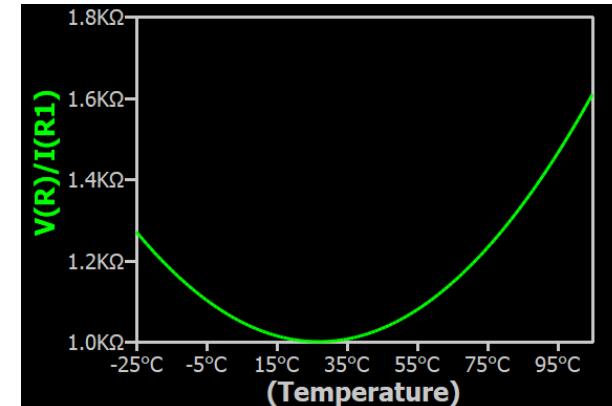
```
.model Rmdl R TC1=0.01  
.plot V(R)/I(R1)  
.dc Temp -25 105 0.001  
.op
```



- TC2
 - TC2 : 2nd order temperature coefficient
 - **Default TC2=0°C⁻²**
 - $RT = R * (1 + TC2 * (T - T_{nom})^2)$
 - TC2 and TC1 can be used together



```
.model Rmdl R TC2=0.0001  
.plot V(R)/I(R1)  
.dc Temp -25 105 1  
.op
```



R. Resistor

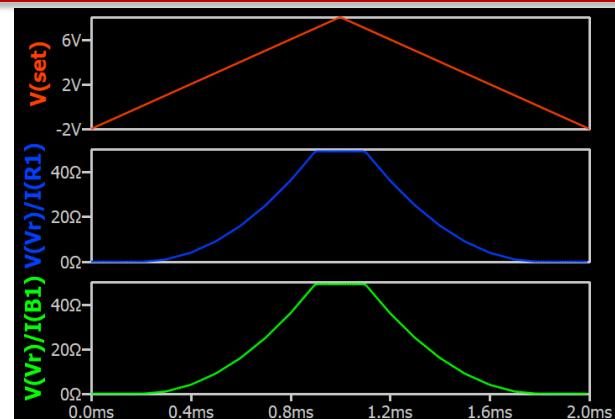
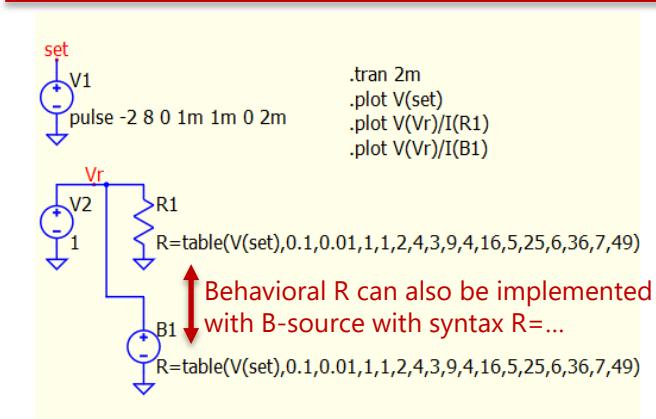
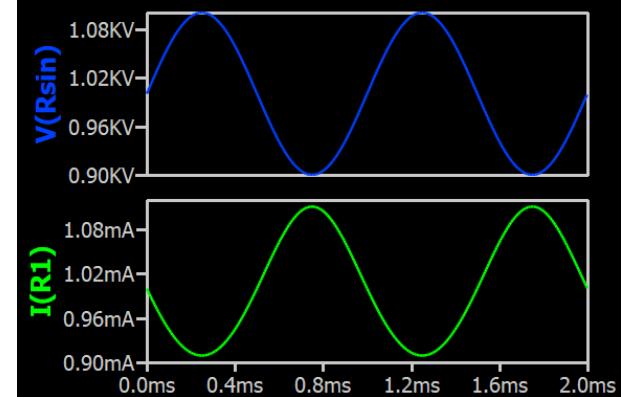
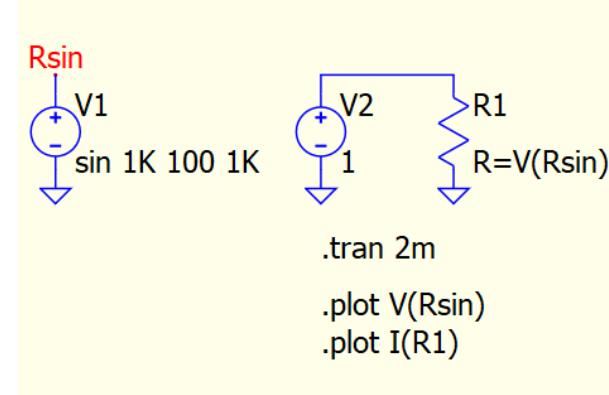
Behavioral Resistor

R. Resistor : Behavioral Resistor (R)

Qspice : Behavioral R Demo 01.qsch ; Behavioral R Demo 02.qsch

- Behavioral Resistor

- To use formula or voltage/current node for resistance, type $R=...$ in <val> of resistor
- Also support to use Behavioral source (B) for behavioral resistor
 - Replace $V=$ expression with $R=$ expression



S. Voltage Controlled Switch

S. Voltage Controlled Switch Model Parameters

- S. Voltage Controlled Switch Model Parameters
 - It is common to define Switch Model for usage as multiple switches in a schematic
 - Syntax: Snnn N1 N2 NC+ NC- <model> [instance parameters]
 - .model <model> SW [model parameters]

Voltage Controlled Switch Model Parameters

Name	Description	Units	Default
ETA ¹	Sub-/over-Threshold conduction	V	0.0
ROFF	Off resistance	Ω	1e6
RON	On resistance	Ω	1.0
TTOL	Temporal tolerance	sec	1e308
VH	Hysteresis voltage	V	0.0
VOFF	Voltage when open	V	0.0
VON	Voltage when closed		
VT	Threshold voltage		

Input Control
Voltage

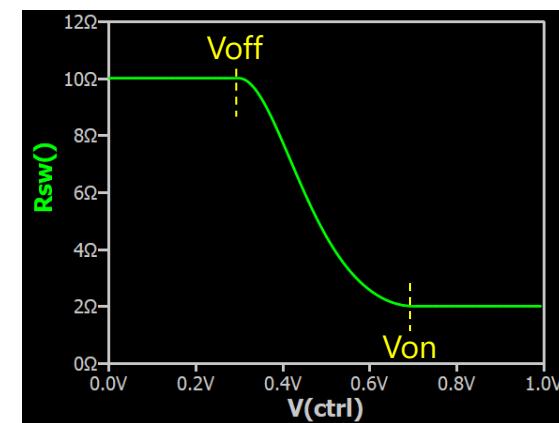
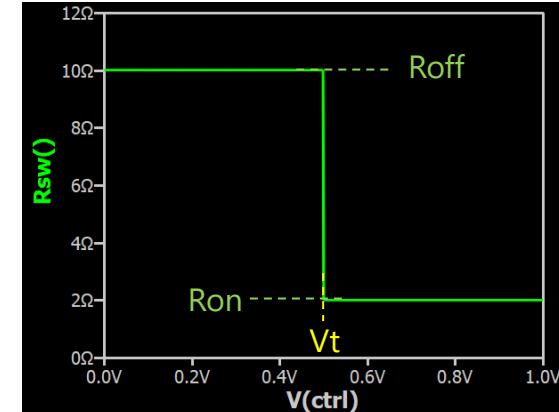
S. Switch Model Params : Ron, Roff, VT, Von and Voff

Qspice : Switch - Ron Roff VT.qsch

- RON, ROFF, VT
 - Ron : On resistance
 - Roff : Off resistance
 - VT : Threshold voltage
 - **Default RON=1Ω**
 - **Default ROFF=1MegΩ**
 - **Default VT=0V**
- VON, VOFF
 - Von : Voltage when closed
 - Voff : Voltage when open
 - **Default VON=0V**
 - **Default VOFF=0V**
 - switch smoothly transitions between on and off
 - If VT and VH are specified, VON and VOFF are ignored

```
.model mSW SW Ron=2 Roff=10 Vt=0.5 VH=0
pulse 0 1 0 1 1 1 4
.tran 4
.func Rsw() V(sw)/I(I1)
.plot Rsw()
.plot V(ctrl)
```

```
.model mSW SW Ron=2 Roff=10 Von=0.7 Voff=0.3
pulse 0 1 0 1 1 1 4
.tran 4
.func Rsw() V(sw)/I(I1)
.plot Rsw()
.plot V(ctrl)
```



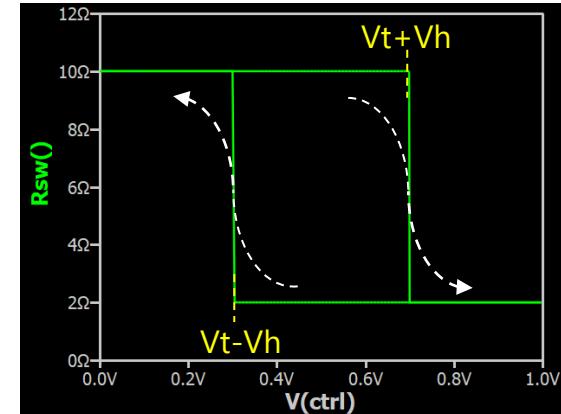
S. Switch Model Params : VH

Qspice : Switch - VH.qsch

- VH
 - V_h : Hysteresis voltage
 - **Default $VH=0V$**

```
.model mSW SW Ron=2 Roff=10 Vt=0.5 Vh=0.2
pulse 0 1 0 1 1 1 4
.tran 4
.func Rsw() V(sw)/I(I1)
.plot Rsw()
.plot V(ctrl)
```

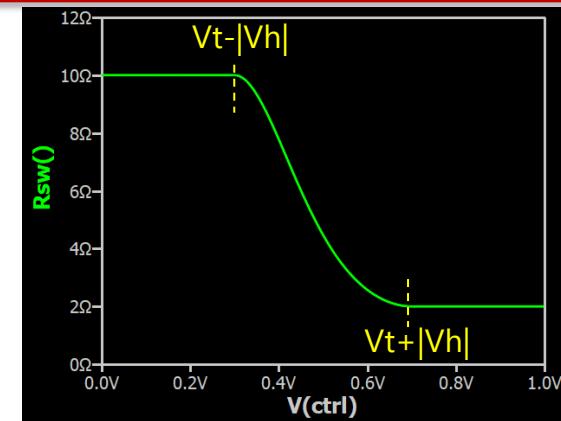
+ve V_h



- VH (-vegitive explains)
 - Negative V_h
 - If VH is negative the switch smoothly transitions between on and off

```
.model mSW SW Ron=2 Roff=10 Vt=0.5 Vh=-0.2
pulse 0 1 0 1 1 1 4
.tran 4
.func Rsw() V(sw)/I(I1)
.plot Rsw()
.plot V(ctrl)
```

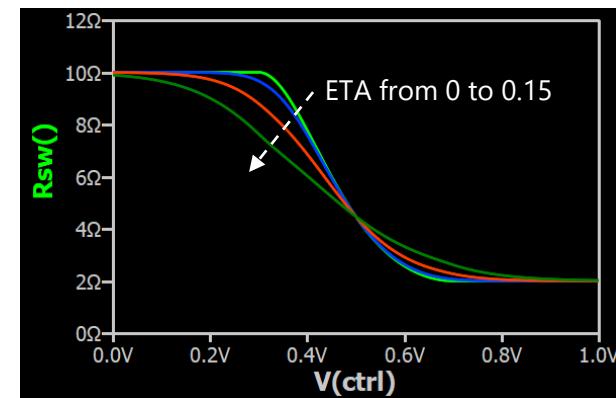
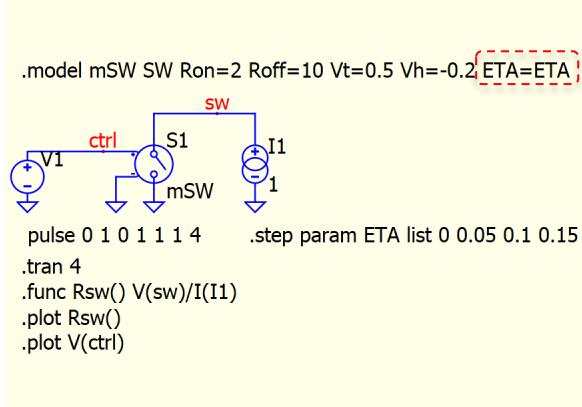
-ve V_h



S. Switch Model Params : ETA

Qspice : Switch - ETA.qsch

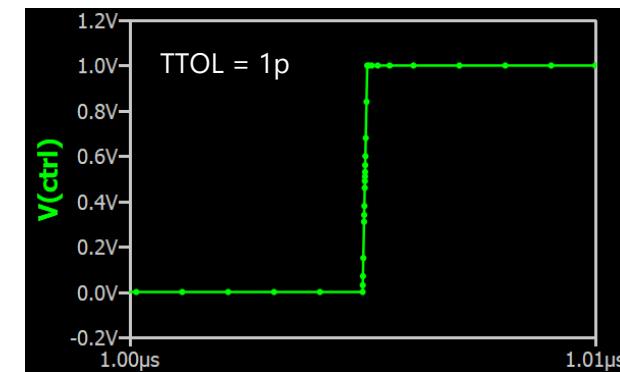
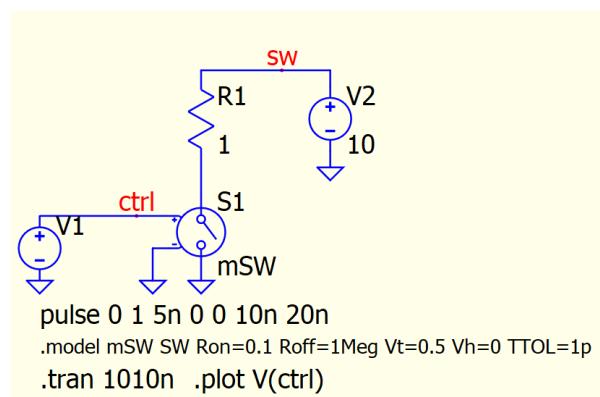
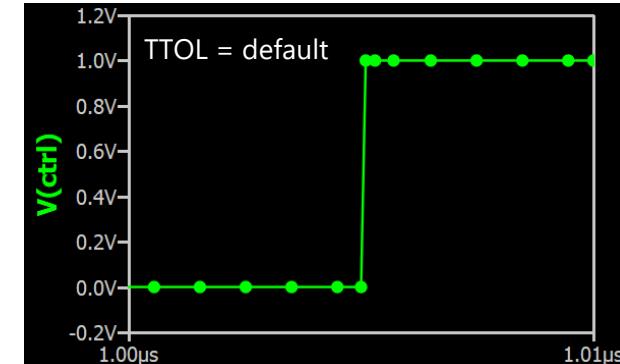
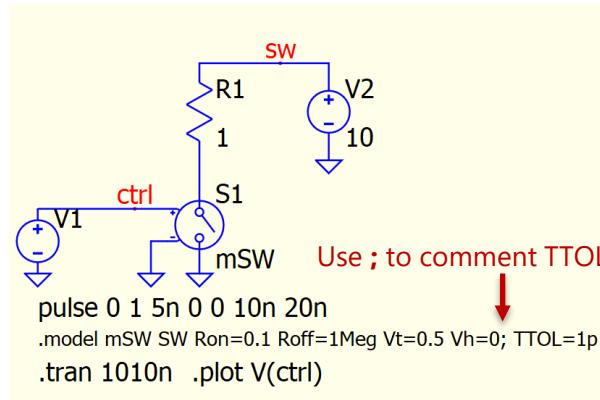
- **ETA**
 - ETA : Sub-/over- Threshold conduction
 - **Default ETA=0**
 - Prevents the control voltage Jacobian from vanishing
 - Only effective in smoothly transitions cases
 - V_t is negative
 - V_{on} / V_{off} are used without V_t and V_h



S. Switch Model Params : TTOL

Qspice : Switch - TTOL.qsch

- TTOL
 - Ttol : Temporal tolerance
 - **Default TTOL=1e308s**
- Usage
 - TTOL allows one to determine how accurately the switch time should be found
 - It only affect timestep at switch time, which maintain simulation speed but improve accuracy at switching or logic action



T. Lossless Transmission Line

T. Lossless Transmission Line Instance Parameters

- T. Lossless Transmission Line
 - Syntax: Tnnn L+ L- R+ R- Zo=<value> Td=<value>

Lossless Transmission Line Instance Parameters

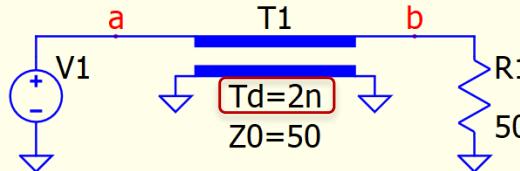
Name	Description	Units	Default
F ¹	Frequency	Hertz	1GHz
NL ¹	Normalized length at frequency given	wavelengths	1/4
TD	Transmission delay	sec	
Z0	Characteristic impedance(aka ZO)	Ω	50Ω

T. Instance Params : TD, F and NL

Qspice : Tline - Td.qsch ; Tline - F NL.qsch

- TD and Z0

- Td : Transmission delay
- Z0 : Characteristic Impedance
- **Default TD is not set**
- **Default Z0=50Ω**
- This simulation terminate transmission line with characteristic impedance Z0, no reflection of signal
- If TD is given, F and NL are ignored



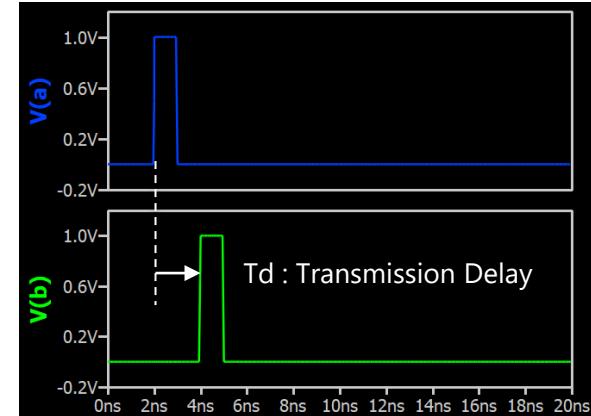
pulse 0 1 2n 0 0 1n 1 1

.options MAXSTEP=1p

.tran 20n

.plot V(b)

.plot V(a)



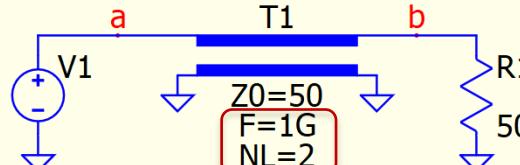
- F and NL

- F : Frequency
- NL : Normalized length at frequency given
- **Default F=1GHz**
- **Default NL=1/4**
- Equation

$$NL = \frac{Length}{Wavelength} = \frac{Length}{\lambda}$$

$$\text{Period per } \lambda : T = \frac{1}{F}$$

$$\text{Delay } T_d = T \times \frac{Length}{\lambda} = \frac{NL}{F}$$



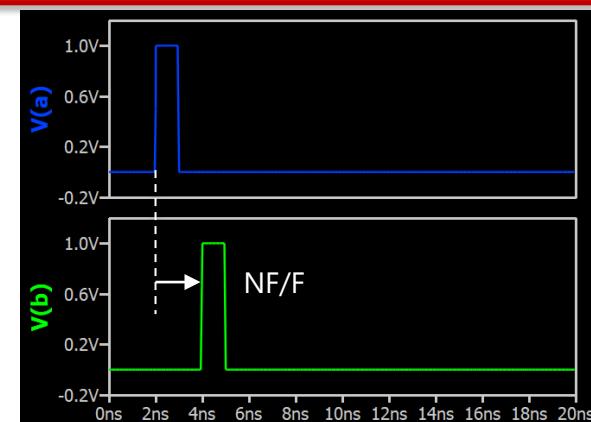
pulse 0 1 2n 0 0 1n 1 1

.options MAXSTEP=1p

.tran 20n

.plot V(b)

.plot V(a)



V. Voltage Source

V. Voltage Source - Instance Params

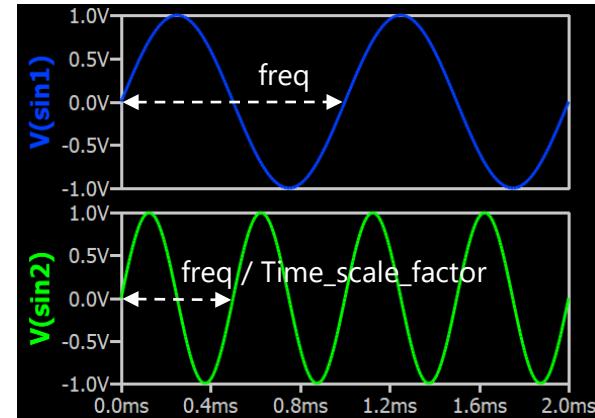
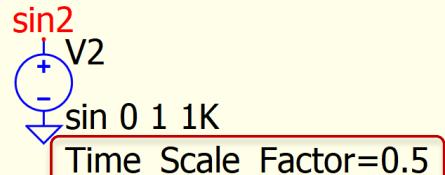
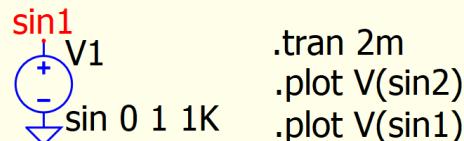
- V. Voltage Source
 - Syntax: Vnnn N+ N- <voltage> [Additional Instance Parameters]

Voltage Source Instance Parameters				
Name	Description	Units	Default	
AC	AC magnitude, optionally followed by phase angle	V, °	0.	
ACMAG	AC Magnitude	V	0.	
ACPHASE	AC Phase	°	0.	
DC	DC source value	V	0.	
EXP	Exponential source description			
LOG	Interpolate between PWL and CHIRP points		(not set)	
PULSE	Pulse description			
PWL	Piecewise linear description			
RSER	Internal series resistance			
SFFM	Single frequency FM description			
SINE	Sinusoidal source description(aka SIN)			
TIMECTRL	Time step control, one of NONE, LIMITS ¹ , BREAKS ² , BOTH	String	LIMITS	
TIME_SCALE_FACTOR	Multiplies times, divides frequencies		1.	
VALUE_SCALE_FACTOR	Multiplies voltages		1.	
XTRAP	Extrapolate beyond PWL and CHIRP points		(not set)	

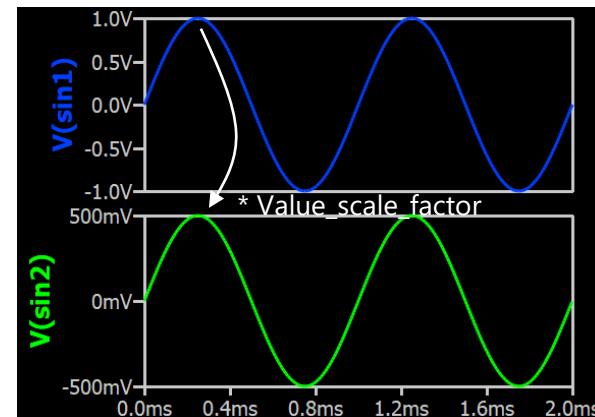
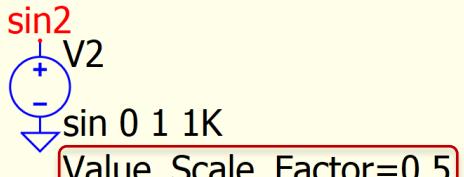
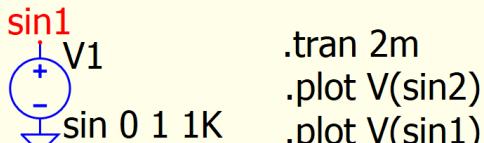
V. Voltage Source - Instance Params : Time/Value_Scale_Factor

Qspice : Vsource - Time_Scale_Factor.qsch / Vsource - Value_Scale_Factor.qsch

- TIME_SCALE_FACTOR
 - Time_Scale_Factor : multiples times, divides frequency
 - Default Time_Scale_Factor=1



- VALUE_SCALE_FACTOR
 - Value_Scale_Factor : multiples voltages
 - Default Value_Scale_Factor=1

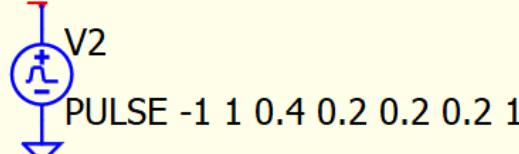


V. Voltage Source : PULSE (Pulse)

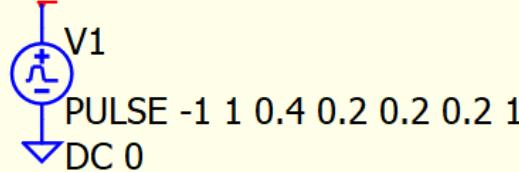
Qspice : Vsource PULSE.qsch

Syntax : PULSE V1 V2 Td Trise Tfall Ton Tperiod

pulse_woDC

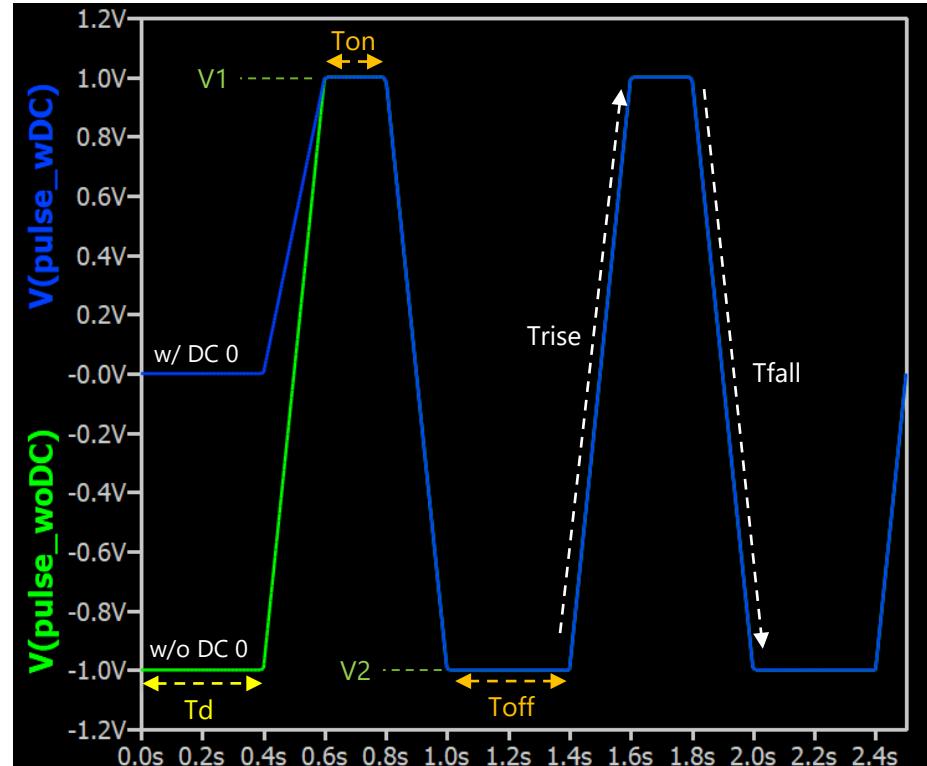


pulse_wDC



.tran 2.5

.plot V(pulse_woDC) V(pulse_wDC)

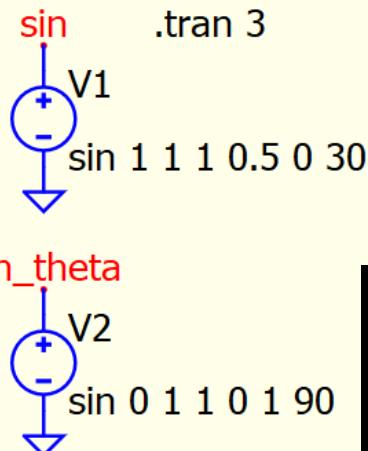


V. Voltage Source : SIN (Sine Wave)

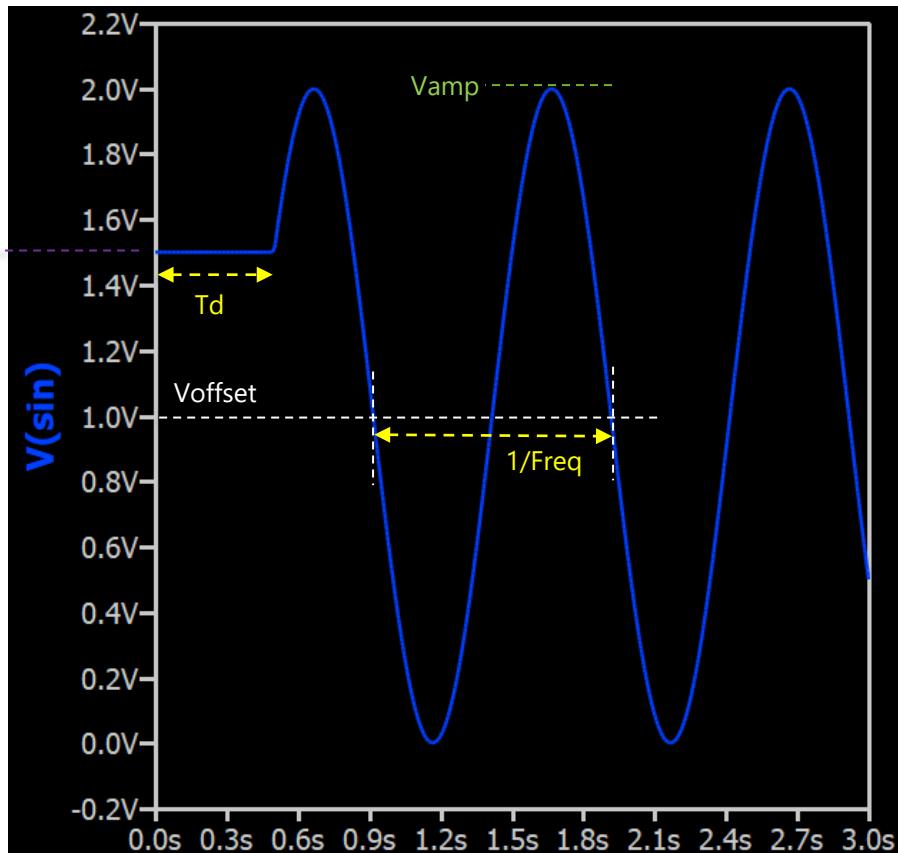
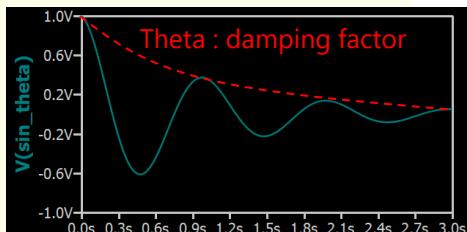
Qspice : Vsource SIN.qsch

Phi : level = $V_{offset} + \sin(\Phi)$
e.g.: $=1+\sin(30^\circ) = 1.5$

Syntax : SIN Voffset Vamp Freq Td Theta Phi



Amplitude drops by
 $e^{-1} \sim 0.378$ in $1/\Theta$ seconds



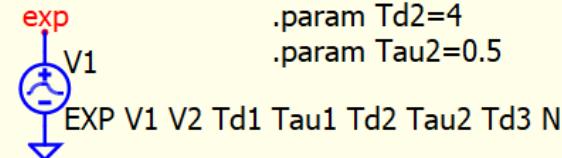
V. Voltage Source : EXP (Exponential)

Qspice : Vsource EXP.qsch

```
.plot V(expTperiod) V(exp)
```

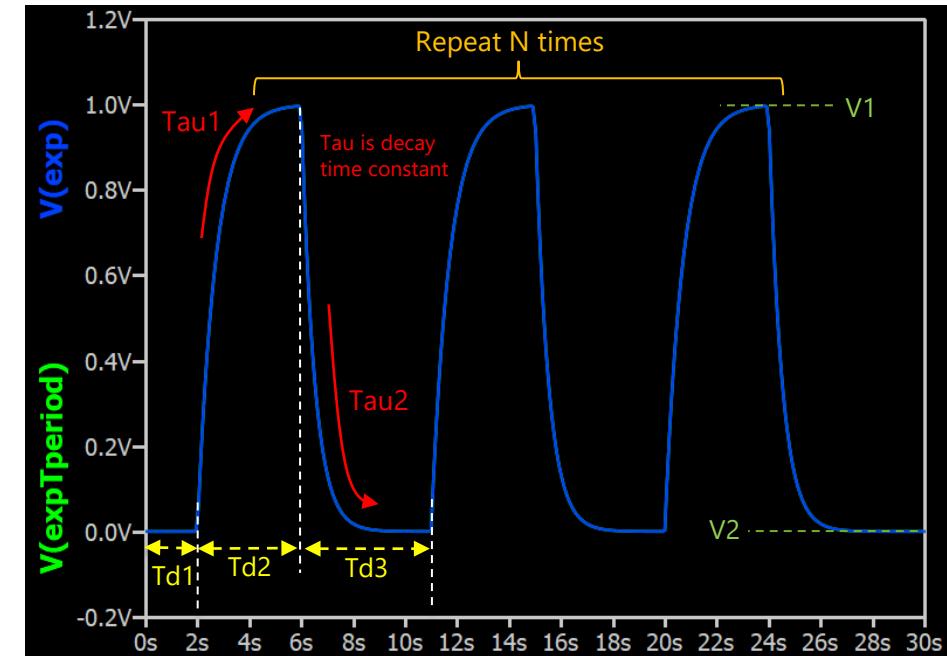
Syntax : EXP V1 V2 Td1 Tau1 Td2 Tau2 Td3 N Tperiod

```
.tran 200          .param V1=0      .param Td3=9  
                   .param V2=1      .param N=3  
                   .param Td1=2      .param Tperiod=50  
                   .param Tau1=0.7  
                   .param Td2=4  
                   .param Tau2=0.5
```



expTperiod

```
EXP V1 V2 Td1 Tau1 Td2 Tau2 Td3 N Tperiod
```

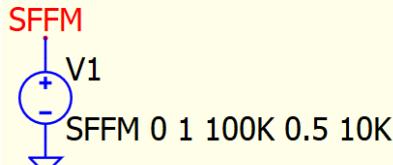


V. Voltage Source : SFFM (Single Frequency FM)

Qspice Vsource SFFM.qsch

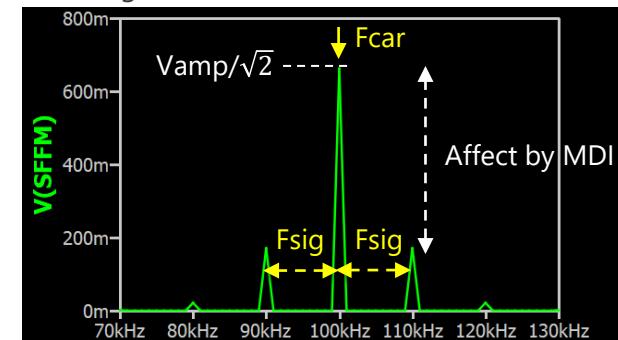
- SFFM
 - Single Frequency FM
 - It is hard to observe FM signal in time domain waveform
 - FFT is used to explain its nature

Syntax : SFFM Voff Vamp Fcar MDI Fsig



.tran 10/10K
.plot V(SFFM)

FFT magnitude is RMS

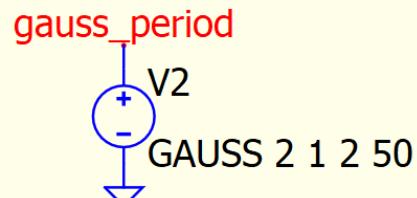
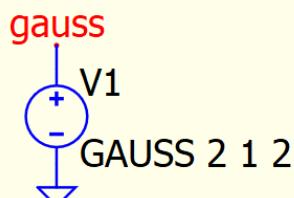


- Transient formula
 - $V_{off} + V_{amp} \sin((2\pi F_{car} \cdot time) + MDI \sin(2\pi F_{sig} \cdot time))$

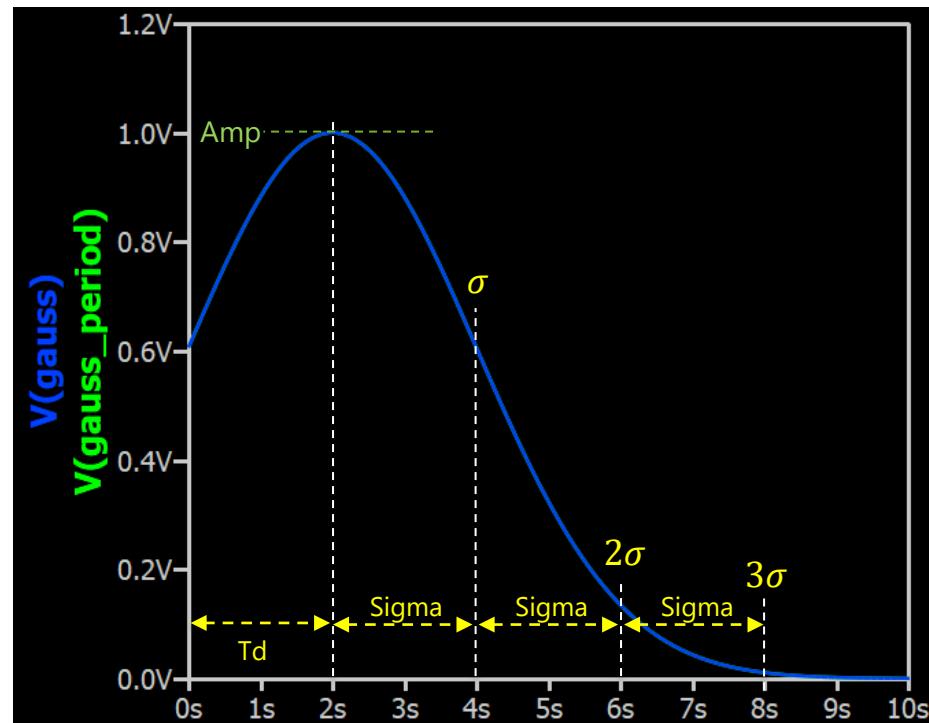
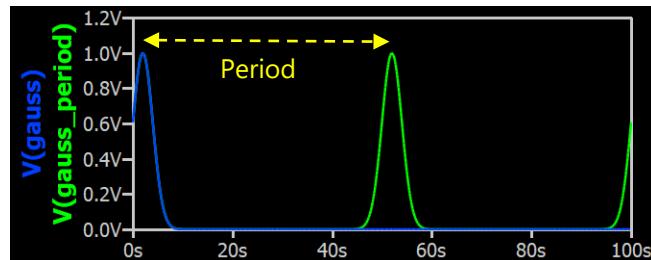
V. Voltage Source : GAUSS (Gaussian Pulse)

Qspice Vsource GAUSS.qsch

Syntax : GAUSS Td Amp Sigma [Period]



```
.plot V(gauss_period) V(gauss)
.tran 100
```

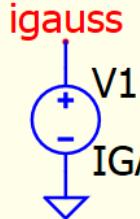


V. Voltage Source : IGAUSS (Imaginary Gaussian Pulse)

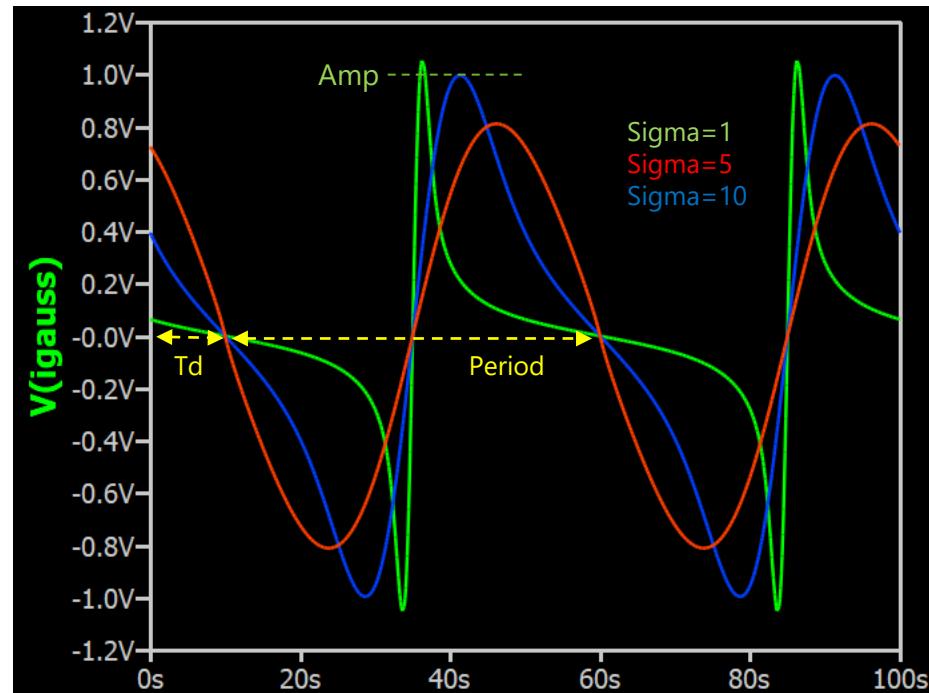
Qspice Vsource IGAUSS.qsch

Syntax : IGAUSS Td Period Sigma Amp

.step param Sigma list 1 5 10



.plot V(igauss)
.tran 100

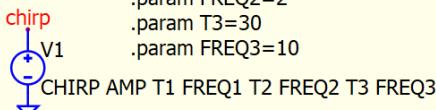


V. Voltage Source : CHIRP (Piece-wise Linear Chirp)

Qspice Vsource Chirp.qsch

Syntax : CHIRP(AMP T1 FREQ1 T2 FREQ2 [...]) [LOG] [XTRAP]

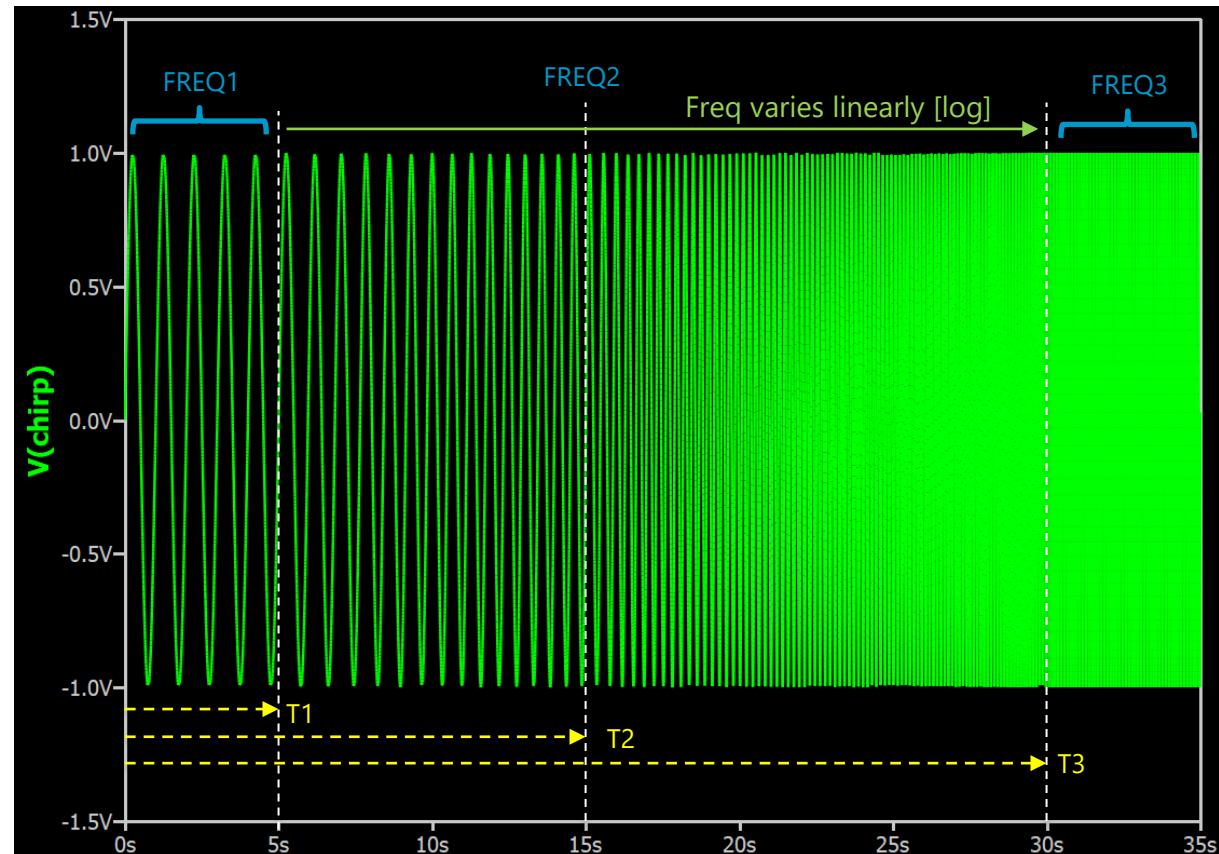
```
.param AMP=1  
.param T1=5  
.param FREQ1=1  
.param T2=15  
.param FREQ2=2  
.param T3=30  
.param FREQ3=10
```



```
.plot V(chirp)  
.tran 35
```

```
.options MAXSTEP=1/1000
```

XTRAP : extrapolate beyond PWL and CHIRP points



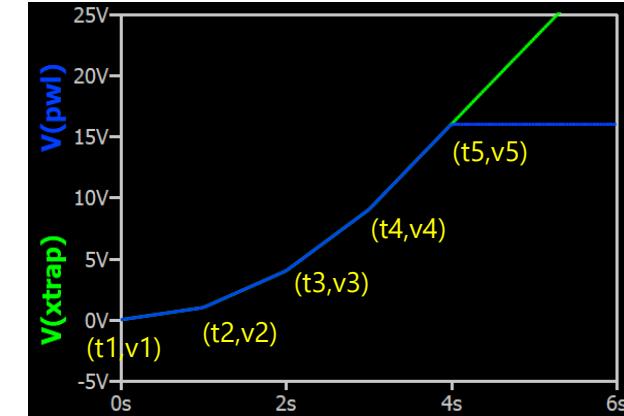
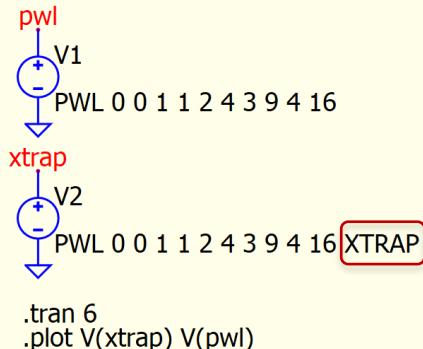
V. Voltage Source : PWL (Piece-wise Linear) – XTRAP and LOG

Qspice : Vsource PWL-Xtrap.qsch/ Vsource PWL-Log.qsch

- Basic Usage and XTRAP

- Standard
 - last value will hold
- Xtrap
 - Extrapolate beyond PWL and CHIRP points

Syntax : PWL(t1 v1 t2 v2 t3 v3...) [LOG] [XTRAP]

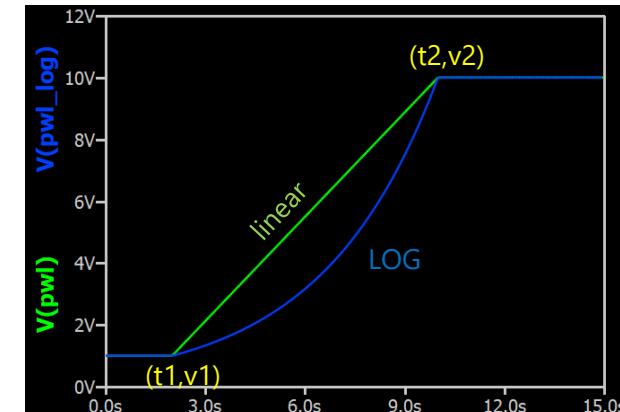
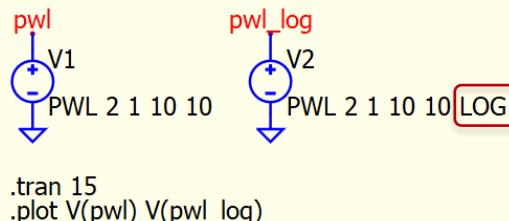


- LOG

- Log

- Interpolate between PWL and CHIRP points with log function

Syntax : PWL(t1 v1 t2 v2 t3 v3...) [LOG] [XTRAP]



V. Voltage Source : PWL (Piece-wise Linear) – REPEAT

Qspice : Vsource PWL-Repeat.qsch

- PWL Repeat Syntax

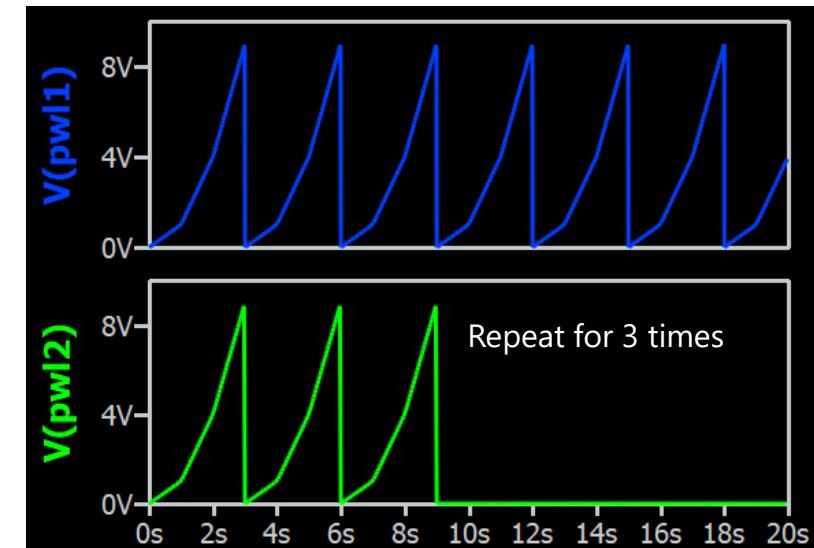
- Vnnn N+ N- PWL **REPEAT FOREVER** t1 v1 t2 v2 t3 v3... **ENDREPEAT**
- Vnnn N+ N- PWL **REPEAT FOR N** t1 v1 t2 v2 t3 v3... **ENDREPEAT**
 - N is number of times
 - ** last voltage value of a repeated PWL will be ignored and forced to be equal to the first value**

Syntax : PWL FOR[EVER] [times] (t1 v1 t2 v2 t3 v3...) Endrepeat

pwl1
V1
PWL REPEAT FOREVER (0 0 1 1 2 4 3 9 3+1p 0) Endrepeat

pwl2
V2
PWL REPEAT FOR 3 (0 0 1 1 2 4 3 9 3+1p 0) Endrepeat

.tran 20
.plot V(pwl2)
.plot V(pwl1)

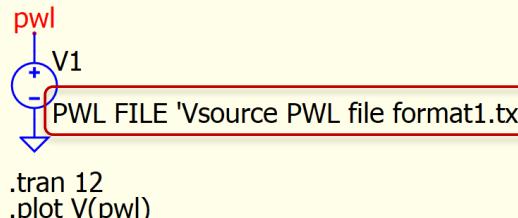


V. Voltage Source : PWL (Piece-wise Linear) – Load from file

Qspice : Vsource PWL file.qsch / Vsource PWL-Repeat-File.qsch

- PWL : load from file
 - Filename is quoted with single ('filename') or double ("filename") quotation
 - Delimiter can be space [] or comma [,]
 - To load from file, syntax is
 - FILE filename
 - Support repeat syntax, but remember last value in repeated PWL is ignored and forced to be equal to first value

Syntax : PWL FILE file.txt [LOG] [XTRAP]



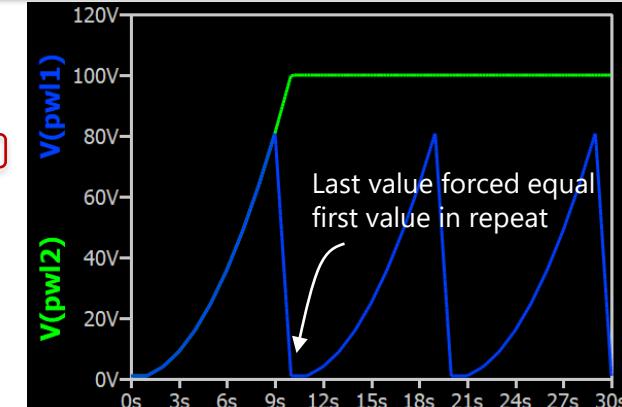
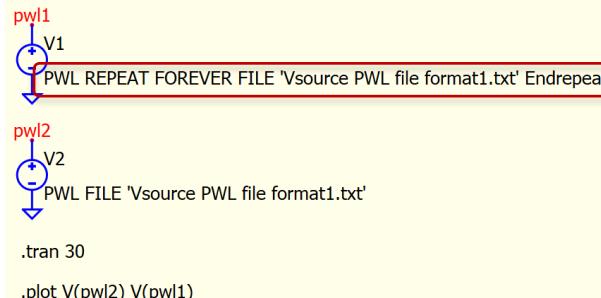
Vsource PWL file format1.txt

1	1	1
2	2	4
3	3	9
4	4	16
5	5	25
6	6	36
7	7	49
8	8	64
9	9	81
10	10	100

Vsource PWL file format2.txt

1	1,1
2	2,4
3	3,9
4	4,16
5	5,25
6	6,36
7	7,49
8	8,64
9	9,81
10	10,100

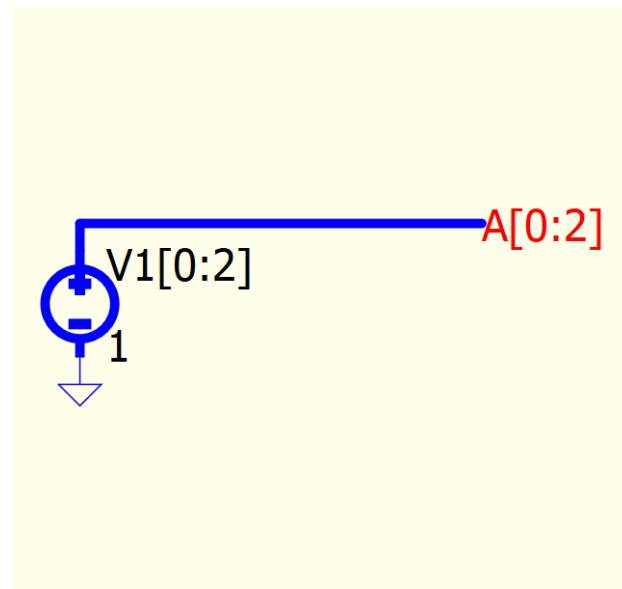
Syntax : PWL FOR[EVER] [times] FILE 'filename' Endrepeat



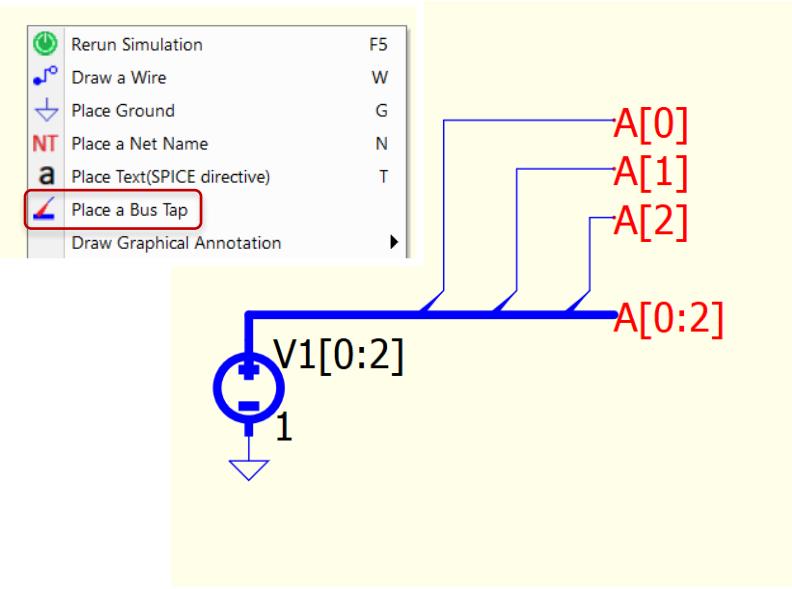
W. Wire and BUS

W. Wire and Bus : Introduction

- [1] Place a voltage source and draw wire
- [2] Rename voltage source to V1[0:2]
- [3] Place net name as A[0:2]
- [4] Now, the wire becomes a bus, in this example, A[m] is voltage of V1[m]

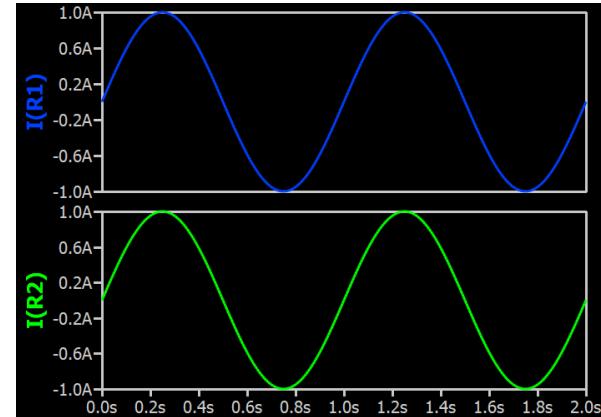
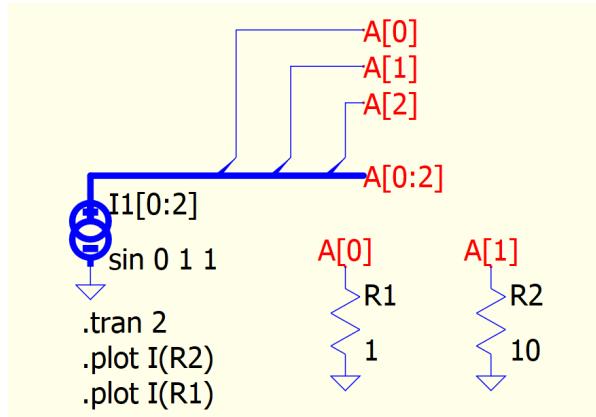


- [5] Right click and select "Place a Bus Tap"
- [6] Place net name to bus tap wire



W. Wire and Bus : Bus for V/I-source

- Identical I-source
 - File : BUS - Isrc.qsch
 - Bus can replicate current or voltage source for multiple nodes usage
 - In netlist
 - $I1[0] 0 A[0] \sin 0 1 1$
 - $I1[1] 0 A[1] \sin 0 1 1$
 - $I1[2] 0 A[2] \sin 0 1 1$
 - ** .dc for $I1$ won't work as three I-sources $I1[0]$, $I1[1]$ and $I1[2]$ in this format



W. Wire and Bus : Bus for Ø-Device

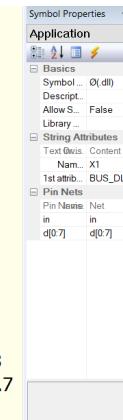
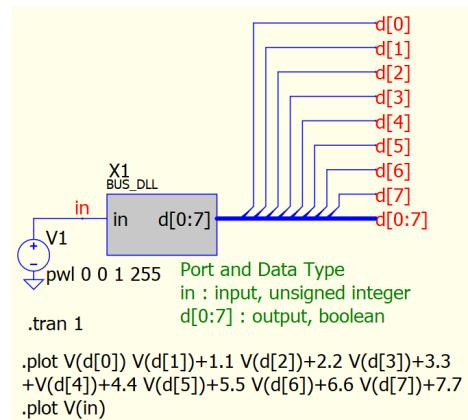
- Bus for Ø-Device

- Files

- BUS_DLL.qsch
 - bus_dll.cpp
 - bus_dll.dll

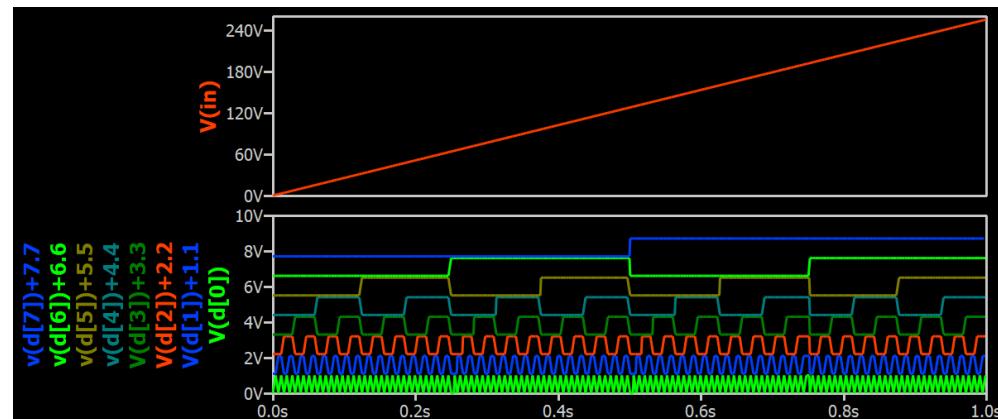
- Procedure

- For Ø-Device, defines an output port with label name with net[0:7] array
 - To output bit, data type should be boolean
 - In template generation, it creates variable name as `net_0_` for bit 0 and `net_7_` for bit 7



```
extern "C" __declspec(dllexport) void bus_dll
{
    unsigned int in = data[0].ui; // input
    bool &d_0 = data[1].b; // output
    bool &d_1 = data[2].b; // output
    bool &d_2 = data[3].b; // output
    bool &d_3 = data[4].b; // output
    bool &d_4 = data[5].b; // output
    bool &d_5 = data[6].b; // output
    bool &d_6 = data[7].b; // output
    bool &d_7 = data[8].b; // output

    // Implement module evaluation code here:
    d_0 = in & 0x01;
    d_1 = in & 0x02;
    d_2 = in & 0x04;
    d_3 = in & 0x08;
    d_4 = in & 0x10;
    d_5 = in & 0x20;
    d_6 = in & 0x40;
    d_7 = in & 0x80;
}
```



Y. Piezoelectric Crystal

Y. Piezoelectric Crystal : Instance Parameters

- Y. Piezoelectric Crystal
 - Syntax: Ynnn N+ N- <frequency1> dF=<value> Ctot=<value> [Q=<value>]

Piezoelectric Crystal Instance Parameters

Name	Description	Units	Default
CTOT	Total capacitance as measured at DC	F	
DF ¹	Difference between series and parallel resonant frequencies	Hz	
FREQUENCY ¹	Resonant frequency	Hz	
IC	Initial internal current(Used with UIC on the .tran)	A	0.0
M	Number of parallel devices		1.0
RSER	Series resistance	Ω	Determined from Q
Q	Quality factor		$1.6e13 \div \text{FREQUENCY}^2$

$$Q = \min(1e6, \frac{1e13}{\text{FREQUENCY}^2})$$

If default equation is used

- If DF > 0 : **Series Resonant Freq = Frequency** and **Parallel Resonant Freq = Frequency + DF**
- If DF < 0 : **Series Resonant Freq = Frequency + DF** and **Parallel Resonant Freq = Frequency**

Y. Piezoelectric Crystal : Formula and Equivalent Circuit

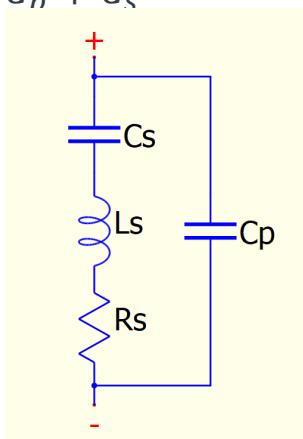
Qspice : Y Crystal - Equivalent Circuit.qsch

- Piezoelectric Crystal Equation

- Series Resonant Frequency : $f_s = \frac{1}{2\pi\sqrt{L_s C_s}}$
- Parallel Resonant Frequency : $f_p = \frac{1}{2\pi\sqrt{\frac{C_p C_s}{C_p + C_s}}}$
- Crystal Oscillators Q-factor : $Q = \frac{X_L}{R} = \frac{2\pi f L_s}{R_s}$
- Total Capacitance : $C_{TOT} = C_n + C_s$

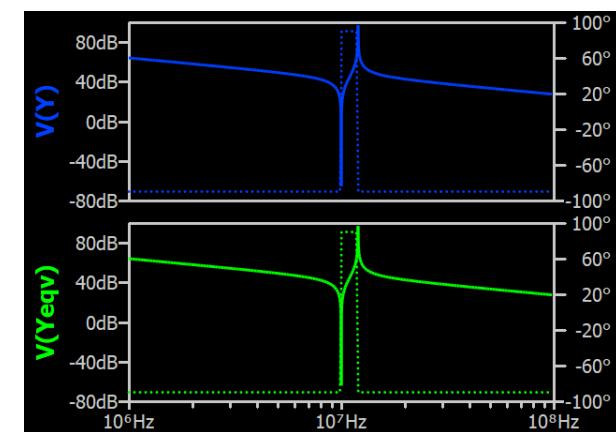
- Calculated Value

- $C_p = \left(\frac{f_s}{f_p}\right)^2 C_{TOT}$
- $C_s = C_{TOT} - C_p$
- $L_s = \frac{1}{(2\pi f_s)^2 C_s}$
- $R = \frac{2\pi f L}{Q}$



.ac dec 1000 1Meg 100Meg
.plot V(Yeqv)
.plot V(Y)

Yeqv



\tilde{A} -Device

Ã-Device

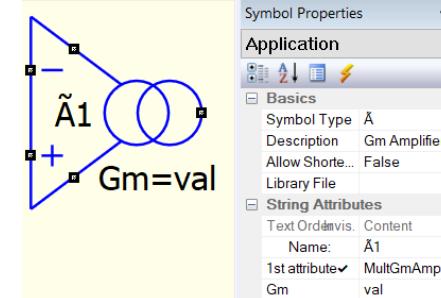
- Ä-Device
 - Syntax

*Ãnnn VDD VSS OUT IN- IN+ MULT+ MULT- IN-- IN++ EN ¥¥¥¥¥¥¥ *<TYPE>* [INSTANCE PARAMETERS]*

- \tilde{A} -device models a highly configurable Gm block than can mimic the behavior of a complementary MOSFET output, there are two types MULTGMAMP and RROPAMP

A-Device Types	
Type	Behavior
MULTGMAMP	Multiplying Gm Amplifier
RROPAMP	Rail-to-Rail Output OpAmp

- In Symbol Properties > 1st attribute
- View > Netlist : from device syntax



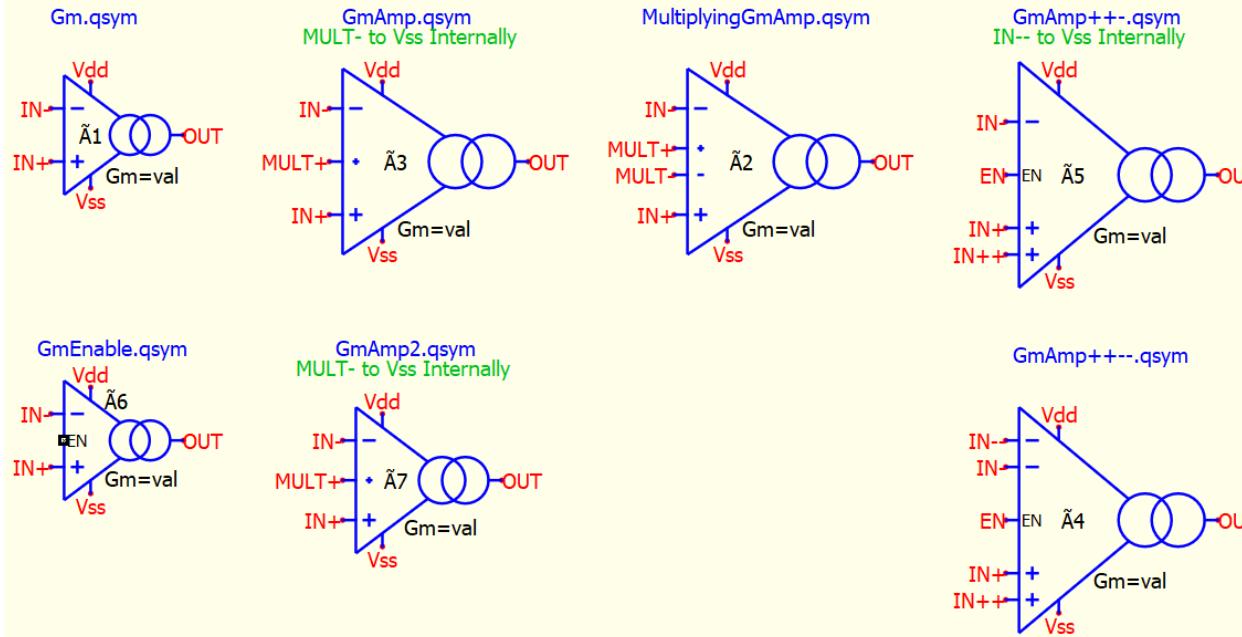
```
* C:\Users\kelvinleung\Documents\QSPICE\Untitled.qsch
A1 Y0 Y1 Y2 Y3 Y4 Y Y Y Y Y Y Y Y MultGmAmp Gm=val
.end
```

\tilde{A} -Device [MULTGMAMP]

- \tilde{A} -Device

- Syntax: **$\tilde{A}nnn\ VDD\ VSS\ OUT\ IN-\ IN+\ MULT+\ MULT-\ IN--\ IN++\ EN\ \#\#\#\#\#\#<TYPE>\ [INSTANCE\ PARAMETERS]$**
- Formula in Linear Region : $I_{out} = GM * V(MULT+, MULT-) * V(\min(IN+, IN++), \max(IN-, IN--))$

Symbols & IP > Behavioral > analog



Ä-Device Instance Parameters in MULTGMAMP

Ä-Device Instance Parameters

Name	Description
CAPINCM	Common eigenmode input capacitance
CAPINNM	Normal eigenmode input capacitance
CAPVDD	Capacitance from output to Vdd
CAPVSS	Capacitance from output to Vss
EN	Equivalent input voltage noise density
ENK	EN corner frequency
FT	3dB bandwidth of transconductance with no voltages slewing
GM	Ideal transconductance
IC	Initial condition of $V_{in} \times V_{mult}$
IN	Equivalent input current noise density
INF	Common mode input current noise density proportional to frequency
INK	IN corner frequency
IOUT	Maximum sourcing current
ISNK	Maximum sinking current
ISNKKNEE	Sharpness of Maximum sinking current limit
ISRC	Maximum sourcing current
ISRCKNEE	Sharpness of max sourcing current limit
M	Number of parallel devices

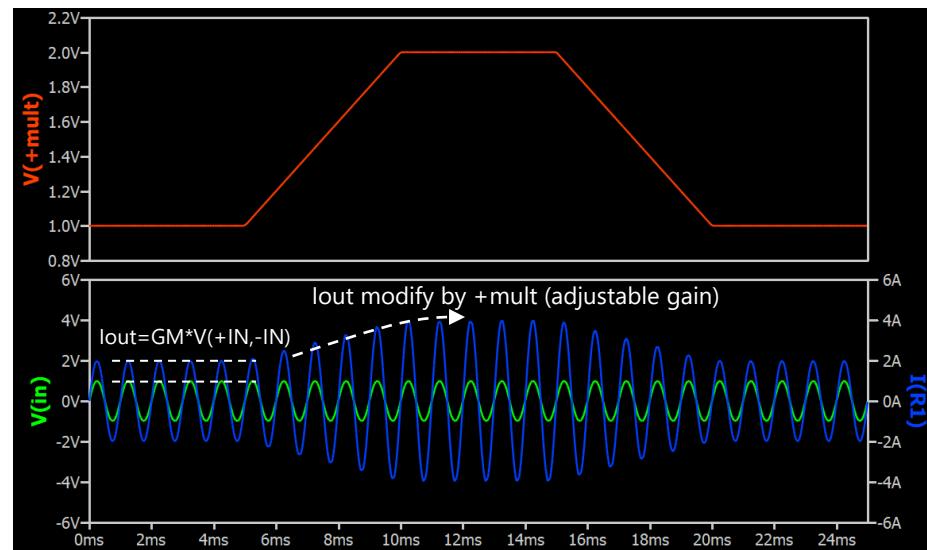
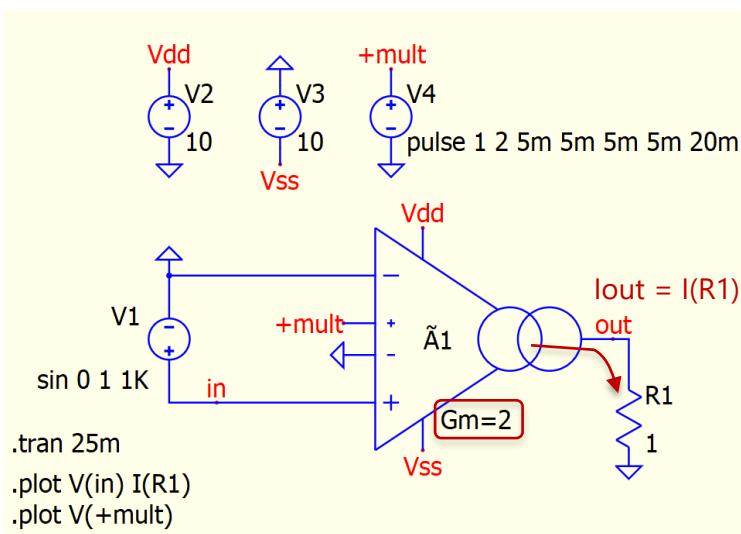
REF	Logic threshold for enable(from Vss)
ROUT	Additional impedance added to output(2*R to Vdd, 2*R to Vss)
TEMP	Instance temperature
TTOL	Temporal tolerance for enable & UVLO
UVLO	Minimum supply voltage
VCROSS	Cross conduction voltage range
VDSAT	Voltage where gm starts to switch over to a resistance
VDSAT1	Voltage where gm starts to switch over to a resistance(top FET)
VDSAT2	Voltage where gm starts to switch over to a resistance(bottom FET)
VINHIGH	Output range measured from positive rail
VINHIGHKNEE	Sharpness of positive input range limit
VINLOW	Input range measured from negative rail
VINLOWKNEE	Sharpness of negative input range limit
VOS1	Offset voltage for input
VOS2	Offset voltage for multiplying input
VOUTMAX	Maximum output voltage measured from negative rail
VOUTMIN	Minimum output voltage measured from negative rail

MULTGMAMP : Ideal transconductance (GM)

Qspice : Multgmamp - Gm.qsch

- Gm : Ideal transconductance

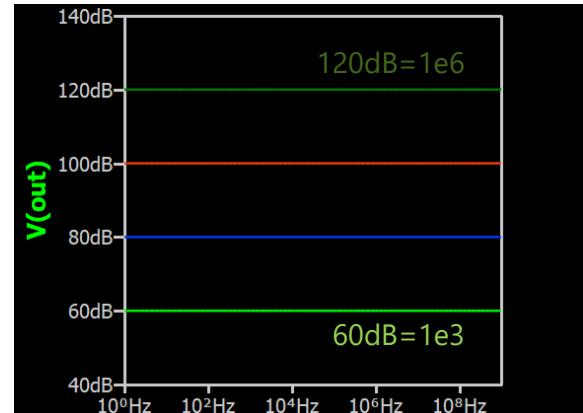
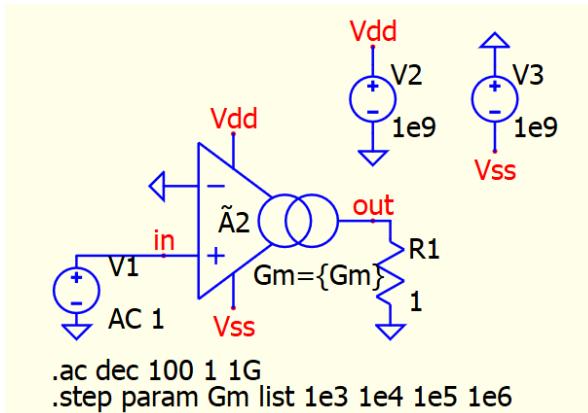
- Without IN++ and IN--, formula becomes $I_{out} = GM * V(MULT+, MULT-) * V(IN+, IN-)$
- For ideal operation amplifier, GM is infinity
- In Qspice, Gm cannot be set to 0



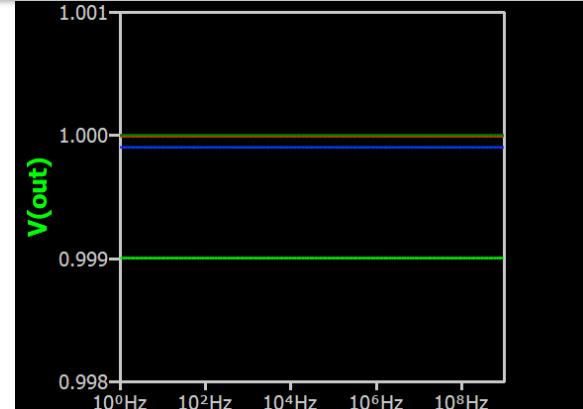
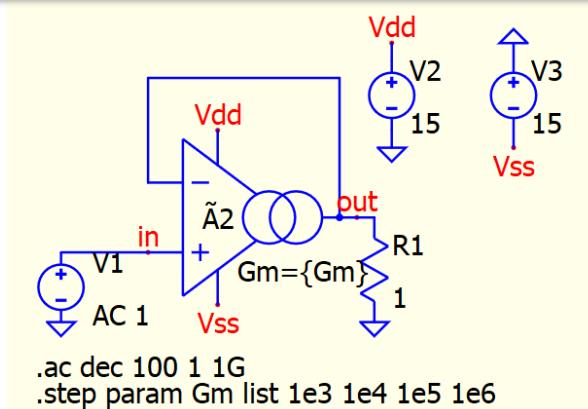
MULTGMAMP : Ideal transconductance (GM)

Qspice : Multgmamp - Gm freq response.qsch ; Multgmamp - Buffer.qsch

- Gm : Ideal transconductance
 - MULTGMAMP has ideal frequency response if without instance parameters
 - No default value of Gm, must define by user



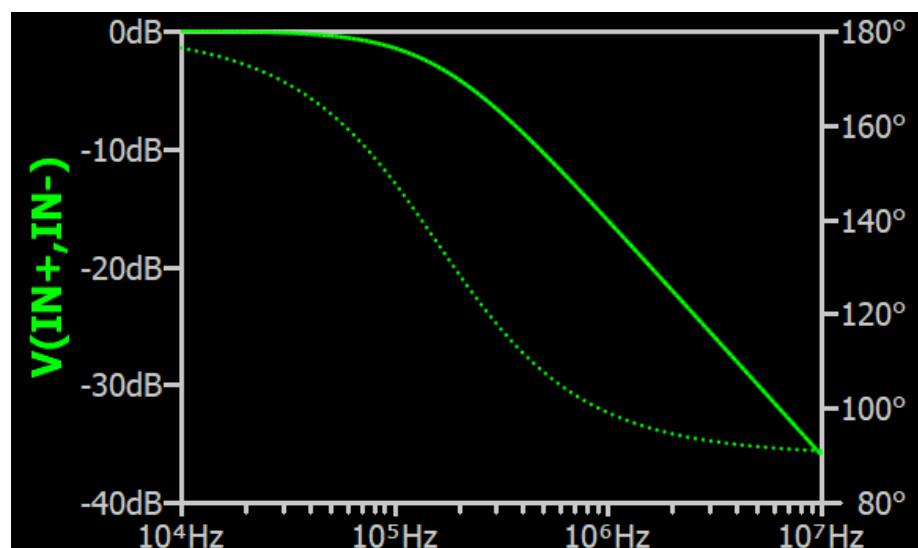
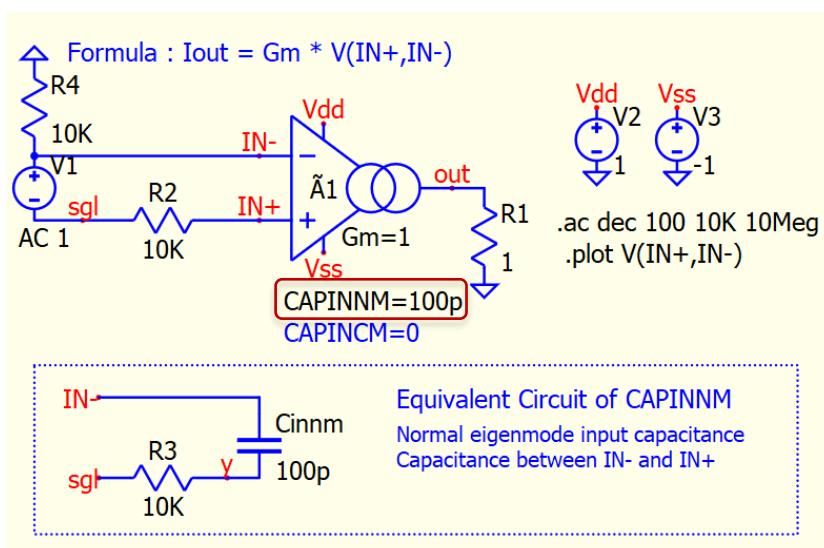
- Demo : Buffer Circuit
 - Demonstrate op-amp close loop ideal characteristic with different Gm value



MULTGMAMP : Normal eigenmode input capacitance (CAPINNM)

Qspice : Multgmamp - Capinnm.qsch

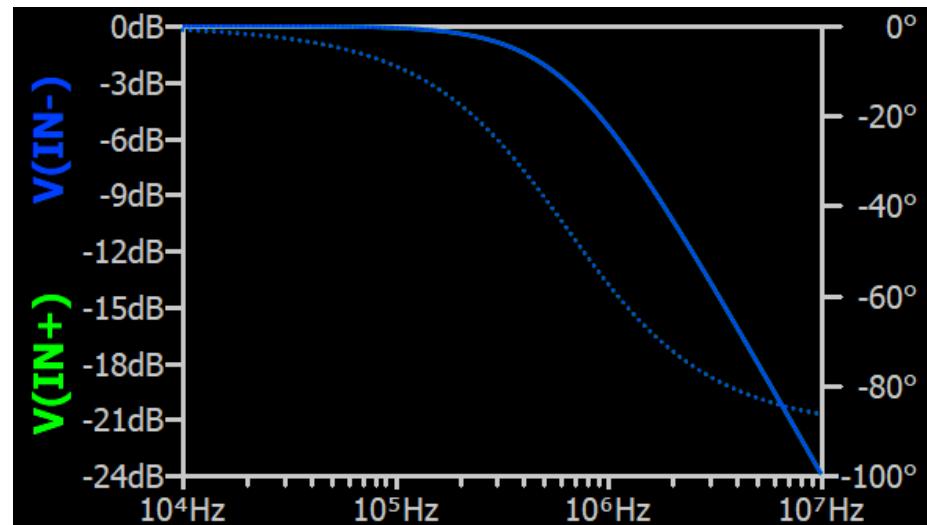
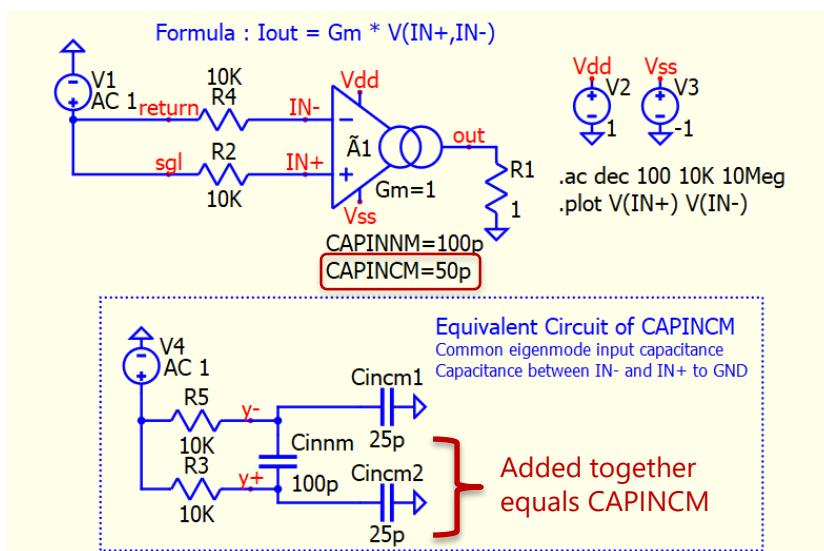
- CAPINNM : Normal eigenmode input capacitance
 - Default CAPINNM=0
 - This capacitance is equivalent between IN- and IN+



MULTGMAMP : Common eigenmode input capacitance (CAPINCM)

Qspice : Multgmamp - Capincm.qsch

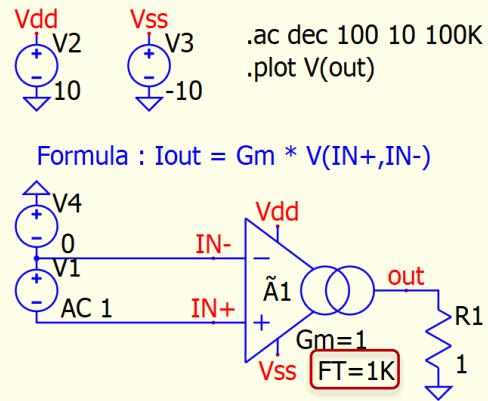
- CAPINCM : Common eigenmode input capacitance
 - Default CAPINCM=0
 - This capacitance is between IN- to GND and IN+ to GND



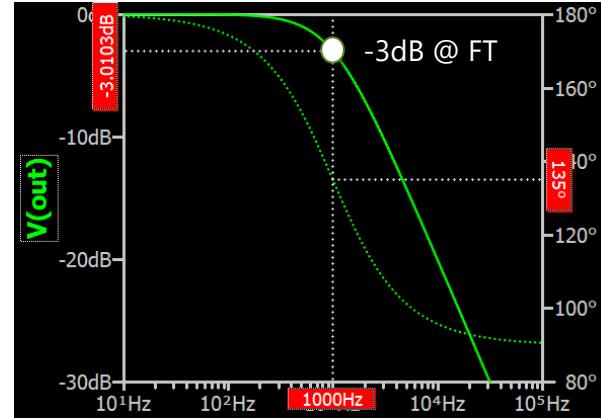
MULTGMAMP : FT 3dB Bandwidth

Qspice : Multgmamp - FT.qsch

- FT (3dB Bandwidth)
 - FT : 3dB bandwidth of transconductance with no voltages slewing
 - **Default FT=0** (i.e. infinite)



```
.ac dec 100 10 100K  
.plot V(out)
```

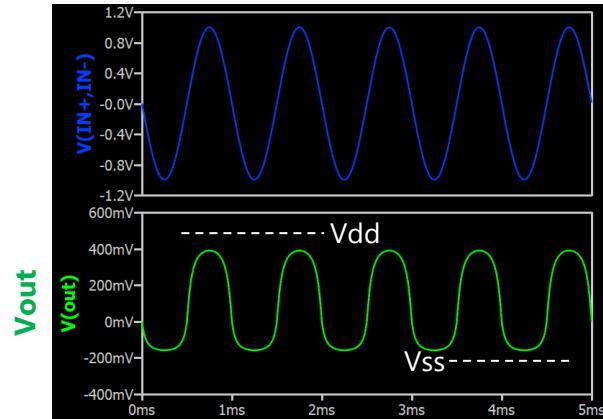
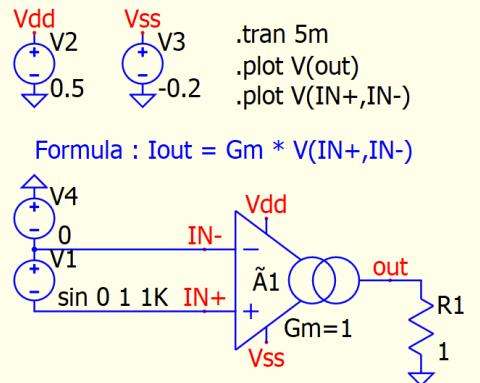


MULTGMAMP : Output Voltage Vdd, Vss and VDSAT

Qspice : Multgmamp - Vdd Vss.qsch ; Multgmamp - VDSAT.qsch

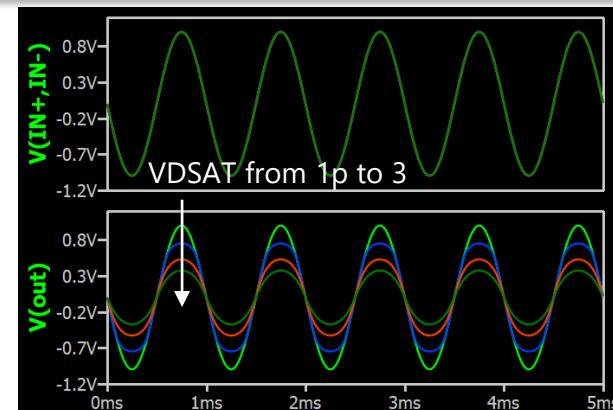
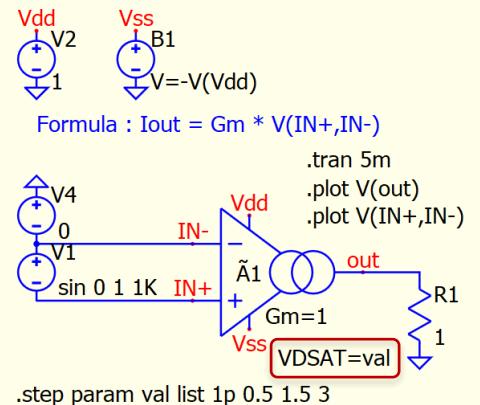
- Vdd and Vss Nets

- This is not parameters but Net 1 and Net 2 in \tilde{A} -Device
- Output voltage swing is limited by Vdd and Vss
- ** In this example, Vout cannot reach Vdd and Vss because a default VDSAT is set**



- VDSAT

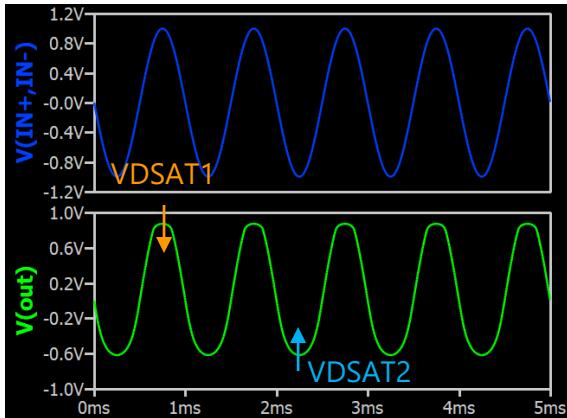
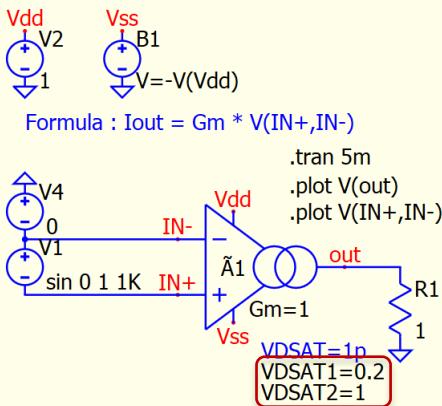
- V_{dsat} : Voltage where gm starts to switch over to a resistance
- Default VDSAT = 0.5**
- VDSAT=0** forced its to default
- VDSAT=1p** for no saturation



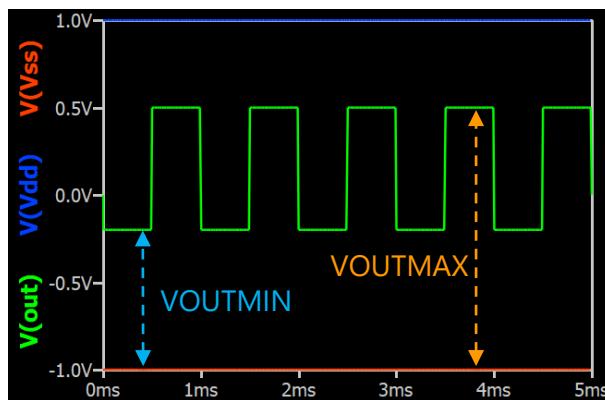
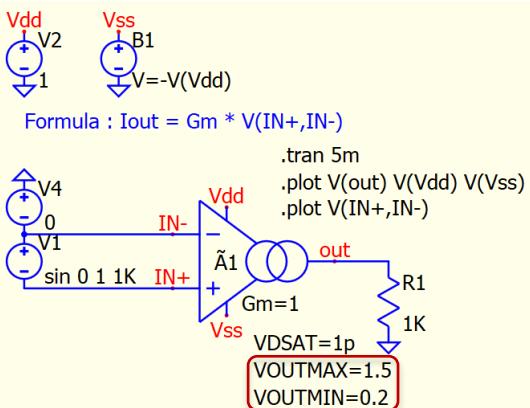
MULTGMAMP : Output Voltage VDSAT1, VDSAT2, VOUTMIN, VOUTMAX

Qspice : Multgmamp - VDSAT1 VDSAT2.qsch ; Multgmamp - VOUTMAX VOUTMIN.qsch

- VDSAT1 and VDSAT2
 - VDSAT1 : Voltage where gm starts to switch over to a resistance (top FET)
 - VDSAT2 : Voltage where gm starts to switch over to a resistance (bottom FET)
 - **Default VDSAT1=VDSAT**
 - **Default VDSAT2=VDSAT1**



- VOUTMIN and VOUTMAX
 - Voutmin : Minimum output voltage measured from negative rail
 - Voutmax : Maximum output voltage measured from negative rail

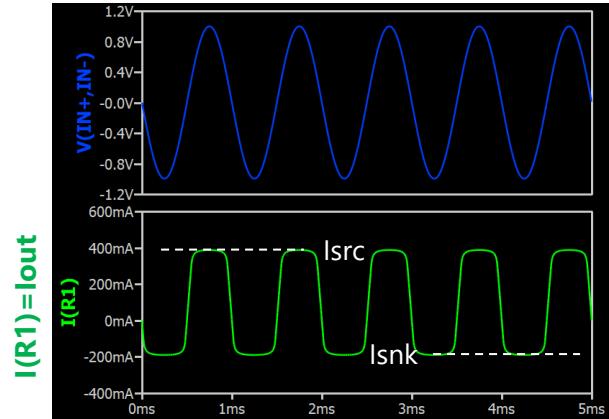
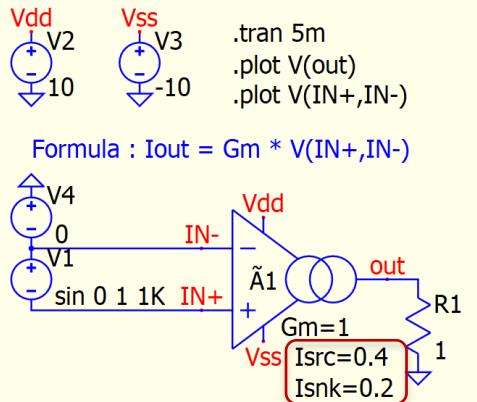


MULTGMAMP : Sink and Src Current (Iout / Isrc, Isnk)

Qspice : Multgmamp - ISRC ISNK.qsch ; Multgmamp - ISRCKNEE ISNKKNEE.qsch

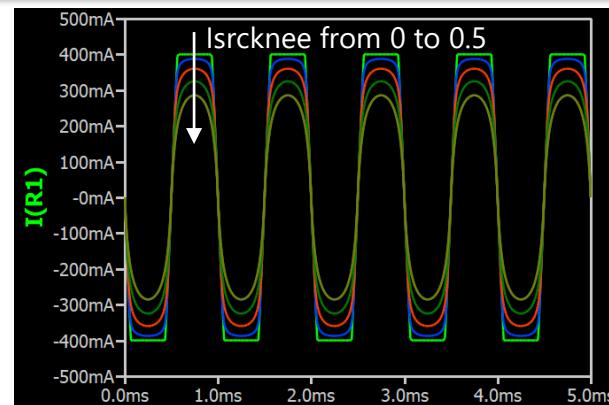
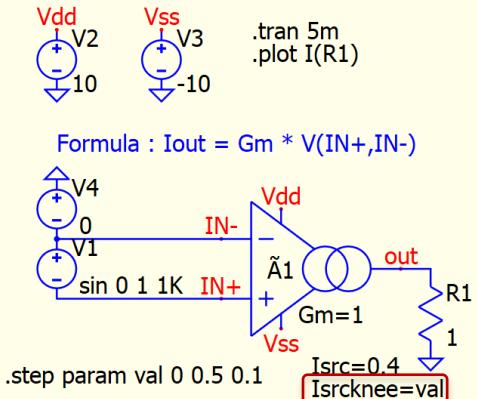
- IOUT/ISRC and ISNK

- Iout/Isrc : Maximum sourcing current (toward load)
- Isnk : Maximum sinking current (toward device)
- **Default ISRC = Infinite**
- **Default ISNK = IOUT or ISRC**
 - i.e. if ISNK not specified, ISNK equals IOUT or ISRC



- ISRCKNEE and ISNKKNEE

- $Isrcknee$: Sharpness of max sourcing current limit
- $Isnkknee$: Sharpness of Maximum sinking current limit
- **Default Isrckness = 0.1**
- **Default Isnkness = Isrcknee**



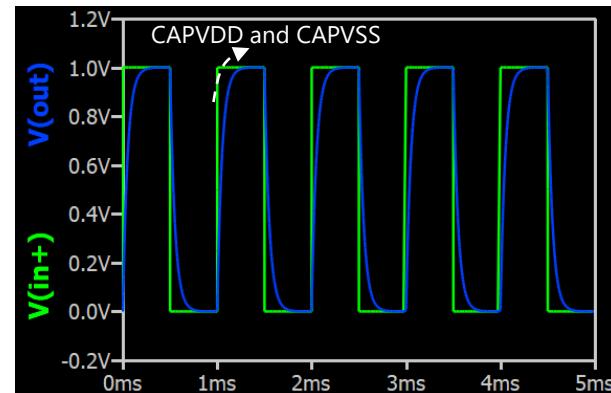
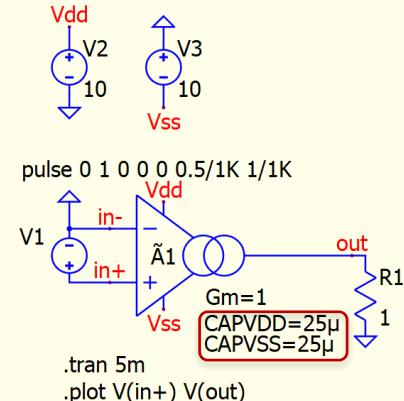
- Important Note

- To have effect, must defines ISRC or ISNK

MULTGMAMP : Output Capacitance (CAPVDD, CAPVSS) and Resistance (Rout)

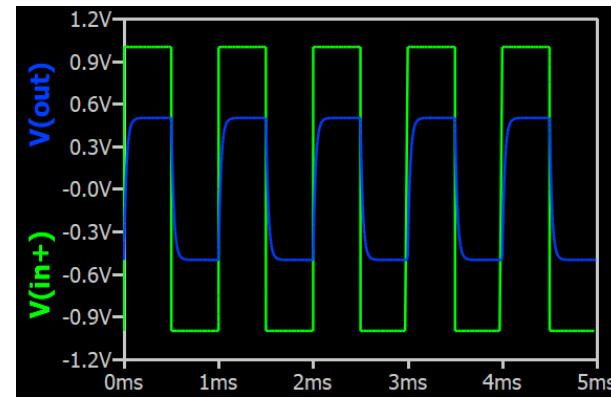
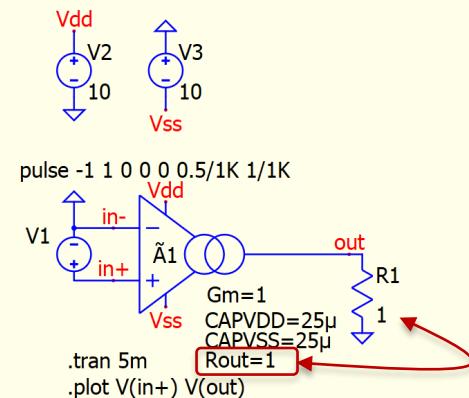
Qspice : Multgmamp - Capvdd Capvss.qsch ; Multgmamp - Rout.qsch

- CAPVDD and CAPVSS
 - CAPVDD : Capacitance from output to Vdd
 - Capvss : Capacitance from output to Vss



• ROUT

- Rout : Additional impedance added to output(2*R to Vdd, 2*R to Vss)
- In this example, Rout equal to amplifier loading, V(out) reduced by halve

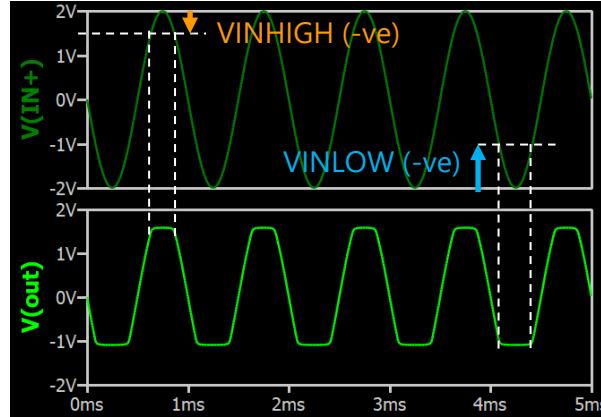
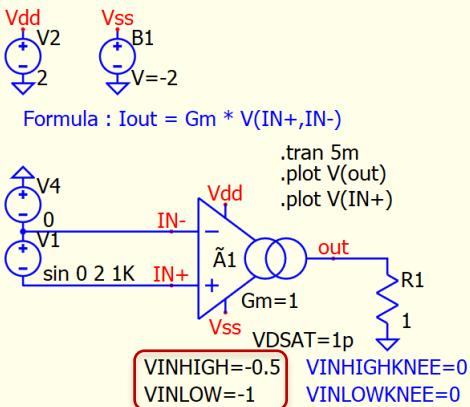


MULTGMAMP : Input Range VINLOW, VINHIGH, VINHIGHKNEE, VINLOWKNEE

Qspice : Multgmamp - VINHIGH VINLOW.qsch ; Multgmamp - VINHIGHKNEE VINLOWKNEE.qsch

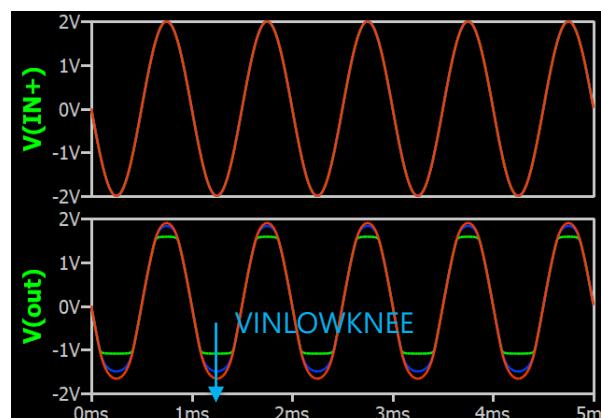
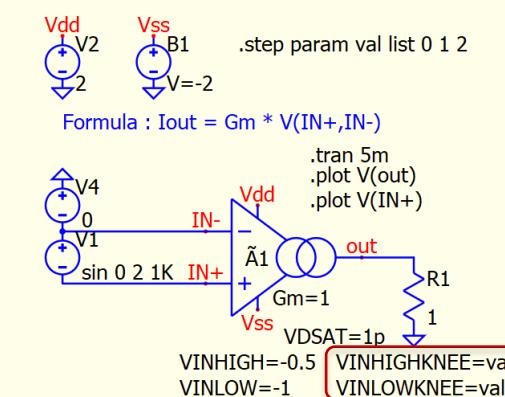
- VINLOW and VINHIGH**

- VINLOW : Input range measured from negative rail
- VINHIGH : Input range measured from positive rail
- Default VINLOW=0**
- Default VINHIGH=0**
- Value is negative**, which limit input range. For example, VINHIGH=-0.5, Input HIGH is limited to $Vdd + VINHIGH = 2 - 0.5 = 1.5$ in this example



- VINLOWKNEE**
VINHIGHKNEE

- Vinlowknee : Sharpness of negative input range limit
- Vinhightknee : Sharpness of positive input range limit
- Default VINHIGHKNEE=0**
- Default VINLOWKNEE=0**
- Increase KNEE soften the sharpness of input range, more output signal to come

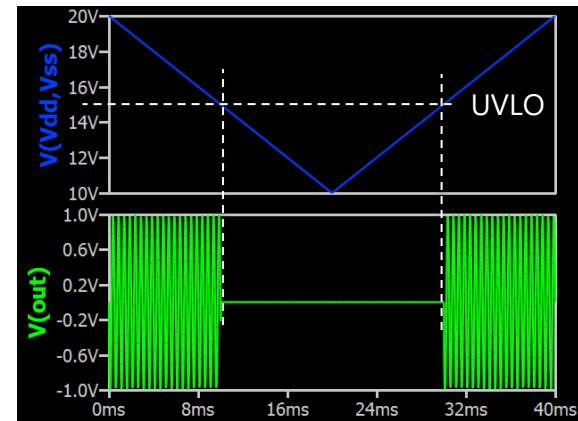
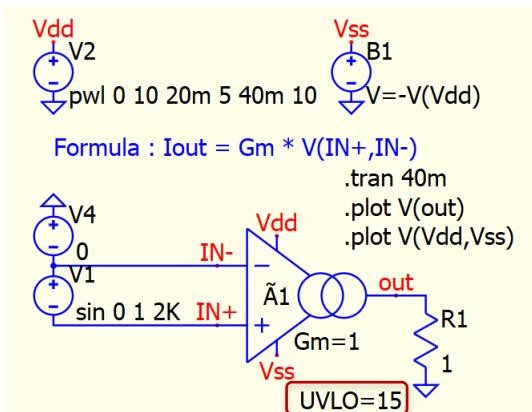


MULTGMAMP : UVLO and VOS1

Qspice : Multgmamp - UVLO.qsch ; Multgmamp - VOS1.qsch

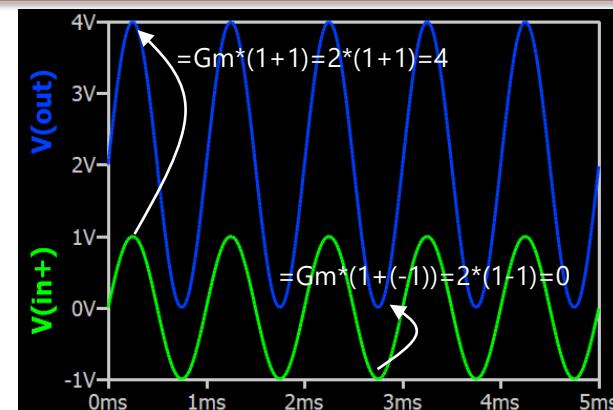
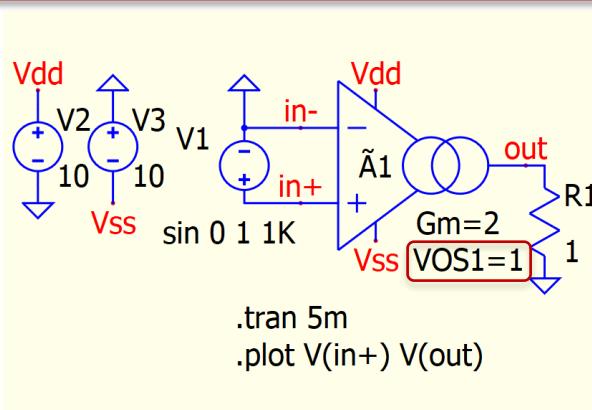
- UVLO

- UVLO : Under Voltage Lock Out - Minimum supply voltage
- Default UVLO is Infinite
- UVLO is compare to supply voltage = $V_{dd} - V_{ss}$



- VOS1

- VOS1 : Offset voltage for input
- $I_{out} = G_m \cdot (VOS1 + V(IN+,IN-))$
 - This parameter is not in HELP formula, but it actually implemented
- Default VOS1 = 0



¥-Device

¥-Device

- ¥-Device
 - Syntax:

`¥nnn N1 N2 N3 N4 N5 N6 N7 N8 N9 N10 N11 N12 N13 N14 N15 N16 <TYPE> [INSTANCE PARAMETERS]`

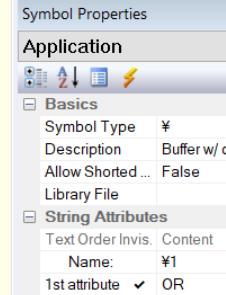
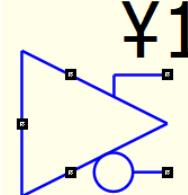
- The ¥-device supplies gate, flop, and a few other types of functional behaviors. The device expects exactly 16 pins, but not all are used. Unused pins must be specified connected to "¥".

¥-Device Types

TYPE	Behavior
AND	AND gate
CLOCKSYNC	Selects between a Sync and Clock inputs
D-FLOP	D-type flip-flop
EXTOSC	Oscillator programmed with an external resistor
HMITT	Schmitt trigger
JK-FLOP	JK-type flip-flop
MONOSTABLE	Retriggerable monostable
OR	OR gate
PS-FLOP	SMPS flip-flop
RS-FLOP	RS-type flip-flop
T-FLOP	Toggle flip-flop
XOR	XOR gate
Φ-DET	Phase/Frequency detector

To Identify what <TYPE> a symbol is

- In Symbol Properties > 1st attribute
- View > Netlist : from device syntax

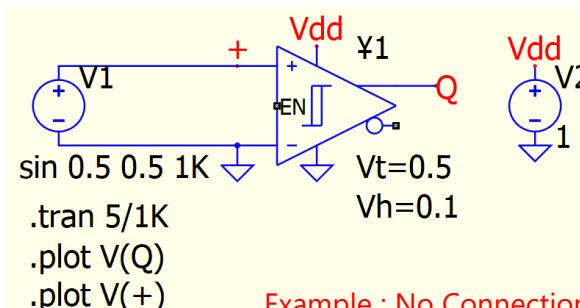


```
* C:\Users\kelvinleung\Documents\QSPICE\Unt
¥1 ¥0 ¥1 ¥2 ¥3 ¥4 ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ OR
.end
```

¥-Device : How EN pin works

Qspice - Logic - EN.qsch

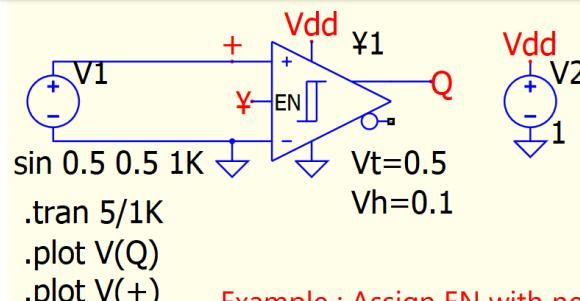
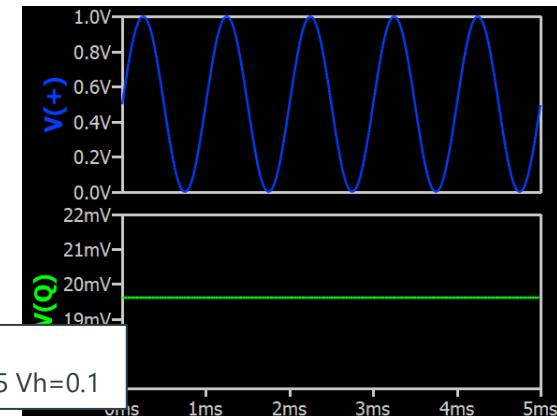
- How EN works
 - If EN is preset in symbol, normally, a signal is used to control its status. Here discuss two situations
 - #1 No connect to EN pin
 - Netlist assign ¥n as net name. EN pin is active to monitor EN signal. In this case, no output will generate
 - #2 Assign EN pin with net ¥
 - ¥ net name is equivalent to unassigned in ¥-device
 - Unassigned EN pin will be considered as Default ENABLE
 - Therefore, a symbol can be created with pin assigned to ¥ for their default



Example : No Connection

Netlist

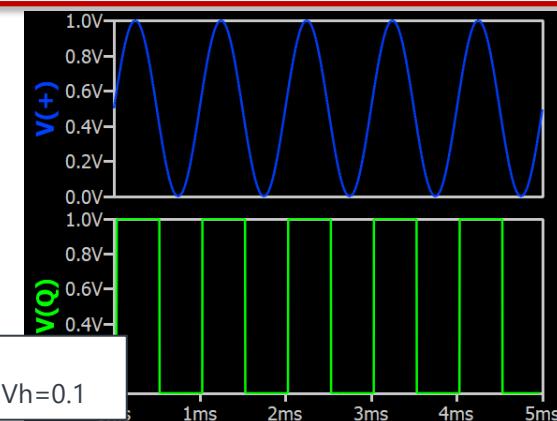
```
¥1 Vdd 0 Q ¥0 + 0 ¥1 ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ HMITT Vt=0.5 Vh=0.1
```



Example : Assign EN with net ¥

Netlist

```
¥1 Vdd 0 Q ¥0 + 0 ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ HMITT Vt=0.5 Vh=0.1
```



¥-Device : HELP > Simulator > Device Reference > ¥-Device
 Common Instance Parameters (example from AND Gate Instance Param)

Name	Description	Units	Default
• CAPVDD	Capacitance from an output to Vdd	F	0.
• CAPVSS	Capacitance from an output to Vss	F	0.
IC	Initial condition(needed, e.g., for a ring osc)		
M	Number of parallel devices		1.
• REF	Logic reference voltage	V	$(Vdd + Vss) \div 2$
• RSINK	Resistance to Vss when output high	Ω	RSRC
• RSRC	Resistance to Vdd when output low(aka ROUT)	Ω	100.
• TD	Delay(aka TD1)	s	0.
• TD2	Asymmetrical delay	s	TD
TEMP	Instance temperature	$^{\circ}\text{C}$	27.
• TFALL	Fall time	s	0.
• TRISE	Rise time	s	0.
• TTOL	Temporal tolerance	s	$1\mu\text{s}$
• UVLO	Minimum Vdd-Vss voltage to operate	V	0.
ZMULT	Impedance multiplier when biased half way		1.

¥ Instance Params : REF Logic Reference Voltage

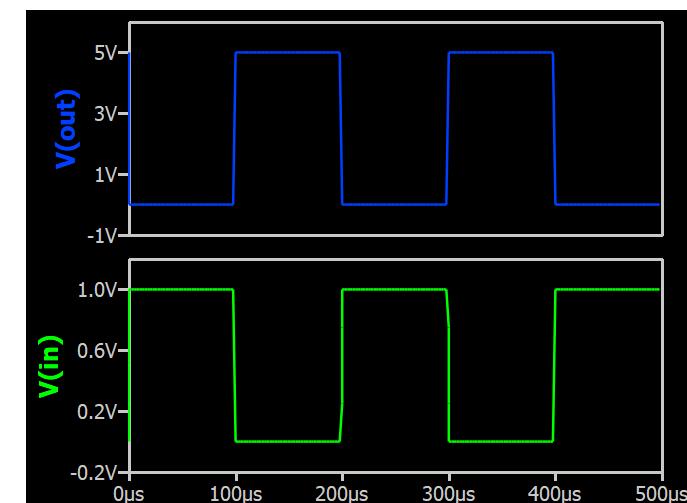
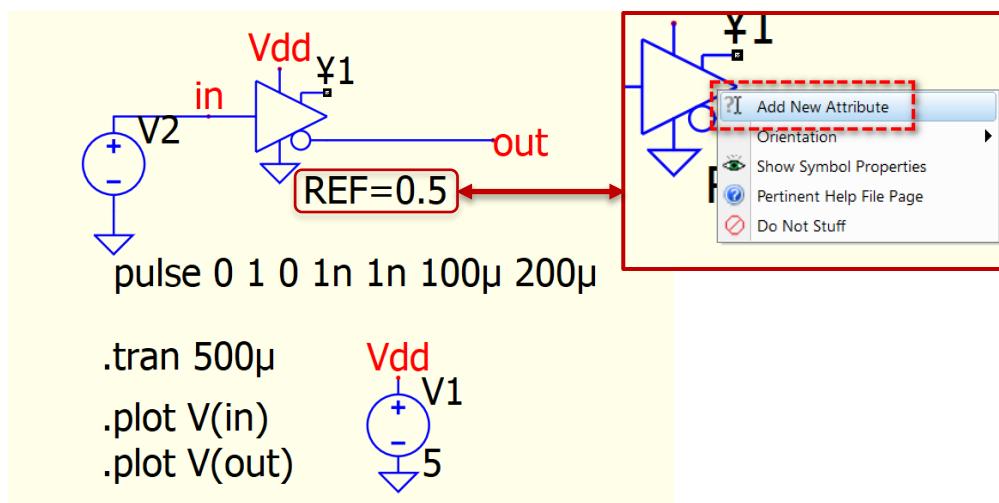
Qspice : Logic - REF.qsch

- REF : Logic reference voltage

- In default, ¥-Device logic threshold is $\frac{Vdd+Vss}{2}$

REF	Logic reference voltage	V	$(Vdd + Vss) \div 2$
-----	-------------------------	---	----------------------

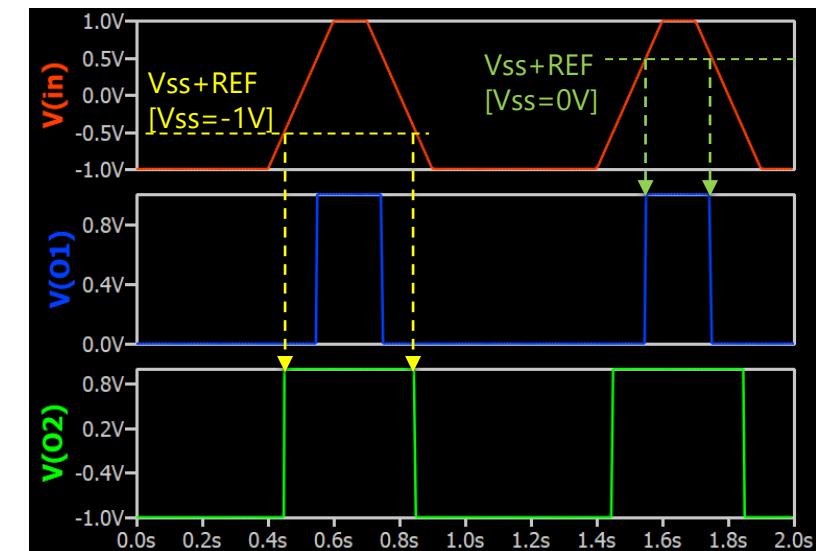
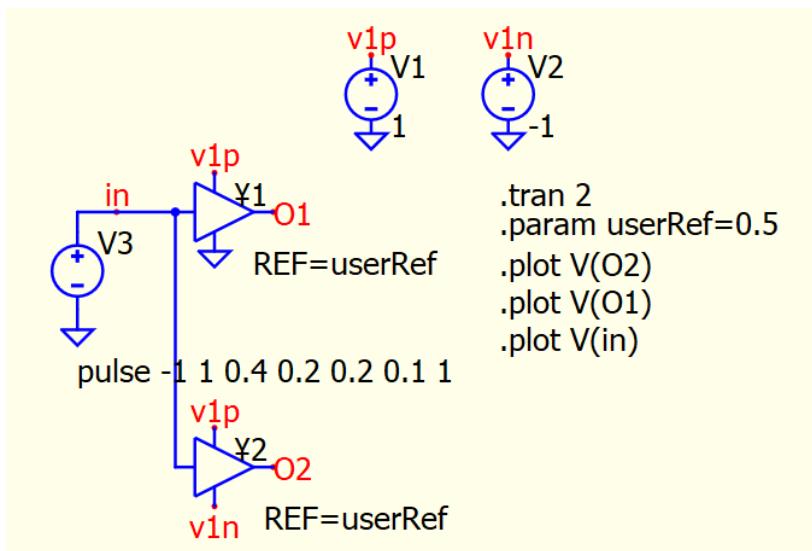
- User can change logic threshold by [right click device] > [Add New Attribute] to add `REF=<value>`
- This example show logic output follows $Vdd/0$ with logic input threshold equal 0.5V to interface with 1V input logic



¥ Instance Params : REF Logic Reference Voltage

Qspice : Logic - REF (Dual Supply).qsch

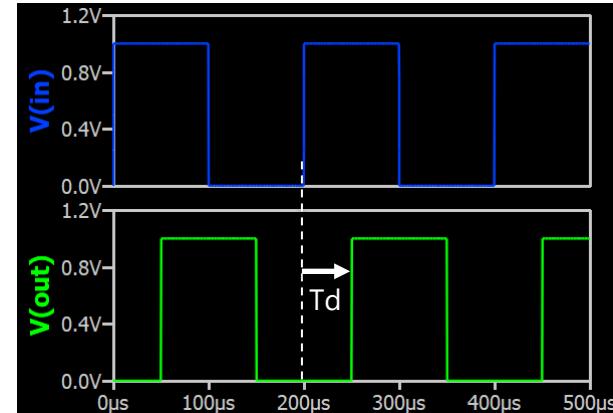
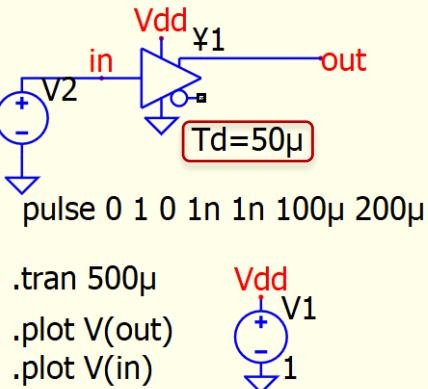
- REF : Logic Reference Voltage
 - REF is not absolute voltage to node 0, but reference to Vss node of ¥-Device
 - In this example, ¥1 and ¥2 are with same REF value, but as ¥1 Vss=0V and ¥2 Vss=-1V, their logic reference is different reference to node 0 (GND). Therefore, even their input is same, their output can be different



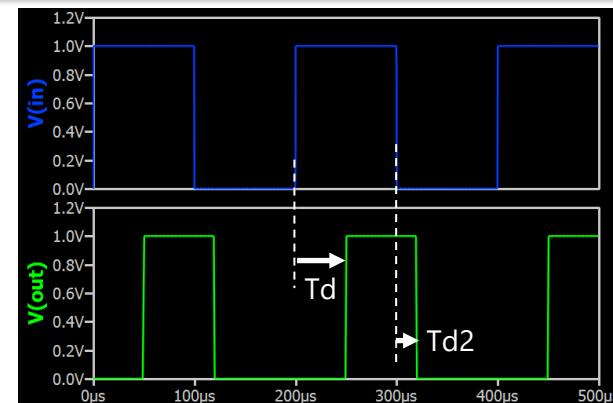
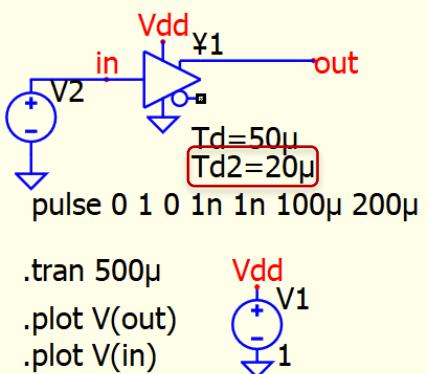
Instance Params : Delay (TD) and Asymmetrical Delay (TD2)

Qspice : Logic - Td.qsch ; Logic - Td Td2.qsch

- TD (Delay)
 - Td : Delay
 - **Default TD=0s**
 - ** If TD2 is not set, both rising and falling delay times are same
 - ** If TD > logic H duration or delay TD2 > logic L duration, output always LOW or HIGH



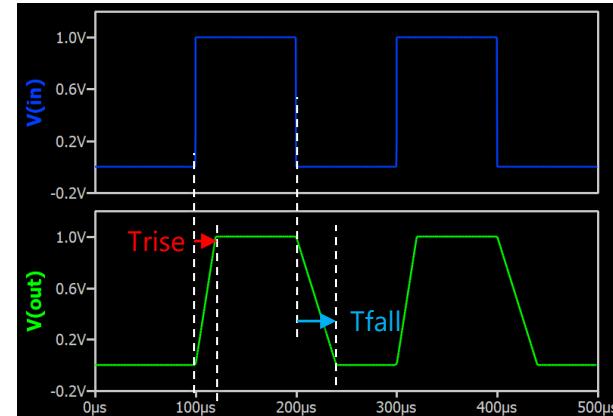
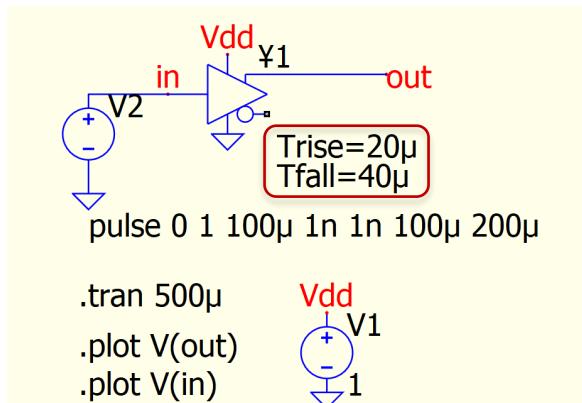
- TD2 (Asymmetrical delay)
 - TD2 : Asymmetrical delay
 - **Default TD2=TD**
 - If different delay times for rising and falling edge, set TD2 for falling edge delay time
(i.e. TD only control rising edge delay time)



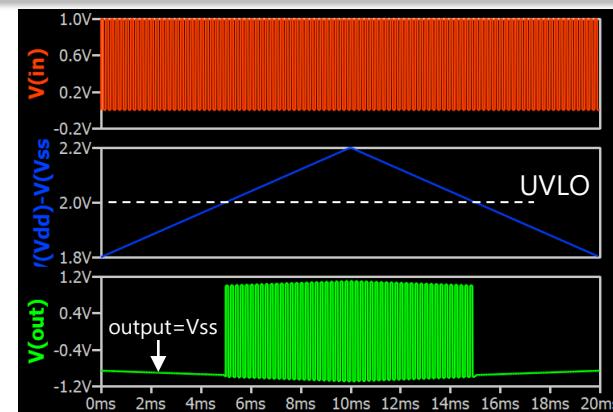
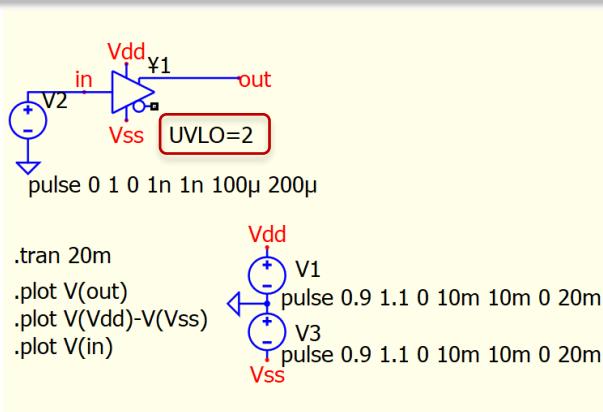
Instance Params : Rise time (Trise), Fall time (Tfall) and UVLO

Qspice : Logic - Trise Tfall.qsch

- TRISE and TFALL
 - Trise : Rise time
 - Tfall : Fall time
 - **Default TRISE=0s**
 - **Default TFALL=0s**



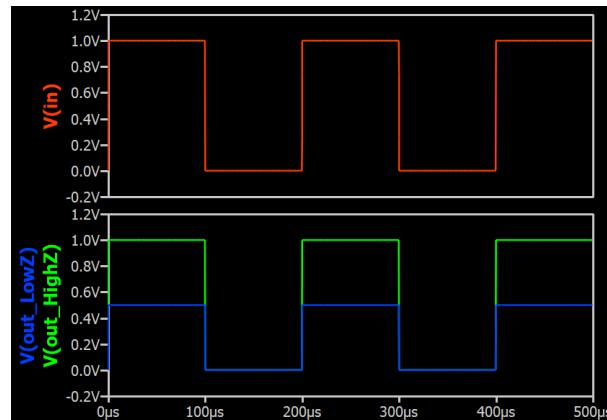
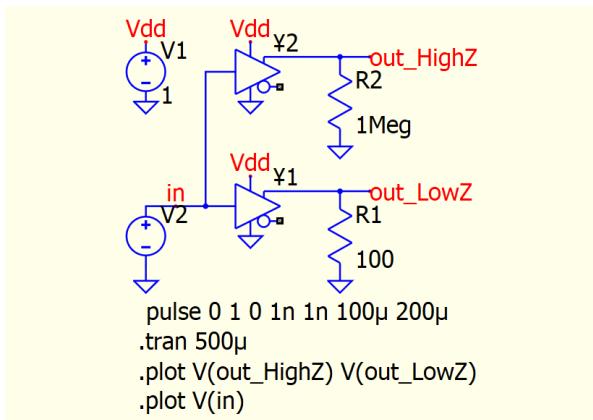
- UVLO
 - UVLO : Under Voltage Lock Out
 - **Default UVLO=0V**
 - UVLO : Minimum Vdd-Vss voltage to operate
 - Output only enabled when Vdd-Vss > UVLO
 - Output equals Vss when gate disable



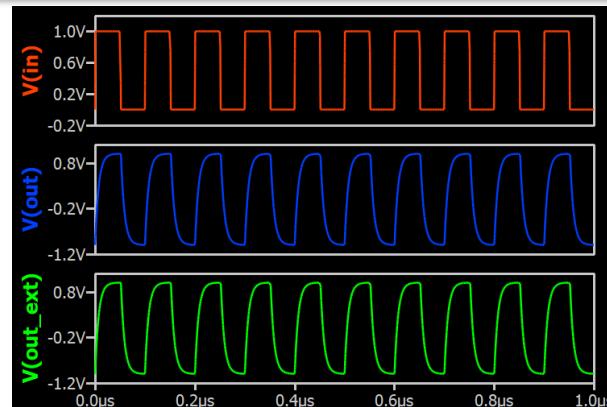
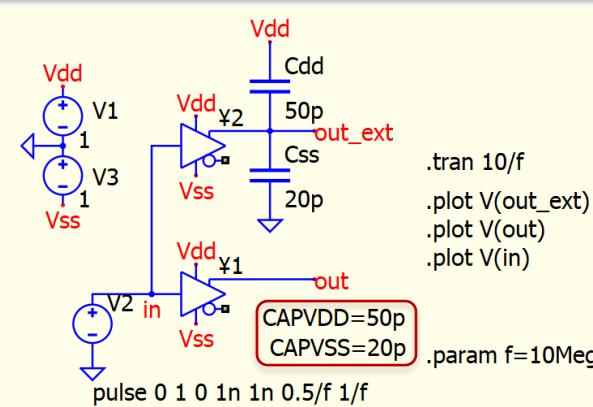
Instance Params : Output R and C (Rsink, Rsrc, Capvdd, CapVss)

Qspice : Logic - RSINK RSRC.qsch ; Logic - Capvdd Capvss.qsch

- RSINK and RSRC
 - RSINK : Res to Vss when o/p high
 - RSRC : Res to Vdd when o/p low
 - **Default RSINK=100Ω**
 - **Default RSRC=100Ω**
- Example
 - This simulation shows loading effect when output to a 100 ohms, where o/p level is reduced to half of Vdd



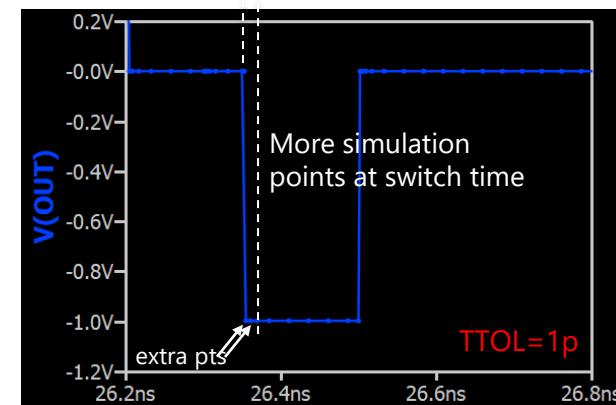
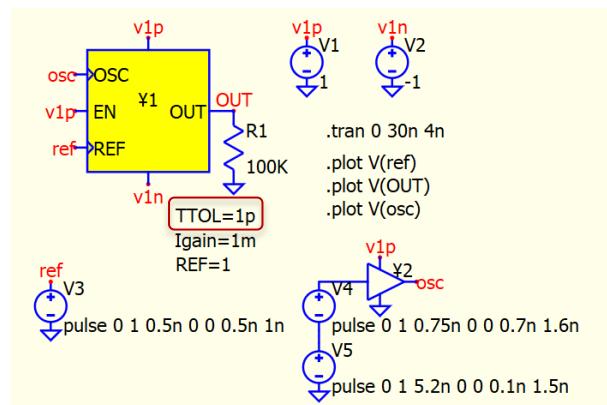
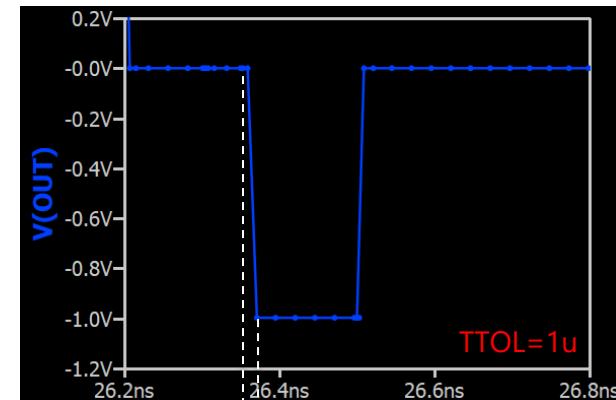
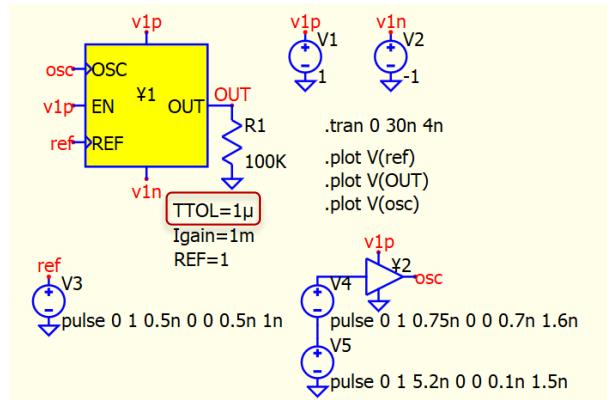
- CAPVDD, CAPVSS
 - Capvdd : Capacitance from an output to Vdd
 - Capvss : Capacitance from an output to Vss
- Explanation
 - Capacitance Capvdd/Capvss equivalent Cdd/Css this example
 - This demo can have frequency response because Rsink=Rsrc=100 internally



Instance Params : TTOL Temporal Tolerance

Qspice : Logic - TTOL.qsch

- TTOL
 - Ttol : Temporal tolerance
 - **Default TTOL=1u**
 - TTOL allows one to determine how accurately the switch time should be found

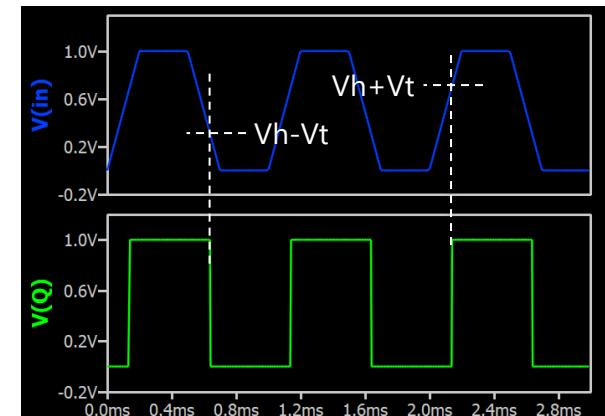
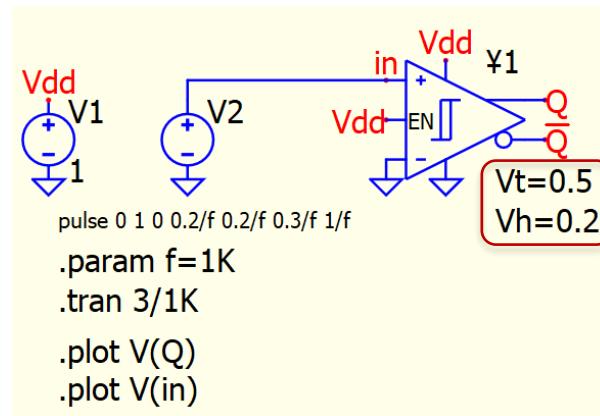


⌘ [HMITT] Instance Params : Threshold (VT) and Half Hysteresis (VH)

Qspice : HMITT - Vt VH.qsch

- VT and VH

- Vt : Threshold voltage
- VH : Half hysteresis voltage
- HMITT is schmitt trigger logic input
- low trip point is $Vt-VH$ and the high trippoint is $Vt+VH$



¥ Truth Table : AND, OR, XOR

Qspice : Truth Table of AND OR XOR.qsch

- AND

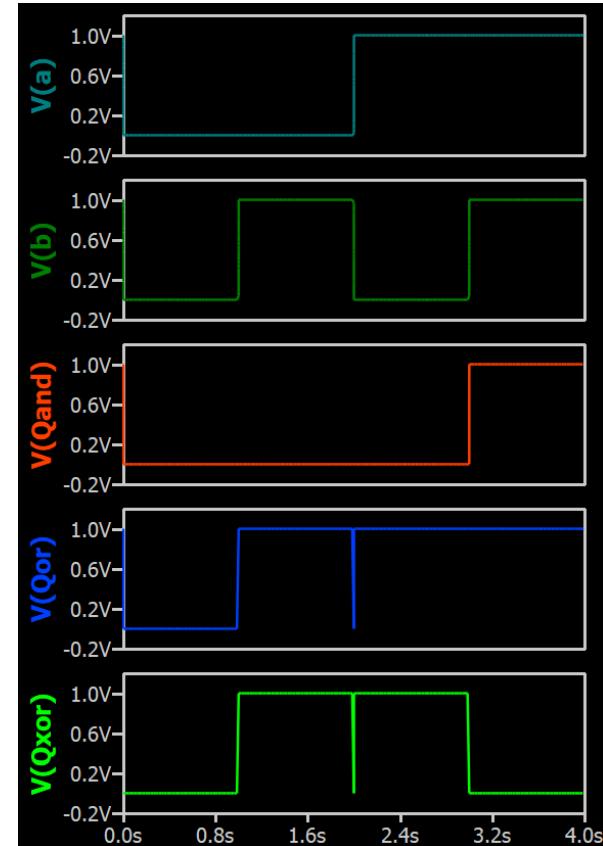
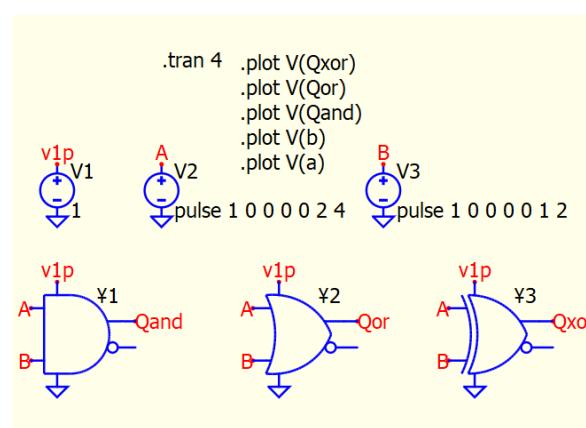
¥-Device AND			
A	B	Q	_Q
0	0	0	1
0	1	0	1
1	0	0	1
1	1	1	0

- OR

¥-Device OR			
A	B	Q	_Q
0	0	0	1
0	1	1	0
1	0	1	0
1	1	1	0

- XOR

¥-Device XOR			
A	B	Q	_Q
0	0	0	1
0	1	1	0
1	0	1	0
1	1	0	1



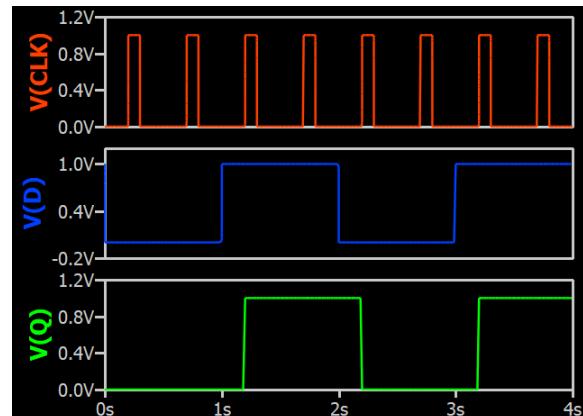
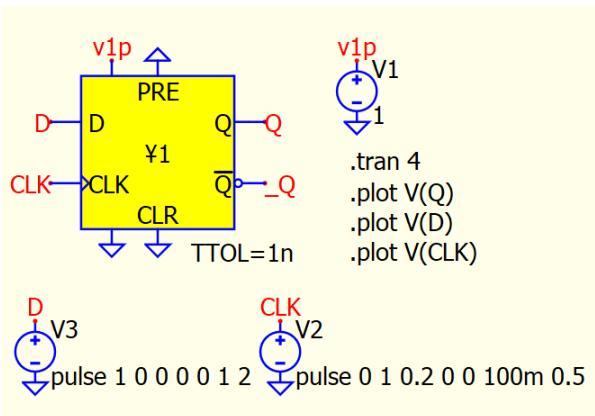
¥ Truth Table : D-FLOP and T-FLOP

Qspice : Truth Table of D-FLOP.qsch ; Truth Table of T-FLOP.qsch

- D-FLOP

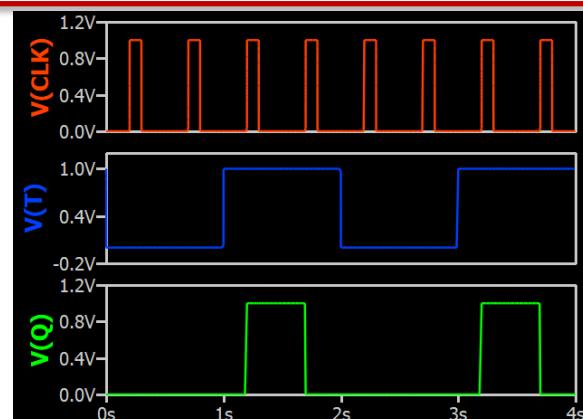
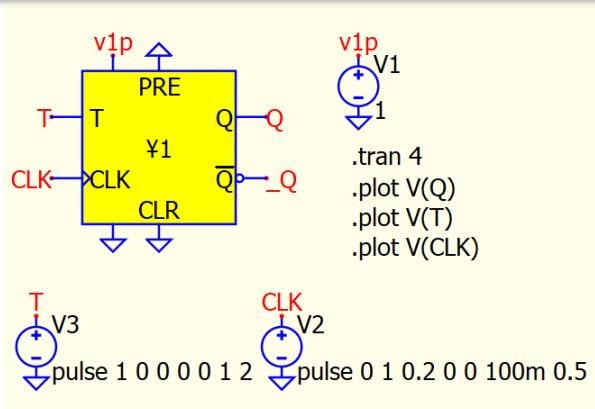
- PRE : Active High (=SET)
- CLR : Active High (=RESET)

¥-Device D-flop					
CLK	D	PRE	CLR	Q	\bar{Q}
↑	0	0	0	0	1
↑	1	0	0	1	0
x	x	0	0	Q	\bar{Q}
x	x	1	0	1	0
x	x	x	1	0	1



- T-FLOP

¥-Device T-flop				
CLK	T	PRE	CLR	Q_{n+1}
↑	0	0	0	0
↑	1	0	0	\bar{Q}_n
x	x	0	0	Q
x	x	1	0	1
x	x	x	1	0

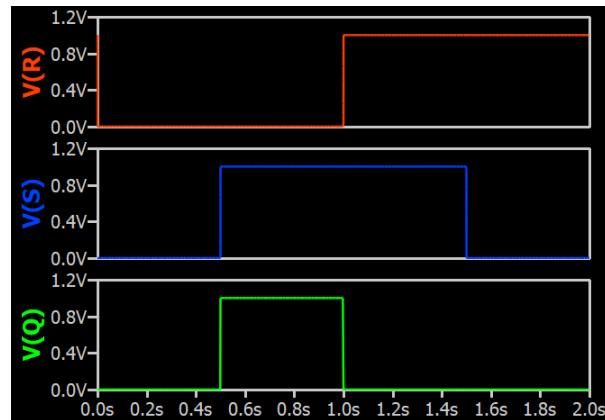
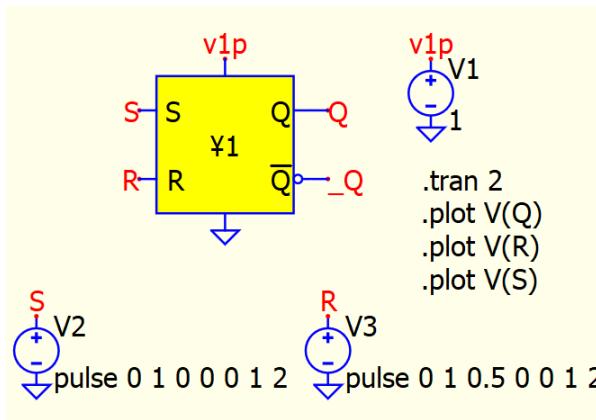


¥ Truth Table : SR-FLOP and JK-FLOP

Qspice : Truth Table of SR-FLOP.qsch ; Truth Table of JK-FLOP.qsch

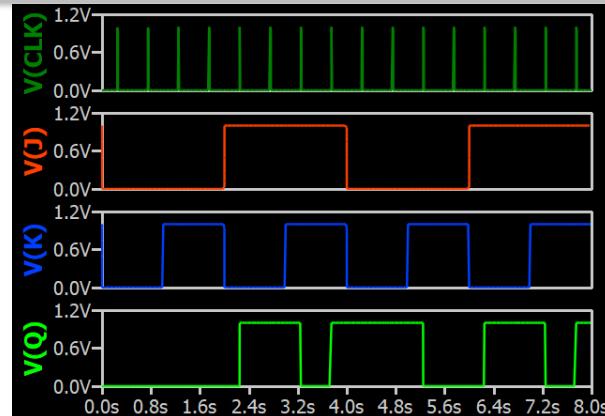
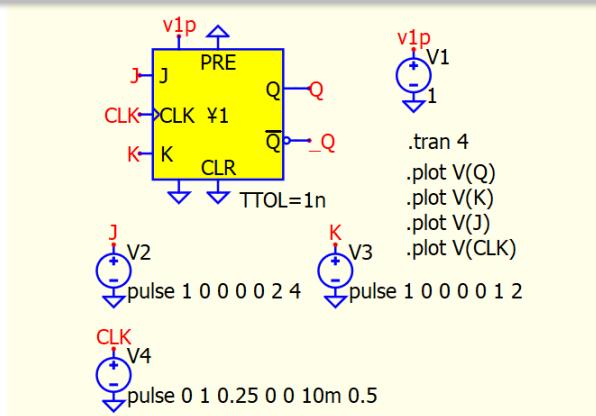
- SR-FLOP

R	S	Q	\bar{Q}
0	0	0	1
0	1	1	0
1	x	0	1



- JK-FLOP

CLK	J	K	PRE	CLR	Q_{n+1}
\uparrow	0	0	0	0	Q_n
\uparrow	0	1	0	0	0
\uparrow	1	0	0	0	1
\uparrow	1	1	0	0	\bar{Q}_n
x	x	x	0	0	Q
x	x	x	1	0	1
x	x	x	x	1	0

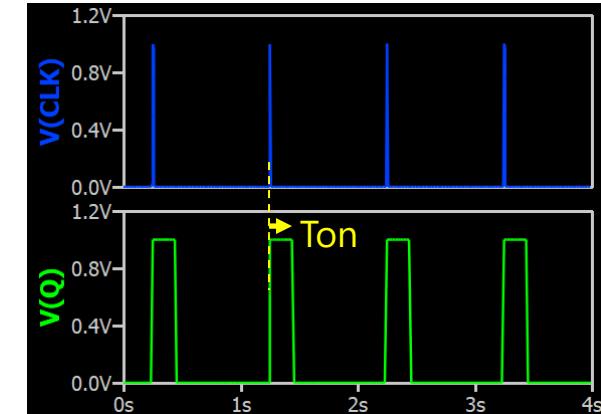
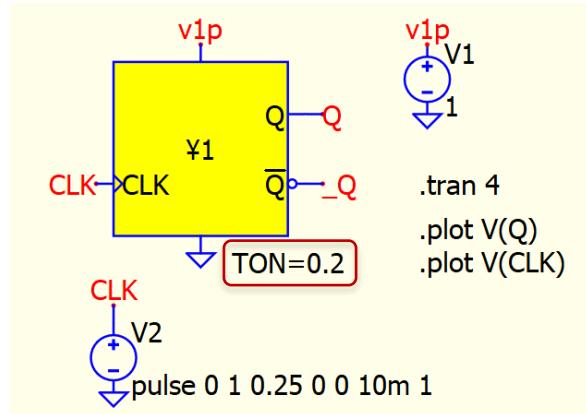


¥-Device Monostable

Qspice : Usage - Monostable.qsch

- Monostable

- TON : Monostable on time
- Default TON=0s**
- Need to add this attribute when Monostable Symbol is called to use in Qspice
- TON must be specified to use Monostable
- CLK trigger a minimum on-time pulse



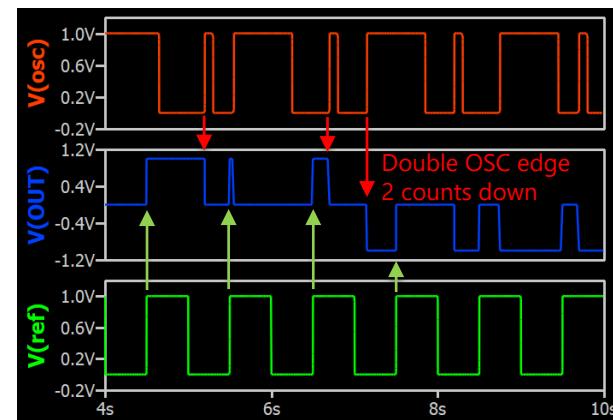
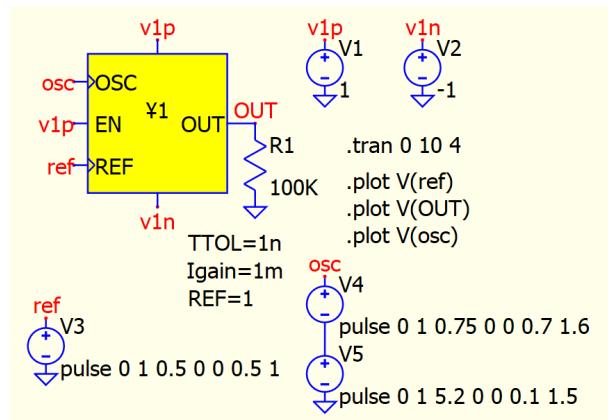
¥ Truth Table : Φ -DET (Phi-Det) [Symbol : PhaseDetector in analog]

Qspice : Truth Table of Phi-Det.qsch

- Φ -DET (Phi-Det)
 - Phase/Frequency Detector

¥-Device Phi-Det		
REF	OSC	OUT
↑	x	Up
x	↑	Down
↑	↑	Unchange

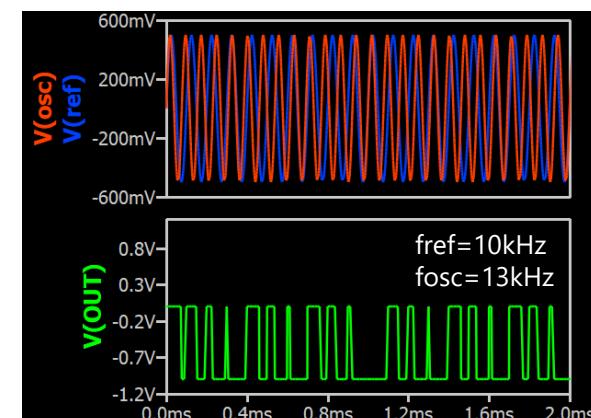
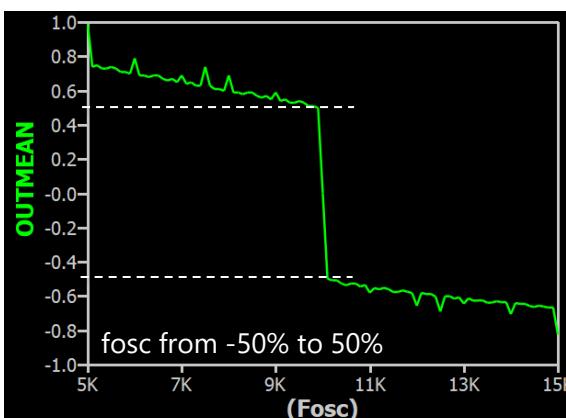
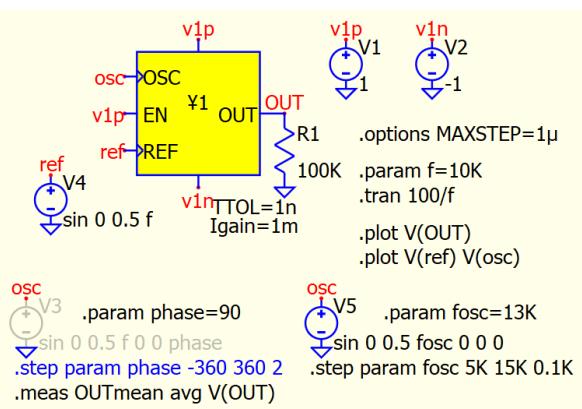
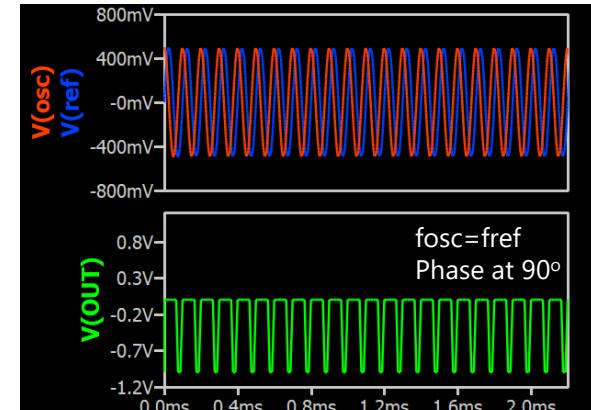
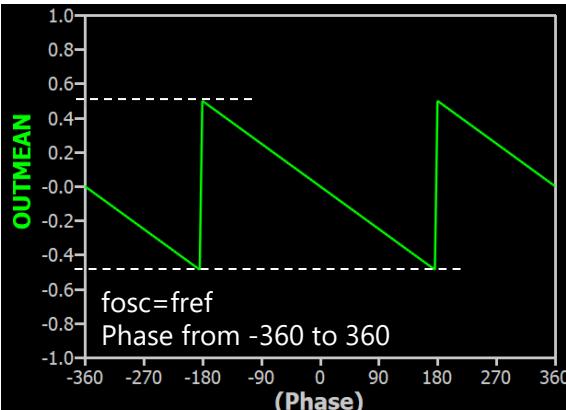
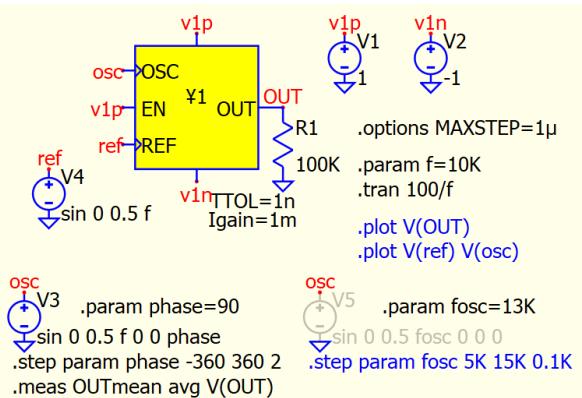
- Important
 - Output is current, not voltage
 - Suggest to set a higher Igain for OUT can reach Vdd/Vss with load (Default Igain only 10µA)
 - This device is a [Vdd, 0, Vss] 3-state counter, therefore, must operate with dual supply
 - REF edge counts up
 - OSC edge counts down



- Phase/Frequency Detection
 - Next slide is simulation results in phase change and frequency change
 - Mean of PWM output pattern can differentiate it is OSC signal phase or frequency deviate from REF signal
 - This is a key component in Phase Lock Loop (PLL)

¥-Device Φ -DET (Phi-Det) : OSC and REF Relationship with OUT

Qspice : Usage - Phi-Det (Freq and Phase).qsch

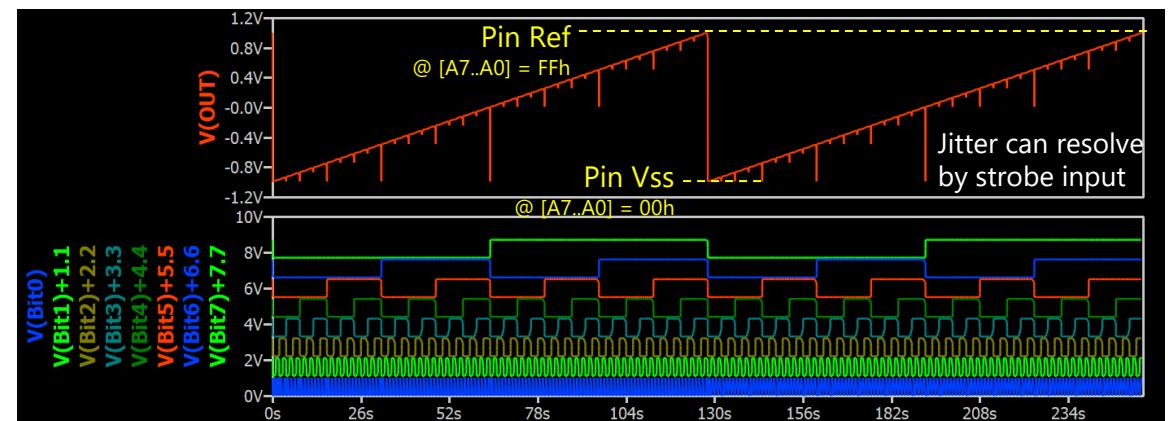
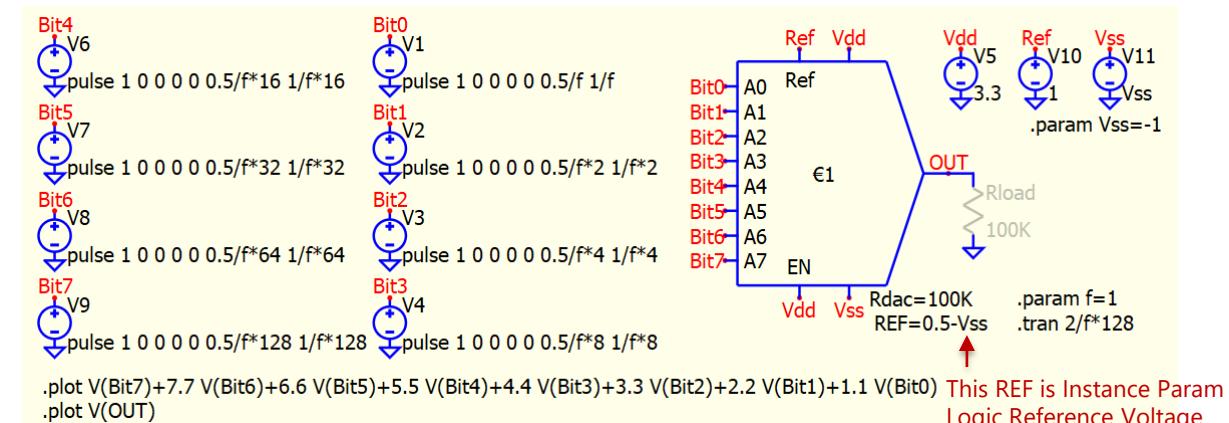


ϵ -Device

€-Device DAC : Build-in Symbol DAC8.qsym

Qspice : DAC - Basic.qsch

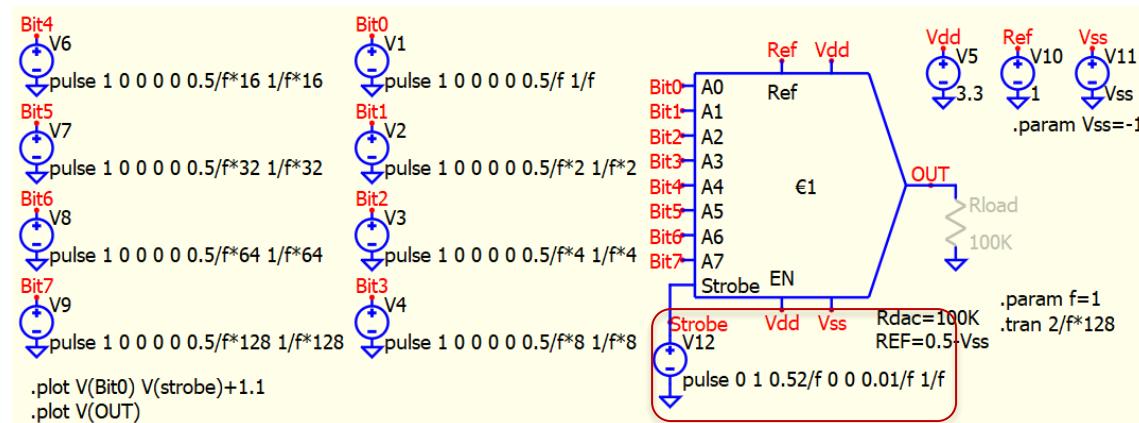
- DAC
 - DAC : Digital to Analog Converter
- Important Pins
 - Ref : the maximum voltage value that the DAC can reach
 - A7 : MSB of input word A
 - A0 : LSB of input word A
 - EN : Enable
- Instance Params
 - Common instance params can refer to €-Device section (e.g. REF)



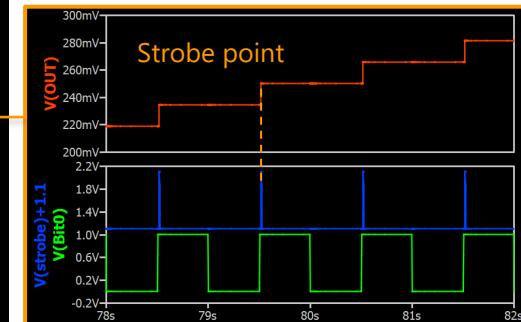
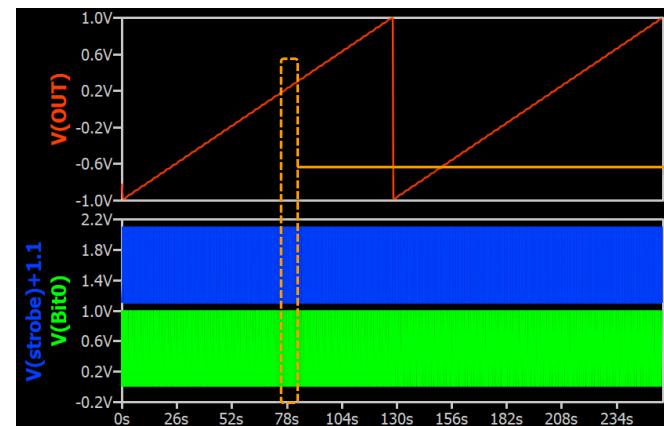
€-Device DAC : Build-in Symbol DAC8strobe.qsym

Qspice : DAC - Strobe.qsch

- Strobe
 - In practice, it named as load DAC strobe (LDAC)
 - This pin transfers all input register data to the DAC registers
 - It resolve jitter in V(out) in previous slide



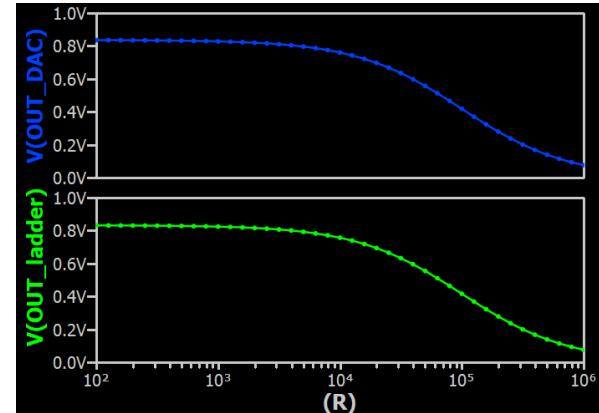
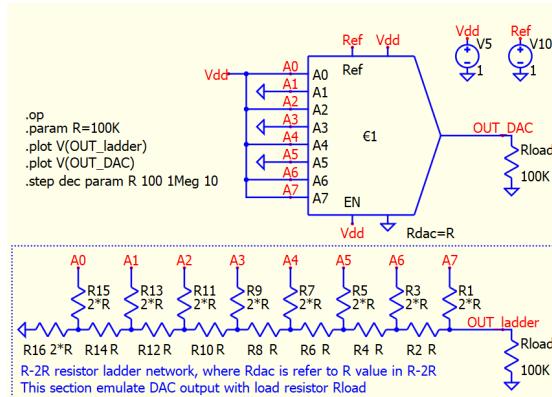
- Symbol
 - Build-in symbol with strobe is
 - DAC8strobe.qsym



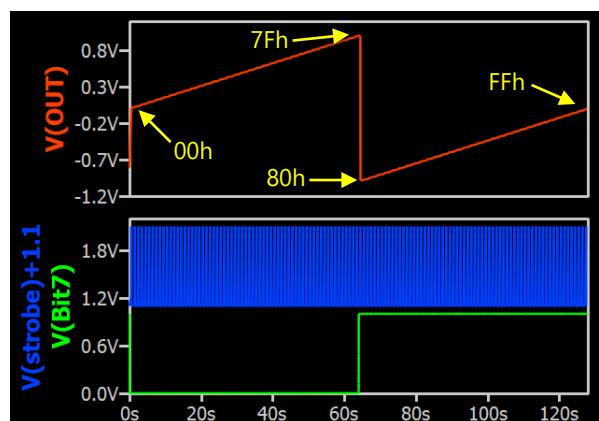
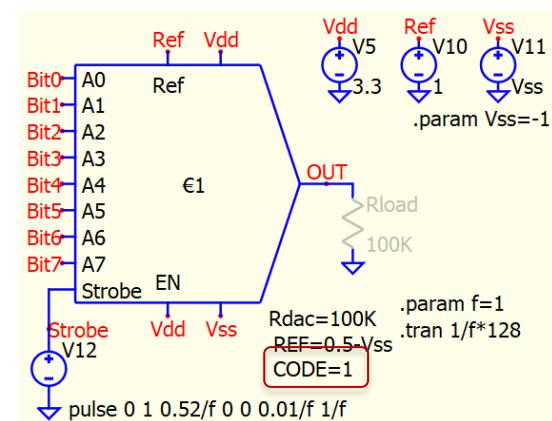
€-Device DAC Instance Params : RDAC

Qspice : DAC - RDAC.qsch ; DAC - CODE.qsch

- RDAC
 - Rdac : R of R-2R DAC
 - R-2R resistor ladder network is inexpensive solution for digital to analog conversion
 - Reference
 - https://en.wikipedia.org/wiki/Resist_ladder
 - Therefore, to prevent loading effect, a voltage buffer should be used in DAC output



- CODE
 - Code : Non-zero maps from $-n$ to $n-1$ to 0 to $2n-1$
 - Default CODE=0**
 - CODE=0 : Unsigned
 - CODE=1 : Signed - two's complement

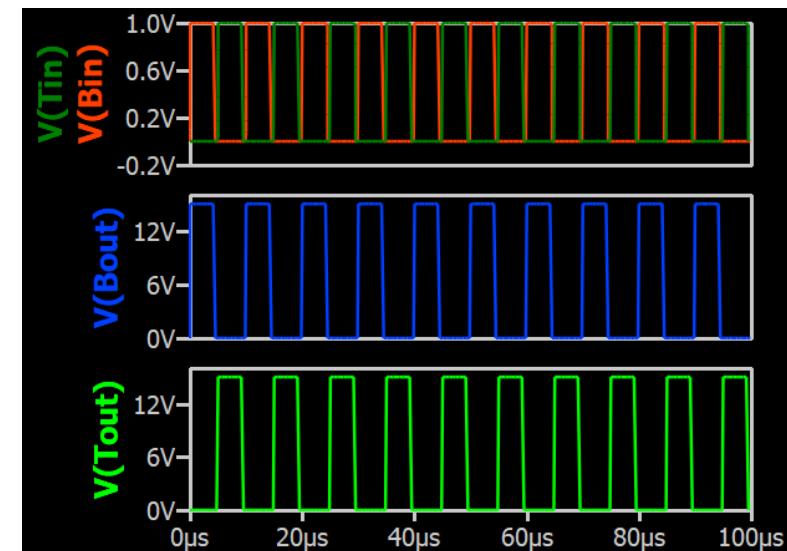
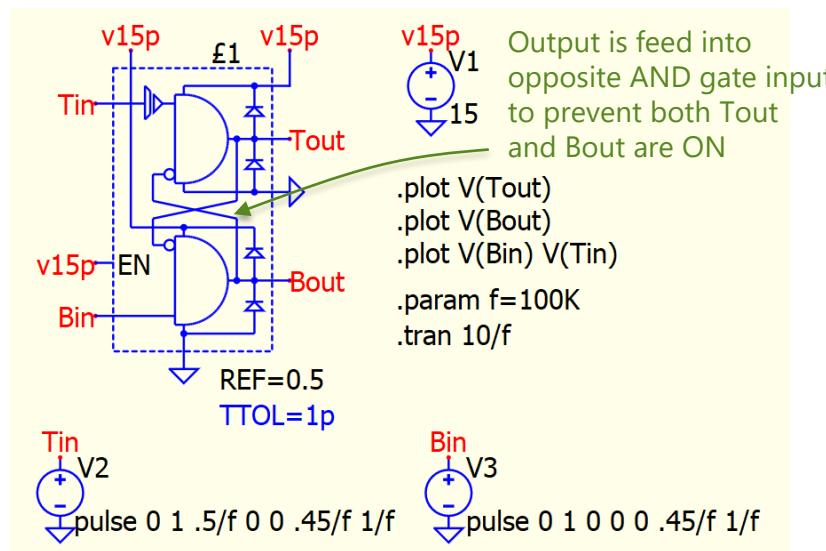


f -Device

f-Device : Dual Gate Driver

Qspice : Dual Gate Driver.qsch

- f-Device Dual Gate Driver
 - Syntax: fnnn Vdd Vss BOOST TOPGATE SW BOTGATE TCTRL BCTRL EN ¥ ¥ ¥ ... GATEDRIVER [INSTANCE PARAMETERS]
 - This behavioral device expects Top Input and Bottom Input has deadtime in between



£ [Dual Gate Driver] Instance Params

Gate Driver Instance Parameters

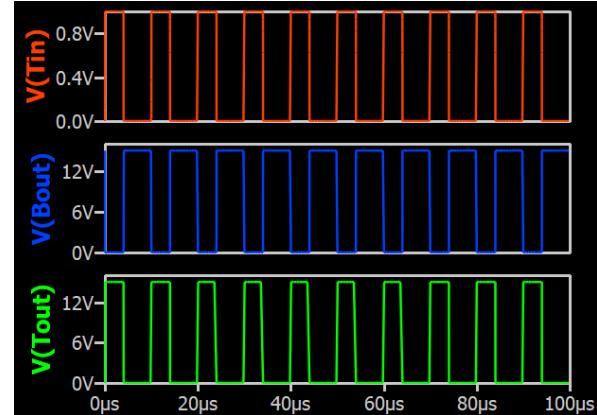
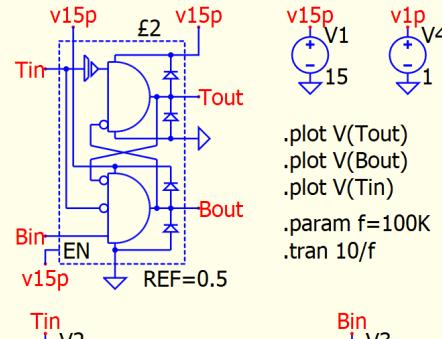
Name	Description	Units	Default
BOOST	Add logic such that the top FET is off if the bottom is controlled to be on		(not set)
BUCK	Add logic such that the bottom FET is off if the top is controlled to be on		(not set)
CAPVDD	Capacitance from a logic output to Vdd(or BOOST)	F	0.
CAPVSS	Capacitance from a logic output to Vss(or SW)	F	0.
M	Number of parallel devices		1.
REF	Logic reference for enable input	V	$(Vdd + Vss) \div 2$
ROFF1	Resistance used to pull bottom FET to VSS	Ω	RON1
RON1	Resistance used to pull bottom FET to VDD	Ω	1.
ROFF2	Resistance used to pull top FET to SW	Ω	ROFF
RON2	Resistance used to pull top FET to BOOST	Ω	RON1
RPASSIVE	Resistance used to pull both FETs' gates low when the driver is not enabled	Ω	1Meg
TEMP	Instance temperature	$^{\circ}C$	27.
TTOL	Temporal tolerance	s	
UVLO	Minimum Vdd-Vss voltage to operate	V	2.

£ [Dual Gate Driver] Instance Params - Buck and Boost

Qspice : Dual Gate Driver (Buck).qsch; Dual Gate Driver (Boost).qsch

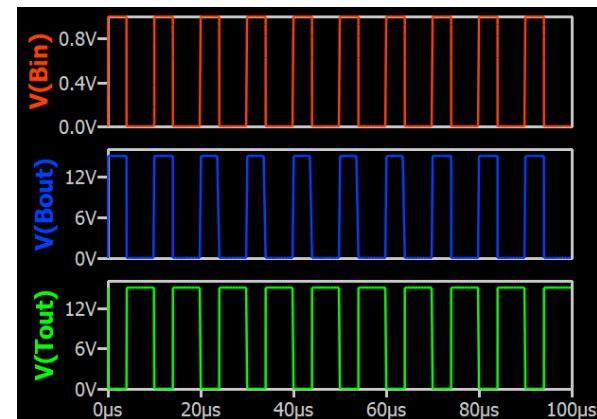
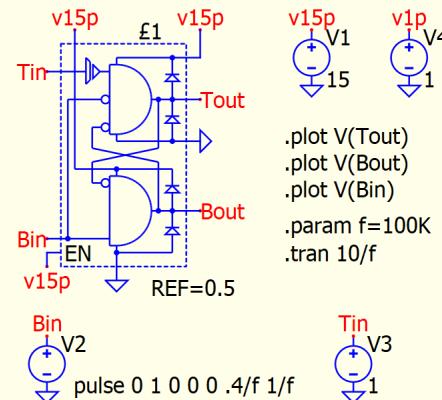
• BUCK

- Add logic such that the bottom FET is off if the top is controlled to on
- **Tin** is inverted to drive Bottom AND gate
 - Bin connects to LOW
- Switch of buck converter is generally at High Side



• BOOST

- Add logic such that the top FET is off if the bottom is controlled to be on
- **Bin** is inverted to drive Top AND gate
 - Tin connects to HIGH
- Switch of boost converter is generally at Low Side

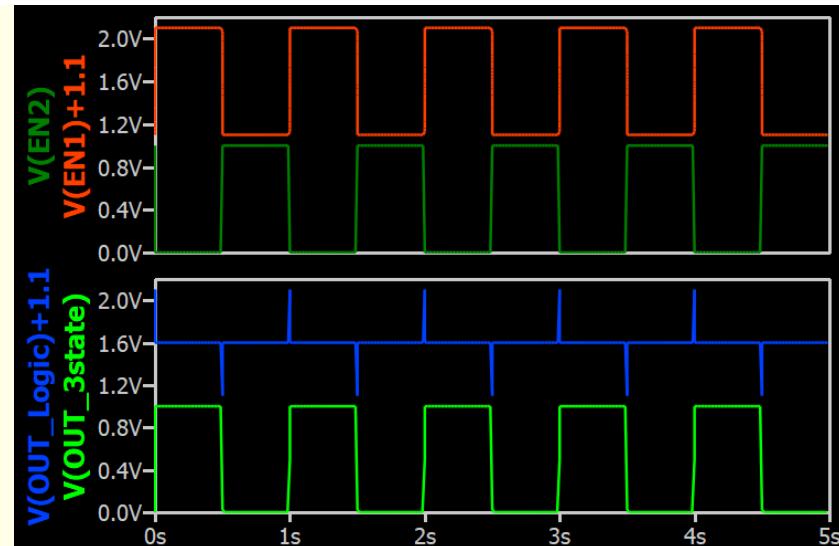
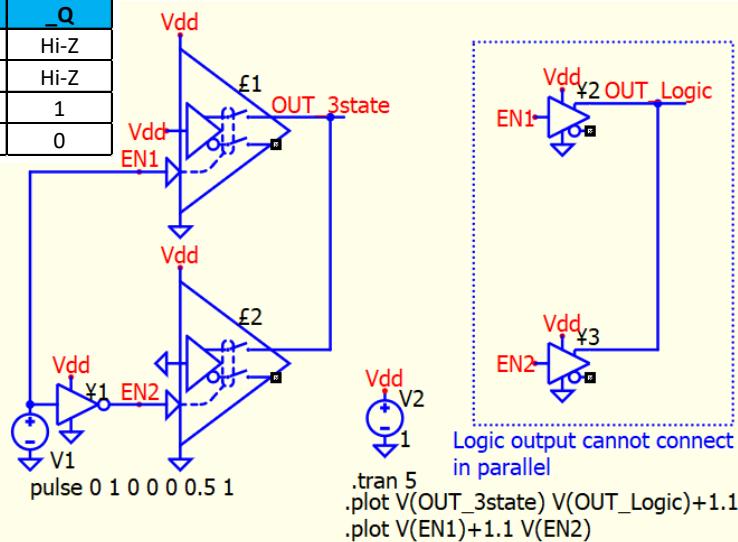


f-Device : Tri-state Buffer

- Tri-state Buffer

- Syntax: fnnn Vdd Vss Q Q̄ IN EN ¥ ¥ ¥ ... 3STATE [INSTANCE PARAMETERS]
- A tri-state output allows multiple circuits to share the same output line(s)
- Output into High-Z when disable

f-Device Tri-state Buffer			
EN	IN	Q	_Q
0	0	Hi-Z	Hi-Z
0	1	Hi-Z	Hi-Z
1	0	0	1
1	1	1	0



\emptyset -Device

Ø-Device Instance Parameters

Ø-Device Instance Parameters

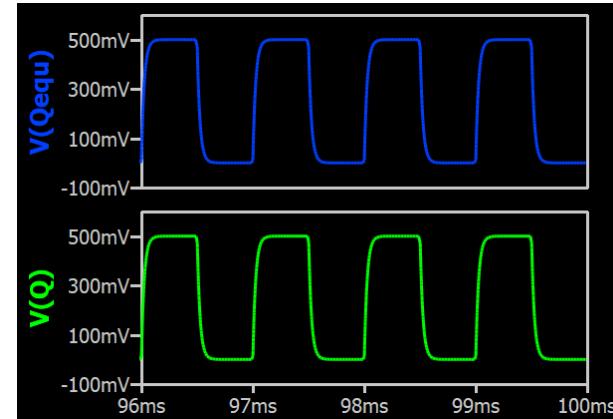
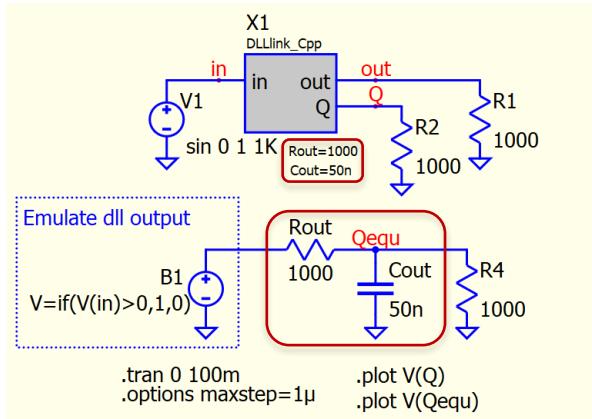
Name	Description	Units	Default
COUT	Output capacitance	C	0.
MAXTIMESTEP	Maximum time between evaluations	s	Infinite
REF	Logic threshold for inputs declared as boolean	V	.5
ROUT	Output impedance	Ω	1000.
VHIGH	Logic high level for outputs declared as boolean	V	1.
VLSB	ADC and DAC incremental voltage for an LSB change for multi-bit binary data types	V	1.

Ø-Device Instance Params : Rout / Cout and Vhigh

Qspice : DLLlink - Rout Cout.qsch / DLLlink - VHIGH.qsch

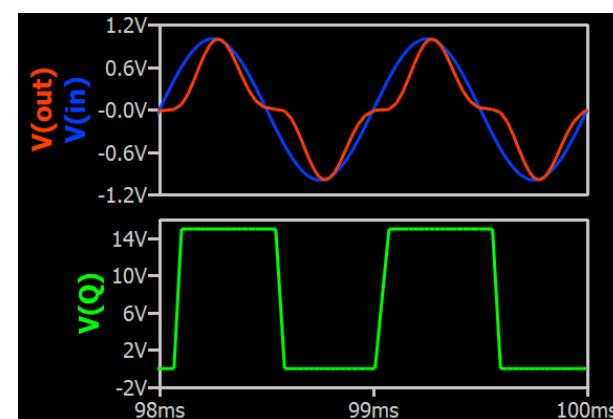
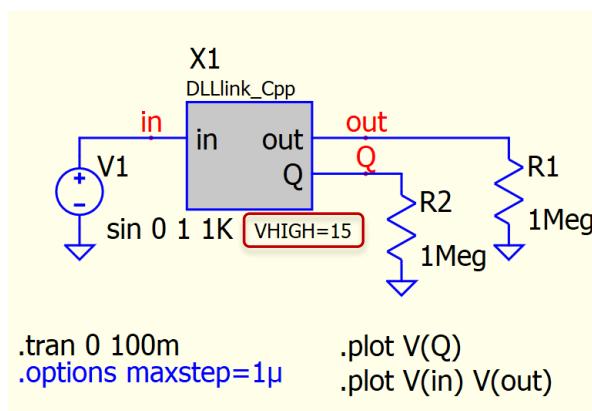
ROUT and COUT

- Rout : Output Impedance
- Cout : Output capacitance
- **Default ROUT=1000Ω**
- **Default COUT=0F**
- Example
 - In this example, it shown circuit arrangement of Rout and Cout in .dll device output



VHIGH

- Vhigh : Logic high level for outputs declared as Boolean
- **Default VHIGH=1V**

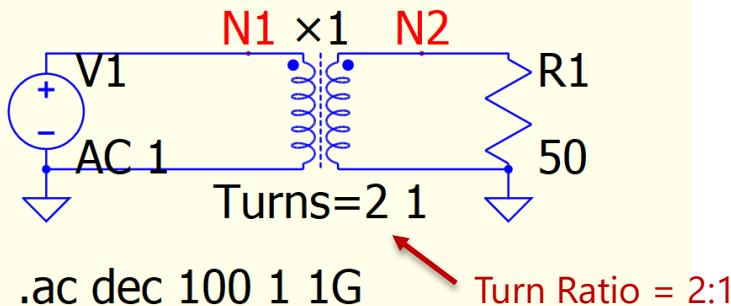


**x-Device
Transformer**

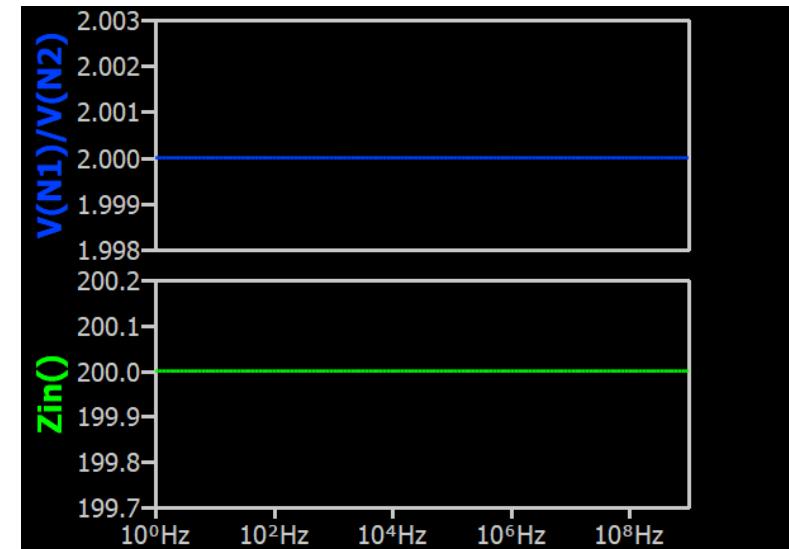
✗-Device: Transformer

Qspice : Transformer - Basic.qsch

- ✗-Device: Transformer
 - Syntax: $\times nnn \text{ «PRI+ PRI- SEC1+ SEC1- SEC2+ SEC2 [...]» } <\text{TURN}=N1\ N2\ N3\ ...>$ [Additional Instance Parameters]
 - Ideal Transformer Equation (Inductance $\rightarrow \infty$)
 - $n = \frac{N_1}{N_2} = \frac{v_1}{v_2}$ and $Z_{N1} = n^2 Z_{N2}$



```
.ac dec 100 1 1G
.func Zin() V(N1)/-(I(V1))
.plot Zin()
.plot V(N1)/V(N2)
```



\times -Device: Transformer Instance Params

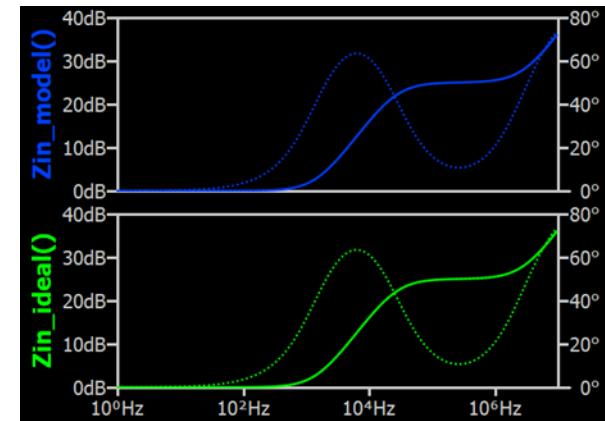
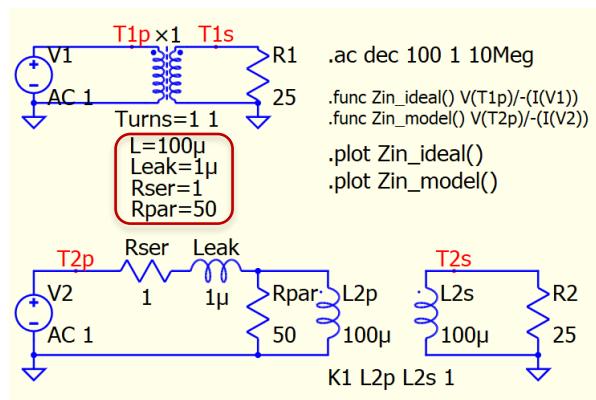
Transformer Instance Parameters

Name	Description	Units	Default
ISAT ¹	Current that drops inductance to SATFRAC of zero-current value	A	Infinite
K ¹	Alternate means of specifying LEAK		1
L	Primary zero-current inductance	H	Infinite
LEAK	Leakage inductance	H	0
LSAT ¹	Inductance asymptotically approached in saturation	H	10% of L
RPAR ¹	Primary parallel resistance	Ω	Infinite
RSER ¹	Primary series resistance	Ω	0.0
SATFRAC ¹	Fractional drop in L at ISAT		0.7
TURNS	List of relative number of turns		

Instance Params : L, Leak, Rser, Rpar, Isat, Lsat, Satfrac

Qspice : Transformer - L Leak Rser Rpar.qsch ; Transformer - Isat Lsat Satfrac.qsch

- L, Leak, Rser, Rpar
 - L : Primary Inductance
 - Leak : Leakage Inductance
 - Rser : Series Resistance
 - Rpar : Parallel Resistance
 - Equivalent model is shown in this simulation



- ISAT, LSAT, SATFRAC
 - Isat : Current that drops inductance to SATFRAC*L
 - Satfrac : Fractional drop in L at Isat
 - Lsat : Inductance asymptotically approached in saturation
 - These parameters are ignored unless L is given

